

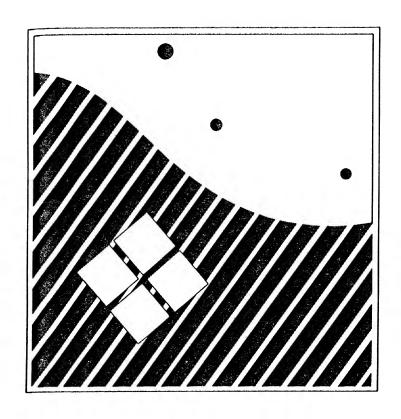
# 最一下「電界效果」共民共憲



パワーMOS FET(海外製) 主要規格付き

復刻版

CQ出版杠



#### ☆規格表ご利用の際のお願い

本規格表の仕様はメーカー発表の資料に基づき作成しておりますが、メーカーによって予告なく規格・外形等を変更する場合がありますので、量産品等、大量に素子を使用して製品を生産する必要のある際には、事前に該当メーカーにお問合わせの上、仕様をご確認ください。

# 

このページは空白です.



規格表の 使 い 方

## FETを活用するための用語の説明

FET関係の記事、文献をはじめてみた 場合、トランジスタでは見馴れない、また 聞き馴れない用語が次から次へととびだし、 誰でも少なからず、面くらうものです。

しかし、これだけで、FETを難解なも のであると決めつけ、敬遠してしまったの では、例えばせっかく宝物の埋めてある場 所につきながら、たまたま掘りおこす道具 を持ち合わせなかったという理由だけで、 すごすごと引き返えすようなもので、実に 惜しむべきことといわねばなりません。用 語というのは、FETの本質を知るための 道具、手段のようなものですから、一通り の知識を身につけておくことは、ぜひ必要 です。

さて、FETの用語、記号は、現在のと ころ統一されていないので、各社それぞれ 独自のものを使っていますが、ここでは、 これらのうち、主なものについて簡単に説 明していきましょう。

まず、最大定格をあらわすものとして、 耐圧関係がいくつかあります。

\*V<sub>GDS</sub>(ドレイン-ソース短絡ゲート-ド はいえません。 レイン間電圧)

3 文字の添字は、トランジスタの場合と 同じで、1番目が起点となる電極、2番目 が入出力の共通電極、最後は第3の電極が 共通電極に対して、どういう状態にあるか を表わします。

3番目にくる添字としては、

**5** ··· 短絡、**0** ··· 開放

x…指定されたバイアス電圧を加える

R…指定された抵抗を接続する などがあります。

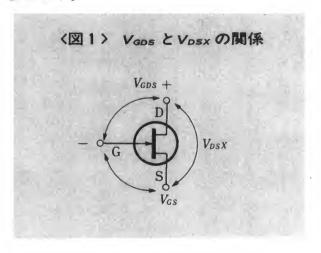
さて、ゲート・ドレイン間の耐圧は、普 通、接合型FETで用いられ、ゲート・ド レイン間のPN接合のブレークダウン電圧 に相当します。

この規格以上の逆電圧をかけて使った場 合、素子のバラツキにより異なりますが、 必ずある電圧でブレークダウン領域に入り 逆電流が急増するためPN接合が破壊され る恐れがあります。したがって、メーカー で保証している最大定格内で使用するよう に設計することが望ましいわけで、定格オ ーバで使って、もしこわれたとしても文句

このゲート・ドレイン間耐圧としては、 VGDSの他に、VGDO、VGDXがありますが、普 通の接合型FETでは、内部構造上、ゲー トに対してドレイン・ソースは対称ですか ら、 $V_{GDS} \simeq V_{GDO} \simeq V_{GDX}$  になります。

#### \* Vosx (ドレイン - ソース間電圧)

これは、主としてMOS型FETの場合 に使われます。というのは、MOS型では ゲート・ドレイン間の耐圧は、酸化膜の耐 圧そのものに相当し、実際回路で問題にな るドレイン・ソース間の耐圧と直接関係が ないためです。これに対し、接合型では、 VGDSとVDSXの間に次のような関係式が 成 立します。



#### $V_{DSX} \simeq V_{GDS} - V_{GS}$

このことは、図1からも明らかで、ドレイン・ソース間に実際加えることができる電圧は、ゲート・ソース間のバイアス電圧により異なりますが、必ずVGDSより小さな値になり、カットオフ時に最小になります。

 $(V_{DSX})_{\min} = V_{GDS} - |V_p|$ 

ここで、Voというのは、ピンチオフ電圧とよばれる、カットオフ時のバイアス値を示します。普通VDSXというのは、カットオフの時の耐圧で表わされますが、接合型の場合、いま述べたように、VDSXに相当するものは、VGDSではなく、VGDSからピンチオフ電圧を差引いたものになりますから、この点充分注意を要します。

#### \* V<sub>GSO</sub> (ゲート - ソース間電圧)

これは、主としてMOS型で用いられ、 トランジスタのVEBOと同様に特にスイッチ ング回路などで問題になります。

#### \*/G (ゲート電流)

接合型で、ゲート・ソース間を順方向にバイアスするとゲート電流が流れはじめ、等価的にトランジスタと同じ動作をし、IDSSよりはるかに大きいドレイン電流が流れます。したがって、ドレイン側の許容損失で普通押えられてしまいますが、ゲート側も一応の目安として最大順方向電流が決めら

れています。これに対しMOSでは、構造上、接合型のゲート順方向電流に相当するものは存在しないので、IcのかわりにIDの最大値が規定されているのが普通です。

#### \*Pd(許容損失)

トランジスタのPcに相当し、周囲温度**25** ℃の時の最大許容値で示されます。

また、実際のパワーは、チャンネルで消費されるので、 $P_{ch}$ (許容チャンネル損失)で表わされることもあります。

#### \* T; (接合部温度)

接合型の場合、トランジスタと同様に $T_i$ で、一方MOS型では、 $T_{ch}$ (チャンネル温度)で表わされるのが普通です。

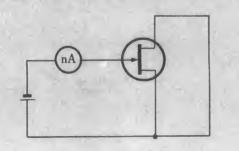
#### 〈電気的特性に関する用語〉

次に電気的特性を表わすのに使われる用 語に話を進めましょう。

#### \*1655 (ゲートしゃ断電流)

これは、入力インピーダンスの目安を与

〈図 2 > IGSS 測定回路 (N チャンネル)



えるもので、ドレインとソースを短絡し、 ゲート・ソース間に逆電圧を印加した時に 流れるリーク電流です(**図2**参照)。

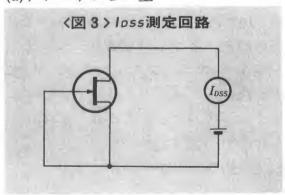
接合型の場合、IGSS はPN接合の逆方向電流に相当しますが、MOS型では、酸化膜を通して流れる電流で、接合型とは桁が違います。したがって、MOSの場合、FETの外囲器や、測定の際用いるソケットの漏洩電流の方が、素子自身を流れる電流より、むしろ大きい場合があります。

#### \* Ipss (ドレイン電流)

ゲートとソースを短絡、すなわち零バイアスの時流れる電流で、この時のドレイン・ソース間電圧としては、ピンチオフ電圧の絶対値より充分大きく、ブレークダウン電圧より小さい、電流が充分飽和している電圧が選ばれます(図3)。

FETを静特性で分類すると図4に示す ように

#### (a)デプレッション型



(b)デプレッション+エンハンスメント型 (c)エンハンスメント型

の3つに分けることができますが、(a)と(c) では、Iossの大きさがまったく対称的です。

すなわち、デプレッション型では、IDSSが、最大飽和電流に相当し、かなり大きな値を示しますが、エンハンスメント型の場合、カットオフ電流になりますから、非常に小さい値になるわけです。

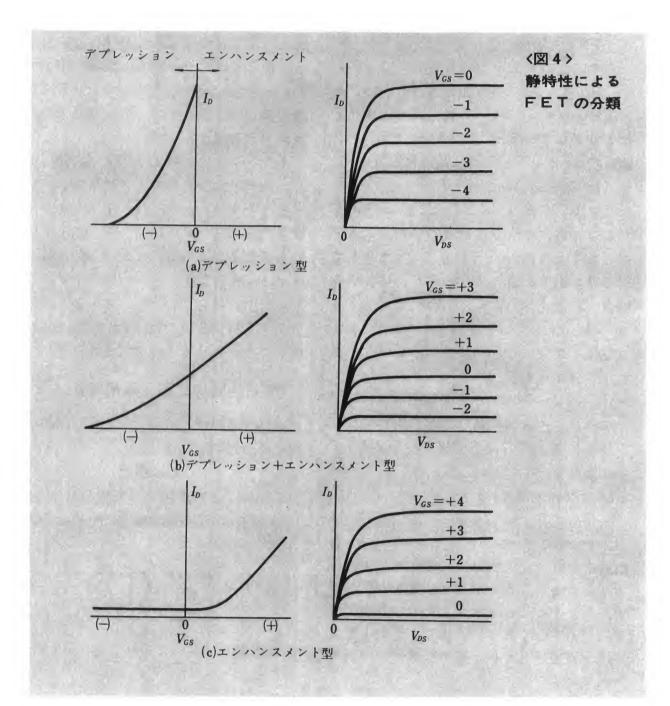
#### \* V。(ピンチオフ電圧)

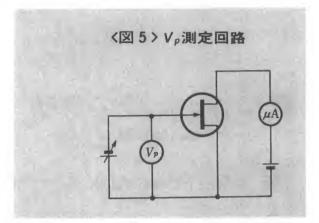
これは、Ioss の説明文中の、(a)と(b)のタイプの場合に適用され、一定のドレイン・ソース間電圧のもとで、バイアスを深くしてゆき、電流が零になる時のゲート・ソース間電圧で、Vp以外にVGSC、VGS(off)(いずれもゲート・ソース・カットオフ電圧とよばれる)などが使われます。

しかし、実際の測定では、電流が零というのは、判定しにくいので、充分小さな規定電流値、メーカーによって違いますが、普通、Io=0.1μA、1μA、10μAの時のバイアス値を読みとります(図5)。

一方、(c)のエンハンスメント型の場合は、 電流が流れはじめる点ということで V<sub>p</sub> で はなくV<sub>th</sub> (スレッシュホールド電圧) が用 いられます (図6)。

#### \*gm(相互コンダクタンス)

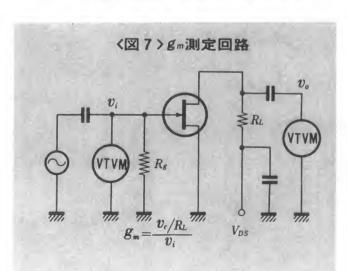


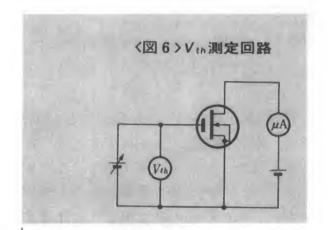


gmの定義は次式で与えられますが、gmの他に | Yfs | (ソース接地小信号順伝達アドミタンス) という記号が用いられることもあります。

$$g_m = \frac{\partial ID}{\partial V_{GS}} \mid_{V_{DS} = -\Xi}$$

またバイアス条件としては、Ioss と同じ 条件が用いられることが多いようですが、 ドレイン電流を規定する場合もあります。



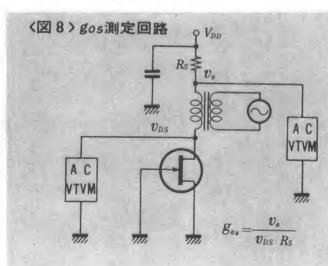


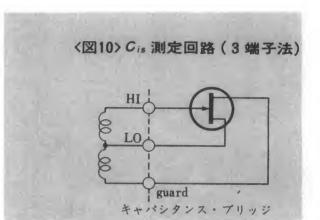
測定回路としては、図7が用いられ、普通、1kHzで測られます。

#### \* gos (出力コンダクタンス)

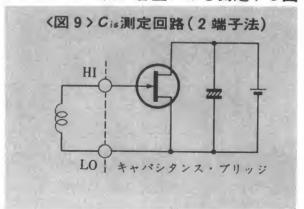
| Yos | と書かれる場合もありますが真空管でいえば、プレート抵抗 rpの逆数に相当するものです。電流によって大きく変化しますが普通は、gmと同じバイアス条件で測定されます (図8)。

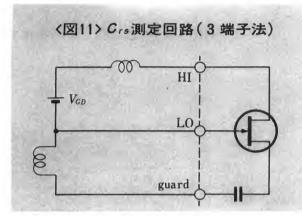
#### \* Cis (ソース接地入力容量)





このCisの測定条件は各社まちまちですが、特に接合型の場合、入力容量は、PNジャンクションの逆バイアス容量になりますから、バイアス条件で値は大きくもなります。しかし、一般に零バルでさくもなります。しかし、一般にで測定方法としてのようです。測定方法としてでするとが多いようです。測定方法として正をかけ、キャパシタンス・ブリッジの2端子と関いたり、あるいは、ドレイン・ブリッジを用いたり、あるいは、ドレイン・ブリッジを用いたり、あるいは、ドレイン・ブリッジを用いたり、あるいは、ドレイン・ブリッジを用いたり、あるいは、ドレイン・ブリッジを用いたり、あるいは、ドレイン・ブリッジを用いたり、あるいは、ドレイン・ブリッジを用いたり、あるいは、ドレイン・ブリッジを開いたり、あるいは、ドレイン・ブリッジを開には電圧をかけずに3端子法で純粋にグート・ソース間の容量だけを測定する図





10の回路などがあります。

#### \* Ccs (ソース接地帰還容量)

低周波同路でも、この Crs が大きいと、 ミラー効果により、等価入力容量が増加し ト限周波数が下がってしまい問題になりま すが、高周波回路では、gmと共に、Crs の

〈図12〉 Vos-10特性例 0.2 ドレイン電流 Io (mA) 0.1 -0.10.2 -0.10 0.1 ドレイン電圧 VDS(V)

なります。すなわち $g_m/C_r$ sは大きければ大 うわけで、測定回路は213になります。 きいほどよいわけです。

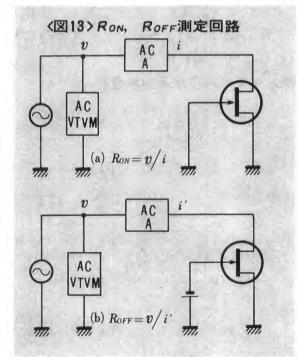
 $C_{rs}$ の測定回路の一例を図11に示します。

#### \* RON (オン抵抗)、ROFF (オフ抵抗)

FETをチョッパに使う場合、この2つ のパラメータが重要な意味をもってきます。

FETの静特性の立ち上がりの部分(3 極管領域)は、トランジスタとちがって、 オフセット電圧が存在しなく、バイアス電 圧により抵抗値が変化する可変抵抗と考え ることができます (図12参照)。

図12で、 $V_{GS}=0$  の時の直線の傾きに相



大きさが高周波特性の良さの一つの目安と 当するのがRon、カットオフ時がRoffとい

### ■略称・記号の説明

#### (1) メーカー名(50音順)

富士通 富士通株式会社

三洋 東京三洋電機株式会社

東芝 株式会社 東 芝

日電 日本電気株式会社

日立 株式会社日立製作所

三菱 三菱電機株式会社

ソニー ソニー株式会社

松下 松下電子工業株式会社

#### (2) 構造

Junction (接合)型

MOS (Metal Oxide Semiconductor)

V Vertical(縦型)

GaAs ガリウム砒素 J型

GaAsSB ガリウム砒素 ショットキバリヤ ゲート型

#### (3) モード

D デプレッション

エンハンスメント

D+E デプレッション+エンハンスメ ント

#### (4)区分

通工 通信工業用

一般 一般用

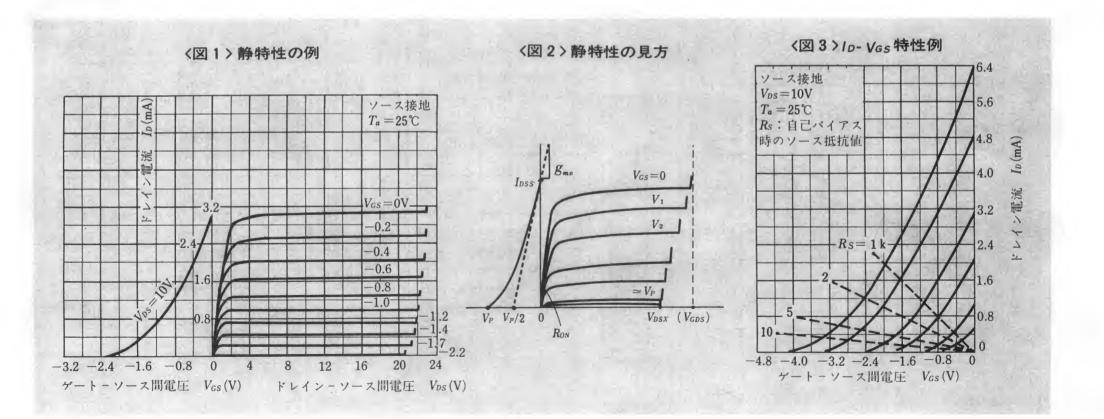
# 特性図の見方・使い方

FETのカタログをみると、各種の特性グラフがのっていますが、ここでは、そのうちの主なものを用途別にいくつか選び、どういう点に注目すればよいか、またどのように活用すればよいか順を追って、みていきたいと思います。

## • 静特性の見方

FETの基本特性である伝達特性と出力 特性を表わしたもので、これ一つあれば低 周波のパラメータは、ほとんどわかってし まうといっても決して過言ではありません。 まず、グラフから、IDSS、ピンチオフ電 圧、VGDS (VDSX) の標準値を知ることがで きます( $\mathbf{図1,2}$ )。

また、伝達特性の各点における傾きを計算すれば、任意のバイアスにおける8m が求



まります。このgm は次に示すように近似式 を用いても、簡単に計算できます。

FETの5極管領域(飽和領域)では、 二乗近似が非常によくあてはまりますが、 これを使うと、

$$I_D = I_{DSS} (1 - V_{GS}/V_p)^2 V_{DS} = -$$
定
$$g_m = \frac{\partial I_D}{\partial V_{GS}} \Big|_{V_{DS}} = -$$
定
$$= \frac{2 I_{DSS}}{(-V_p)} (1 - V_{GS}/V_p)$$

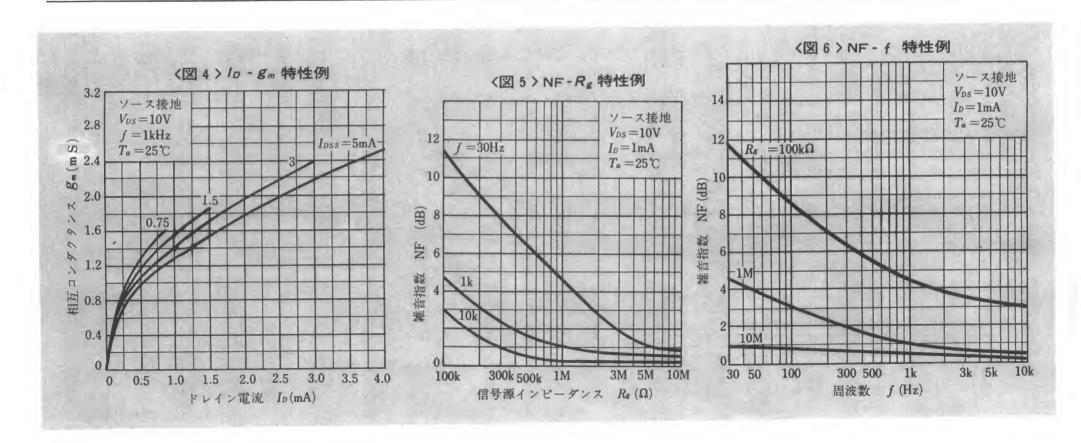
$$=g_{mo} (1 - V_{GS}/V_{p})$$
 $\subset \subset \mathcal{C},$ 
 $g_{mo} = \frac{2 I_{DSS}}{(-V_{p})}$ 

このようにして、各バイアスにおけるgm が求まったら、次の関係式からオン抵抗も 計算できます。

$$\begin{bmatrix} RoN \end{bmatrix} \stackrel{I_D=0}{V_{GS}=V_1} = \begin{bmatrix} 1/g_m \end{bmatrix} V_{GS} = V_1$$

gos, Roff も静特性から求めようと思えば、求まりますが、誤差が大きく実用にはなりません。

また、出力特性のパラメータになっている、ゲート - ソース間のバイアスの符号を みれば、デプレッション、エンハンスメン トのどのモードで働く素子か判断できます。



### 用途別にわけた特性の見方

以上、示したように静特性というのは、 FETの特性の基礎となるもので、カタログには不可欠のものですが、他の特性は用途によって、当然かわってきます。そこで、次に各用途別に分けて主な特性をみていきましょう。

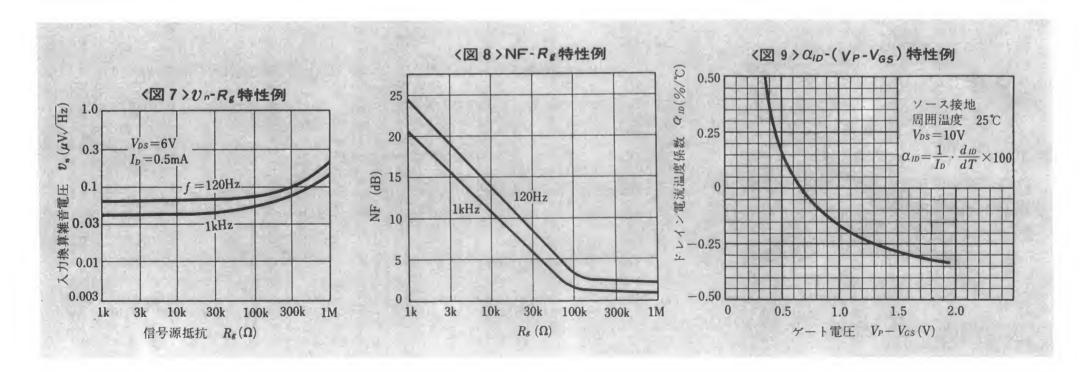
#### ■直流、低周波增幅用

まず、② 3・のID-VGS、② 4 の $ID-g_m$  のように素子のバラッキを併せ示したグラフがあれば、机上の計算だけで、簡単に回路の基本設計ができます。

次に、低信号レベル増幅回路としてどう してもかかせないのが、雑音特性です。雑 音特性は、一般に測定条件により大きく変 化するので、雑音の対信号源インピーダン ス、対周波数、対ドレイン - ソース間電圧、 対ドレイン電流特性などが必要になります (図5,6)。

NF(雑音指数)の他に、入力換算雑音電圧で雑音特性を表わす方法がありますが、このうち、対信号源インピーダンス特性はNF $-R_8$ 特性と形が違いますから、両者を単純に比較することはできません。

例えば、**図7**と**図5**をみると、**図7**の方が低信号源インピーダンスで雑音特性がよ



さそうですが、 $\mathbf{Z}$ 7の $\mathbf{v}_n$ を信号源抵抗から発生する熱雑音電圧を計算し、 $\mathbf{N}$  Fに換算すると $\mathbf{Z}$ 8 になり、 $\mathbf{Z}$ 5 と同じ傾向になることがわかります。

図7では、 $v_n$ の単位として、 $\mu V/\sqrt{Hz}$ が使われていますが、これは、帯域幅で規格化したもので、例えば、 $R_s$ の抵抗の熱雑音電圧はボルツマン定数をK、絶対温度をTとすれば

$$v_N = \sqrt{4 K T R_g \Delta f}$$

で表わされますが、 $V_n$ と同じ単位に直せば、 $V_n = \sqrt{4 KTR_g}$  になるわけです。

最後に直流増幅器の設計にぜひ必要なものとして、FETの各パラメータの温度特性関係のグラフがあります。

これには、ID, gm, IGSSの標準値の温度特性を示したものと $\mathbf{29}$ のように、バイアスと温度係数の関係を表わしたものがあります。

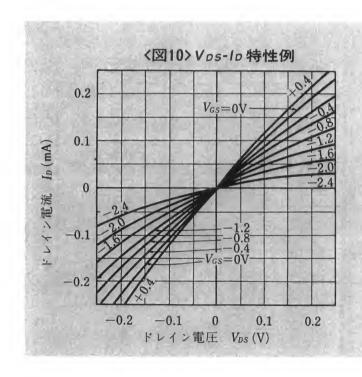
例えば図9の場合は、ピンチオフ電圧よ

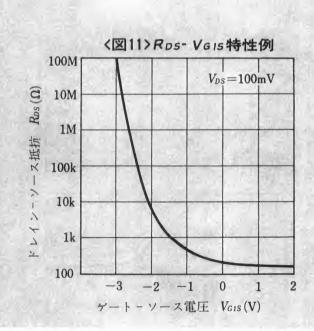
り約0.65 V高いバイアスで使えば、ドレイン電流の温度係数を零に押えることができるということを意味しています。

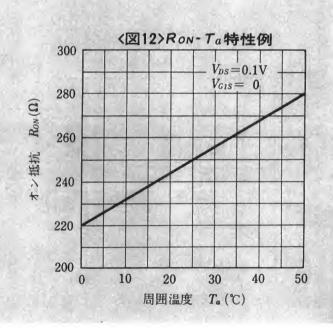
#### ■チョッパ用

**FET**の立上がりの部分の特性が重要になってくるので、**図10**のような小レベルの出力特性が示されます。

FETの種類は違いますが図10で、Vosを 一定にして、ドレイン・ソース抵抗ーゲー







またチョッパ用の場合、ホン抵抗やオフ 抵抗の温度特性を知る必要があり、一例を 図13に示します。

#### ■高周波用

普通、高周波回路の設計には、Yパラメ ータが一番使われるので、Yパラメータの 周波数特性、電圧電流依存性などが中心に なります。図14に、ソース接地、図15にゲ

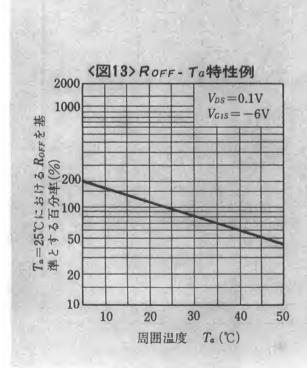
トーソース電圧特性を求めたのが図11です。 ート接地のYパラメータの一例を示します。 によって、ある程度自由に利得の大きさが

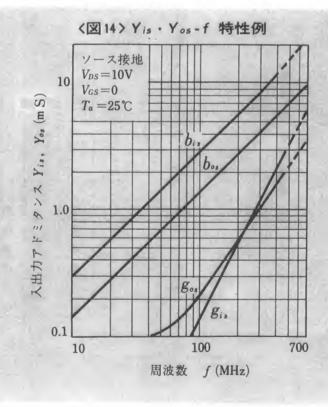
特性グラフではありませんが、高周波用 較しても意味がありません。 として、問題になるものとして、高周波電 すなわち各メーカーのカタログにのって 力利得、雑音指数があります。

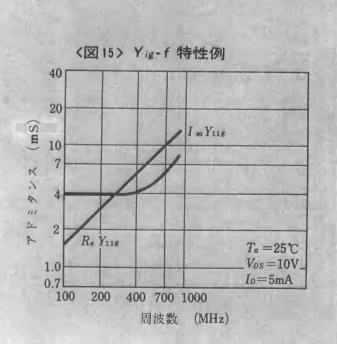
ンピーダンスに合わせて、入力側でノイズ とで、個々の素子の比較は、同一の測定回 マッチングをとったような形で、普通測定 されるので、それほど問題はありませんが、 電力利得の方は、極端にいえば、測定回路

変えられるので、P.G.の絶対値だけを比

いるのは、それぞれの測定回路で測った場 雑音指数の方は、各素子の最適信号源イ 合に、それだけの利得が得られるというこ 路で測るか、あるいは、Yパラメータから 計算するよりしょうがありません。







				用	途	ダ高 D	コン	低姓	低	周	波	ピ	チ	S	可	髙	V R H	U	S R H	索引	(頁)		
型	名					ンスロース 口に 入力インド	コンデンサ・マイ	低雑音増幅回路	電圧増	ドライ	出	デオ増	ョッパ回	W	変抵抗回	周波出	FF	R H F F M I	F F M I	規 格 一	特性	備	考
		社 名	構造	モード	区分	路门	7	路	幅	バ	カ	幅	路	路	路	カ	χ̈́	X	x	覧	図		
2SJ17		ソニー	J	D	般		•													34			
<b>" 18</b>		"	J(V)	11	"						•									34	_		
" 22		11	J	11	"		•													34			
" <b>3</b> 9		三 菱	MOS	11	"	•		•												34	'83年	$2SJ\times2$	
" <b>4</b> 0		11	J	11	11				•						•					34	134		
<b>" 43</b>		松下	"	11	"	•		•												34	135		
<i>11</i> 44		日電	"	"	"			•				100 May 100 - 100 May								34			
" <b>4</b> 5		11	"	"	"	•						- Carrier of a second		1						34			
" <b>4</b> 8		日 立.	MOS	E	"						•									34	'83年		
" <b>4</b> 9		"	"	11	11						C									34	'83年		
<i>"</i> 50		"	11	11	"						•									34	'83年		
<i>"</i> 55		"	MOS	"	11						•									34	136		
<i>"</i> 56		"	"	"	"						•									34	136		
″ 56⊕		"	"	"	通 工		and the second s	a Matara Constant						•		•				40	136		
<i>"</i> 68		"	J	D	般			•												34	'84年		
<i>"</i> 69		"	"	"	"			•		- martine is high different to a significant										34	'84年		
<i>"</i> 70		"	"	"	11			•					Acres, and the second stem							34	'84年		
<b>"</b> 72		東芝	"	"	11	•		•												36	'83年		
<i>"</i> 73		"	"	"	"	•		•												36	'84年	2SJ×2	
" 74		"	"	"	"	•		•		***************************************				-		Constitution of the second				36	'84年		
<i>"</i> 75		"	"	"	"	•		•					The state of the s	THE RESERVE OF THE PARTY OF THE						36	'84年	2SJ×2	
<i>"</i> 76		日 立.	MOS	E	"						•			•		•				36	137		
<i>"</i> 77		"	"	"	"						•			•		•				36	137		
" 77 €		"	"	"	通 工	a Controllation	n dere die desemble de de la contra de				. 4 . 4 . 4 . 4 . 4 . 4 . 4 . 4 . 4 . 4		-	•		•				40	137		
<i>"</i> 78		"	"	"	般	and the second				Augusto Stranger .	•			•		•				36	137	AND DESCRIPTION OF PERSONS	
<i>"</i> 79		"	"	"	"			***********	- No May Street		•		TOTAL STREET, ST.	•		•		-		36	137		CR.A- 2010 - C-PT
″ 79 <b>®</b>		"	11	"	通 工.							- stare recently to	WORK IN A SEC.	•		•	and the second			40	137	angularia della mandri estado della	asertas rues rues
<i>"</i> 81		"	,,	"	- 般						•	and the second second	THE PERSON NAMED IN	TO THE OWNER OF THE PERSON NAMED OF						36	'83年	Andreas de la companya de la company	marite Will colonistics (see
<b>" 82</b>		"	"	"	"						•								*************	36	'83年		Philip School of Con-

				用	途	ダ高 D	コン	低	低	周	波	ピ	チ	S	可	髙	V	U	S R H	索引	(頁)		esti-randifiçõe et
	4.					ダ高 D ンカイ	デン	音	電	۲	出	デ	ョッ	w	変抵	周	RH	R H F F	FF	規	特	/##;	考
型	名					スイA ロンC	コンデンサ・マイク	低雑音増幅回路	圧増	ライ		オ 増	パ 回	[0]	抗回	波出	M I	M I	M I	格一	性	備	Æj
		社 名	構造	モード	区分	路门	1	路	幅	バ	カ	幅	路	路	路	カ	x	X	X	覧	図		
2SJ 83		日 次	MOS	E	般						•									36	'83年		
" 84		松下	J	D	"	•														36	138		
<i>"</i> 96		日立、	MOS	E	"						•			•		•				36	139		
" 99		"	"	"	"						•			•		•				36	140		
<i>"</i> 100		"	"	"	"						•			•		•				36	140		
" 101		"	"	"	"						•			•		•				38	141		
" 102		"	"	"	"						•			•		•				38	141		
<i>"</i> 103		東芝	J	D	"	•									•					38	142		
<i>"</i> 104		"	"	"	"	•									•					38	143		
" 105		11	"	"	"	•									•					38	142		
" 106		11	"	"	"	•									•					38	142		
" 107		"	"	"	"	•									•					38	143		
" 108		"	""	"	"	•		•												38	'84年		
" 109		"	"	"_	"	•		•												38	144	2SJ×2	
" 110		"	"	"	11	•									•					38	145		
" 111		"	"	11	"	•		•							f					38	145		
" 112		日 立	MOS	E	"									•		•				38	146		
" 113		"	"	"	"									•		•				38	146		
" 114		"	"	"	"									•		•				38	147		
" 115 ·		東芝	"	"	"						•									38	148		
" 116		日立	"	"	"									•		•				38	149		
" 117		"	"	"	"	17-1		77		1				•		•				38	150		
" 118		"	"	"	"			£.						•		•				38	140		
" 119		"	"	"	"									•		•				38	140		
<i>"</i> 120		"	"	"	"									•		•				38	151		
" 122		"	"	<i>"</i>	"									•		•				38	152		
" 123		東芝	"	"	"					. ]	•			•						38	153		
" 125		三菱	J	D	"				•						•					38	134		
" 126		東芝	MOS	E	通 工.									•						40			
3S J 11A		日電	"	"	"	•	•							•						40	'82年	3SJ×2	

The state of the s			用	途	グ高D	コン	低	低	周	波	ť	チ	S	可	高	V	Ü	S R H	索引	(頁)		
			<u> </u>	~~	ン人C カ・	デン	雅音	電	۴	出	デ	3	w	変抵	周	R H F F	RHFF	FF	規	特	1	ا بد
型名					スイA ロピ	コンデンサ・マイク	低雑音増幅回	圧	ラ		オ 増	パ	0	抗	波出	М	М	M	格	性	備	考
	社名	構造	モード	区分	路し	イク	回路	增 幅	イバ	カ	幅	回 路	路	四路	カ	X	X	I X	覧	図		
2SK11	東芝	J	D	通 工.	•							•	•						42	'82年		
" 12	"	"	"	"			•					•	•						42	'82年		
" 15	"	"	"	"	•		•												42	'82年		
″ 16⊕	日立	"	"	"	•														42	'82年		
" 18	東芝	"	"	"	•														42		2SK×2	
" 18A	".	"	"	"	•														42		2SK×2	
" 23A	ソニー	"	"	般			•					•		•		•			42			
" 30ATM	東芝	"	"	"	•		•												42	'83年		
<i>"</i> 33	三菱	"	"	"												•			42	'82年		
" 34	"	"	"	"	•		•												42	'82年		
" 37	日電	"	11	"												•			42	'83年		
" 38A	三菱	MOS	D+E	"	•	ap				-						•			42	'83年		
<i>"</i> 40	日 立.	J	D	"	•		•												42	'82年		
" 42	ソニー	"	"	"							•					•			44	'82年		
<i>"</i> 43	"	"	"	"			•				•								44	'83年		
" 43\$	"	11	"	通 工	•		•						•						44	'83年		
" 43\$-D	"	"	"	11	•		•						•	•					44	'83年		
" 46	三菱	"	"	般	•	•	•												44	'82年	to VAPA Per at 10 miles and an analysis and a second secon	
" 48	東芝	"	"	通工	•		•		Teach Street Street Street		and the second								44	'82年	Andrew Committee of the State o	
<i>"</i> 49	日電	"	"	般					and Charges and a little of							•			44	'82年	The sales of the s	
<i>"</i> 54	日 立.	"	11	"							Carlo C. Againmeter					•			44	'82年	Million And Male in Residence of the State of	
<i>"</i> 55	"	"	"	"										Total State of State		•			44	'82年	A STATE OF THE PROPERTY OF THE STATE OF THE	
<i>"</i> 57	日電	"	11	"									- The additional activities			•			44	'83年	A STATE OF THE PARTY OF THE PAR	
<i>"</i> 58	ソニー	"	11	"	•		***************************************		Communication of the last of the con-	- CONTRACTOR						Jan 201 . 101 July 201		ALAN DE STATISTE	44		2SK×2	
<i>"</i> 59	日 立.	"	"	"		•					restriction of the		The second se	Marine Marini and Audit		and and made a control of the state of the s			44	'83年		
<i>"</i> 60	ソニー	J(V)	"	"	a destruction continues of	aged - Markey As been			- Adams with the	made or make a minute	******	-positions now						21 NOT 1 21 NOT 1 PROFES	44	'83年	and a service on larger tree	Anna Six
<b>"</b> 63	"	11	11	11	•	and the state of the					A		•				Table President Committee	and the suspense of	44	'83年	The same process and the	
<i>"</i> 65	松下	J	"	11		•	**************************************		- refregerablish redshift this is	antique for Historia sandra				n. C. Commy a				******	44	'83年	AND DESCRIPTION OF THE PARTY OF	*,
" 66	"	"	"	11	•		•		•	an rames of	Comment to Make t	well serve	egana myae	151		to their warm of	na Tookise e	and the property of the second	44	'83年		AND WEST PROPERTY.
<b>"</b> 67	日電	"	"	11	**********	•	and the second s						PERSON THE TOP I				****	altique alteri	44			
			أبقابسممسيانيما	4			-					-								L	And the second of the second of the second of	

			用	<del></del>	ダ高 D		低	低	周	波	ピ	+	S	可	髙	v	U	S	索引	(寶)		
			<i>H</i> ;	LAT.	ンガ・	コンデンサ・マイク	雑音	電	۲	出	デ	3	W	変	周	RHFF	RHFF	RH FF	規	特		
型名				_	スイA	サ	増	甩 圧	トラ	1 111	オ	7		抵抗	波	l			格		備	考
		· · · · · · · · · · · · · · · · · · ·			回 <sub>と</sub> C	マイ	幅回	增	1		増		回	回	出	M	M	M I		性		
	社 名	構造	モード	区分	路!	ク	路	幅	バ	カ	幅	路	路	路	カ	IX	X	X	覧	図		
2SK 67A	日電	J	D	般		•													46	'83年		
<i>"</i> 68	"	"	"	"	•				arthitic to the attended					•					46	'83年		
" 68A	"	"	"	"	•		•							•					46	'83年		
" 72	東芝	"	"	通 工.	•		•												46		$2SK\times2$	
" 73	松下	"	11	般	•				•										46	-		
" 79	ソニー	J(V)	"	"	•				•				•						46	'83年		
<i>"</i> 83	松下	J	"	"			1									•			46	'83年		
" 84	"	"	"	"	•		•												46	'83年		
<i>"</i> 85	日電	GaAsSB	"	通 工.														•	46	'83年		
<i>"</i> 92	"	J	"	般		•													46	'83年		
<i>"</i> 93	ソニー	"	11	"		•													46	'83年		
" 94	日電	"	7)	"			•							•					46	'83年		
<i>"</i> 97	ソニー	"	"	"	•														46	'83年	2SK×2	
" 103	日電	"	"	"		•													48	-		
" 104	"	"	"	"			•							•					48	'83年		
" 105	"	"	"	"			•							•					48	154		
<i>"</i> 107	ソニー	"	"	"	•		•					•				•			48	'83年		
<i>"</i> 108	三菱	"	"	"			•							•					48	155		
″ 109A	"	"	"	"	•		•			7									86	155	2SK×2	
<i>"</i> 110	"	"	"	"			•												48	156		
<i>"</i> 111	11	"	"	"	•		•												48	'83年	2SK×2	
" 112	東芝	11	"	通 工	•		•					•	•						48	'83年		
" 113	"	11	<b>))</b> -	"								•	•	•					48	'83年		
" 117 <sub>.</sub>	"	11	"	一般	•		•									1			48	'83年		
" 118	"	11	"	11	•	•	•										*		48	'83年		
<i>"</i> 119	日電	"	"	通 工.	•									•					48	'83年		
″ 120	ソニー	11	"	一般												•			48	'83年		
<i>"</i> 121	11	"	"	"	•		•				•		•				_		48			
<i>"</i> 123	松下	"	"	"		•													48	157		
" 124	日 電	GaAsSB	"	"														•	48	'83年		

			<b></b> 用	<del></del>	ダ高D	コン	低	低	周	波	۲	チ	s	可	髙	V	ู้ บู	S	索片	(頁)		
					ン入C カ・	デン	雑  音	電	ド	出	デ	ョッ	w	変抵	周	RHFF	RHFF	RHFF	規	特		
型名					スイA ロンC	サラ	増幅	圧	ラ		オ増	ノペ		抗	波出	М	М	М	格	性	備	考
	社名	構造	モード		路し	コンデンサ・マイク	低雑音増幅回路	増幅	イバ	カ	幅	回路	路	四路	力	I	I X	I X	覧	図		
2SK125	ソニー	J	D	— 般										•		<b> </b>	<b> </b>		48	'84年		
" İ27	松下	11	"	"	•		•												50		İ	
" 127A	"	"	"	"	•		•												86			
" 128	"	11	"	11	•		•												50	158		-
<b>" 130</b>	日電	11	11	"			•							•					50	'83年		
″ 130A	"	"	11	"			•									<u> </u>			86	'83年		
" 131	"	"	"	"			•												50	159	2SK×2	
" 133	日 立.	MOS	Е	"						•									50	'83年		
" 134	"	"	"	11						•									50	'83年		
" 135	"	11	"	"						•					****			-	50	'83年		
" 136	松下	J	D	"	•		•												50	160		
" 137	"	" .	"	"			•									-			50	-		
″ 137A	"	"	"	"			•												50	_		
" 138	日電	GaAsSB	"	"														•	50	'84年		
" 140	"	"	"	"														•	50	'84年		
" 141	11	J	"	通 工	•									•					50	'83年		
" 141A	"	"	"	"	•									•					50	'83年		
" 146	東 芝	11	"	般	•		C												50	'84年	2SK×2	
" 147	"	"	"	"			•												50	'83年	a Albert Lande Cases Will advise have a life for miles and a life of the lands	
″ <b>14</b> 8	松下	11	"	"												•			50			
" 149	日電	11	"	通工												•	•		50	'84年		
" 152	ソニー	"	"	般			•				•					•			52	'84年		
″ 154	松下	"	11	11												•			52		and the second of	
" 155	"	"	"	11	•														52	161		
" 156	三、洋	"	11	"		•													52	'83年		
″ 158	松下	"	11	"			•												52	_		
" 160	日電	"	"	"			•							•		•			52	154		
″ 160A	"	"	"	"			•							•		•			86	154		
" 161	東芝	"	"	"												•			52	'83年		
" 162	日電	"	"	"			•												52	'84年		

		_	用	途	ダ高 D	コシ	低	低	周	波	۲	+	s	可	髙	V	Ü	S	索马	(頁)		Name and Associated Association of
			_		ン人C カ・	デン	雑  音	電	۴	出	ア	ョッ	w	変抵	周	R H F F	R H F F	R H F F	規	特		
型名					スイA ロピ		低雑音増幅回路	圧増	ライ		オ増	パロ	回	抗回	波出	M	M	М	格	性	備	考
	社名	構造	モード	区分	路し	イク	路路	幅	バ	カ	幅	路路	路	路	カ	X	X	X	覧	図		
2SK163	日電	J	D	般			•												52	'84年		
<b>" 165</b>	松下	"	"	"							•								52	162		
" 168	日 立.	"	"	"												•			52	'83年		
" 169	松下	"	"	"	•		•												52	_		
" 170	東芝	"	"	"	•		•												52	'83年		
" 171	三. 菱	"	"	"	•		•												52	'83年	2SK×2	
" 175	日立	MOS	Е	"						•									52	163		
" 176	'"	"	"	"						•									54	163		
″ 176®	"	"	"	通 工.									•		•				86	163		
" 184	東芝	J	D	般	•		•												54	'83年		
<b>" 185</b>	ソニー	"	"	11	•		•												54	-	2SK×2	
" 186	日 立.	"	"	"			•												54	'84年		
" 187	"	"	"	"			•												54	164		
″ 190	"	"	"	"			•												54	'84年		
<i>"</i> 191	"	"	"	11			•												54	'84年		
" 192A	東芝	"	"	"												•			54	'84年		
<b>" 193</b>	日電	"	"	"												•			54	'84年		
" 194	"	"	"	11			•												54	'84年	2SK×2	
<b>" 195</b>	"	"	,,	11												•			54	'84年		
″ 196 ⊕	日 立.	MOS	E	通 工									•		•				54	'84年		
" 197	"	J	D	一般									, ,			•			54	'84年		
<i>"</i> 198	松下	"	. "	"	•														54	158		
<b>" 199</b>	"	"	"	"												•			54	_		
<b>" 201</b>	日電	GaAs	"	"														•	56	'84年		
" 203	"	"	"	11											-			•	56	'84年		
<b>" 208</b>	東芝	J	"	"		•													56	'83年		ý
" 209	"	"	,,	"	•								h 1)	1			( )		56	'83年		
" 210	" "	"	"	"												•			56	'84年		
" 211	"	"	,,	"			7		72			Y				•			56	'83年		
" 212	三洋	"	"	"												•			56	'84年		

and the second section of the section of the section		Carrie Steel Committee of the Committee	用	途	ダ高D	7,	低	低	周	波	۲	チ	S	可	高	V	ű	S	索引	(頁)	
			\ \ \ \	~•	ン入C カ・	コンデンサ・マイク	低雑音増幅回	電	۴	出	デ	ョッ	w	変抵	周	R H F F	RHFF	RHFF	規	特	/#: ±b/.
型名					スイA ロンC	サマ	増幅	圧	ラ		オ 増	パ		抗	波出	M	M	M	格	性	備考
	社名	構造	モード	区分	1 6 1	イク	回 路	増幅	イバ	カ	幅	回路	路	回路	カ	I X	X	X	覧	<b>3</b>	
2SK213	日立	MOS	E	般						•			•		•				56	165	
" 214	"	"	11	"						•			•		•				56	165	
″ 214⊗	"	"	11	通 工									•		•				86	165	
" 215	"	11	"	般						•			•		•				56	165	
<b>" 216</b>	"	"	"	"						•			•		•				56	165	
″ 216®	"	11	11	通 工									•		•				86	165	
<b>" 217</b>	"	J	D	般								_				•			56	'84年	
<b>" 218</b>	松下	"	"	"							•								56	166	
″ 220⊕	日 立	MOS	E	通 工									•		•				56	'84年	
″ 221⊕	"	"	11	11									•		•				56	'84年	
" 222	三洋	J	D	般			•												56	167	
<b>" 223</b>	"		"	"					•										56	'84年	
<b>" 22</b> 5	日 立.	MOS	E	11			_			•									56	168	
<b>" 226</b>	"	"	11	11						•									58	168	
<b>" 227</b>	"	"	11	11						•									58	168	
<b>" 238</b>	日電	J	D	11												•			58	'84年	Angelous and the second and the seco
" <b>24</b> 0	東芝	11	"	11	•		•												58	'84年	2SK×2
" 241	"	MOS	D+E	11															58	'84年	
" 242	三洋	J	D	11		_										•			58	169	
" 246	東芝	"	"	"	<b>C</b>											****			58	'84年	
" 2 <b>4</b> 7	松下	"	11	"	•										a monta a c				58	170	
″ 258⊕	日立.	MOS	Е	通 工.									•		•	Acres III to minute interes		and the same of the same	60	'84年	and the second s
″ 259⊕	"	,,,,,	<i>"</i> '	"									•		•		es an all or read over		60	'84年	water contest on and service at the polyage to the
″ 260⊕	"	"	11	"							and the second	Contract to 1	•		•	was a second			60	'84年	
" <b>26</b> 5	東芝	J	D	般	•		•			***						and the makes	man man Profession agency				2SK×2
" 266	11	11	11	11		•			-M. m. h. a c t	ANT Y MANAGEMENT OF THE			AND THE OWNERS				a distance for him process		60	171	and the same of th
" 277	日電	MOS	Е	通 工					are not be asset				•	diameter (n. 1986)	- carting and the Colon	and the state of t			62	172	
" <b>27</b> 8	"	11	"	11						. AMAR DO SERVE		a rigi austra	•	today of the same	Section of the section of				62	172	angiga - garancana ang at rangsanana at rangsaran (sa
<b>" 280</b>	"	GaAs	D	般													and the second of the second of	•	62	'84年	
" 281	11	11	"	"												•	•	•	62	'84年	

			用	<del></del>	ダ高 D	コン	低	低	周	波	ť	Ŧ	S	可	髙	V	U	S	索引	(頁)		
型名			\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	~	入 ン スカイン 回 し こ こ こ こ れ る し こ し こ し に し に し に し に し に し に り に り に り に り に	コンデンサ・マイク	低雑音増幅回	電圧増	ドライ	H	デオ増	ョッパ回	W □	変抵抗回	周波 出	RH FF M	R H F F	М	規 格 一	特 性	備	考
	社 名	構造	モード	区分		7	路	幅	バ	カ	幅	路	路	路	カ	X	X	I X	覧	図		
2SK283	三洋	j	Ď	般					•										62	'84年		
" 286	日 沈.	MOS	Е	"						•			•		•				62	173		
″ 287 <b>®</b>	"	"	11	通工									•		•				62	174		
″ 288®	"	"	"	"									•		•				62	174		
<b>" 291</b>	"	J	D	般	•						-								62	175		
" 292	日電	"	"	"												•			62	'84年		
" 293	"	MOS	Е	通 工									•						62	176		
" 293A	"	"	11	"									•						62	176		
" 29 <b>4</b>	日 立.	11	11	般									•		•				62	177		
<i>"</i> 295	"	11	"	"									•		•				62	177		
<i>"</i> 296	"	11	"	11									•		•				62	'84年		
<i>"</i> 298	"	11	"	"									•		•				62	178		
<i>"</i> 299	"	, <i>11</i>	"	"									•		•				62	178		
<i>"</i> 301	松下	J	D	"	•								•						64	179		
<i>"</i> 302	東芝	MOS	D+E	11												•			64	'84年		
<i>"</i> 303	三洋	J	D	"	•									•					64	180		
<i>"</i> 304	"	11	"	"	•									•					64	180		
<i>"</i> 308	日立	MOS	E	"									•		•				64	'84年		
<b>" 310</b>	"	"	"	"									•		•				64	181		
<b>" 311</b>	"	"	"	"									•		•				64	181		
<b>" 312</b>	"	"	11	"									•		•				64	182		
<b>" 313</b>	"	"	11	"								A	•		•				64	182		
<b>" 314</b>	日電	J	D	通 工			•	HE											64	183		
<b>" 315</b>	三洋	"	"	一般											1	•			64	184		
<i>"</i> 316	松下	"	"	"							•								64	185		
<b>" 317</b>	日立	MOS	E	"														*	64	186	other desired	
<b>" 318</b>	"	, "	"	"											•				64	187		
<i>"</i> 319	"	"	"	"									•		•				64	188		
<b>"</b> 320	"	"	"	"									•		•				64	188		
<i>"</i> 321	松下	J	Ď	"	•						•								64	189		

			用	途	ダ高 D	7,	低	低	周	波	ť	Ŧ	s	可	髙	v	U	S	索引	(頁)		***************************************
#U #			<u>`</u>	~	入C ン力・ スイA	コンデンサ・マイク	低雑音増	電	۴	出	デ	ョッ	w	変抵	周	RHFF	RHFF	RH FF	規	特	/#:	.±b/.
型名					スイA ロンC	サマ	増幅	圧増	ライ		オ増	パ回	回	抗回	波出	М	M	M	格一	性	備	考
	社 名	構造	モード	区分	路丨	イク	幅回路	幅	バ	カ	幅	路	路	路	カ	I X	X	I X	覧	図		
2SK322	日 立.	J	D	般	•	A PROPERTY AND A PROPERTY OF THE PARTY OF TH				neth militär kauset und net i 1888.	•								64	190		
" 323	"	"	"	"	•														64	191		
" 324	東芝	MOS	Е	通工									•						64	192		
<i>"</i> 325	"	"	"	"									•						64	193		
<i>"</i> 330	"	J	D	— 般	•									•					66	194		
<i>"</i> 331	三洋	"	"	"		•													66	'83年		
<i>"</i> 332	"	11	11	"	•														66	195	2SK×2	
<i>"</i> 333	"	"	"	"	•														66	196	2SK×2	
<i>"</i> 334	"	"	"	"		•													66	'83年		
<i>"</i> 336	"	MOS	Е	"										•					66	197		
<i>"</i> 337	日電	"	11	通工									•						66	198		
" 3 <b>4</b> 3	日 立.	"	"	般						•			•		•				66	199		
" 344	"	"	11	11						•			•		•				66	199		
" <b>34</b> 5	"	"	11	"						•			•		•				66	200		
" 346	11	"	"	"						•			•		•				66	200		
" 347	"	"	"	"									•		•				66	201		
" 3 <b>4</b> 9	"	"	"	"									•		•				66	202		
<i>"</i> 350	"	"	"	"									•		•				66	202		
<i>"</i> 351	"	"	"	"									•		•				68	203		
<i>"</i> 352	"	"	"	"									•		•				68	204	CONTRACTOR OF THE CONTRACTOR O	
<i>"</i> 353	日電	GaAs	D	"														•	68	205		
<i>"</i> 354	"	"	"	"														•	68	206	Action and action to	
" 354 A	"	"	"	11														•	90	206	gar marker's complete account of a marketine	
<i>"</i> 355	東 芝	MOS	Е	通 工.					1		·		•						68	207	manual designation of the second of the seco	
" 356	"	"	"	"			-						•						68	208		
<i>"</i> 357	"	"	"	11									•						68	209	Control of the Contro	
<i>"</i> 358	"	"	"	"		1							•						68	210	- management and their real who	
" 359	日 立.	"	D+E	般			- Alleganian Janus Artendard					ME although the control for the "Thin do the	***********	and the second square for the	and the same security and	•			68	211		Transfer and
″ 360	"	"	"	"			and the half and any or other tree						*********	Service State on the Color of	-1-4	•			68	211	more successful flow over the first staff of the	e) with the second record of
" 362	東芝	J	D	"	•														68	212	an according to the second to the second of	The Charlest Consistent Martin

				١٨.	ダ高D	7	低	低	周	波	۲	+	S	īſ	髙	v	U	S	委員	(頁)	T	Productivity (Constitution)
	`		用	途	>ŽC	デ	雑		-	I	デ	3	1	変	周	RH	RHFF	RHFF		T	-	
型名				_	入力 ンカイA	コンデンサ・マイク	1. 音增幅回	電圧	ドラ	出	オ	ツラマ	W	抵抗	波	i			規 格	特	備	考
		,			スイA 回じ	マイ	帽回	増	1		増	[0]			出	M I	M I	M		性		
	社名	構造	モード	区分	路丨	ク	路	幅	バ	カ	幅	路	路	路	カ	X	X	X	覧	図		
2SK363	東芝	J	D	般	•									•					68	213		
<i>"</i> 364	"	"	"	"	•									•					68	214		
" 365	"	"	11	"	•									•					68	212		
<i>"</i> 366	"	"	"	"	•	_								•					68	214		
<i>"</i> 367	"	"	"	"	•														68	215		
" 368	"	"	"	"	•														68	215		
<i>"</i> 369	"	"	11	"			•												68	'83年		
" 370	"	"	"	"			•												68	'83年		
<i>"</i> 371	"	"	"	"			•												68	'83年		
″ 372	"	"	11	"	•									•					68	213		
<i>"</i> 373	"	"	11	"	•														68	216		
″ 37 <b>4</b>	松下	"	"	"	•								•						68	179		
<i>"</i> 375	日立	MOS	E	"									•		•				68	217		
<i>"</i> 376	三洋	J	D	"		•													70	218		
" 377	"	"	<i>"</i> .	"		•													70	218		
<i>"</i> 378	松下	GaAs	"	, "													•		70	219		
" 379	"	MOS	Е	"									•						70	220		
″ 380	"	11	"	"									•						70	221		
<b>" 381</b>	三菱	J	D	"				•						•					70	222		
" 382	日 立.	MOS	E	"									•		•				70	223		
<b>"</b> 383	" .	"	"	"									•		•				70	224		
″ 384	"	"	, "	"									•		•				70	225		
" 385	東芝	"	"	通 工									•						70	226		
<i>"</i> 386	"	"	" ,	"									•						70	227		
" 387	"	"	"	"									•						70	. 228		
" 388	"	"	"	"		•							•						70	229	***************************************	
<i>"</i> 389	"	J	D	一般	•		•												70	230	2SK×2	
<i>"</i> 398	日 立	MOS	Е	"									•		•				70	231		
<i>"</i> 399	"	"	"	"									•		•				70	232		
″ 400	- "	"	"	"									•		•				70	233		

Marie S. Marie Common and Anthonis (Common Section Common Section			用	途	ダ高 D	コン	低	低	周	波	Ľ	チ	S	可	高	v	Ü	S	索弓	(頁)		and the second s
型名					入C カ・	コンデンサ・マイク	低雑音増幅回路	電	۴	出	デュ	ョッ	w	変抵	周洪	RHFF	RHFF	R H F F	規	特	/#:	考
2 名					スイA ロンC	サマ	幅	圧増	ライ		オ増	パロ	0	抗回	波出	М	M	M	格	性	備	<b>4</b> 5
	社名	構造	モード	区分	路	イク	路路	幅	バ	カ	幅	路	路	路	カ	X	X	I X	覧	図		
2SK401	日 立.	MOS	Е	般									•		•	<b></b>			72	234		
" 402	"	"	"	"									•	<b> </b>	•				72	235		
" 403	"	"	"	"									•		•				72	235		
" 404	三洋	J	D	"				•											72	236		
" 405	東芝	MOS	E	11						•									72	237		
" 406	日電	GaAs	D	11														•	72	238		
" 407	"	"	11	"														•	72	238		
" 408	日 立.	MOS	Е	11											•				72	239		
" 409	11	"	11	"											•				72	239		
" 410	11	"	11	"											•				72	240		
" 411	11	11	11	11								Con a Grant Con and a Grant Con a Grant Con and a Grant Con and a Grant Con and a Grant Con a Grant Con a Gran	•		•				72	241		
" 412	11	11	. "	11									0		•				72	242		
" 413	, 11	"	"	11									•		•				72	243		
<i>"</i> 414	"	"	"	11									•		•				72	243		
" 415	"	"	"	11									•		•				72	244		
" 416	11	"	"	"									•		•				72	245		
" 417	東 芝	11	11	通 工									•						72	246	A CORPORATION OF THE PARTY OF T	
" 418	"	11	"	"									•						72	247	and property and the second	
" 419	11	11	"	"									•			-			72	248	A CONTRACTOR OF THE PARTY OF TH	
" 420	11	"	"	11															72	249		
" 421	_11	11	"	"									•						72	250	and the second second second second second	
" 422	11	"	11	11									•						72	251	access, James of Added Thinky , Agricultural Translation	
" <b>423</b>	11	11	11	"									•				7,300		72	252		
" 424	日電	"	"	"							-		•						72	253		
" 425	"	J	D	般			•												72	254	The second second	
" 426	"	"	11	11			•			nelv attorne						*****			74	254		
" 427	三洋	"	"	"				•								•			74	255		
" 428	日立	MOS	E	"			TO A NOT THE OWNER.						•		•				74	256	manner transcript with the	a webs marrueria
" 429	"	"	"	"		-				ate A all a Comments		and references to the second	•		•	w		weet 18 information	74	257		n on a common PV mon Source
" <b>4</b> 30	"	"	"	"				er eterography in Trades				ore no see as the	•		•	***********		and a second and a	74	258		Taget School of Colors and

			<del></del> 用	<del></del>	ダ高 D	7.	低	低	周	波	Ľ	+	S	वि	高	V	U	S	索马	(頁)		
			\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	742	ンカ・	デ	低雑音	電	۲	Ж	デ	ョッ	w	変抵	周	RHFF	RHFF	RHFF	規	特		
型名				_	スイA ロンC	サウ	増	圧	ラ		オ	18		抗	波	M	М	M	格	性	備	考
	社 名	構造	モード	区分	四ピ	コンデンサ・マイク	幅回路	増幅	イバ	カ	増幅	四路	路	回路	出力	IX	I	I	覧	X		
2SK431	日立	J	D	- 般	•														74	164		
" 433	三菱	"	"	"			ender hadron or charge, and o	•						•					74	222		and and the Police of the State
" 435	H .V.	"	"	"	•		•												74	259		
" 436	三洋	"	"	"				•								•			74	255		
" 437	松下	GaAs	"	"											man ja maja Militariya a melikada jarah			•	74	260		
″ 437Đ	"	"	11	"														•	90	260		-
<b>" 438</b>	"	"	"	"														•	74	260		-
" <b>43</b> 9	日次	MOS	D+E	"												•			74	211		
" 440	"	"	Е	"									•		•				74	261		-
" 441	"	"	"	"									•		•				74	262		
" 442	東芝	"	"	"						•			•						74	263		
" 443	三洋	J	D	"							•								74	264		
" 444	"	"	"	"							•								74	264		
" 445	"	"	"	"							•								74	264		
" <b>44</b> 6	日電	MOS	E	"									•						74	265		
" 447	東芝	"	11	通 工									•						74	266		
" 448	日電	"	"	"									•						74	267		
" 449	"	"	"	"									•						74	268		
" 453	"	"	"	"															76			
" 454	"	"	"	"											•				76	-		
" 455	東 芝	J	D	一般		•												[1,7]	76	269		
" 456	"	"	"	"		•													76	269		
" <b>4</b> 57	日 並.	GaAs	"	"													•	•	76			
" <b>4</b> 58	日電	MOS	E	通工									•						76	_		
" 459	"	"	"	"									•						76	-		
″ 462	"	"	11	般									•						76			
" 463	"	"	"	通工									•						76			
" 464	"	"	"	"									•						76	_		
" 468	"	"	"	— 般									•						76	_		
ıı 470	. 11	"	"	"									•				,		76	_		

		ter a cargo a compression		t siller halter in destruction of the siller and th	用	途	ダ高 D	コ	低	低	周	波	ピ	チ	s	可	高	v	U	S	索引	(頁)		LICELANIA CANDRAGAMA
					ж	Æ	ᆺᅕᆠ	F	雑辛	僧	k.	ш	1	3		変	1	RH	RH	RH	#1	At:		
Section   Sec	型	名				_	1 7 / 4 1	サ	増			ш	オ	1			波	Ì				i	備	考
Section   Sec				·			回じ	マイ	唱回					回		0		I	I	I				
7 482   7 8 7 8 9 8 9 9 9 9 9 9 9 9 9 9 9 9 9 9			社 名	構造	モード	区分	路丨	ク	路	幅	バ	カ	幅	路	路	路	力	X	X	X	覧	図		
1 492   三後   3	2SK477	•••	日電	MOS	Е	通工									•						78			
1 493			"	"	11			notice and the second second			~~!~				•						78			
N				J	D	般				•						•					78	155		
# 505 目記 n n n n n n n n n n n n n n n n n n	" 493		三洋	"	"	"							•								78	270		
## 507		-	日立	"	"	"	•		•													259	Annah ara an an an an an an an an an an an an an	-
# 508			日電	"	"	"	•	and the second spile of					•								80	271		
1	<i>"</i> 507		"	"	"	11	•						•							-	80	271		
# 512	<i>"</i> 508	-	"	"	11	11	•						•								80	271		
1	<i>"</i> 511		日立	MOS	Е	"									•		•				80	272		
1	<i>"</i> 512		"	"	"	"									•						80	273		
1	<i>"</i> 513		"	11	"	"									•		•				80	274		
N   520	<i>"</i> 518		日電	J	D	"										•			-		80	275		
1   525   東芝 MOS   E	<i>"</i> 519		"	"	"	"										•					80	275		
n 526       n n n n n n n n n n n n n n n n n n n	<i>"</i> 520		"	"	"	"										•					80	275		
1 527	<i>"</i> 525		東芝	MOS	E	通 工.									•						80			
## 528	<i>"</i> 526		"	"	"	"									•						82	-		
n 529       n n n n n n n n n n n n n n n n n n n	<i>"</i> 527		"	"	"	"									•						82			Econolis of the Wild co. Mill appet
## 530	<i>"</i> 528		"	"	"	"									•						82			
1 531	<i>"</i> 529		"	"	"	"						-			•						82	-		
# 532	<i>"</i> 530		"	"	"	11									•						82	- 1		
# 534 日立 # # # # # # # # # # # # # # # # # #	<i>"</i> 531		"	11	"	11									•						82	-		
# 535	<i>"</i> 532		"	"	"	"									•						82			
# 537     東芝	<i>"</i> 534		日 立.	"	"	般									•						82	276	- Inc. of the State of the Stat	
# 538     #	<i>"</i> 535		"	"	"	"									•			Annualis ha hard			82	277	the god and delig Special operations	
# 538     # 1	<i>"</i> 537		東芝	"	"	通 丁.									•						82	-	بمناه المقاوليات الدامة المستجوم	
n 539     n n n n n n n n n n n n n n n n n n n	<i>"</i> 538		"	_ "	"	"				and the same of the same of the		rakomo an Arekalikuske sak	*****		•						82	-	الإنجاز والمتاركة والمتارك	
" 572	<i>"</i> 539		"	"	"	11									•						-			
" 573	" 572		"	"	"	般									•	Care Cities of State of	region parties are re-	***************************************				Service de Light Spanners de la constante de l	and the transfer to proper the second section of	POTTON STREET, TO
	<i>"</i> 573		"	"					- Andrews College Co.	**************************************				-	•								t Windowsky, "Indianal team opposition of the second	Andrew Street Street Street
	2N4392		日電	J	D	通 工			ALI FALLER IN MERCHAN			والتومي لمستحمل		•	•						42	'83年	etanisti dinastan ilina di sensa	de anno la la la la la la la la la la la la la

			<del></del> 用	<del></del>	ダ高 D	7.	低	低	周	波	Ľ	+	s	可	髙	V	U	S	索引	(頁)		
			<u> </u>	~~	ン人C カ・	コンデンサ・マイク	雑音増	電	۴	出	デ	3 "	w	変抵	周	R H F F	RH FF	R H F F	規	特		
型名					スイA ロンC	サラ	増幅	圧	ラ		オー	14	回	抗	波山	M	М	М	格	性	備	考
	社名	構造	モード	区分	路し	イク	幅回路	増幅	イバ	カ	増幅	四路	路	路	出力	I X	I X	I X	覧			
2N4393	日電	J	D	通工								•	•						42	'83年		
3SK 14	"	·MOS	D+E	"	•							•							92	'82年		
″ 20⊕	日立	"	11	"	•														92	'83年		
<i>"</i> 21⊕	"	"	"	"								•							92	'83年		
" 22	東芝	J	D	般												•			92			
" 28	"	"	"	通 工	•		•				•				-	•			92	'83年		-
" 29	日電	MOS	D+E	"	•							•						-	92	'83年	,	
" 37	ソニー	"	"	一般												•			96		DG	
″ 38A	東芝	"	Е	通工								•							92	'83年		
<i>"</i> 39	松下	"	D+E	般												•			96	'83年	DG	-
" 39©	"	"	"	通工												•			96		DG	
" 40	日電	"	. 11	一般												•			96	'83年	DG	
" <b>4</b> 5	日立.	"	"	"												•			96	'83年	DG	
" 47	日電	"	11	通工										•		•			96	285	DG	
" 48	ソニー	"	"	般													•		96		DG	
" <b>4</b> 9	松下	"	"	"												•			96	'83年	DG	
" 49NC	"	"	"	"												•			96	_	DG	
" 49©	"	"	"	通工												•			96		DG	
<i>"</i> 51	日 立.	11	"	般												•			96	'83年	DG	
<i>"</i> 53	"	"	"	"													•		96	'83年	DG	
<i>"</i> 59	東芝	"	"	通工												•			96		DG	1-1
<i>"</i> 60	日 立.	"	"	— 般												•			96	286	DG	
" 61	ソニー	"	"	"												•			96		DG	
<i>"</i> 63	東芝	"	"	通工												•			96		DG	
<i>"</i> 66	松下	"	"	一般										-			•		96	-	DG	
<i>"</i> 70	日立	"	"	"													•		96	'83年	DG	
" 71	日電	J	D	"		•													94	287		
" 72	松下	MOS	D+E	"												•			96	'84年	DG	
<i>"</i> 73	東芝	"	"	"												•			96	'83年	DG	
" 74	日電	"	"	"												•			96	'84年	DG	

		en magazini diperiorita di Arrivo di Arrivo	用	·····································	ダ高 D	コ	低	低	周	波	۲	チ	S	可	高	v	U	s	索片	(頁)		**************************************
			ж	Æ	ン入C カ・	デ	低雑音増	電	۴	出	デ	3	w	変	周	RH	RHFF	RHFF	規	特		
型名				_	スイA	コンデンサ・マイク	増幅	圧	- ラ		オ	ツノペ		抵 抗	波	M	M	M	格	性	備	考
					回じ C	マイ	幅回路	増	1	١.	増	回	口	(D)	出	I	I	I		1		
	社 名	構造	モード		路丨	ク	路	幅	バ	カ	幅	路	路	路	カ	X	X	X	覧	図		~
3SK 77	東芝	MOS	D+E	般												•			98	'83年	DG	
" 79	松下	"	"	"													•		98		DG	
<i>"</i> 80	日立	"	"	"					and the second s								•		98	'84年	DG	
<i>"</i> 81	"	"	"	11												•			98	288	DG	
<i>"</i> 82	"	"	11	"													•		98	289	DG	
" 83	"	"	"	"												•			98	'84年	DG	
" 85	"	"	"	11												•			98	'84年	DG	
" 87	日電	"	"	11													•		98	'84年	DG	
" 88	"	"	"	"													•		98	'84年	DG	
<i>"</i> 95	日 立	"	"	"													6		98	'84年	DG	
<i>"</i> 96	"	"	"	"		umuquak sittistiisiisiisi										•			98	290	DG	-
<i>"</i> 97	松下	GaAs	D	"												-	•		98	'84年	DG	
″ 100	"	MOS	D+E	"													•		98	291	DG	
" 101	東芝	"	"	"												•			100	'84年	DG	
" 102	"	"	"	"											~ ************************************		•		100	'84年	DG	to the second discount of the second
" 103	日 立.	"	"	"											a Marine Manada de Provincio		•		100	292	DG	Automorphism and industrial
" 104	"	"	"	"													•		100	293	DG	CONTRACTOR OF STREET
″ 104 V	"	"	"	"												•	and an artist of the second		102		DG	AND AND ADDRESS OF A STATE OF A S
" 107	三洋	"	"	"											AND AND ADDRESS OF THE PARTY OF	•			100	315	DG	(9 1.100 m. a. 10.100 a.m.)
" 108	11	"	Е	"												•			100	294	DG	Allen and Allen the Shallberrath from Washer
" 113	日立	GaAs	D+E	"					****								•		100	295	DG	
" 114	東芝	MOS	"	,,						e e					A Spring and American	•			100	296	DG	PARTICIPATION TO A STATE OF THE
" 115	"	"	"	"										ence for one			•		100	-	DG	
	松下	"	"	"												•			100	297	DG	entre entre
" 121	東芝	GaAs	D	"													•		100	298	DG	and the state of t
" 123	日電	MOS	D+E	"													•		100	299	DG	eter, personalus estate trace.
" 126	東芝	"	"			August des Comme										•			102	300	DG	Contract of the state of the state of the first
" 127	<i>"</i>	,,	,,	"													•		102	301	DG	
" 129	松下	GaAs	D	<i>"</i>							- tr/((, )   p. an- q. r						•		102			
" 131	日電	MOS	-D+E		s. P. Briston or Co. Difference .	and the second													102	302	DG	
101	11 14	MOD	17   17															1	AVE	074	WW.	سنسيده مسيوه مسي

			<del></del> 用	<del></del>	ダ高 D	コン	低	低	周	波	ť	Ŧ	S	可	髙	V	Ü	S	索马	(真)		
					ン人 C カ・	デン	雅音	電	۴	出	デ	ョッ	W	変抵	周	R H F F	R H F F	R H F F	規	特	/#	
型名					スイA ロピ	コンデンサ・マイク	低雑音増幅回	圧増	ライ		オ増	パ回	0	抗回	波出	M	M I	M	格一	性	備	考
	社 名	構造	モード	区分	路丨	イク	路路	幅	パ	カ	幅	路	路	路	カ	X	X	X	覧	図		
3SK132	日電	MOS	D+E	般													•		102	303	DG	
" 13 <b>3</b>	"	"	"	11													•		102	304	DG	A
<i>"</i> 136	日 立	"	"	"												•			102	288	DG	
" 137	"	"	"	"	-8												•		102		DG	
" 138	"	"	11	"													•		102	292	DG	-
" 140	東 芝	GaAs	D	"													•		102	305	DG	
. " 141	松下	"	"	"													•		102			
<i>"</i> 145	東 芝	MOS	D+E	"													•			306	DG	
" 146	"	"	"	"													•		86	306	DG	
<b>" 150</b>	"	"	"	"												•			102	307	DG	
" 15 <b>1</b>	"	"	"	"												•			104	307	DG	
FLC 08ME	富士通	GaAs	D	"														•	86	278		
" 15ME	11	"	"	"														•	86	278		
" 30ME	11	"	"	"														•	86	278		
" 081 WF	"	"	"	"														•	86	279		
" 151WF	"	"	"	"														•	86	279		
" 301MG	"	"	"	"														•	86	279		
FLM3472	"	"	"	"															86			
" 4450	"	"	"	"														•	86	_		
" 5964	"	"	"	"														•	86			. 1
" 6 <b>47</b> 2	"	"	11	- 11														•	88	-		
" 71 <b>7</b> 7	"	"	11	"														•	88	_		
<i>"</i> 7785	"	"	"	"														•	88			
FLS09/ME	"	"	"	"						1 = 1								•	88	280		
" 16/ME	"	"	"	"														•	88	280		
" 31/ME	"	"	"	"														•	88	280		
" 50/ME	"	"	11	"														•	88	280		-
FLX03MB	"	"	"	"														•	88	'84年		
" 06MB	"	"	"	"														•	88	'84年		
" 12MB	"	"	"	"														•	88	'84年		

FSC05FA   富士通   GaAs	用		用 途	ダ高D	コン	低	低	周	波	۲	チ	S	可	高	V	Ü	S	索引	(頁)		
FSC05FA   富士通   GaAs				スカインC スカインC	コンデンサ・マイク	低雑音増幅回路	電圧増	ドライ	出	デオー増	ョッパロ	W	変抵抗尿	周 波 出	RH FF	R H F F	RH FF	規 格 一	特性	備	考
## 06FA ## ## ## ## ## ## ## ## ## ## ## ## ##	モード	社名		路し	イク	路路	幅	パ	カ	幅	路路	路	路路	カ	I X	I X	I X	覧	図		angang and and and and and and and and and and
## 001 FA ## ## ## ## ## ## ## ## ## ## ## ## ##	D	富士通	) 一般														•				
FSX51W/WF	"	11	, ,,														•		_		
## 52W/WF ## ## ## ## ## ## ## ## ## ## ## ## ##	"	* "	, ,,											<u> </u>			•				
## 53W/WF ## ## ## ## ## ## ## ## ## ## ## ## ##	"	"	, ,,														•	88	'84年		
M21F	"	"	, ,,														•	88	'84年		
# 46F ## ## ## ## ## ## ## ## ## ## ## ## ##	"	"	, ,,,														•	88	'84年		
### 1975 ####### 1975 #### 1975 ### 1975 ### 1975 ### 1975 ### 1975 ### 1975 ### 1975 ### 1975 ### 1975 ###	-	松下	- "		•									-					_		
MGF-1100 三菱 GaAs n -1202 n n n n n n n n n n n n n n n n n n	D	"	) "			•	•											40		2SJ×2	
n -1202       n       n         n -1402       n       n         n -1403       n       n         n -1404       n       n         n -1412       n       n         n -1801       n       n         n -1802       n       n         n -2116       n       n         n -2117       n       n         n -2124       n       n         n -2124 F       n       n         n -2148       n       n         n -2148 F       n       n         n -2172       n       n	"	"	, ,,,	•														88	281	2SK×2	
" -1402       " "         " -1403       " "         " -1404       " "         " -1412       " "         " -1801       " "         " -1802       " "         " -2116       " "         " -2124       " "         " -2124 F       " "         " -2124 G       " "         " -2148 F       " "         " -2148 G       " "         " -2172       " "	"	三菱	, ,,													•	•	103	308	DG	
1402	"	"	, ,,														•	88	309		
n -1403       n       n         n -1404       n       n         n -1412       n       n         n -1801       n       n         n -1802       n       n         n -2116       n       n         n -2117       n       n         n -2124       n       n         n -2124F       n       n         n -2124G       n       n         n -2148       n       n         n -2148F       n       n         n -2172       n       n	"	"	, ,,														•	88	310		
"" -1404       "" ""         "" -1412       "" ""         "" -1801       "" ""         "" -1802       "" ""         "" -2116       "" ""         "" -2117       "" ""         "" -2124       "" ""         "" -2124 F       "" ""         "" -2124 G       "" ""         "" -2148       "" ""         "" -2148 G       "" ""         "" -2172       "" ""	"	"	"														•	88	311		
" -1412     " "       " -1801     " "       " -1802     " "       " -2116     " "       " -2117     " "       " -2124     " "       " -2124 F     " "       " -2124 G     " "       " -2148 F     " "       " -2148 G     " "       " -2172     " "	"	"	" "														•	88	312		
n     -1801     n     n       n     -1802     n     n       n     -2116     n     n       n     -2117     n     n       n     -2124     n     n       n     -2124 F     n     n       n     -2124 G     n     n       n     -2148 F     n     n       n     -2148 G     n     n       n     -2172     n     n	"	"	"														•	88	312		
" -1802     " "       " -2116     " "       " -2117     " "       " -2124     " "       " -2124 F     " "       " -2124 G     " "       " -2148     " "       " -2148 F     " "       " -2148 G     " "       " -2172     " "	"	"	"														•	90	313		
n     -2116       n     -2117       n     -2124       n     -2124 F       n     -2124 F       n     -2124 G       n     -2148 F       n     -2148 F       n     -2148 G       n     -2172	"	"	"														•	90	313		
n     -2117     n     n       n     -2124     n     n       n     -2124 F     n     n       n     -2124 G     n     n       n     -2148 B     n     n       n     -2148 F     n     n       n     -2148 G     n     n       n     -2172     n     n	"	"	"														•	90			
" -2124     " "       " -2124 F     " "       " -2124 G     " "       " -2148     " "       " -2148 F     " "       " -2148 G     " "       " -2172     " "	"	"	"														•	90			
n     -2124 F       n     -2124 G       n     -2148       n     -2148 F       n     -2148 G       n     -2172       n     -2172	"	"	"														•	90	314		
n     -2124 G       n     -2148       n     -2148 F       n     -2148 G       n     -2172       n     -2172	"	"	"														•	90	314		
" -2148       " -2148F       " -2148G       " -2172	"	,, ;	11														•	90	314		
n     -2148F       n     -2148G       n     -2172	"	"	"											Administration — A con-			•	90	315	and the state of t	
n -2148G n n n n n n n n n n n n n n n n n n n	"	"	"														•	90	315	saganasi in naman ini kemandan Gillion ander 💯	
" -2172 " "	"	"	"												Alle de la Company		•	90	315		
AND DESCRIPTION OF THE PROPERTY OF THE PERSON OF THE PERSO	"		"												MALE PROPERTY.		•	90	316	The second secon	
" -2205 " " "	"	",	"						A CAMP TO STATE OF THE STATE OF								•	90	316		
" -X34M " "	"														Larry Manager		•	90	316	article and the second of the	e money and
Congression of the Congression o	E											•						94	282	2SK×2モジュ	ール
" 1220B " "	"											•						94	283	2SK×2モジュ	-

			_	用	<del></del>	夕高 D	7,	低	低	周	波	ť	+	s	可	髙	V	Ü	S	索马	(頁)	
				\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	~	ン人C カ・	デン	雑   音	薍	۴	出	デ	ョッ	w	変抵	周	RHFF	R H F F	R H F F	規	特	
型	名					スイA ロピ	コンデンサ・マイク	低雑音增幅回路	圧増	ライ		オ増	八回		抗回	波出	M	M	M	格一	性	備考
		杜名	構。造	モード	区分	路	1	路路	幅	バ	カ	幅	路	路	路	カ	I X	I X	I X	覧	図	
PM4550C		日立	MOS	Е	般									•						94	284	2SK×2モジュー
TX-429D		ソニー	"	"	"													•		94		抵抗ゲート
μΡΛ33Λ		日電	"	"	通工	•							•							94	'82年	3SJ×2
" 34A		"	11	D+E	"	•							•							94	'82年	3SK×2
" 60A		"	J	D.	"	•														90	'83年	2SK×2
" 61A		"	"	"	"	•														90	'83年	2SK×2
" 62C	are year control of	"	"	"	一般												-	•		90	'83年	2SK×2
" 63H	a management and the control	"	11	"	"	•			•											90	'83年	2SK×2
" 68H		11	11.	"	"	•		•	•		-									90	'83年	2SK×2
" 70A		"	"	"	通 工	•														90	'83年	2SK×2
" 71A		11	"	"	"	•														90	'83年	2SK×2
					1														1111			
			4.00											-			-					
												-	-									
																				-		
F-0-1-10-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1				L											L				1			

このページは空白です.



規格一覧表 外形寸法図

Γ								最 大	定札	答(Ta	=25°C)							電	気 的	) 特	性	(Ta	=25°C)					
	#V	名	社	名	用 途	構造	V <sub>GDS</sub>	VDSX	VGSO VGSS*	IG	Pd	T <sub>i</sub>	Icss	max	I	oss (mA	1)	V	GS(0[[]),	V <sub>th</sub> *(V	)		g <sub>m</sub> (m	S) μ*		8	os (mS	
							V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> ** (V)	I <sub>D</sub> *	Pch*	(°C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	In (μA)	min	typ	max	V <sub>DS</sub> (V)	In (mA)	typ	Ω) m
Ī	2SJ11		東	芝	DC,低周波 チョッパ	J	20			-10	100	150	1	10	-0.05	-0.9	-10	0.7	5.0	-10	-0.1	0.1		0.6	-10	IDSS		Γ
ľ	2SJ12		n		11	"	20			-10	100	150	0.1	10	-0.09	-0.9	-10	0.7	5.0	-10	-0.1	0.1		0.6	-10	,,		T
ľ	2SJ13		"		n	"	20			-100	600	150	10	10	-1.0	-12	-10	1.0	6.0	-10	-0.1	1.5		6.0	-10	"		
Ī	2SJ15		富士	通	DC, 低周波	"	18*		15	-10	200	175	50	9	-1.	5typ	-12		6.0	-10	-10	0.2	1.0	3.0	-12	"		
I	2SJ16		"		n.	"	18*		15	-10	200	175	10	9	-1.	5typ	-12		6.0	-10	-10	0.2	1.0	3.0	-12	"		
ľ	2SJ17		ソニ	-	コンデンサ・マイク	"	20*		0.3	0.5	10	85	0.1	0.1	1	so  -0.16	-9					0.2			- 9			1
T	2SJ18		"		低周波電力增幅	J(V)	170*		分類有	(A) -0.55	63W	120	I <sub>DGO</sub> -100μA	V <sub>DG</sub> -100	0.22			7.5	25	-60	-100mA		4 .		-20	-1A	16Ω*	T
	2SJ19	,	В	電	低周波ドライバ	"	140*	-140	30	-20 -100*	800	150	10μΑ	20	-1.8	-48	-5	1)					30*		-10	-10	1.5	1
Ī	2SJ20		,,	1	低周波電力增幅	"	100*	-100	40	-100 -10A*	100W	150	100μΑ	30	-3A	-8A	-5	5.5	16.5	-35	-50mA	2 *	4 *		-10	-1A	10*	
	2SJ22		ソニ	-	コンデンサ・マイク	J	80*		0.5	0.5	50	85	I <sub>DGR</sub> -0.05	V <sub>GD</sub>	-0.3	-0.7	-20					0.2			-20			
	2SJ39		Ξ	菱	低周波	"	50*		50	-10 -20*	150 unit	125*	1	30	-1	-12	-10		6	-10	-10	1.5			-10	Ibss		T
ľ	2SJ40		"	1	低周波電圧増幅 アナログSW	"	50*			-10	300	125*	1	30	-1	-12	-10	0.3	6	-10	-10	1.5	4		-10	,,		T
I	2SJ43		松	下	低周波	"	50			20*	250	125	0.1μΑ	30	-0.5	-12	-10	0.2	3	-10	-10	3	9		-10	"		1
	2SJ44		В	電	低周波・低雑音	"	40*	-40	40	-10 -30*	400	125	1	20	-1	-18	-10	0.2	1.5	-10	-10	7	9		-10	-1		
ſ	2SJ45		11	1	低周波	"	40*	-40	40	-10 -30*	400	125	1	20	-1	-18	-10	0.2	1.5	-10	-10	7	9		-10	-1		1
	2SJ47		B	立	低周波電力增幅	MOS		-100	±14°	-7A*	100W*	150*						0.	-1.5	-10	-100mA	0.6	(S)	1.3	-10	≃-3A		T
Ī	2SJ48		"		"	"		-120	±14°	-7A*	100W*	150°						-0.15	-1.45	-10	-100mA	0.7	(S)	1.4	-10	-3A		T
	2SJ49		"		II.	"		-140	±14°	-7A*	100W*	150°						-0.15	-1.45	-10	- 100mA	0.7	(S)	1.4	-10	-3A		T
	2SJ50		"		"	"	·	-160	±14*	-7A*	100W*	150*						-0.15	-1.45	-10	-100mA	0.7	(S)	1.4	-10	-3A		
	2SJ51		"		低周波・低雑音	J	40*	-40	40*	-10 -200*	800*	125*	10	40	-6	-50	-10	0.2	1.1	-10	-10	33	40		-10	-5	- 10	
	2SJ55		"	1	低周波 <b>電</b> 力增幅	MOS		-180	± 20°	-8A*	125W*	150°						-0.15	-1.45	-10	-100mA	0.7	(S)	1.4				
	2SJ56		,,		"	11		-200	±20°	-8A*	125W*	150*						-0.15	-1.45	-10	-100mA	0.7	(S)	1.4	=+=6			
	2SJ68		n		低周波, 低雑音	J		-40	40*	-10 -30*	300	150°	10	30	-1.6	-12	-10	0.13	1.5	-10	-10	8	12		-10	-3		
	2SJ69		"		"	"		-40	40*	-10 -30*	300	150°	10	30	-2.5	-20	-10	0.13	1.5	-10	-10	18	21		-10	-3		1
ſ	2SJ70		"		"	,,,		-40	40*	-10 -200*	800	150°	10	30	-6	-50	-10	0.13	1.5	-10	-10	35	45		- 10	-5		1

					電	须(	的特	<u> 11:</u>	(Ta=	25°C)							//> bb El	外		
Cis	(pF)			C,,	(pF)			NF (f	=1kHz, l	$R_{R} = 1M\Omega$	(dB)	NF	(f=100	MHz) (	dB)	その他	代替品		44	名
typ	max	$V_{GS}(V)$ $I_D(mA)^{\bullet}$	V <sub>DS</sub> (V)	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	Vos (V)	typ	max	V <sub>DS</sub> (V)	In (mA)	typ	max	Vos (V)	ID (mA)	••	型名	形		
2	4	1	0			City and Associate and Association and Associa	and the state of t	1		-10	Inss							2	2SJ11	
2	4	1	0	The second second second second second	A STATE OF THE STA	-		0.5		-10						A STATE OF THE STA		2	2SJ12	
8	12	1	0					入力换	算雑音電	压 5μVm	ax (VDS	=-10  V	$I_D = -$	1mA, ⊿	f=10~1	$R_{\rm g} = 1 M\Omega$		35	2SJ13	
6		1	0					4		-6	-0.5					A Quantation in transmissed and for all models or comes produced for the company of the company		1	2SJ15	
6		1	0		1			4		-6	-0.5							1	2SJ16	
										Andrew March Control						S/N=52dB		47	2SJ17	
190		15	0					V <sub>ON</sub> =	- 10Vm	ax (I <sub>G</sub> =	-0.2A,	$I_D = -3$	A, t=1	00ms)		2SK60とコンプリメンタリ		45	2SJ18	
								μ=101	min (V <sub>D</sub>	s = -10\	/, I <sub>D</sub> =-	10mA)				2SK69とコンプリメンタリ		41	2SJ19	
710		-100*	-10													2SK70とコンプリメンタリ		42	2SJ20	
																S/N=52dB		48	2SJ22	
20		0	-10	1	<u> </u>			(f=		$R_{g} = 100k$ $  -10$				IDSS	リッ/Ipssス s=50mV	$\pm 0.85 \text{min} \ (V_{DS} = -10 \text{V})$ $\pm 7.85 \text{min} \ (V_{DS} = -10 \text{V})$ $\pm 7.85 \text{max} \ (V_{DS} = -10 \text{V})$		81	2SJ39	
18		0	-10								typ (f=	1kHz, V	$_{DS} = 10$ m $_{DS} = 5$ m/s			2SK381とコンプリメンタリ		151	2SJ40	
22		0	-10	3.6		0*	-10	N			R <sub>s</sub> =100k			<del></del>				80A	2SJ43	
50		0	0	10		0*	-10			NV=20	mVmax (	(指定回路	各による	)	L			53A	2SJ44	
50		0	-10	10		0*	-10			NV=50	mVmax (	( ,	,	)				53A	2SJ45	
900		-5		40		5*			VDS	S(sat) = -	12Vmax	$(I_D = -7)$	7A, V <sub>GD</sub>	=0)		2SK132とコンプリメンタリ		28A	2SJ47	
900		5	-10	40		5*	-10					"				2SK133とコンプリメンタリ		28A	2SJ48	
900		5	-10	40		5*	-10					<i>II</i>				2SK134とコンプリメンタリ		28A	2SJ49	
900		5	-10	40		5*	-10					ıı		-,		2SK135とコンプリメンタリ		28A	2SJ50	
								1	3	(R <sub>g</sub> =	1kΩ)   -5					2SK151とコンプリメンタリ	2SJ70	97	2SJ51	
,000		5	-10	50		5*	-10		V <sub>DS</sub>		12Vmax	$(I_D = -8)$	SA, V <sub>GD</sub>	=0)	L	2SK175とコンプリメンタリ		28A	2SJ55	
,000		5	-10	50		5*	-10				,	"				2SK176とコンプリメンタリ		28A	2SJ56	
32		0	-10	7.5		0*	-10		$V_N = 25$	mVmax						A CONTRACTOR OF THE PROPERTY O		79	2SJ68	
82		0	-10	19		0*	-10		$V_N = 20$	mVmax								79	2SJ69	
150		-5*	-10						$V_N = 10$	mVmax								97	2SJ70	$\exists$

Γ									最 大	. 定 棺	{ (Ta	=25°C)							電	気 的	」 特	性	(Ta=	=25°C)					
	Đ.	名	社名	í	用	途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	VDSX	Vgso Vgss*	I <sub>G</sub>	Pd	T <sub>i</sub>	IGSS	max	In	ss (mA	.)	1	JGS(off),	Vth*(V	)		g <sub>m</sub> (m	S) μ*		g	. (mS	
								V <sub>GDX</sub> ** (V)	Voss*	V <sub>GS</sub> x**	I <sub>D</sub> *	Pch*	Tch* (*C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	Ι <sub>D</sub> (μΑ)	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max
2S	J72		東	ž (1	氏周波,	低雑音	J	25			-10	600	125	1	25	-5	-30	-10	0.3	2	-10	-0.1	(I <sub>DS</sub>	s=-5	mA)	10	IDSS		
2S	J73		"		"		"	25			-10	600 unit	125	1	25	-5	-30	-10	0.3	2.0	-10	-0.1	25	40		-10	"		
2S	J74		"		n		"	25			-10	400	125	1	25	-1	-20	-10	0.15	2.0	-10	-0.1	8	22		-10	"		
2S	J75		"		n		n	25			-10	400 unit	125	1	25	-2.6	-20	-10	0.15	2.0	-10	-0.1	15	22		-10	"		
25	J76		日 3		氏高周波電		MOS		-140	±15*	-500°	30W*	150°						-0. <b>2</b>	-1.5	-10	-10mA	20	35		-20	-10		
2S	J77		"		"		"		-160	±15*	-500*	30W*	150°	-					-0.2	-1.5	-10	-10mA	20	35		-20	-10		
2S	J78		11		n		"		-180	±15*	-500°	30W*	150*						-0.2	-1.5	-10	-10mA	20	35		-20	-10		
2S	J79		"		n		"		-200	±15*	-500°	30W*	150*						-0.2	-1.5	-10	-10mA	20	35		-20	-10		
2S	J81		"	1	氏周波電	力增幅	"		-120	±15*	-7A*	100W*	150*				*		-0.15	-1.45	-10	-100mA	0.7	(S) 1	1.4	-10	-3A		
2S	J82		"		"		"		-140	±15*	-7A*	100W*	150°						-0.15	-1.45	-10	-100mA	0.7	(S) 1	1.4	-10	-3A		
2S	J83		"		"		"		-160	±15*	-7A*	100W*	150*						-0.15	-1.45	-10	-100mA	0.7	(S) 1	1.4	-10	-3A		
2S	J84		松	F i	低周波		J	15			-10, -20	200	125	0.1μΑ	15	-0.5	-12	-10	0.2	3	-10	-10		9		-10	IDSS		
25	J88			1						*																			
2S	J89		-	1								000									*		*						
2S	J90		東	芝 1	低周波,	低雑音	J	30			-10	200 unit	125	10	30	-2.6	- 20	-10	0.2	2.0	-10	-0.1	8 (5	22		-10	IDSS		-
25	J91		"	1	氏周波電 	力增幅	MOS		-140	±8*	-8A*	120W	150*	±1μA	±8				-0.8	-2.4	-10	-100mA	1 (5	1.5	ļ	-10	-2A		
-	J92		"	+	"		"		-140	±8*	-7A	100W	150*	±1μA	±8				-0.8	-2.4	-10	-100mA	1	1.5		-10	-2A		-
-	5J93			+																			1-		-				
-	J94		-	+	-		-	1												-					-				
-	3J95		-		低高周波電	力増幅	Mos																	(S)		10	0.4		
-	SJ96	-	日:	¥ ;	高速度電	カSW	MOS		-60	±20*	-8A*	100W*	150*	± 1μΑ	± 20				-0.2	-1.5	-10	- 10mA	1	(S) 1.6	2.5	-10	-3A		-
-	3J97		-	+		····												,			-								-
-	5J98		-	.	低高周波電	力增幅	Mac	-				100777					(		-	-				(S)			4.4		-
-	5J99		B .		高速度電	カSW			-140°	±20*		100W*	150*	±1μA	± 20		-1	-120	-2	-5	-10	-lmA	1	1.8 (S)		-10	-4A		-
25	SJ100		"		"		"		-160°	± 20*	-8A*	100W*	150*	±1μA	±20		-1	-140	-2	-5	-10	-1mA	1	1.8		-10	-4A		

					電	気	的特	性	(Ta=	25°C)									1	外		
Cis	(pF)			C,,	(pF)			NF (f	=1kHz,	$R_g = 1M\Omega$	a) (dB)	N	F (f=10	OMHz) (	dB)	+ o	)	他	代替品		<b>7</b> 9	名
typ	max	$V_{GS}(V)$ $I_{D}(mA)^{\bullet}$	V <sub>DS</sub> (V)	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)				型名	形		
185		0	-10	55		10	$l_D=0$	$(R_{R} = 1)$	100Ω) 2	-10	-5	NF=1	0dBmax	$\begin{pmatrix} V_{DS} = - \\ R_g = 10 \end{pmatrix}$	-10V, I 0Ω, f=	D=−5mA) 2SK147とコ	ンプリメ	ンタリ		74A	2SJ72	
185		0	-10	55		10	$I_D = 0$	1	2	(R <sub>g</sub> =	=100Ω)   —5		$\Delta V_{GS} = 2$	0mVmax	1	2SK146とコンプリメ	<b>ノタリ</b>			98	2SJ73	
105		0	-10	32		10	$I_D = 0$	0.5	2		=1kΩ)   -1					2SK170とコンプリメン	ノタリ	ik. Maran na Papanini Palika kan da ining da panini		90	2SJ74	
105		0	-10	32		10	$I_D=0$	0.5	2		=1kΩ)   -1		△V <sub>GS</sub> =2	0mVmax		2SK240とコンプリメン	/タリ			99	2SJ75	
120		-10*	-10	4.8		-10mA	-10		Vos	· • • · · · · · · · · · · · · · · · · ·	2Vmax (	$I_D = -10$	mA, V <sub>G</sub>	o=0)		2SK213とコンプリメン	クリ			116A	2SJ76	
120		-10*	-10	4.8		10mA	-10					"				2SK214とコンプリメン	クリ			116A	2SJ77	
120		-10*	-10	4.8		-10mA	-10					"			in maj (i magay), p <b>atrio</b> il pagagay (m)	2SK215とコンプリメン	タリ			116A	2SJ78	
120		-10*	-10	4.8		-10mA	10					"				2SK216とコンプリメン	タリ			116A	2SJ79	
900		5	-10	40		5*	-10		Vus	((sat) = -	12Vmax	$(I_D = -$	7A, V <sub>GD</sub>	=0)		2SK225とコンプリメン	タリ			117A	2SJ81	
900		5	-10	40		5*	-10					"				2SK226とコンプリメン	タリ			117A	2SJ82	
900		5	-10	40		5*	-10					n				2SK227とコンプリメン	タリ			117A	2SJ83	
22		0	-10																	103A	2SJ84	
																					2SJ88	
		_																			2SJ89	
95		0	-10	29		10			2	$(R_g = -10)$									2SJ109	75	2SJ90	
1,500		0	-10	90		0*	-10		CD	s=460pl	Ftyp (V	os = -10	V, V <sub>G</sub> s=	=0)					2SJ115	118	2SJ91	
1,500		0	-10	90		0*	-10					"							2SJ115	119	2SJ92	
																					2SJ93	
																					2SJ94	
																8			-8		2SJ95	
850		5	-10						VDS(O)	$N_0 = -4V$	max (ID	=-5A,	V <sub>GS</sub> == -	·15V)		2SK286とコンプリメン	タリ			117A	2SJ96	
																					2SJ97	
																					2SJ98	
1,050		0	-10	80		0*	-10		VDS(O)	$c_0 = -2V$	max (I <sub>D</sub>	=-4A	V <sub>GS</sub> = -	15V)		2SK343とコンプリメン	タリ	*	D.	117B	2SJ99	
1,050		0	-10	80		0*.	-10				,	,				2SK344とコンプリメン	タリ			117B	2SJ100	7

<u> </u>		Ī		ſ		最 大	定析	咨 (Ta	=25°C)							電	気 的	勺 特	性	(Ta	=25°C)					
型	名	社名	用途	構造	V <sub>GDS</sub>	V <sub>DSX</sub>	VGSO VGSS*	I <sub>G</sub>	Pd	Ti	Icss	max	Iı	ss (mA	<b>(</b> )	,	VGS(off),	Vth*(V	7)		g <sub>m</sub> (m	S) μ*		g	.s (mS	
					VGDX** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> **	ID*	Pch*	Tch* (*C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	Ι <sub>D</sub> (μΑ)	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	r <sub>D</sub> * typ	max
2SJ101		日立	低高周波電力増幅 高速度電力 SW	MOS		-40°	±20*	-5A*	30W*	150*	±1μA	± 20		-1	-30	-2	-5	-10	-1mA	0.5	(S) 1		-10	-3A		
2SJ102	;	"	"	"		-60*	±20*	-5A*	30W*	150°	±1μA	±20		-1	-50	-2	-5	-10	-1mA	0.5	(S) 1		-10	-3A		
2SJ103	}	東芝	低周波, アナログSW	J	50			-10	300	125	1	30	-1.2	-14	-10	0.3	6	-10	-0.1	1	4		-10	IDSS		
2SJ104		"	"	"	25			-10	400	125	1	25	-2.6	-20	-10	0.2	2	-10	-0.1	(I <sub>D</sub> :	ss=-5	mĄ) 	-10	"		
2SJ105		"	"	"	50			-10	200	125	1	30	-1.2	-14	-10	0.3	6	-10	-0.1	1	4		-10	"		
2SJ106	1	"	"	"	50			-10	150	125	1	30	-1.2	-14	-10	0.3	6	-10	-0.1	1	4		-10	"		
2SJ107	•	"	"	"	25			-10	200	125	1	25	-2.6	-20	-10	0.2	2	-10	-0.1	(I <sub>D</sub> :	ss = -5	mA)	-10	"		
2SJ108		"	低周波, 低雑音	"	25			10	200	125	1	25	-2.6	-20	-10	0.15	2	-10	-0.1	8	22	<u>L</u>	-10	. "		
2SJ109	)	"	"	"	30			-10	200	125	1	30	-2.6	20	-10	0.2	2	-10	-0.1	8	$ss = -3$ $\begin{vmatrix} 22 \end{vmatrix}$	L	-10	"		
2SJ110	1	"	低周波増幅 アナログSW	"	25			-10	400	125	1	25	-5	-30	10	0.3	2	-10	-0.1	25	s = -1		-10	"		
2SJ111		"	低周波, 低雑音	"	25			-10	400	125	1	25	-5	-30	-10	0.3	2	-10	-0.1	30	s = -5	mA)	-10	"		
2SJ112		日立	高速度電力 SW 高周波電力増幅	MOS		-100°	±20*	-10A*	100W*	150*	±1μA	±20		-1	-80	-2	-5	-10	-1mA	1.5	(S) 2		-10	-5A		
2SJ113		"	"	"		-100°	± 20*	-10A*	100W*	150*	±1μA	±20		-1	-80	-2	5	-10	-1mA	1.5	(S) 2		-10	-5A	ļ	
2SJ114		"	"	"		200*	± 20°	-8A*	100W*	150°	±1μA	± 20		-1	-160	-2	-5	-10	-1mA	1	(S) 1.8		-10	-4A		
2SJ115		東芝	低周波電力增幅	"		-160*	±20°	-8A*	100W	150	±1	±20				-0.8	-2.8	-10	100mA	1	(S) 2		-10	-2A		
2SJ116		日立	高速度電力 SW 高周波電力増幅	"		-400°	± 20*	-8A*	125W*	150*	± 1μA	±20		-1	-320	-2	5	-10	-1mA	1	(S) 1.6		- 20	-4A		
2SJ117		"	"	"		-400*	± 20°	-2A*	40W*	150*	± 1μA	± 20		-1	-320	-2	-5	-10	-1mA	0.4	(S) 0.7		-20	-1A		
2SJ118		"	"	"		-140°	±20°	-8A*	100W*	150*	±1μA	± 20		-1	-120	-2	-5	-10	-1mA	1	(S) 1.8		-10	-4A		
2SJ119		"	. 11	"		-160°	± 20°	-8A*	100W*	150*	±1μA	± 20		-1	-140	-2	-5	-10	-1mA	1	(S) 1.8		-10	-4A		
2SJ120		"	"	"		-40°	± 20°	-2A*	10W*	150*	±1μA	± 20		-1	- 35	-1	-4	-10	-1mA	0.1	(S) 0.25		-10	-1A		
2SJ121			de Mantida 1. Zero						pana , saas no philosophy		F 4100 - WT-800 (1470 to 1770										(8)		and the second second		ann aga anthreisean	- management or follower from the
2SJ122		H .Ý.	高速度電力SW高周波電力増幅	MOS		-60*	± 20°	-10A*	50W*	150*	±1μΑ	± 20		-1	-50	-2	-5	-10	-1mA	1.5	(S) 2.2 (S)		-10	-5A		
2SJ123		東芝	低周波電力増幅  高速SW	"		-70°	± 20°	-10A*	30W	150	±1	± 20		-1	<b>-70</b>	-1	-3	-5	-1mA	1	1.7		<b>-5</b>	-2A		
2SJ124			11 The No. 400 at . Last 227			- Taget - Wayner Aland	aan laan da ka aa aa	ga Nguna memebaskatan																	,	
2SJ125	helicana antika	三菱	低周波電力増幅  アナログSW	J	50*			-10	150	125*	1	30	-1	-12	-10	0.3	6	-10	-10	1.5	4		-10	Ipss	المحصف مست	L

					T)	<b>%</b> ( )	的 特	Μ: (Ta = 25°C)	//s bb //	外	
Cis	(pF)			C,.	(pF)			NF $(f=1kHz, R_g=1M\Omega)$ $(dB)$ NF $(f=100MHz)$ $(dB)$ そ の 他	代替品		型名
typ	max	V <sub>GS</sub> (V) I <sub>D</sub> (mA)*	V <sub>DS</sub> (V)	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	型名	形	
660		0	-10	140		0 *	-10	$V_{DS(ON)} = -1.2 V_{max} (I_D = -3A, V_{GS} = -15V)$ 2SK345 $\varepsilon = -2 V_{max}$		116B	2SJ101
660		0	-10	140		0 *	-10	" 2SK346とコンプリメンタリ		116B	2SJ102
18		0	-10	3.6		10	$I_D = 0$	$R_{DS(ON)} = 270\Omega \text{ typ } (V_{DS} = -10 \text{mV}, V_{GS} = 0, I_{DSS} = -5 \text{mA})$ 2SK246 $\varepsilon$ 3 $\varepsilon$ 3 $\varepsilon$ 7 $\varepsilon$ 9 $\varepsilon$ 9 $\varepsilon$ 10		82B	2SJ103
105		0	-10	32		10	$I_D = 0$	$R_{DS(ON)}$ = 40 $\Omega$ typ ( " ) 2SK364 $\varepsilon$ $\exists$ $z$ $z$ $z$ $z$		82C	2SJ104
18		0	-10	3.6		10	$I_D=0$	R <sub>DS(ON)</sub> =270Ω typ ( " ) 2SK330とコンプリメンタリ		70A	2SJ105
18		0	-10	3.6		10	$I_D = 0$	$R_{DS(ON)}=270\Omega$ typ ( " )		105A	2SJ106
105		0	-10	32		10	$I_D = 0$	$R_{DS(ON)}=40\Omega \text{ typ }($ " ) $2SK366 \text{ $\angle 3$} \text{$\angle 7$} \text{$ } \text$		70B	2SJ107
105		0	-10	32		10	$I_D = 0$	$(f=10Hz, R_g=1k\Omega)$ 1   10   -10 -1   2SK370とコンプリメンタリ		70B	2SJ108
95		0	-10	25		10	$I_D = 0$	$(f=10Hz, R_f=1kΩ)$ 1.5   11   -10   -1		148	2SJ109
185		0	-10	55		10	$I_D = 0$	$R_{DS(ON)}=20Q \text{ typ } (V_{DS}=10 \text{mV}, V_{GS}=0, I_{DSS}=-15 \text{mA})$ 2SK363 $\geq 2 \times 7 \text{ J} \times 9 \text{ J}$		82C	2SJ110
185		0	-10	55		10	$I_D = 0$	$(R_g=100\Omega)$ 1   2   -10   -5   2SK369 \(\text{2}\) \(\text{2}\)\(\text{7}\) \(\text{7}\)		82C	2SJ111
1,100		0	-10	90		0.	-10	$V_{DS(ON)} = -1.75 V_{max} (I_D = -5A, V_{CS} = -15V)$ 2SK398とコンプリメンタリ		28B	2SJ112
1,100		0	-10	90		0.	-10	" 2SK399とコンプリメンタリ		149	2SJ113
1,000		0	-10	70		0.	-10	$V_{DS(ON)} = -3.2 V_{max} (I_D = -4V, V_{CS} = -15V)$ 2SK400 $E = -2 V_{max} V_{DS(ON)} = -3.2		149	2SJ114
800		0	-10	110		0 *	-10	$V_{DS(ON)} = -7V_{max} (I_D = -5A, V_{GS} = -10V)$ 2SK405とコンプリメンタリ		119	2SJ115
1,400		0	-10	25		0 •	-10	$V_{DS(ON)} = -9V_{max} (I_D = -4A, V_{GS} = -15V)$ 2SK298とコンプリメンタリ		28B	2SJ116
520		0	-10	15		0 *	-10	$V_{DS(ON)} = -7V_{max}$ ( $I_D = -1A$ , $V_{GS} = -15V$ ) 2SK310とコンプリメンタリ		116B	2SJ117
1,050		0	-10	80		0 •	-10	$V_{DS(ON)} = -2V_{max} (I_D = -4A, V_{GS} = -15V)$ 2SK413とコンプリメンタリ		149	2SJ118
1,050		0	-10	80		0.	-10	" 2SK414とコンプリメンタリ		149	2SJ119
150		0	-10	25		0.	-10	$V_{DS(ON)} = -1.5 V_{max} (I_D = -1A, V_{GS} = -15V)$ 2SK416 $E = -1.5 V_{max} (I_D $		150	2SJ120
											2SJ121
1,200		0	-10	170		0 *	-10	$V_{DS(ON)} = -1V_{max} (I_D = -5A, V_{GS} = -15V)$ 2SK428とコンプリメンタリ		116B	2SJ122
650	~~~	0	-10	250		0 *	-10	$V_{DS(ON)} = -2.8V_{max} (I_D = -7A, V_{GS} = -15V)$ 2SK442とコンプリメンタリ		138	2SJ123
											2SJ124
18		0	-10					$R_{DS(ON)}=220Q \text{ typ } \begin{pmatrix} f=1 \text{kHz}, & V_{DS}=10 \text{mVrms} \\ V_{GS}=0, & I_{DSS}=5 \text{mA} \end{pmatrix}$		152	2SJ125

			T		T	Ī	最大	定 柞	咨 (Ta	=25°C)					-		電	気 自	勺 特	性	(Ta	=25°C)					
<i>5</i> 9	名	社名	用	途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	V <sub>DSX</sub>	V <sub>GSO</sub> V <sub>GSS</sub> *	IG	Pd	T <sub>i</sub>	Icss	max	I	oss (m <i>l</i>	<b>A</b> )	,	VGS(off),	V <sub>th</sub> *(\	7)		gm (m	S) μ*		8	gos (mS	(Ω)
						V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> ** (V)	I <sub>D</sub> *	Pch*	Tch* (*C)	(nA) (pA)*	V <sub>G</sub> s (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	I <sub>D</sub> (μA)	min	typ	max	V <sub>DS</sub> (V)	ID (mA)	typ	max
2SJ126		東芝	DC-DC	コンバータ	MOS		-60 <b>*</b>		-10A*	40W							-1.5	7 <sub>th</sub> )   -3.5		-1mA		(S) 2.5		-10	-5A		
2SJ127																											
2SJ128																											
2SJ129																											
2SJ130										100																	
2SJ131																											
2SJ132																											
2SJ133										-																	
2SJ134																											
2SJ135																											
2SJ136																											
2SJ137																											
2SJ138																											
2SJ139																											
2SJ140																											
2SJ141																					No. 20 and the Spinster, the spinster, which we shall not be a spin of the spi						
2SJ142																									Samuel Company of the		
2SJ143								annium and adversed to																			
2SJ144				Carrier (A. A. Carrier (A. A. Carrier (A.	punco-sir pi - sprinnistan								- m. m. man and the second														
2SJ49®		日立	高速度	電力SW	MOS		-140	±14*	-7A*	100W •	150*		and the second of the	and the form of the life			-0.15	-1.45	10	-100mA	0.7	(S) 1	1.4				
2SJ50⊕		"		"	"	ACRES 0 11 FE	-160	±14*	-7A*	100W*	150*						-0.15	-1.45	-10	-100mA	0.7	(S) 1	1.4				
2SJ56⊕		11	高周波 高速度	電力増幅 電力 SW	"		<b>∸200</b>	± 20°	-8A*	125W*	150*			er woman water new	-3	-160	-0.55	-3	-10	- 100mA	0.7	(S) 1	1.4	-10	-3A	Name of State (St	
2SJ77®		"	The second of the second of	11	"		-160	±15*	- 500°	30W*	150*			samples (			-0.2	-1.5	-10	-10mA	20	35		- 20	-10		-
2SJ79®		"		"	"		200	± 15*	-500°	30W*	150*						-0.2	-1.5	-10	10mA	20	35		-20	-10	Carrier was	and the second second
M46F		松下	低周波		J	30	-30		-30*	250	125				- 20	-10						8		10	loss		

	and the second				Æ	Ж	的特	÷ 11:	(Ta=	= <b>25</b> *C)		e de como de la Constitución de la Constitución de la Constitución de la Constitución de la Constitución de la						外		7
Cii	(pF)			Crs	(pF)	~		NF (f	=1kHz,	$R_{R} = 1M\Omega$	1) (dB)	NF	(f=100	MHz) (	dB)	そ の 他	代替品		型名	
typ	max	V <sub>GS</sub> (V) I <sub>D</sub> (mA)	V <sub>DS</sub> (V)	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub>	typ	max	V <sub>DS</sub> (V)	ID (mA)	typ	max	V <sub>DS</sub> (V)	In (mA)		型名	析		
	antiquità con Mississian de	- And Sur- 111-60-11-12			T	and the control of the second			Rosco		max (ID	=-5A,	$V_{GS} = -$						2SJ126	
and the same and a	Andrews (indicense of 172 - 187						The state of the s	and the property of the second											2SJ127	1
										e de la constitución de la const	e gander smak-minus — mellinderssorrin f	enterente de Vanantena							2SJ128	1
									Particular con Albertage P		American seasons official	ar Britain o Anaile Maeir Freigh (Me	and the second s						2SJ129	1
										**************	La Marie Mar		eritaer distribution and en distribution				and the second s		2SJ130	1
											alemanda (Sause and Alemand Anna Anna Anna Anna Anna Anna Anna A	and the second of the second of the second	e namel de cale d'année en d'establisse						2SJ131	1
										-				per committe de l'establica de l'internation de l'establica de l'e					2SJ132	
			Manager (Same Hole of Control										The state of the s	-				1	2SJ133	
												andre affect to a series and the discussion of	Auto-Provident Provident	norma a Publication de la Constantina					2SJ134	1
							h-p							and a state was about the					2SJ135	
					***************************************														2SJ136	
																			2SJ137	1
																			2SJ138	1
																			2SJ139	1
																			2SJ140	1
																and an all control to the section of			2SJ141	
																			2SJ142	1
		the state that he shall be																	2SJ143	1
																			2SJ144	1
900		5	-10	40		5 *	-10		Vos	(sat) = -1	12Vmax (	$I_D = -7$	A, V <sub>GD</sub> =	=0)		2SK134⑪とコンプリメンタリ		28A	2SJ49®	٦,
900		5	-10	40		5 *	10				"	Andrew Marketon (d. 1984). 19	\$-1.00 Person Pe			2SK135母とコンプリメンタリ		28A	2SJ50∰	١,
1,200		5	-10	60		5			VDS(O	N) = -6V	max (I <sub>D</sub> =	=-4A,	$V_{GS} = -$	15V)				28A	2SJ56∰	
120		-10*	-10	4.8		-10mA	-10		VDS	sat)=-2	Vmax (ID	=-10m	A, V <sub>GD</sub>	=0)				116A	2SJ77®	1
120		-10°	-10	4.8		-10mA	-10				"		a					116A	2SJ79®	
	-							2.5		(R <sub>g</sub> =	1kΩ)	T				M47Fとコンプリメンタリ			M46F	1

Γ		-					最 大	定 1	참 (Ta	=25°C)							電	気 自	り 特	15.	(Ta	=25°C	)		,		
	型名	1	社 名	用 途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	Vosx	V <sub>GSO</sub> V <sub>GSS</sub> *	I <sub>G</sub>	Pd Pch*	T <sub>j</sub>	IGSS	max	I	oss (m <i>l</i>	<b>A</b> )	'	las(off),	Vth*(V	)		gm (m	nS) μ*			gos (mS	( <b>Q</b> )
1						V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> **	$I_D^*$ $(mA)$	(mW)	(,C)	(nA) (pA)*	V <sub>G</sub> s (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	I <sub>D</sub> (μA)	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max
2	N4392	E	電	SW, チョッパ	J	-40*	40	-40	50	300	200	-100*	-20	(パル) 25	ス測定)   75	20	-2	-5	20	1nA							
2	N4393		11	"	,,	-40°	40	-40	50	300	200	-100	-20	(パル)	ス測定)	20	-0.5	-3	20	1nA							
2	SK11	¥	芝	DC, 低周波 チョッパ	"	-20			10	100	150	-1	-10	0.3	6.5	10	-0.5	-6.0	10	0.1	0.7		3.2	10	IDSS		
2	SK12	T	"	"	"	- 20			10	100	150	-0.1	-10	0.45	5.0	10	-0.65	-4.5	10	0.1	0.8		3.2	10	"		
2	SK13	1	"	DC, 低周波 チョッパ	"	-12	-		10	100	150	-0.1	-10	0.45	5.0	10	-0.65	-4.5	10	0.1	0.8		3.2	10	"		
2	SK15		11	DC, 低周波,低雑音	"	-20			10	100	150	-0.1	-10	0.45	5.0	10	-0.65	-5.0	10	0.1	0.8		3.2	10	"		
2	SK16®	E	立	直1十	"			-20*	10,10*	100*	150*	-1	-6	0.5	7.0	6	-0.5	-5.0	6	0.1	1	3	6	6	"		
. 2	SK17	¥	泛芝	1	"	-20			10	100	125	-1	-10	0.3	6.5	10	-0.5	-6.0	10	0.1	0.7	2.0		10	"		
2	SK18	T	li	DC	"	-40			10	200	150	I <sub>G</sub> -0.1	V <sub>DS</sub> = 10V I <sub>D</sub> = 0.4mA	0.45	2.8	10	-0.65	-3.5	10	0.1	0.8		3	10	"		
2	SK18A	T	"	li .	"	40			10	200	150	I <sub>G</sub> -0.1	V <sub>DS</sub> = 10V I <sub>D</sub> = 0.4mA	0.45	2.8	10	-0.65	-3.5	10	0.1	0.8		3	10	"		
. 2	SK19TM	T	"	FM, VHF	"	-18*	AND THE PARTY OF T		10	200	125	-10	-1	3	24	10	-1.2		10	1		7		10	"		
	SK23A-8 SK23A-9	1,	·=-	DC, VHF	"	-27°		-9	10, 20*	250	100	-10	-6	2.7	12.1	10	-0.45	-3.85	10	30	2.7			10	"		MHz) 05
2	SK24	E	洋	低周波 AM/RF	"	-40	40*	-40	10	100	125	-10	-10	0.6	24	10		-6	10	10	1.5		12	10	"		
2	SK25	T	"	FM, RF, MIX	"	-18	18*	-18	10	100	125	-100	-10	0.6	24	10		-7.2	10	10		6		10	"		
2	SK30	耳	芝	低周波	"	-50			10	100	125	-1	-30	0.3	6.5	10	-0.4	-5.0	10	0.1	1.5			10	"		
2	SK30ATM	T	"	低周波、低雑音	"	-50			10	100	125	-1	-30	0.3	6.5	10	-0.4	-5.0	10	0.1	1.2			10	"		
2	SK33	E		FM, VHF	"	-20*			10	150	125*	-100	-1	2.5	20	10	-1	-8	10	10	4.5	7		10	"		
2	SK34	1	n	低周波, 低雑音	,,	-50°			10	150	125*	-10	- 10	0.3	12	10	-0.3	-6.0	10	10	1.0	3		10	"	0.01	
2	SK37	H	T	FM, RF/MIX	"	-20*		-15	10,20*	100	125*	-10	-10	0.5	6	5	-0.3	-4.5	5	10	1.5	2		5	0.5		
2	SK38	Ξ	菱	堙感知器,DC	MOS		20	±10	20*	100	100*	-1*	-10	0.4	.5	10		-9	10	10	0.5	0.8		10	1	0.01	
2	SK38A		"	- "	"		20	±10	20*	100	100*	-1*	-10	0.1	7	10		-5	10	10	1	1.5		10	1	0.02	
2	SK39	1	=-	エレクトレット マイクロフォン	J	-20°						-0.25	-0.1	(I <sub>D</sub> 0.035		9					0.09		0.55	9			order Name on
2	SK39A		"	コンデンサ・マイク	"	-20*		-0.5	0.5,1*	10	85	-0.25	0.1	(I <sub>D</sub> 0.048		9					0.11		0.67	9	Fra ng apadasananni Mer		
2	SK40	E	Ý.	低周波, 低雑音	"	-50		<b>−50</b> *	10	100*	150*	-10	- 30	0.6	6.5	15	-0.4	-5.0	15	0.1	1			15			
2	SK41	E	洋	FM, RF/MIX	"	-18			10	200	125	-10	-1	0.6	24	10			10	10		7		10	Inss		

					U	须(	的特	ř 11:	( Ta =	25°C)							/b #6 F1	外	
Ci.	(pF)			C <sub>r</sub> ,	(pF)			NF (f	= 1kHz, 1	$R_{\epsilon} = 1M\Omega$	(dB)	NF	f (f=100	MHz) (	dB)	そ の 他	代替品型名		型名
typ	max	$V_{GS}(V)$ $I_{D}(mA)^{\bullet}$	V <sub>DS</sub> (V)	typ	max	$V_{GB}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	Vos (V)	I <sub>D</sub> (mA)	typ	max	V <sub>DS</sub> (V)	In (mA)		型名	形	
9	14	0	20	2.7	3.5	-7*	0		ro	s(ON) = 6	)Ω max	$(V_{GS}=0,$	I <sub>D</sub> =6m	A)				73	2N4392
10	14	0	20	3	3.5	-5*	0		rp	s(ON) == 10	0Ω max	$(V_{GS}=0$	, I <sub>D</sub> =1n	nA)				73	2N4393
3	5	-10	0															2	2SK11
3	5	-10	0						3	10	0.45							2	2SK12
2.3	3.5	-10	0						2	10	0.45						2SK12	2	2SK13
3	5	-10	0			,		(R <sub>6</sub> =	10kΩ)   3	10	0.45			Vnci	<sub>P, P)</sub> =4μ\	$V_{\text{max}} \begin{pmatrix} V_{\text{DS}} = 5V, & I_{\text{D}} = 0.45\text{mA} \\ R_{\text{g}} = 10\text{k}\Omega, & \Delta f = 5 \sim 50\text{Hz} \end{pmatrix}$		2	2SK15
9	-	-1	6	2		-6	0	0.15μ	V/√Hz	6	0.5					$R_{ON} = 350 \Omega \text{ typ } (V_{DS} = 0.1 \text{V}, V_{GS} = 0)$		3	2SK16⊕
4	6	0	0	1.2	2.0	-10	- 0	1		10	IDSS						2SK30ATM	7	2SK17
4.5	6	V <sub>GD</sub>	=0	2.0	2.5	-10	0	⊿IVG	sı – V <sub>GS</sub>	2 / <b>/</b> Ta=	100µV/*	C max (	$V_{DS} = 10^{\circ}$ $T_a = 0 \sim 6$	$I_D = 2$	$00\mu$ A)			19	2SK18
4.5	6			2	2.5	-10	0	⊿IVa	sı-V <sub>GS</sub>	2 / <b>/</b> Ta=	20μV/°C		$V_{DS} = 10^{\circ}$ $T_a = 0 \sim 6$					19	2SK18A
4	,	0	0	0.45	0.65	-10						2.0	3.5	10 (V <sub>DD</sub> )		PG=20dB typ (f=100MHz)	2SK192A	82A	2SK19TM
5		0	10	1.8		0.	10	13nV,	/√Hz	10	IDSS	2		10	IDSS	PG=18dB typ (f=100MHz)		5	2SK23A-8 2SK23A-9
7.4			10	2.0			10	1	2.5	10			N	F=10dB	max (f=	=30Hz, $R_g = 1M\Omega$ , $V_{DS} = 10V$ )	2SK44SP	6	2SK24
				1.1		0.	10					2.5		10	3	PG=21dB typ (f=100MHz)	2SK41NP	6	2SK25
8.2		0	0	2.6		-10	0	(f=1201 0.5	Hz, R <sub>s</sub> =	=100kΩ)   15	I <sub>DSS</sub>						2SK30ATM	7	2SK30
8.2		0	0	2.6		-10	0		Hz, R <sub>z</sub> =	=100kΩ)   15	IDSS			*				82B	2SK30ATM
				0.5		0*	10					2.5		10	Inss	PG=20dB typ (f=100MHz)		153A	2SK33
8		0	10	1.5		0.	10	(f=1001 3.0	Hz, R <sub>g</sub> =	=100kΩ) 10	0.1							153B	2SK34
				1	1.5	0.	5											10	2SK37
6		0	0																2SK38
8		0	0															11	2SK38A
	******************																	12	2SK39
									L	L	S/N	=50dB	min (VDS	=9V, C	Cin = 100p	$_{\rm oF}$ , $V_{\rm in}$ =-60dBS, $f$ =1kHz)	2SK93	12	2SK39A
6.7		0	15	1.6		0.	15	(f=	120Hz, 5	R <sub>s</sub> =100	cΩ)   I <sub>DSS</sub>							13	2SK40
				0.35	0.75	0.	10	-	<u> </u>	- 10	-200		3.5	10	3	PG=22dB typ (2SK41NPを名称変更したため同型名) (t=100MHz) (で旧タイプのものがある、45ページ参照)		57A	2SK41

					T	最大	定	皆 (Ta	=25°C)	-	<u> </u>					電	気 自	勺 特	i 14:	(Ta	=25°C)					
	型名	社名	用 途	構造	V <sub>GDS</sub>	VDSX	V <sub>GSO</sub> V <sub>GSS</sub> *	Ic	Pd	Τ̈́i	Icss	max	I	DSS (m/	<b>A</b> )		VGS(off),	Vth*(	V)		g <sub>m</sub> (m	S) μ*			gos (mS	
					V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> ** (V)	ID*	Pch*	Tch*	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)		min	typ	max	V <sub>DS</sub> (V)	ID (mA)	typ	(Ω) max
*	(旧)2SK41	三章	⊭ FM, RF/MIX	J	-18*			10	150	125	-10	-1	0.6	24	10			10	10		7		10	IDSS		
	2SK42	ソニー	FM/AM, RF	"	-10*	10		10 (I <sub>S</sub> )	50	65			1	5	4	-0.3		4	100	3.5	5.5		4	"		
	2SK43	"	低周波, 低雑音	,,	-30*		-30	5,20*	300	100*	-1	-15	0.9	14.3	10	-0.18	-1.49	10	30	6.3			10	"		
	2SK43\$	"	DC, 低周波	"	-30*		-30	5,20*	300	100	-0.1	-15	0.9	14.3	10	-0.18	-1.49	10	30	6.3			10	,,		
	2SK43\$-D	"	DC, アナログSW	"	-30*		-30	5,20*	300	100	-0.1	-15	8.1	14.3	10	-0.72	-1.49	10	30	14			10	"		
	2SK44	三泽	牟 低周波,低雑音	,,	-20	20*		10	100	125	-1	-10	0.06	3	10		-4	10	1	0.6	2		10	"		
*	(旧)2SK44	"	低周波, 低雑音	,,	-20	20*		10	100	125	-1	-3	0.06	3	10		-4	10	1	0.6	2		10	11		
*	2SK45	日省	DC, 高周波	"	-22*	20	-22	10,20*	100	150	-10	-10	0.5	6	5	-0.3	-4.5	5	10	1.5	2		5	0.5		
	2SK46	三	ゼ コンデンサ・マイク	"	-30*			10	150	125	10	-10	0.3	3	10	-0.3	-5	10	10	1	3		10	IDSS	0.01	
*	2SK47	日電	【低周波・髙周波	"	-20*		-15	10,20*	200	125	-10	-10	0.5	6	5	-0.3	-4.5	5	10	1.5	2		5	0.5		
	2SK48	東き	低周波, 低雑音	"	-20			10	100	150	-0.1	-10	0.3	3	10	-0.35	-2.3	10	0.1	1		5	10	Inss		
	2SK49	日旬	FM, RF	"	-20*			10,10*	72 (60°C)	80	-50	-0.5	0.5	6	5		-2.5	5	10	1.9	5.5		5	"		
*	2SK50	松了	ーエレクトレット コンデンサ・マイク	"	-10*	10		2,2*	20	80			0.07 (R <sub>L</sub> =	1.0 2.2kΩ)	4.5					0.35 (Ri	=2.2kg	Ω)	4.5	(V <sub>GS</sub> )		
	2SK54	日立	VHF, RF/MIX	"	-15*			10	150*	125*	-10	-0.5	0.8	5	10	-0.3	-5.5	10	10	3	6		10	Inss		
	2SK55	"	"	"	-18*			10	150*	125*	-10	-0.5	3	14	10	-0.3	-5.5	10	10	3	8		10	"		
*	2SK56	松丁	VHF, RF	"	-10	10		10,10*	100	125	-0.5μA	-1	0.7	10	5		-4	5	10		4		5	"		
	2SK57	日賞	高周波増幅	"	-20*		-15	10,20*	100	125	-10	-10	0.5	6	5	-0.3	-4	5	10	1.5	2		5	0.5		
- 1	2SK58		DC, VHF		-27*		<b>-9</b>	10,20*	270	100	-10	-6	1	16.5	10	-0.45	-4.95	10	30	2.7			10	Ibss		
H	2SK59	日 立	コンデンサ・マイク	"	-30		- 30°	10 (A)*	50	125*	-1 I <sub>DGO</sub>	-10 V <sub>DG</sub>	0.3	1.4	10	-0.4	-5	10	0.1	1			10	"		
ŀ	2SK60		低周波電力增幅	J(V)	- 170°		分類有	0.5, 5	63W	120	100μΑ	100	- The Control State of State on the Control State of Stat		***************************************	-7.5	- 25	60	100mA		4 •		20	1A	16Ω*	
ŀ	2SK61-LV		FM, VHF	J	-18*			10	200	125	-10	-0.5	1	6	10	-0.4	-4	10	1		9		10	Ipss		
ŀ	2SK63		小信号電圧増幅	J(V)	-120°		-10	200*	470	120	- 200	-6	$(R_S=2)$	.2kΩ)			-9.5	100	300	(R <sub>S</sub> =2	2kΩ)		50	V <sub>GS</sub>	0.5	
ŀ		松下	ダンス変換	J	-12*	12		2,2*	20	80			0.04	0.8	4.5					0.3	0.5		4.5	0	a managaran da alam d	
ŀ	2SK66	II At	低周波,低雑音	"	-55*			10	100	125	-100	-30	0.3	6.5	10	-0.4	-5	10	0.1	1.2			10	IDSS		
L	2SK67	日電	コンデンサ・マイク	"	-20*	20		10,10*	80	100			0.02	1			-0.8	5	1		1.5		5	"		

					Æ	気	的特	产性	(Ta=	25°C)								外		1
Cia	(pF)			C,,	(pF)			NF (f	=1kHz,	$R_g = 1M\Omega$	a) (dB)	NF	f (f=10	OMHz) (	dB)	そ の 他	代替品		型名	
typ	max	$V_{GS}(V) = I_{D}(mA)^*$	V <sub>DS</sub>	typ	max	V <sub>GD</sub> (V) V <sub>GS</sub> (V)*	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)		型名	形		
				0.35	0.75	0 *	10						3.5	10	3	PG=22dB typ (f=100MHz)	2SK41	14	(旧)2SK41	*
				0.085	0.12		4						2.5	4	IDSS	PG=12dB min (f=100MHz)		15	2SK42	
13		0	10	2.4		0.	10	13nV	/√Hz		10kΩ)   I <sub>DSS</sub>							16	2SK43	
13		0	10	2.4		0.	10	13n V,	/√Hz	(R <sub>g</sub> =	10kΩ)   I <sub>DSS</sub>							16	2SK43®	
13		0	10	2.4		0.	10	13n V	/√Hz	(R <sub>g</sub> =	10kΩ)   I <sub>DSS</sub>			A STATE OF THE STA		$R_{ON}=80\Omega \text{ max } (V_{DS}=0.1V, V_{GS}=0)$		16	2SK43\$-D	1
			AND RESERVED AND ASSESSMENT													(2SK44SPを名称変更したため同型名で) 旧タイプのものがある。		58A	2SK44	1
-																	2SK44	28	(旧)2SK44	*
4	5.5	0	5	1	1.5	0.	5	(f=1 1.5	MHz)	5	0.5							30	2SK45	*
8		0	10	1.5		0.	10	(f=100	Hz, R <sub>s</sub> =	=100kΩ) 10	0.1							20	2SK46	1
4.5		0	5	1.5	2	0.	5											18	2SK47	*
5	8	-10	0					(f=120 0.5	Hz, R <sub>s</sub> =	=100kΩ)   10	0.45			V <sub>N(P,</sub>	$p_0 = 4 \mu Vr$	$\max \left( \begin{array}{c} V_{DS} = 5V,  I_{D} = 0.45 \text{mA} \\ R_{g} = 10 \text{k}\Omega,  \Delta f = 5 \sim 50 \text{Hz} \end{array} \right)$		2	2SK48	1
5	6.5	0	5	0.07	0.25	0.	5					3.5	6	5	I <sub>DSS</sub>	PG=18dB typ (f=100MHz)		40	2SK49	1
÷			. A MARINE MARINE AND THE TAX A PROPERTY AND					V <sub>N</sub> =	4μVmax	(V <sub>DS</sub> =	4.5V, R	L=2.2k	Ω, C <sub>0</sub> =	7oF)			2SK65	80D	2SK50	*
3		0	10	0.4	0.6	0*	10					2.0	3.5	10 (V <sub>DD</sub> )		PG=15dB typ (f=100MHz)		37A	2SK54	1
3		0	10	0.4	0.6	0.	10					2.0	3.5	10 (V <sub>DD</sub> )		PG=18dB typ (f=100MHz)		37A	2SK55	
4		0	5	0.1		0.	5						4.5	5	1	PG=12dB min (f=100MHz)	2SK83	80D	2SK56	*
									maile that the second and the second	ar randominatorios de Personaldo	A Mirarilla Austriana (Mirarilla Austriana)	krok disserse desembradismister de Process							2SK57	1
				2		0.	10			⊿V <sub>GS</sub> =	100mVm	x (V <sub>DS</sub> =	=10, I <sub>D</sub> =	1mA)				49	2SK58	
								(f=120I 0.5	Hz, R <sub>g</sub> =	100kΩ) 10	I <sub>DSS</sub>							50	2SK59	*
190		-15	0								0.2A, l	<sub>D</sub> =3A,	t=100m	s)		2SJ18とコンプリメンタリ		45	2SK60	İ
				0.1	0.25	-5						2.5	3.5	(V <sub>DD</sub> )		PG=18dB typ (f=100MHz)		82A	2SK61-LV	
16		4	50					(f=10H	$R_g = 30$	500kΩ) 50	4		L	$\mu = 15$	min 30tyr	o (V <sub>DS</sub> =50V, I <sub>D</sub> =40mA)		51	2SK63	
								NV = 4			.5V, Rs	$=2.2k\Omega$	, C <sub>G</sub> =1	0pF)				- 52	2SK65	
8.2		0	0	2.6		-10	0	(f=120F 0.5	Iz, R <sub>g</sub> =	100kΩ) 15								80D	2SK66	
5.5		0	5					<u> </u>			F typ (	$V_{DS} = 5V$	, V <sub>GS</sub> =(	 ))				60	2SK67	

I				1			最大	定析	各(Ta=	=25°C)							電	気 的	) 特	性	(Ta	=25°C)					
	型名	;	社 名	用途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	V <sub>DSX</sub>	VGSO VGSS*	IG	Pd Pch*	Ti Tch*	Icss	max	Iı	oss (mA	<b>A</b> )	'	/GS(off),	V <sub>th</sub> *(V	)		g <sub>m</sub> (m	S) μ*		g	os (mS	
						V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	Vcsx** (V)	I <sub>D</sub> *	(mW)	(°C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	Ι <sub>D</sub> (μΑ)	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	r <sub>D</sub> * typ	max
	2SK67A		日電	エレクトレットコンデンサ・マイク	J	-20 <b>*</b>	20		10,10*	80	100			0.02	0.54	5		-0.8	5	1		1.5		5	IDSS		
ı	2SK68		"	低周波	"	-50°		-50	10,20*	250	125	-1	20	0.5	12	10	-0.13	-1.5	10	10	4	12		10	"		
	2SK68A		"	低周波,低雑音	"	-50°		-50	10,20*	250	125	-1	- 20	0.5	12	10	-0.13	-1.5	10	10	4	12		10	"		
*	2SK69		"	低周波ドライバ	J(V)	-140*	140	-30	20,100*	800	150	10μA	-20	1.8	48	5						30*		10	10	1.5	
*	2SK70		11	低周波電力增幅	"	-100°	100	-40	100 10A*	100W	150	−100µA	-30	3A	8A	5	-5.5	-16.5	35	50mA	2 *	4 *		10	1A	6 <b>*</b>	
Ī	2SK72		東芝	DC	J	- 20			10	200	150	I <sub>G</sub> -0.1	$V_{DS}=10V$ $I_D=0.4mA$	0.6	6.5	10	-0.5	-3.3	10	0.1	1.5		6.5	10	I <sub>DSS</sub>		
	2SK73	7	公 下	低周波(高電圧)	"	-200*	50		100*	5W	150				100	30					8			30	"		
	2SK79		ソニー	小信号電圧増幅	J(V)	-120°		-10	20,200*	750	120	200	-6					-9.5	100	300		14		50	4	0.5	
	2SK83	1	松 下	VHF/RF	J	-25*	23		15, 15*	100	150	-50	-1	0.5	12	5		-3.	5	10	1.9	4		5	IDSS		
	2SK84		"	低周波, 低雑音	"	-55*			10	100	125	-100	-30	0.3	6.5	10	-0.4	5	10	0.1	1.2			10	"		
	2SK85		日電	X バンド 低雑音増幅・発振	GaAs SB	-10*	5		100*	500	125			30	100	3	-1.5		3	100					fosc		
*	2SK87⊕		日立.	低周波,低雑音	J	-50		<b>−50</b> *	10	100*	150*	-10	-30	0.3	6.5	15	-0.4	-5	15	0.1	1			15	IDSS(m	nax)=5	(typ) .5GHz
	2SK88																										
*	2SK89	ا	立	低周波電力增幅										1730 W 100 M 100 M 100 M													
	2SK90		***************************************	-																							
	2SK91	_ -																									
	2SK92	- 1	3 電	エレクトレットコンデンサ・マイク	J	-20*	20		10,10*	80	100			0.02	1			-0.8	5	1		1.5		5	IDSS(m	ax)=5	(typ) 5GHz
ŀ	2SK93	`	ノニー	II FELSE	"	-20°		-0.5	0.5	10	85	-0.25	-0.1	(I <sub>DS</sub>   0.018		9					0.11		0.67	9			
-	2SK94	- -	3 電	低周波, アナログSW	"	-50°	50	-50	10,20*	150	125	-5	-20	0.5	12	10	-0.13	-1.5	10	10	4	12		10	loss		
F	2SK95	_									v Biomero NA art vij Frig																of Mary (1980) As Million or the
ŀ	2SK96																		innella salas indication di salas	ndrej elkikosi karantiko eril			- Milliand and the same of the same of the same of the same of the same of the same of the same of the same of	* ******		-	and the second s
+	2SK97	- :	/ニー	DC, 低周波	J	-30*		-30	5,20*	210	100*	-1	-15	0.9	14.3	10	-0.18	-1.49	10	30	6.3			10	loss		and the second
-	2SK98			Barthari - water art and and an own and the garden and agreement and a				- all Turner, heads, and			and the second second	mare are assisted			reliadioness, where the	and the second	man in mass of the la										
-	2SK99			SE SENT OF SET OF SERVICES OF SET OF SERVICES OF SET OF SE			e majorie un e se s	-																			
Ľ	2SK100																										

					電	3( )	的特	÷ 11:	( Ta =	=25°C)							代替品	外		
Cis	(pF)			Crs	( <b>pF</b> )			NF (f	=1kHz,	$R_{R} = 1M\Omega$	1) (dB)	NF	(f=100	MHz) (	dB)	その他	型名		型多	.
typ	max	$V_{GS}(V)$ $I_{D}(mA)^{\bullet}$	V <sub>DS</sub> (V)	typ	max	$V_{GB}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	ID (mA)	typ	max	V <sub>DS</sub> (V)	ID (mA)		76 61	形		_
5.5		0	5						(	$C_{\rm os} = 2.7$	pF typ(	$V_{DS} = 5V$	, V <sub>GS</sub> = (	<b>)</b> )				60	2SK67A	_
13		0	10	2.6		0.	10											53A	2SK68	
13		0	10	2.6		0.	10	(R <sub>g</sub> =	=1kΩ)   1.5	10	IDSS					NF=5dB typ $\begin{pmatrix} V_{DS}=10V, & V_{GS}=0 \\ R_g=1k\Omega, & f=10Hz \end{pmatrix}$		53A	2SK68A	
								μ=10m	in(V <sub>DS</sub> =	=10V, I <sub>D</sub> =	=10mA)					2SJ19とコンプリメンタリ		41	2SK69	,
430	CONTRACTOR OF THE PERSON	100*	10													2SJ20とコンプリメンタリ	2SK389	42	2SK70	_];
	9	-10	0					(f=120 0.5	Hz, R <sub>s</sub> =	=100kΩ)   10	0.45		⊿VGs	=10mV	max (VD	$I_D = 10V$ , $I_D = 0.05$ , 0.2, 0.4mA)		43	2SK72	
					and rights of the product of the pro													54	2SK73	
16		4 *	50					(f=10l	Iz, R <sub>s</sub> =	=500kΩ)   50	4			$\mu = 1$	5min 30t	yp ( $V_{DS} = 50V$ , $I_{D} = 4mA$ )		55	2SK79	
4		0	5	0.07	0.15	0.	5					-	3.5	5	1	PG=12dB min (f=100MHz)		80B	2SK83	
8.2		0	0	2.6		-10	0	(f=120	Hz, Rg	=100Ω)   15								52	2SK84	
												(f=8	GHz) 4.5	3	10	MAG=11dB typ (f=8GHz)		56	2SK85	1
7.2		0	15	2.1		0.	15	(f=120	Hz, R <sub>s</sub> =	100kΩ)	IDSS							61	2SK87⊕	١,
																			2SK88	
																			2SK89	,
																A COMMITTED AND A COMMITTED AND AND AND AND AND AND AND AND AND AN			2SK90	
																			2SK91	1
5.5		0	5					Cos=	2.7pF t	yp (V <sub>DS</sub> =	=5V, V	cs=0)						18	2SK92	1
								S/N=	50dB mi	in (V <sub>DS</sub> =	=9V, Cg	=100pF,	1kHz,	V <sub>1N</sub> =-	60dB)			62	2SK93	1
13		0	10	2.6		0*	10											78	2SK94	1
																			2SK95	1
																			2SK96	1
				2.4			10											49	2SK97	1
				= , •			-												2SK98	1
																			2SK99	1
																			2SK100	1

ſ		Τ			V 2 2000 20 0000.0		最 大	定 柞	答(Ta	=25°C)							電	気 自	5 特	性	(Ta	=25°C)					
١	型名	社	上名	用 途	構造	$\begin{matrix} V_{\text{GDS}} \\ V_{\text{GDO}} \end{matrix}^*$	Vosx	V <sub>GSO</sub> V <sub>GSS</sub> *	I <sub>G</sub>	Pd Pch*	T <sub>j</sub> T <sub>ch</sub> *	IGSS (nA)	max	I	oss (m <i>l</i>	<b>A</b> )	,	VGS(off),	V <sub>th</sub> *(\	/)		g <sub>m</sub> (m	S) μ*		g	os (mS	
						V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> ** (V)	(mA)	(mW)	(*C)	(pA)*	V <sub>G</sub> s (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	$I_{D}$ $(\mu A)$	min	typ	max	V <sub>DS</sub>	ID (mA)	typ	max
I	2SK101		***************************************																								
I	2SK102																										
I	2SK103	B	電	エレクトレット コンデンサ・マイク	J	-20*	20		10,10*	80	100			0.02	1		-	-0.8	5	1		1.5		5	IDSS		
	2SK104		"	髙周波, 低周波	"	-30*		-30	10,20*	250	125	-10	-30	0.5	12	5	-0.25	-4.5	5	10	1.5	4.1		5	"		
	2SK105		"	低周波	11	- 50 <b>*</b>	50	-50	10,20*	250	125	-1	-30	0.5	12	5	-0.25	-4.5	5	10	1.5	2.1		5	0.5		
*	2SK106	В	立	低周波,低雑音	"			-50 <b>*</b>	10,20*	300*	125*	-10	-30	0.5	12	10	-0.13	-1.5	10	10	4.5	13		10	IDSS		
Ī	2SK107	7	=-	DC, VHF	"	-27*		-9	10,20*	250	100	-10	-6	2.7	12.1	10	-0.45	-3.85	10	30	2.7			10	"		
Ī	2SK108	Ξ	菱	低周波, 低雑音 アナログSW	"	-50 <b>*</b>		50	10,20*	300	125*	-1	-30	1	12	10		-3	10	10	6	15		10	"		
*	2SK109		"	低周波,低雑音	"	50*		-50	10,20*	150 unit	125*	-1	-30	1	12	10		-3	10	10	6	12		10	"	0.01	
l	2SK110		"	"	"	-30*		-30	10,50*	900	125*	-1	-20	2.5	35	5		-2	5	10	35	45		5	5		
l	2SK111		"	"	"	<b>−30</b> *		-30	10,50*	200 unit	125*	-1	-20	2.5	35	5		-2	5	10	35	45		5	5		
Ī	2SK112	東	芝	DC,低雑音 チョッパSW	"	50			10	250	150	-0.1	-30	1.2	9	15	-0.25	-1.2	15	0.1	7		34	15	IDSS		
	2SK113		"	アナログSW チョッパSW	"	-50			10	250	150	-0.1	-20	5	150	20	-0.3	10	20	0.1							
Ī	2SK114																										
	2SK115	T		hand though the all groups in a day of the state of the s																							
	2SK116																										
Ī	2SK117	東	芝	低周波, 低雑音	J	-50			10	300	125	-1	-30	1.2	14	10	-0.2	-1.5	10	0.1	4	15		10	Inss		
	2SK118		"	コンデンサ・マイク	"	-50			10	100	125	-1	-30	0.3	6.5	10	-0.4	-5.0	10	0.1	1.2			10	"		
Ī	2SK119	El	T	DC, アナログSW	"	-30*	30	-30	10,20*	250	150	-0.1	- 20	0.5	12	10	-0.2	-4.5	10	10	1.0	4.2		10	"		
	2SK120	7	=-	VHF, RF, MIX	"	-15*		and court of the state of	10*	200	85			1	5.	4	-0.3		4	100	3.5	5.5	-	4	"		
	2SK121	1	"	DC,低雑音 SW	"	-30*		-50	5,20*	300	100	-1	-15	0.9	14.3	10	-0.18	-1.49	10	30	6.3			10	"		
	2SK122										M																
	2SK123	松	下	エレクトレットコンデンサ・マイク	J	-20*	20		2.2*	200	100			0.13	0.47	4.5					0.9	1.6		4.5	Ipss		
	2SK124	B	電	X バンド 低雑音増幅・発振	GaAs SB	-8*	5		100*	500	125	***************************************	and the second	30	100	3	-1	-	3	100							
	2SK125	ソ	=-	UHF, RF, MIX	J	- 25*		- 25	10,100*	500*	120 *	- 10	-15	30	75	10	- 2	-6	10	100	10	14		10	10		

					7E	Ж	的特	M:	(Ta=	25°C)							代替品	外	
Cis	(pF)			Cr	(pF)			NF (f	=1kHz,	$R_g = 1M\Omega$	(dB)	NF	(f=100	MHz) (	dB)	その他			型名
typ	max	$\begin{bmatrix} V_{GS}(V) \\ I_D(mA)^* \end{bmatrix}$	V <sub>DS</sub>	typ	max	$V_{GB}(V)$ $V_{GS}(V)$	Vos (V)	typ	max	V <sub>DS</sub> (V)	In (mA)	typ	max	V <sub>DS</sub> (V)	In (mA)	AND THE RESIDENCE OF THE PARTY	型名	形	
																			2SK101
																	-		2SK102
5.5	A A CONTRACTOR OF THE PARTY OF	0	5					Cos=	=2.7pF t	yp (V <sub>DS</sub> =	=5V, Vo	s=0)				The state of the s		63	2SK103
4.1	6	0	10	0.9	1.3	0.	10											40	2SK104
4.1	6.0	0	10	0.9	1.3	0 *	10											53A	2SK105
									V <sub>N</sub> =	= 130dB	max					2SK106Aも廃止	2SK186	79	2SK106
5		0	10	1.8			10	(R <sub>g</sub> =	10kΩ)	10	IDSS	2		10	IDSS	PG=18dB typ (f=100MHz)		62	2SK107
20		0	10						=100Hz,   2.5	R <sub>g</sub> =1k	Ω)					$R_{DS(ON)} = 70Q \text{ typ} \begin{pmatrix} f = 1 \text{kHz}, & V_{GS} = 10 \text{mVrms} \\ V_{GS} = 0, & I_{DSS} = 5 \text{mA} \end{pmatrix}$		153B	2SK108
20		0	10						0Hz, Rg=	=10kΩ)   10	1			△VGS	== 50mVm	$_{\text{max}} (V_{\text{DS}} = 10V, I_{\text{D}} = 1 \text{mA})$		84	2SK109
55		5*	5					1	(R <sub>g</sub> =	100Ω)   5	5					$R_{DS(ON)}=18\Omega \text{ typ } \begin{pmatrix} f=1\text{kHz}, & V_{DS}=10\text{mVrms} \\ V_{GS}=0, & I_{DSS}=10\text{mA} \end{pmatrix}$		154	2SK110
55	41	5 *	5					1 (	$R_g = 100$	Ω)	5			△Vcs	= 30mVm	$I_{\text{DS}} = 5V,  I_{\text{D}} = 5\text{mA})$		84	2SK111
12		0	15	3		0.	15	(R <sub>g</sub> =	=1kΩ)	15	1					NF=10dB max $\begin{pmatrix} V_{DS}=15V, I_{D}=1mA \\ f=10Hz, R_g=1k\Omega \end{pmatrix}$		69	2SK112
10	14	0	20	3	5		0		<u> </u>							$R_{DS(ON)}=100\Omega$ max $(V_{GS}=0, I_{D}=1$ mA)		69	2SK113
																			2SK114
																			2SK115
																			2SK116
13		0	10	3		-10	$I_D = 0$	(R <sub>g</sub> =	=1kΩ)	10	0.5					NF=10dB max $\begin{pmatrix} V_{DS}=10V, I_D=0.5mA \\ R_g=1k\Omega, f=10Hz \end{pmatrix}$		82C	2SK117
8.2		0	10		2.6	-10	$I_D=0$		)Hz, R <sub>g</sub> =	100kΩ)	IDSS					1		70A	2SK118
4.8	6.0	0	10	1.2	1.5	0 *	10	0.5	- <u></u>	10								71	2SK119
4.6		0	4	0.14	0.17		4					1.9	2.5	4	Ipss	PG=16dB typ (f=100MHz)		64	2SK120
13		0	10	2.4		0 *	10	0.1	$R_g = 10k$	Ω)   10	I <sub>DSS</sub>							62	2SK121
								0.1		10									2SK122
													NV	=4μVm	$ax (V_D =$	$=4.5V$ , $R_L=2.2kΩ$ , $C_0=10pF$ )		131	2SK123
		ll	c) max=	=80GHz	typ							(f=1	2GHz)	3	10	MAG=11dB typ (f=12GHz)		56	2SK124
				2.6	3	-10			<del> </del>				ト接地)	10 (V <sub>DG</sub> )	10	PG=12.5dB typ ゲート接地 (f=100MHz)		72	2SK125

					\	最大	·	各 (Ta	=25°C)	r	ļ		1			電	気 白	<b>9</b> *	+ 性	(Ta	=25°C)			r		
型名	3	社 名	用 途	構造	V <sub>GDS</sub> *	V <sub>DSX</sub> V <sub>DSS</sub> *	V <sub>GSO</sub> V <sub>GSS</sub> *	I <sub>G</sub>	Pd Pch*	T <sub>j</sub>	Icss (nA)	max	I	oss (mA	1)	'	/GS(off),	V <sub>th</sub> *(\	7)		g <sub>m</sub> (m	S) μ*		8	gos (mS	(Ω)
	_				V <sub>GDX</sub> **	(V)	V <sub>GSX</sub> **	(mA)	(mW)	(°C)	(pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	In (μA)	min	typ	max	V <sub>DS</sub> (V)	ID (mA)	typ	ma
2SK126																					<u> </u>					
2SK127	1	2 下	低周波	J	-50 <b>*</b>		-50	20*	250	125			0.5	12	10					3			10	IDSS		
2SK128	1	"	低周波, 低雑音	"	-30*	30	-30	10, 20*	250	125	-100	-30	0.5	12	10	-0.1	-1.5	10	10	4	12		10	"		
2SK129																										
2SK130		3 電	低周波, アナログSW	J	-30*	30	-30	10,50*	250	125	-1	-20	5	30	5		-1.5	5	10	28			5	IDSS		
2SK131		"	低周波, 低雑音	"	-30*	30	-30	10,50*	250 unit	125	-1	20	5	30	5		-1.5	5	10	28	32		5	5		
2SK132	I	立	低周波電力增幅	MOS		100	±14*	7A*	100W*	150*						0	1.5	10	100mA	0.6	(S)	1.3	10	3A		
2SK133		"	ıı ıı	"		120	±14*	7A*	100W*	150*						0.15*	1.45*	10	100mA	0.7	(S)	1.4	10	3A		
2SK134		"	11	"		140	±14*	7A*	100W*	150*						0.15*	1.45*	10	100mA	0.7	(S) 1	1.4	10	3A		
2SK135		"	"	11		160	±14°	7A*	100W*	150°						0.15*	1.45*	10	100mA	0.7	(S)	1.4	10	3A		
2SK136	ŧ.	2 下	低周波,低雑音	J	-30*	30	-30	10, 20*	250	125	-100	- 20	0.5	20	10	-0.1	-2	10	10	5	21		10	Ipss		
2SK137 2SK137A		"	"	11	-15*	15		50*	100	125				40	5						80		5	Inss		
2SK138	E	電	Xバンド、 RF、OSC	GaAs SB		5	-10	100*	300	125*	-1μΑ	-5	30	100	3	-1.5		3	100	15	27		3	10		
2SK139												- 20														
2SK140	E	電	Xバンド、 RF、OSC	GaAs SB		5	-8	100*	300	125	- 10µA	-5	30	100	3	-1.0		3	100	20	35		3	10		
2SK141 2SK141A		"	DC, アナログSW	J	-30*	30	-30	10,20*	250	150	-100° -5°	-20	0.5	12	10	-0.2	-4.5	10	10	1.0	4.2		10	Inss		
2SK142																									on the second	
2SK143																										
2SK144																										
2SK145												and the second second					******			44,						
2SK146	東	芝	低周波, 低雑音	J	-40			10	600 unit	125	-1	-30	5	30	10	-0.3	-1.2	10	0.1	(I <sub>DSS</sub> =	=5mA)		10	5	and an arrange of the second s	eur .une. Midreu r 1894
2SK147		"	n,	"	-40			10	600	125	-1	-30	5	30	10	-0.3	-1.2	10	0.1	(I <sub>DSS</sub> = 30			10	Ibss		
2SK148	松	: 下	VHF, RF	"	-25	23		10,10*	100	125				12	5					1.9			5	"		
2SK149	В	電	UHF, RF, MIX	"	-20*		-10	10,35*	350	150	- 50	-8	8	32	10	-0.35	-2.2	10	10		30		10	"		- Linear I
2SK150	東	芝	低周波, 低雑音	,,	-50			10	200 unit	125	-1	- 30	1	14	10	-0.3	-2	10	0.1	5	12		10	3		

				annadi yakan ili ili ili ili ili ili ili ili ili il	U	沉	的特	11:	( Ta =	25°C)							代替品	外		٦
Cis	(pF)			C.	(pF)			NF (f	== 1kHz, 1	$R_{\rm g} = 1M\Omega$	(dB)	NF	F (f=100	MHz) (	(dB)	その他			型名	3
typ	max	$V_{GS}(V)$ $I_{D}(mA)^{\bullet}$	V <sub>DS</sub>	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	In (mA)	typ	max	Vos (V)	ID (mA)		型名	形		
																			2SK126	
9		0	10	2		-3*	10		NV = 80r	nVmax (	$(V_{DS}=10$	$V$ , $I_D = 1$	1mA, R	=100kΩ	2)	2SJ43とコンプリメンタリ		80	2SK127	
14		0	10	3.5		0 *	10	0.6	R <sub>e</sub> =1kΩ   1.5	2)   10	IDSS							80A	2SK128	
																			2SK129	-
55		5 *	10	10		5mA	10											53A	2SK130	
55		5 *	10	10		5mA	10	NV	=35mVm	nax, Ins	s/l/Inss	大=0.9r	min, ⊿Vo	s = 20m	Vmax			109	2SK131	
600		5		10		-5*			\	V <sub>DS(sat)</sub> =	12Vmax	$(I_D = 7A$	, V <sub>GD</sub> =	0)		2SJ47とコンプリメンタリ		28A	2SK132	
600		-5	10	10		-5*	10					"	anatonae mailfeoideoilleána		Andrew Committee of the	2SJ48とコンプリメンタリ		28A	2SK133	
600		-5	10	10		-5*	10					"			Market and Company of the Company of	2SJ49とコンプリメンタリ		28A	2SK134	
600		-5	10	10		-5*	10					"			estuado de decido de esta esta esta esta esta esta esta est	2SJ50とコンプリメンタリ	<u> </u>	28A	2SK135	
13		-3	10	5		-3*	10	(	$R_s = 1k\Omega$	2)	IDSS							80A	2SK136	
																		83	2SK137 2SK137	A
	I	(fos	c) max	=55GHz	typ							2.6	(f=8	GHz)	10	MAG=12dB typ (f=8GHz)		100	2SK138	
							-												2SK139	
	I	(fos	c) max:	=80GHz	typ	<u> </u>						2.7	(f=1 3.5	2GHz)	10	MAG=11dB typ (f=12GHz)		100	2SK140	
4.8	6.0	0	10	1.2	1.5	0	10											73	2SK141 2SK141	4
																			2SK142	
																			2SK143	
																			2SK144	
· · · · · · · · · · · · · · · · · · ·		1 7 7						7 7 9	17-1										2SK145	
75		0	10	15		-10	$I_D=0$	1	R <sub>s</sub> =1009	2)	5	Δì	V <sub>GS</sub> = 20n	Vmax (	$V_{DS} = 10^{\circ}$	V, I <sub>D</sub> =5mA) 2SJ73とコンプリメンタリ		85	2SK146	
75		0	10	15		-10	$I_D=0$	(	$R_{g} = 1000$	2)	5	N	F=10dB	max (VR	$V_{DS} = 10 \text{ V}$ $R_g = 100 \Omega$	(, I <sub>D</sub> =5mA) 2SJ72とコンプリメンタリ , f=100Hz)		74A	2SK147	
												2.5		5	1			101	2SK148	
7.5		3*	10	2	<b></b>	3mA	10				1	(4- 2	 ート接地, 	f=4001	MHz)	(ゲート接地) PG=12dB typ (f=400MHz)	-	102A	2SK149	
15		0	10	3		-10		(	$R_z = 1k\Omega$	2)	1		∆V <sub>GS</sub> =:	30mVmax		NF=10dB max $\begin{pmatrix} V_{DS}=10V, I_D=1mA \\ R_g=1k\Omega, f=10Hz \end{pmatrix}$	2SK272	75	2SK150	

1	and the state of t	Natural Carry	T	T			T T	最 大	定札	各 (Ta:	=25°C)							電	気 白	勺 特	性	(Ta	=25°C)					
	型	名	社	名	用 途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	V <sub>DSX</sub>	V <sub>G</sub> so V <sub>G</sub> ss*	Ic	Pd	Ti	Icss	max	Ιι	oss (mA	<b>(</b> )	1	GS(off),	Vth*(V	7)		g <sub>m</sub> (m	S) μ*		g	os (mS	
							V <sub>GDX</sub> **	Voss*	V <sub>GS</sub> x**	ID*	Pch*	Tch*	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub>	min	max	V <sub>DS</sub> (V)		min	typ	max	V <sub>DS</sub>	I <sub>D</sub> (mA)	r <sub>D</sub> * typ	max
*	2SK151		日	立	低周波,低雑音	J	-40°	40	-40*	10, 200*	800*	125	-10	-40	6	50	10	-0.2	-1.1	10	10	33	40		10	5		
	2SK152		ソニ		高周波/低周波, 低雑音	"	-15°		-15	5,50*	300	100	-2	-7	9.5	42	5	-0.55	-2	5	100	21	30		5	IDSS		
	2SK153			7	IŁ>★庄 目																							
	2SK154		松	下	VHF, RF	J	-20*	20		10,30*	350	125				18	10					2.5			10	IDSS		
	2SK155		"		低周波,低雑音	"	-20°		-20	30*	400	125	-100	-20	0.5	30	10	-0.1	-1.5	10	10	8	45		10	"		
1	2SK156		Ξ	洋	コンデンサ・マイク	"	-20*			10	100	125			0.06	1.5	10									-	40.00 PA 100 (IV) - 100 (IV)	
*	2SK157		日	立	低周波	"			-50°	10,20*	150*	125*	-10	-30	0.5	12	10	-0.13	-1.5	10	10	4.5	10		10	IDSS		
	2SK158		松	下	ji	11	55			10	70	125				6.5	10						1.2		10	"		
- 1	2SK159			1																							-	
ı	2SK160		日	軍	低周波, VHF	J	-30°		-30	10,20*	150	125	-10	-30	0.5	12	5	-0.25	-4.∙5	5	10	1.5	2.1		5	0.5		
	2SK161		東	芝	FM, VHF	"	-18*			10	200	125	-10	-0.5	1	10	10	-0.4	-4	10	1		9		10	Inss		
ı	2SK162		B	電	低周波,低雑音	"	-40*	40	-40	10,50*	400	125	-1	-20	5	30	5	,	-1.2	5	10	40	45		5	5		
ı	2SK163		"	1	"	"	-50°	50	-50	10,30*	400	125	-1	-20	1	18	10	-0.2	-1.2	10	10	7	9		10	1		
Ī	2SK164			1		-																						
ı	2SK165		松	下	広帯域低雑音 ビデオカメラ	J	-15*		-15	5,50*	300	100*	-2	-7	8	32	5		-3	5	100	3	14		5	IDSS		
ı	2SK166																											
1	2SK167								and the state of t		***************************************																	
Ī	2SK168		B	立	VHF, RF, MIX, OSC	J	-30*		-1*	10,20*	200*	150*	-10	-0.5	4	20	5		-3	5	10	8	10		5	Inss		
	2SK169		松	下	低周波,低雑音	"	-15	15		50°	400	125				50	5											
Ī	2SK170		東	芝	"	"	-40			10	400	125	-1	-30	2.6	20	10	-0.2	-1.5	10	0.1		22		10	Ibss	manganama annas (s). Vi	
Ī	2SK171		Ξ	菱	"	"	-20*		-20	10,80°	200 unit	125*	-1	-10	5	60	5		-2	5	10		10		5	8	an aggress that year	
	2SK172																						a a sand on the control of the	~	make or on all 1984	The second of th		
	2SK173																	and the amount of the said.	and the second second	per stroppy of a superplan		a. Shika sayan nomerinin		and the same of			e as	
	2SK174																A	Larrage Control	and the same of th		and the Windows			and the second			بدداء ويجيزون	
	2SK175		B	立.	低周波電力增幅	MOS		180	± 20°	8A*	125W*	150*						0.15*	1.45*	10	100mA	0.7	(S) 1	1.4	10	3A		

									····							T				
	guestaniques, Take		and the second s	T	電	気	的特	-	(Ta=	anne a Ministra de Amello de		1		and the State of t		-	代替品	外		
Cis	( <b>pF</b> )		F. A. A. P. P. P. C. C. C. C. C. C. C. C. C. C. C. C. C.	Crs	(pF)		agencials (Continuous and the second	NF (f	=1kHz, 1	$R_{R} = 1M\Omega$	a) (dB)	NF	(f=100	MHz) (	dB)	その他			型名	í.
typ	max	$I_D(mA)^{\bullet}$	V <sub>DS</sub> (V)	typ	max	V <sub>GD</sub> (V) V <sub>GS</sub> (V)*	V <sub>DS</sub>	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)		型名	肝多	-	
								0.5	R <sub>s</sub> = 200Ω   1	1 10	5		<u></u>	<u></u>		2SJ51とコンプリメンタリ	2SK190	97	2SK151	
8	9	0	5					1.2n	e <sub>n_</sub> (F V√Hz	( <sub>8</sub> =0)   5	10	1.8	L ゲート接. 	地)   5	10			57A	2SK152	
									ļ				ļ	ļ	ļ				2SK153	
												1.5	<u>L</u>	10	<u></u>			80B		
40		-3	10	17		-3*	10						e <sub>n</sub> =	=0.7nV/	√Hz typ	$(V_{DS}=10V, V_{GS}=0, f=1kHz)$		80A	2SK155	
	Z <sub>in</sub> =	=20MΩ m	in (f=1	lkHz)					<b>.</b>	V <sub>N</sub>	0 = -110	dB (VIN	=0)		·			58A	2SK156	
	-									<u> </u>					<b></b>		2SK323	87A	2SK157	
								(	f=120H;	15								103	2SK158	
		, ,																	2SK159	
4.1		0	10	0.9		0.	10											78A	2SK160	_
					0.15	-10						2.5	3.5	10 (V <sub>DD</sub> )		PG=18dB typ (f=100MHz)		70C	2SK161	
55		0	10	10		0 *	10	(f=100 1.1	Hz, R <sub>g</sub> =	=100Ω)   5	5		<u></u>		<u></u>			53A	2SK162	
13		0	10	3.2		0*	10			NV=20	mVmax (	指定回路	なによる)					53A	2SK163	
																			2SK164	
<b>7</b> .5		0	5															80C	2SK165	
																			2SK166	
																			2SK167	
6.8		0	5	0.1		0 *	5					1.7		5	IDSS	PG=27dB typ (f=100MHz)		89	2SK168	
																			2SK169	
30		0	10	6		I <sub>D</sub> =0	10	0.5	(R <sub>g</sub> =	1kΩ) 10	1		NF=10d	IB max (	$V_{DS} = 10$	$PV$ , $I_D = 1 \text{mA}$ , $R_g = 1 \text{kQ}$ , $f = 10 \text{Hz}$		82C	2SK170	
200		5 *	5					(f=100	Hz, R <sub>s</sub> =	=100Ω) 5	5		<del></del>	⊿Vcs	== 50mVm	nax (V <sub>DS</sub> =5V, I <sub>D</sub> =5mA)		84	2SK171	_
																			2SK172	
																			2SK173	
																			2SK174	
700		-5	10	8		-5*	10		v	DS(sat)=1	12Vmax	$(I_D=8A,$	$V_{GD} = 0$	)		2SJ55とコンプリメンタリ		28A	2SK175	

			T				最大	定札	答(Ta	=25°C)							電	気 的	) 特	性	(Ta	=25°C)					
型	名	社名	月	途	構造	V <sub>GDS</sub>	Vosx	VGSO VGSS*	Ic	Pd	T <sub>i</sub>	Icss	max	I	oss (mA	<b>A</b> )	,	VGS(off),	V <sub>th</sub> *(\	J)		g <sub>m</sub> (m	S) μ*		8	os (mS	i) (Ω)
						V <sub>GDX</sub> ** ( V )	V <sub>DSS</sub> *	V <sub>GSX</sub> ** (V)	I <sub>D</sub> *	Pch* (mW)	Teh*	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)		min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max
2SK176	;	日立	低居	波電力増幅	Mos		200	±20*	8A*	125W*	150*						0.15*	1.45*	10	100mA	0.7	(S) 1	1.4	10	3A		<u> </u>
2SK177	7																										<u> </u>
2SK178	3					-							Annual Control of the State of														
2SK179	)																										ļ
2SK180	)																										
2SK181	2 (2 )																										
2SK182	2																										
2SK183	3							1-31.1																			
2SK184		東芝	低居	波,低雑音	J	-50			10	200	125	-1	-30	0.6	14	10	-0.2	-1.5	10	0.1	4	15		10	Ibss		
2SK185	,	ソニー	低居 RF	波,低雑音	"	-30 <b>*</b>		-30	5,20*	320	100*	-1	-15	0.9	14.3	10	-0.18	-1.49	10	30	6.3			10	"		
2SK186	;	日立	低馬	波,低雑音	,,		40	-40°	10,30*	300*	150*	-10	-30	1.6	12	10	-0.13	-1.5	10	10	8	12		10	3		
2SK187	,	"		11	"		40	-40°	10,30*	300*	150°	-10	-30	2.5	20	10	-0.13	-1.5	10	10	18	21		10	3		ļ
2SK188	3																		and the second section to the second								
2SK189		日 立.	低馬	波,低雑音																							
2SK190	)	"		n .	J	40*	40	-40*	10 200*	800*	150*	-10	-30	6	50	10	-0.13	-1.5	10	10	37	45		10	5		
2SK191		"		"	"	-15°	15	-15°	10 500*	1W*	150*	-1	-8	10	200	5		-3	10	10	75	100		10	8		
2SK192	A	東芝	FM,	VHF, RF	"	-18*			10	200	125	-10	-1	3	24	10	-1.2	-3	10	1		7		10	Ibss		
2SK193		日電	FM,	RF	"	-20*	20		10,10*	250	150	-100	-0.5	0.5	8	5		-2.5	5	10	2.3	3.5		5	0.5		
2SK194		"	低馬	波,低雑音	"	-40°	40	-40	10,50*	400 unit	125	-1	-20	5	24	5		-1.2	5	10	40	45		5	5		
2SK195		"	FΜ,	RF	"	- 20°	20		10,10*	250	125	-100	-0.5	0.5	8	5		-2.5	5	10	2.3	3.5		5	0.5		
2SK196	<b>(D)</b>	日立	高周	波電力増幅 度電力 SW	MOS		160*	±14	500*	800*	150*				2	120	0.2*	2*	10	10mA	50		anana mara ri	10	200		
2SK197		"	VHI	, RF, MIX	J	-18*		- ains row Hendel would	10,20*	150*	150*	-10	-0.5	2	14	10	-0.3	-4	10	10	3	8		10	loss		
2SK198		松下	低馬	波	"	-30*	30		10,20*	150	125	- 100	-30	0.5	12	10	-0.1	-1.5	10	10	4	12		10	"		
2SK199		"	VHI	, RF	"		15		15,15*	100	125	and the second second	o a difficulty is the control of the	and the balls of the	12	5					1.9			5	"		
2SK200																											

					Æ	% (	的特	<b>11</b> :	( Ta =	= <b>25°</b> C)							代替品	外	
Cis	(pF)			Crs	(pF)			NF (f	= 1kHz, 1	$R_{\rm g} = 1M\Omega$	a) (dB)	NF	(f=100	MHz) (	dB)	その他			型名
typ	max	$V_{GS}(V)$ $I_{D}(mA)^{*}$	V <sub>DS</sub> (V)	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	ID (mA)	typ	max	V <sub>DS</sub> (V)	ID (mA)		型名	F5	
700	THE PERSON NAMED IN	-5	10	8		-5*	10		,	V <sub>DS(\$41)</sub> =	12Vmax	$(I_D=8A$	$V_{GD} = 0$	)		2SJ56とコンプリメンタリ		28A	2SK176
												And the second of the 180 (Albertane)							2SK177
			and committee and the state of			an district of Alban Service, State Service													2SK178
																			2SK179
					Anna de Maria de Maria														2SK180
																			2SK181
																		ļ	2SK182
									1011	D - 11								ļ <u>.</u>	2SK183
13		0	10	3		-10	$I_D=0$	5		$\begin{array}{c c} R_g = 1k \\ \hline 10 \end{array}$		/37 1	01/ 1/					70B	2SK184
				2.4		0.	10									0mVmax (V <sub>DS</sub> =10V, I <sub>D</sub> =1mA)		86	2SK185
20		0	10	3.7		0*	10					$V, I_D=3$						79	2SK186
41		0	10	8	ļ	0,	10	e <sub>n</sub> =1	.nV/√Hz	typ (Vi	os = 10V,	$I_D = 3mA$	A, R <sub>g</sub> =0	), f=1kl	Hz)			79	2SK187
																	0CK100		2SK188 2SK189
																	2SK190	97	2SK199
75		5 *	10						.75n V / √			$V$ , $I_D=5$	omA, Rg	=0, 1=	IKHZ)			97	25K190 2SK191
					0.65	-10		1.1		ìo	=20Q)   8	1.8	3.5	10 (V <sub>DD</sub> )		PG=24dB typ (f=100MHz)		70C	
5	6.5	0	 5	0.07	0.05	0 *	5					3	6	5		PG=21dB typ (f=100MHz)		<del> </del>	2SK193
55	0.5	0	10	10	0.23	0.	10	NV=	: 35mVma	x(指定	<b> </b>			(V <sub>DD</sub> )	= 20mVm	$\max (V_{DS}=5V, I_{D}=5mA)$		109	2SK194
5	6.5	0	 5	0.07	0.25	0.	5			1	[	3	6	5		PG=21dB typ (f=100MHz)		40	2SK195
90		10*	10	0.07	0.20			ton=2	Ons tvo.	toff=30n	styp (Va	s = 10V,		$(V_{DD})$	L 150Ω)			121A	2SK196⊕
3.4		0	10	0.38		0.	10			T							01	87B	
14		0	10	3.5		0.	10											103A	2SK198
							523										1	103	2SK199
	A															CONTRACTOR CONTRACTOR			2SK200

				T	T	最 大	定札	各(Ta	=25°C)		<u> </u>	*********				電	気 的	) 特	性	(Ta	=25°C)					
型	名	社名	用 途	構造	V <sub>GDS</sub>	Vosx	VGSO VGSS*	IG	Pa	T <sub>i</sub>	Icss	max	Iı	oss (mA	<b>A</b> )	1	GS(off),	Vth*(V	")		g <sub>m</sub> (m	S) μ*		g	os (mS	
					V <sub>GDX</sub> ** (V)	Voss*	VGSX**	I <sub>D</sub> * (mA)	Pch*	Tch* (*C)	(nA) (pA)*	V <sub>G</sub> s (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)		min	typ	max	V <sub>DS</sub> (V)	ID (mA)	typ	max
2SK201		日電	C~Xバンド 中出力増幅発振	GaAs		10	-10	400*	1.3W	175	-3μA	5	180	400	3	-3	-7	3	1mA	35	50		3	100		
2SK202																										
2SK203		日電	C~Xバンド 中出力増幅発振	GaAs		10	-10	180*	0.8W	175	-1.5μA	-5	90	180	3	-3	-7	3	500	18	30		3	50		
2SK204																										
2SK205																										
2SK206																		-								
2SK207										_																
2SK208		東芝	コンデンサ・マイク	J	50			10	100	125	-1	-30	0.3	6.5	10	-0.4	-5	10	0.1	1.2			10	Ipss		
2SK209		11	低周波	"	-50			10	150	125	-1	-30	0.6	14	10	-0.2	-1.5	10	0.1	4	15		10	"		
2SK210		"	VHF, RF	"	-18			10	100	125	-10	-1	3	24	10	-1.2	-3	10	1		7		10	"		
2SK211		11	FMチューナ VHF, RF	"	-18*			10	150	125	-10	-0.5	1	10	10	-0.4	-4	10	1		9		10	"		
2SK212		三洋	FM, RF	"	-20*			10,20*	200	125	-10	-0.5	0.6	12	5		-2.5	5	10	2	6		5	"		
2SK213		日立	低/高周波電力増幅 高速度電力 S W	Mos		140	±15*	500*	30W*	150*						0.2*	1.5*	10	10mA	20	40		20	10		
2SK214		"	ıı	"		160	±15*	500°	30W*	150°						0.2*	1.5*	10	10mA	20	40		20	10		
2SK215		"	"	"		180	±15*	500°	30W*	150°						0.2*	1.5*	10	10mA	20	40		20	10		
2SK216		"	"	"		200	±15*	500*	30W*	150*						0.2*	1.5*	10	10mA	20	40		20	10		
2SK217		"	VHF, RF	J	-30*			10,20*	150*	150°	-10	-0.5	2.5	12	5		-2.5	5	10		8		5	Inss		
2SK218		松下	ビデオカメラ	11	-15*		15	5,50*	300	100	-2	-7	5	42	5		-3	5	100	15	30		5	"		
2SK219																										
2SK2200	ED	日立	高周波電力増幅 高速度電力 S W	MOS		160*	±20*	8A*	100W*	150°				1	120	0.4*	3*	10	10mA	600	900		10	3A		
2SK2210	ED	"	"	"		200*	±20°	8A*	100W*	150*				1	160	0.4*	3*	10	10mA	600	900		10	3A		
2SK222		三 洋	低周波・低雑音	J	-40	40*		10	300	125	-1	-20	0.6	12	10		(typ) -0.5	10	10	-survey right time - throughten	17		10	Ipss	same control	
2SK223		"	髙電圧ドライブ	"	80	80*		10	400	125	-1	-30	1.2	24	30	(typ) -0.75		30	10	and the second second	20		30	"		
2SK224								T. Paris												eriands up moves					**********	
2SK225		日 立.	低周波電力増幅	MOS		120	± 15*	7A*	100W*	150*						0.15*	1.45*	10	100mA	0.7	(S) 1	1.4	10	3A		

					A	4(	的特	<b>** **</b> 1:	( Ta ==	25°C)		·					代替品	外	
Ci,	(pF)			Cr	(pF)			NF (f	= 1kHz, 1	$R_{\kappa} = 1M\Omega$	(dB)	NF	f (f=100	MHz) (	dB)	し そ の 他	型名		型名
typ	max	$\begin{bmatrix} V_{GS}(V) \\ I_D(mA)^* \end{bmatrix}$	V <sub>DS</sub>	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	In (mA)	typ	max	V <sub>DS</sub> (V)	In (mA)		715 71	形	
												(f=8	BGHz)	4	15	MAG=9dB typ (f=8GHz)	-	120	2SK201
																AND CONTRACT MADE CONTRACT TO SERVICE			2SK202
												(f=8 2.6	BGHz)	4	10	MAG=11dB typ (f=8GHz)		120	2SK203
													anima in the 196 from			and and distriction. The distriction of the first of specific and the control of		ļ	2SK204
																			2SK205
																			2SK206
																			2SK207
8.2	AND THE PERSON NAMED IN COLUMN	0	10	2.6		-10	$I_D=0$	0.5		Hz, R <sub>g</sub> =	=100kΩ)   Inss							105A	2SK208
13		0	10	3		-10	$I_D=0$	1 (	$R_g = 1k\Omega$	)   10	0.5							105A	2SK209
					0.65	-10						1.8	3.5	(V <sub>DD</sub> ) 10		PG=24dB typ (f=100MHz)		105B	2SK210
					0.15	-10						2.5	3.5	(V <sub>DD</sub> ) 10		PG=18dB typ (f=100MHz)		105B	2SK211
4		0	5	0.04	0.15	0 *	5					3.5	6	(V <sub>DD</sub> ) 5	IDSS	PG=21dB typ (f=100MHz)		58B	2SK212
90		10*	10	2.2		10mA	10		Vı	DS(sat) = 2	Vmax (I	D == 10m A	A, V <sub>GD</sub> =	0)		2SJ76とコンプリメンタリ		116A	2SK213
90		10*	10	2.2		10mA	10					<i>y</i>				2SJ77とコンプリメンタリ	-	116A	2SK214
90		10*	10	2.2		10mA	10					''				2SJ78とコンプリメンタリ		116A	2SK215
90		10*	10	2.2		10mA	10					'I				2SJ79とコンプリメンタリ		116A	2SK216
				0.1		0*	5											87 B	2SK217
8		0	5															80C	2SK218
																			2SK219
600		-5	10			$(I_D = 2A$ $t_{on} = 25n$	$V_{GS} = 1$	15V, Ri off=45ns	_=15Ω) s typ									28A	2SK220∰
600		-5	10				,											28A	2SK221®
14		0	10	3.5		0.	10	(f:	=100Hz,   3	R <sub>g</sub> =1k	$\Omega$ ) $I_{ extsf{DSS}}$							57B	2SK222
12		0	30	2.5		0.	30	1	R <sub>s</sub> =10kΩ	2)   10	3							57B	2SK223
																			2SK224
600		-5	10	10		-5*	10	1	t <sub>on</sub> = 180n	ıs typ, t	off=60ns	typ (V	op=20V,	$I_D=4A$	)	2SJ81とコンプリメンタリ		117A	2SK225

	144-144 IV-16-16		7	intiliapoy jugo kyriinteid, apinalooniintiiginjagisi dhin sajaallootilarin kir			最大	定相	各(Ta	=25°C)		Ī		V			電	気 的	5 特	性	(Ta	=25°C)					
型	名	社	名	用 途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	V <sub>DSX</sub>	V <sub>GSO</sub> V <sub>GSS</sub> *	IG	Pd	T <sub>i</sub>	Igss	max	Īı	oss (m <i>A</i>	<b>A</b> )	v	GS(off),	$V_{th}^*(V$	)		g <sub>m</sub> (m	S) μ*		g	os (mS	(Ω)
						V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GS</sub> x** (V)	I <sub>D</sub> *	Peh*	Tch* (*C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	I <sub>D</sub> (μA)	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max
2SK226	3	日	立.	低周波電力増幅	MOS		140	±15*	7A*	100W*	150*						0.15*	1.45*	10	100mA	0.7	(S)	1.4	10	3A		
2SK227	7	"		"	"		160	±15*	7A*	100W*	150*						0.15*	1.45*	10	100mA	0.7	(S)	1.4	10	3A		
2SK228	3																										
2SK229	)										to at the total to																
2SK230	)																										
2SK231																											
2SK232																											
2SK233																											
2SK234											Magalagare continue a committee for the																
2SK235																											
2SK236																											
2SK237																											
2SK238		B	電	FMチューナ	J	-20°	20		10, 10*	150	125	-100	-0.5	0.5	8	5		-2.5	5	10	2.3	3.5		5	0.5		
2SK239																											
2SK240		東	2 1	低周波,低雑音	J	-40			10	400 unit	125	-1	-30	2.6	20	10	-0.2	-1.5	10	0.1	15	22		10	Ipss		
2SK241		"	]	FM, VHF	MOS		20	±5	30 <b>*</b>	200	125*	±50	±5	1.5	14	10		-2.5	10	100	1.5	10		10	"		
2SK242		Ξ	羊	高周波電力增幅	J	-20*			10, 20*	150	125	-10	-0.5	0.6	12	5		-2.5	5	10	2	6		5	. "		
2SK243		***************************************									and the second s								arana di mang aran								
2SK244		-	_																								
2SK245																											
2SK246		東	ا ځ	OC,インピーダンス 変換、定電流回路	J	-50			10	300	125	-1	-30	1.2	14	10	-0.7	6	10	0.1	1.5			10	IDSS		
2SK247		松	F	<b>立帯域低雑音増幅</b>	"	-15*		-15	5, 20°	150	100*	-2	-7	0.5	12	5		-3	5	100	3			5	"	والمعارضة المراجع والمعارضة والمعارضة والمعارضة المراجعة والمعارضة المراجعة والمعارض والمعارضة والمعارضة والمعارضة والمعارض والمعارض والمعارض والم	ways from services
2SK248																			Populario de completados								
2SK249			_																and the same of the same of the same of the same of the same of the same of the same of the same of the same of								
2SK250																											

					雅	么	的特	<u> 11</u> :	(Ta=	25°C)		•						外	
Ci.	(pF)			C,,	(pF)			NF (f	=1kHz, l	$R_{\rm g} = 1M\Omega$	(dB)	NF	f=100	MHz) (	dB)	その他	代替品		型名
typ	max	$V_{GS}(V)$ $I_{D}(mA)^{\bullet}$	V <sub>DS</sub> (V)	typ	max	$V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	In (mA)	typ	max	Vos (V)	In (mA)		型名	形	
600		-5	10	10		-5*	10		t <sub>on</sub> = 180	nstyp, t	o11=60ns	typ (Vi	DD == 20 V,	$I_D = 4A$	)	2SJ82とコンプリメンタリ		117A	2SK226
600		-5	10	10		-5*	10					n 				2SJ83とコンプリメンタリ		117A	2SK227
																			2SK228
																			2SK229
																And Annual and Annual and Annual Annu			2SK230
																			2SK231
																			2SK232
																			2SK233
																			2SK234
																			2SK235
																			2SK236
																			2SK237
5	6.5	0	5	0.07	0.25	0.	5					3		5		PG=21dB typ (f=100MHz)		78B	2SK238
																			2SK239
30		0	10	6		-10	$I_D=0$	(f=10 1	Hz, R <sub>g</sub> =	=1kΩ)   10	1					2SJ75とコンプリメンタリ		110	2SK240
3		0	10	0.035	0.05	0.	10					1.7	3	10	IDSS	PG=28dB typ (f=100MHz)		70C	2SK241
4		0	5	0.04	0.15	0.	5			and the same of th		3.5	6	5	I <sub>DSS</sub>	PG=24dB typ (f=100MHz)		126B	2SK242
			-																2SK243
																			2SK244
																			2SK245
9		0	10	2.5		-10	$I_D=0$											82B	2SK246
7.5		0	5															103A	2SK247
								7 3											2SK248
																			2SK249
									Marie (Section 18 Sector 18 August 18 August 18 August 18 August 18 August 18 August 18 August 18 August 18 Au										2SK250

ſ							最大	定 柞	各 (Ta	=25°C)		I					電	気 自	的 特	· 性	(Ta	=25°C)					
	型	名	社名	用 途	構造	V <sub>GDS</sub>	V <sub>DSX</sub>	V <sub>GSO</sub> V <sub>GSS</sub> *	IG	Pd	T <sub>i</sub>	IGSS	max	I	uss (m	<b>A</b> )	,	VGS(off),	Vth*(V	7)		gm (m	S) μ*		g	os (mS	
						V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> ** (V)	ID* (mA)	Pch*	Tch*	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	Ι <sub>D</sub> (μΑ)	min	typ	max	V <sub>DS</sub> (V)	ID (mA)	r <sub>D</sub> * typ	max
	2SK251																										
	2SK252													_													
	2SK253																										
	2SK254																										
ſ	2SK255																										
	2SK256																										
	2SK257																										
	2SK2580	BD	日立	高周波電力増幅 高速度電力 SW	MOS		250*	±20*	8A*	125W*	150*				1	200	0.4*	3*	10	10mA	0.9	S)   1.3		10	3A		
	2SK2590	BD	"	"	"		350*	±20*	5A*	125W*	150*				1	280	0.4*	3 *	10	10mA	0.6			20	3A		
	2SK2600	Ð	"	"	"		400*	± 20*	5A*	125W*	150*				1	320	0.4*	3 *	10	10mA	0.6	S)   1		20	3A		
۲ [	2SK261		"	低周波電力増幅																							
۲	2SK262		"	"																							
-	2SK263		"	"																							
-	2SK264		"	"																							
	2SK265																										
	2SK266		東芝	コンデンサ·マイク インピーダンス変換	J	-15 <b>*</b>			10	100	125		ΙD	=0.6m	Amax (	$V_{DD} = 6$	V, R <sub>L</sub> =	1kΩ, ′	ゲート,	ソース	; 15pF	ショート	.)				
	2SK267																									×	
	2SK268																										
	2SK269																										
	2SK270		東芝	低周波,低雑音	J	-40			10	300 unit	125	-10	-30	1	20	10	-0.2	-2	10	0.1	8	20		10	3		
	2SK271		"	低周波電力增幅	MOS		140	±8	8A*	120W	150*	±1μA	±8				0.8	2.4	10	0.1A	1	1.5		10	2A		
	2SK272		"	11	"		140	±8	7A*	100W	150*	±1μA	±8				0.8	2.4	10	0.1A	1	1.5		10	2A		
-[	2SK273		三菱	S〜Xバンド 低雑音増幅	GaAs		8	-6	100*	300	150			30	100	3	-1	-5	3	100	20	30		3	30		
	2SK274		"	"	"		8	-6	100*	300	150			30	100	3	-1	- 5	3	100	25	35		3	30		
	2SK275		"	11	"		8	-6	100*	300	150			30	100	3	-1	-5	3	100	25	35		3	30		

				·	U	<i>i</i> 1	的特	į Μ:	( Ta ==	25°C)		T. 24 . 22 . 22 . 22 . 22 . 22 . 22 . 22					代替品	外	
Cia	(pF)			C,	(pF)			NF (f=	1kHz, F	$R_{\rm g} = 1 M\Omega$	a) (dB)	NF	(f=100	MHz) (	dB)	そ の 他			型名
typ	max	$\begin{bmatrix} V_{GS}(V) \\ I_D(mA)^* \end{bmatrix}$	V <sub>DS</sub>	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	In (mA)	typ	max	V <sub>DS</sub> (V)	In (mA)		型 名	形	
																The second section is the contest of			2SK251
	the month of the state of																		2SK252
																			2SK253
	A CONTRACTOR OF COMPANY		and the second second																2SK254
																			2SK255
																			2SK256
	and the same of the same to the same of th									in hand? White Committee the									2SK257
800	e deductive e conserva-	5	10					to	n=25ns	typ, to	rf = 140ns	typ (ID	=2A, V	cs = 15 V	')			28A	2SK258®
800		-5	10	15		-5						"						28A	2SK259⊕
800		-5	10	15		-5						"						28A	2SK260⊕
	<u> </u>																2SK213/214		2SK261
					<u> </u>					and the second s							"		2SK262
							ne to the manual or the order										"		2SK263
																	"		2SK264
																			2SK265
	Zin	=200MΩ	min (V	$V_{DD} = 6V$ ,	$C_g = 15_1$ f = 50H	pF)			V <sub>N</sub> :	== 40mVn	nax (VDD	=6V, F =80dB.	$C_s = 1k\Omega$ $C_s = 15p$	F)				155	2SK266
				1836,															2SK267
																			2SK268
																			2SK269
25		0	10	5.5		-10		(R	$\frac{1}{2} = 1 k\Omega$	) 10	1		L	⊿V <sub>GS</sub> :	=30mVm	$ax (V_{DS}=10V, I_{D}=1mA)$		75	2SK270
800		0	10	60		0*	10				Wmax ()	I <sub>D</sub> =5A,	V <sub>G</sub> s=8V	')		2SJ91とコンプリメンタリ	2SK405	118	2SK271
800		0	10	60		0*	10				,	)				2SJ92とコンプリメンタリ	2SK405	119	2SK272
最大乳	 発振周波	LL 数 50GH:	z typ									(f=12 4.5	(GHz)	3	10	(MGF-1400)		122	2SK273
	"	70GH:	z typ				***************************************					(f=12	(GHz)	3	10	(MGF-1402)		122	2SK274
	"	70GH:	z typ									(f=4 0.8	GHz) 1	3	10	(MGF-1412)		122	2SK275

Γ		Τ		-			最 大	定析	子 (Ta	=25°C)							電	気 的	り 特	性	(Ta	=25°C)					
	型名	;	社 名	用途	構造	V <sub>GDS</sub>	Vosx	V <sub>GSO</sub> V <sub>GSS</sub> *	IG	Pd	Ti	Icss	max	Iı	oss (mA	1)	1	VGS(0ff),	V <sub>th</sub> *(\	7)		gm (m	S) μ*		g	. (mS	
ı						V <sub>GDX</sub> **	V <sub>DSS</sub> *	V <sub>GSX</sub> **	ID*	Pch*	Tch*	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub>	min	max	V <sub>DS</sub> (V)		min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	r <sub>D</sub> * typ	max
*	2SK276	=	. 菱	S~Xバンド 低雑音増幅	GaAs		6	-6	80*	200	150			30	80	3	-1	-5	3	100	20	30		3	30		
ł	2SK277	F	電	大電流SW	MOS		350*	±20*	7A*	100W	150	±100	±20		10	350	0.4	3	10	50mA	0.6	S)   <b>1</b>		10	3A		
ŀ	2SK278	+	n	"	"		400*	± 20*	7A*	100W	150	±100	±20		10	400	0.4	3	10	50mA	0.6	3)   <b>1</b>		10	3A		
*	2SK279	  =	·	S〜Xバンド 中電力増幅	GaAs		8	-6	250*	1W	150			150	250	3	-2	-6	3	100	70	90		3	100		
ı	2SK280	E		X~Kuバンド ・低雑音増幅	"		5	6	100*	270	125*	-10μA	-5	20	100	3	-0.5	-6	3	100	20	40	100	3	10		
1	2SK281	+	"	VHF~Cバンド 低雑音増幅	"		5	-6	120*	300	125	-10μA	-5	30	120	3	-0.8	-6	3	100	20	40	100	3	10		
	2SK282	1	~				_																				
İ	2SK283	Ē	. 洋	高電圧ドライバ	J	-80	80*		10	150	125	-1	-30	1.2	17	30	(typ) -0.75		30	10		20		30	IDSS		
Ī	2SK284						and the same of the same																				
Ī	2SK285																										
Ī	2SK286	E	立.	低高周波電力增幅 高速度電力 S W	MOS		60	±20*	8A*	100W*	150°	±1μA	±20			_	0.2*	1.5*	10	10mA	1	(S) 1.4		10	3A		
Ī	2SK287®		"	高周波電力増幅	"		60*	±20*	8A*	100W	150				1	50	0.4	3	10	10mA		S)   1.4		10	3A		
Ī	2SK288®		"	"	"		80°	± 20*	8A*	100W	150				1	60	0.4	3	10	10mA		3)   <b>1.4</b>		10	3A		
*	2SK289⊕		"	"	"		80*	±20*	8A*	100W	150				1	60	0.2	3	10	10mA	1	5)   1.4		10	3A		
*	2SK290⊕		"	"	<i>"</i> .		100*	±20*	8A*	100W	150				1	60	0.2	3	10	10mA	1	5)   1.4		10	3A		
	2SK291		"	高周波低雑音增幅	J	-15 <b>*</b>		-15	5,50*	300*	150*	-10	-7	6	50	5		-3	5	100	25	45		5	IDSS		
	2SK292	E	電	FMチューナ	"	-20°	20		10,10*	200	125	-100	-0.5	0.5	8	5		-2.5	5	10	2.3	3.5		5	0.5		
	2SK293		"	高耐圧高速度 大電流 S W	MOS		300°	±20*	7A*	100W	150*	±100	± 20		5	300	0.4	3	10	50mA	0.6	(S)		10	3A		
	2SK294	E	立	高周波電力增幅 高速度電力 S W	"		80*	± 20°	5A*	30W*	150*	±1μA	±20	ermana untu ar <sub>es</sub> anteteri	1	65	1*	5 *	10	1mA	0.5	(S) 0.8		10	3A	endende de endende	
	2SK295		#	"	"		100*	± 20*	5A*	30W*	150*	±1μΑ	±20	napolitano a madeira espe	1	80	1*	5 *	10	1mA	0.5	(S) 0.8		10	3A		
	2SK296		"	"	"	mainste mesassamide e	300*	±20*	1A*	30W*	150°	±1μA	±20	******	1	240	1*	4.5*	10	1mA	0.2	(S) 0.4		10	500	ana mayar akkirilik	
	2SK297	_	Nanana and The		an law massifices is	name de l'Architectura			name or a second or the land of the land o		***		a mandron and a contra				rakas Verse lebetar				16		amandan bilan bir bar	er militaria teri de e con			
	2SK298	E	<i>1</i> /.	高周波電力増幅 高速度電力 S W	MOS	en agric and Milliagologic street and	400*	±20*	8A*	100W*	150*	±1μA	±20	eriorie de deservat es su	1	320	1.	5 *	10	1mA	1.2	3)   1. <b>7</b>   (8)		10	4A		
	2SK299	1	"	"	"		450°	±20°	8A*	100W*	150°	±1μΑ	±20		1	360	1.	5*	10	1mA	1.2	(S) 1.7	······································	10	4A		
Ŀ	2SK300																					L					

																T	1	J <sub>r</sub> 1		٦
	general menseus in man-	a ilan kananan kalabahan da		1	T	久 1	的特	ř <u>M:</u>	(Ta=	=25°C)		1		And the Annual Control of	described to the second		代替品	外		
C.,	(pF)			Cr	(pF)			NF (f	=1kHz,	$R_{\kappa} = 1Ms$	(B) (dB)	NI	F (f=100	MHz) (	dB)	その他	型名		型名	
typ	max	$V_{GS}(V)$ $I_{D}(mA)^{\bullet}$	V <sub>DS</sub> (V)	typ	max	$V_{GB}(V)$ $V_{GS}(V)$	Vos (V)	typ	max	Vos (V)	ID (mA)	typ	max	Vos (V)	ID (mA)		Н (1	形		i
最大	発振周波	数 90GH	z typ									(f=1 2.8	.8GHz)	3	10	(MGF-1403)		122	2SK276	*
950	1,500	5	10	10		-5*	10	Vos	(ON) = 6 V	max, R	DS(ON) = 1	.5Ω max	$(V_{GS} = 1$	5V, In=	=4A)			108	2SK277	
950	1,500	-5	10	10		-5*	10		annach Service et an an an an Alberton.	udrika dilikusikal Aleksahus dan	************	"		AND THE RESERVE TO STATE OF THE PARTY OF THE				108	2SK278	
最大	発振周波	数 45GH	z typ							直線電	カ利得 90	dB typ (i	f=8GHz)			(MGF-1801)		122	2SK279	*
			**************************************				ge 4.4 halfa anni a anthon bhe anna 200				-	(f=1 2.3	5GHz)	3	10	MAG=8dB typ (f=15GHz)		123	2SK280	
				<b>†</b>							1		BGHz)	3	10	MAG=10dB typ (f=8GHz)		123	2SK281	
		and the second of the second o									AND A SHEET PROPERTY OF	1		400m atr 2 400 to 100 atr					2SK282	
12		0	30	2.5		0*	30							maketing of the control of				126	2SK283	1
					<del> </del>						1					en generalisan any ana mpambah di dayan ana ana dadalah adan an amanamakan dan adah di Soudh at taub an an amanamakan an an an an an an an an an an an an a			2SK284	1
											-		The state of the s						2SK285	
500		-5	10						v	DS(ON) = 4	      Vmax ()	$l_{D}=5A$ .	V <sub>GS</sub> = 15	l V)	L	2SJ96とコンプリメンタリ		117A	2SK286	
500		-5	10					1		-			=2A, V		·)			117A	2SK287®	
500		-5	10								Allerdan Bandard (1978) - Harris	"						117A	2SK288®	1
500		5	10									<del></del>	***************************************					28A	2SK289®	*
500		-5	10															28A	2SK290⊕	*
8.5		0	5					e <sub>n</sub> =1.	2nV/√F	Iz tvp (	$V_{DS} = 5V$	$I_D = 5m$	A, R <sub>g</sub> =	0, f=10	OkHz)			37B	2SK291	1
5	6.5	0	5	0.07	0.25	0 *	5			Γ	T	3	6	5	IDSS	PG=21dB typ (f=100MHz)		104A	2SK292	1
950	1,500	-5	10	10		-5*	10			1	V <sub>DS(ON)</sub> =	=5. <b>2</b> Vma	ax, Rose	ON)=1.3	Ω max (	$V_{GS}=15V$ , $I_D=4A$ )		108	2SK293	1
450		0	10	140		0 *	10		VDS	s(ON)=1.	7Vmax (	$I_D=3A$	$V_{GS} = 15$	5V)				116B	2SK294	1
450		0	10	140		0*	10					,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,						116B	2SK295	1
140		0	10	23		0.	10	-	Vı	OS(ON) = 4	Vmax (I	D=1A,	$V_{GS} = 15V$	/)				116B	2SK296	1
											<u> </u>								2SK297	1
800		0	10	20		0*	10	l	V	)s(on)=7	Vmax (I	D=4A,	$V_{GS} = 15$	7)	L	2SJ116とコンプリメンタリ		28B	2SK298	1
800		0	10	20		0 *	10											28B	2SK299	1
													-						2SK300	1

		Γ			T	I	最 大	定 柞	各 (Ta	=25°C)			***************************************		-	*****	電	気 的	勺 特	性	(Ta	=25°C)					
粗	名	社	名	用 途	構造	V <sub>GDS</sub>	Vosx	VGSO VGSS*	IG	Pd	T <sub>j</sub>	Icss	max	I	DSS (m/	<b>A</b> )		VGS(off),	Vth*(	7)		gm (m	S) μ*		8	gos (mS	
						V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> **	$I_D^*$ $(mA)$	Pch*	(°C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)		min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	(Ω) max
2SK301		松	下	低周波增幅,SW	J	55*	55	55	10,30*	250	125	-10	-30	0.5	20	10		-5	10	10	2.5	7.5		10	IDSS		
2SK302	:	東	芝	VHF, RF	Mos		20	±5	30*	150	125	±50	±5	1.5	14	10		-2.5	10	100		10		10	"		
2SK303		Ξ	洋	低周波電力増幅	J	-30	30*		10,20*	150	125	-1	-20	0.6	12	10		-4	10	1	2.5	6		10	"		
2SK304		"		"	"	-30	30*		10,20*	150	125	-1	-20	0.6	12	10		-4	10	1	2.5	6		10	"		
2SK305																											
2SK306																											
2SK307				THE R. P. STREET, M. P. STREET, M. P. STREET, M. P. STREET, P. STR																							
2SK308		B	立	高周波電力増幅	MOS		120*	±20*	10A*	100W*	150*	±1μA	±20	_	1	100	1 *	4.5*	10	1mA	1.5	S)   2		10	5A		
2SK309											_,																
2SK310		日	立.	高周波電力増幅 高速度電力SW	MOS		400*	±20*	3A*	40W*	150*	±1μA	±20		1	320	1 *	5 *	10	1mA	0.6	(S)		10	2A		
2SK311		"		"	"		450*	±20*	3A*	40W*	150*	±1μA	±20		1	360	1.	5 *	10	1mA	0.6	(S) 1		10	2A		<u> </u>
2SK312		"		"	"		400*	±20*	12A*	125W*	150*	±1μΑ	±20		1	320	1 *	5 *	10	1mA	1.5	(S) 2.5		10	6A		
2SK313		"		"	"		450*	±20*	12A*	125W*	150*	±1μA	±20		1	360	1 *	5 *	10	1mA	1.5	(S) 2.5		10	6A		
2SK314		B	電イ	<b>低周波,低雑音</b>	J	-40*	40	-40	10,50*	250	150	-100*	-20	5	30	10	-0.5	-3	10	10	8	12		10	5		
2SK315		=	洋 ]	FMチューナ	"	-20*			10,25*	200	125	-10	-0.5	2.5	24	5		-3.5	5	10	6	12		5	IDSS		
2SK316		松		ビデオカメラ	"	-10*		-10	5,50*	200	100*	-2	-7	5	24	5		-3	5	100	15			5	"		
2SK317		日		HF,VHF 電力增幅	MOS		180*	±20°	8A*	120W*	150*				1	140	0.5*	3 *	10	1mA	0.9	(S) 1.25		20	3A		
2SK318		"	1	"	"		180*	±20*	4A*	70W*	150*			and different residues in the first	1	140	0.5*	3 *	10	1mA	0.4	(S) 0.6		20	1.5A	and the same of the	
2SK319		"		高周波電力増幅 高速度電力SW	"		400*	± 20*	5A*	50W*	150*	±1μA	±20	and the second s	1	320	1.	5 *	10	.1mA	1	(S) 1.5		10	3A	-	
2SK320		"	_	"	"		450°	±20*	5A*	50W*	150*	±1μA	±20		1	360	1*	5 *	10	1mA	1	(S) 1.5		10	3A	er processor and the second of	
2SK321		松	F	広帯域低雑音増幅 ビデオカメラ	J	-15°		-15	5,50*	200	100*	-2	-7	5	42	5	own per ownerself street 990 o	-3	5	100	15	30		5	Ipss		
2SK322		E :	Ý. F	IF広帯域増幅	"	-15°		-15	5,50*	150*	150°	-10	-7	6	50	5		-3	5	100	25	45		5		ar and formation	and the second
2SK323		"	1	氏周波增幅	"			-40*	10,30*	150*	150*	-10	-30	1.6	12	10	-0.13	-1.5	10	10	8	12		10	3		and the second second
2SK324		東	2 1	高速高電圧 S W	MOS	a constitution que	400	± 20*	10A*	120W	150*	±100	±20	e algorithm was rec	1	400	1.5	3.5	10	1mA	3	(S) 5		10	5A	erene pers	and homeland some
2SK325		"		"	"		450	±20*	10A*	120W	150*	±100	±20		1	450	1.5	3.5	10	1mA	3	(S) 5		10	5A		

Ci, (I					電	<b>然</b> 1	的 特	11:	( I a	25°C)	Control of the State of State	-					(1) 44 13	外	
	pF)			C,	(pF)			NF (f	=1kHz, I	$R_{x} = 1M\Omega$	(dB)	NF	(f=100	MHz) (	dB)	その他	化特品		型名
typ	max	$\begin{bmatrix} V_{GS}(V) \\ I_D(mA)^* \end{bmatrix}$	V <sub>DS</sub>	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	In (mA)	typ	max	V <sub>DS</sub> (V)	ID (mA)		型名	肟	
6.5		0	10	1.9		0 *	10	0.5	120Hz,	$R_g = 100$ $10$	kΩ) Loss			**************************************	e especial out in the	The arabinor of the finishes the classes of the finishes and the finishes are the finishes and the finishes and the finishes are the finishes and the finishes and the finishes are the finishes and the finishes are the finishes and the finishes are the finishes are the finishes and the finishes are the finishes	and a state of the	80A	2SK301
3	and the second second	0	10	0.035	0.05	0 *	10					1.7	3	10	IDSS	PG = 28dB  typ  (f=100MHz)		105B	2SK302
5	MATERIAL PROPERTY OF A PROPERTY OF	0	10	1.5		0 *	10	11					-					126A	2SK303
5		0	10	1.5		0.	10		A - May row of street and									58A	2SK304
				a accessing of months cover	Access water access fill when you		and the second second							and Publishers W. S. Str. and Str.					2SK305
	ALL STREET, ST					a an enderson										And the second control of the second			2SK306
	and the second comments.				and the state of t				and the second							Si dia namin'ny fisika ny taona na kaominina na kaominina na kaominina ny fisika dia kaominina ny fisika na kaominina ny fisika na kaominina ny fisika ny fi			2SK307
1,130		0	10	80		0.	10		VD	S(ON)=1.	5Vmax	$(I_D=5A,$	$V_{GS} = 1$	5V)		A second administration of the design of the second of the		28B	2SK308
					are									Lander Lander		7			2SK309
440		0	10	13		0*	10		Vı	DS(ON)=8	Vmax (1	$I_D=2A$ ,	V <sub>cs</sub> = 15	V)	1	2SJ117とコンプリメンタリ		116B	2SK310
440		0	10	13	-	0.	10					"	# 400 gaya 14 to 17 to 18 to 1					116B	2SK311
1,500	******	0	10	35		0.	10		V <sub>D</sub> :	s(on) = 5.	4Vmax (	$(I_D=6A,$	$V_{GS} = 1$	5V)	· · · · · · · · · · · · · · · · · · ·	,		28B	2SK312
1,500		0	10	35		0 *	10					"						28B	2SK313
9		0	10	2.6		0.	10	0.6	(R <sub>g</sub> =	1kΩ)	5		NF=10	dB max	$(V_{DS}=1)$	10V, $I_D = 5mA$ , $R_g = 1k\Omega$ , $f = 10Hz$ )		73	2SK314
8		0	5	0.08	0.3	0.	5		1.0			2.2	4	5	IDSS	PG=23dB typ (f=100MHz)		58B	2SK315
	5	5 *	5															103A	2SK316
600		5	0	0.5		-50			Vi	os(on)=6	Vmax (I	D=4A	$V_{GS}=10$	V)	1	P <sub>0</sub> =120W min (f=100MHz)		129	2SK317
300		5	0	0.3		-50			Vı	OS(ON)=6	Vmax (I	D=2A	V <sub>GS</sub> =10	V)		Po=90W typ (f=100MHz)		129	2SK318
800		0	10	20		0*	10		Vos	S(ON)=5.	5Vmax (	$I_D=3A$	$V_{GS}=1$	5V)				116B	2SK319
800		0	10	20		0.	10			***		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,				The state of the s		116B	2SK320
8		0	5												Ī			103A	2SK321
															-			87A	2SK322
															<b> </b>			87A	2SK323
1,500	2,000	0	10	150	300	0 *	10		Vn	S(ON) = 7	Vmax (I	L p=10A.	$V_{GS} = 10$	V)	L			134	2SK324
	2,000	0	10	140	300	0.	10			S(ON) = 81								134	2SK325

	-			1		最 大	定	各(Ta	=25°C)	***********						電	気 自	内 特	性	(Ta	=25°C)	)				
型	名	社名	用 途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	V <sub>DSX</sub>	VGSO VGSS*	Ic Ip*	Pd Pch*	T <sub>i</sub>	IGSS	max	I	oss (m <i>l</i>	A)	,	VGS(off),	Vth*(V	/)		g <sub>m</sub> (m	s) μ*		8	os (mS	.) (Ω)
					V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> **	(mA)	(mW)	Tch*	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	Ι <sub>D</sub> (μΑ)	min	typ	max	V <sub>DS</sub> (V)	ID (mA)	typ	max
2SK32	6																									
2SK327	7																									
2SK328	8																									
2SK329	9																									
2SK330	)	東芝	低周波, 定電流回路, アナログSW	J	-50			10	200	125	-1	-30	1.2	14	10	-0.7	-6	10	0.1	1.5	4		10	I <sub>DSS</sub>		
2SK331	ı	三洋	コンデンサ・マイク	"	-20 <b>*</b>			10	100	125			0.06	1.5	10											
2SK332	2	"	差動増幅	"	-40	40*		10,20*	200 unit	125	-1	-20	1.2	12	10	(typ) -0.5		10	10		17		10	I <sub>DSS</sub>		
2SK333	3	"	"	"	-80	80*		10,20*	200 unit	125	-1	-30	1.2	12	30		-3	30	10	5	15		30	"		
2SK334		"	コンデンサ・マイク	"	-20*			10	100	125			0.06	1.5	10											
2SK335	;		And the second of the second o																							
2SK336	;	三洋	アナログSW	Mos		50 <b>*</b>	±12	400*	600	125	10	10		1μΑ	20	0.3	2.5	10	100	20	35		10	50		
2SK337		日電	高耐圧SW	"		500°	±20*	±100*	10W	150*	±100	±20		10μΑ	500	1	5	10	1mA	10	30		10	20		
2SK338	3																									
2SK339																										
2SK340							-																			
2SK341															-											
2SK342																										
2SK343		日立	低高周波電力増幅 高速度電力 S W	моѕ		140*	± 20°	8A*	100W*	150*	±1μA	±20		1	120	2 *	5 <b>*</b>	10	1mA	1	(S) 2		10	4A		
2SK344		"	"	"		160*	± 20°	8A*	100W*	150*	±1μA	±20		1	140	2 *	5 <b>*</b>	10	1mA	1	(S) 2		10	4A		
2SK345		"	"	"		40*	± 20°	5A*	30W*	150*	±1μA	± 20		1	30	2 *	5 <b>*</b>	10	1mA	0.5	(S) 0.9		10	3A		
2SK346		"	"	"		60*	±20°	5A*	30W*	150*	±1μA	± 20		1	50	2 *	5 *	10	1mA	0.5	(S) 0.9		10	3A		
2SK347		"	高周波電力増幅 高速度電力SW	"		400*	± 20*	1A*	10W*	150*	±1μA	±20		1	320	1 *	5 *	10	1mA	0.1	(S) 0.3		10	0.5A		
2SK348			The state of the s							market should be sell to											1					
2SK349		日 立	高周波電力増幅 高速度電力 S W	MOS		400*	± 20°	10A*	100W*	150°	±1μA	±20		1	320	1.	5 °	10	1mA	1.3	(S) 2.5		10	5A		
2SK350		"	"	"		450°	±20°	10A*	100W*	150°	±1μA	± 20		1	360	1.	5 *	10	1mA	1.3	(S) 2.5		10	5A		

					Æ	须 (	的特	<b>1</b> 11.	(Ta=	25°C)								代替品	外	
Cis	(pF)			Crs	(pF)			NF (f	=1kHz, F	$R_{\rm g} = 1 M\Omega$	(dB)	NF	(f=100	MHz) (	dB)	そ の	他	型名		型名
typ	max	$V_{GS}(V)$ $I_{D}(mA)$	V <sub>DS</sub> (V)	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	ID (mA)	typ	max	V <sub>DS</sub> (V)	In (mA)			H. 11	形	
												. ,,				And the state of t				2SK326
																				2SK327
-																	anna garaganna anna 19 a 1984 i Mallacha an ain an Aire Anna			2SK328
			and the state of t	The second secon													alle en cappe en grage de carbonista la proposition de la literatura de la literatura de la literatura de la l			2SK329
9		0	10	2.5		-10	$I_D = 0$			Ro	s(ON) = 32	20Ω typ	$(V_{DS}=1)$	mV, Vo	s=0, I	oss=5mA) 2SJ105とコンプリ	メンタリ		70A	2SK330
Zin=	20MΩ r	nin (f=1	kHz)							V <sub>NO</sub> =	-110dB	max (V	$I_{\rm IN}=0$						127	2SK331
13		0	10	3		0.	10	0.6	$R_c = 1k\Omega$	)   10	I <sub>DSS</sub>			⊿Vcs	== 30m Vm	$ax (V_{DS} = 10V, I_D = 1mA)$			107	2SK332
11		0	30	2		0.	30	1	$R_e = 10kS$	30	3			⊿V <sub>G</sub> s	= 30mVm	$ax (V_{DS} = 30V, I_D = 1mA)$			107	2SK333
Zin=	=20MΩ r	nin (f=1	kHz)		and the second s					V <sub>NO</sub> =	-110dB	max (V	7 <sub>IN</sub> =0)		And the second second				106	2SK334
			-																	2SK335
17		0	10	2.2		0.	10									$R_{DS(ON)} = 12\Omega \text{ typ } (V_{DS} = 10)$	/, I <sub>D</sub> =10mA)		57A	2SK336
20	100	0	10	1		0.	10		Rosco	ON)=100	Ω max ('	V <sub>GS</sub> = 10	$V, I_D=2$	0mA)					135	2SK337
																				2SK338
		<u> </u>	~~~										***************************************							2SK339
																				2SK340
																				2SK341
																				2SK342
800		0	10	60		0.	10		V	S(ON)=2	Vmax (I	D=4A,	$V_{GS} = 15$	V)	1	2SJ99とコンプリメンタリ	******************		117B	2SK343
800		0	10	60		0.	10				,	,				2SJ100とコンプリメンタリ			117B	2SK344
350		0	10	80	-	0.	10		VDS	S(ON)=1.	2Vmax (	$I_D=3A$ ,	V <sub>GS</sub> =1	5V)		2SJ101とコンプリメンタリ			116B	2SK345
350		0	10	80		0.	10				,	,				2SJ102とコンプリメンタリ			116B	2SK346
125		0	10	6		0.	10		V <sub>DS</sub>	(ON)=6V	max (I <sub>D</sub>	=0.5A,	$V_{GS} = 1$	5V)			100 (C. 1. 2000) \$ 100 (C. 1. 100 (C. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 1. 100 (C. 1		150	2SK347
	777												1	*********	Andrew Statement					2SK348
,500		0	10	35		0.	10		V <sub>DS</sub>	S(ON) = 4.	5Vmax (	$I_D=5A$ ,	$V_{GS}=1$	5V)	1	Andrew Marketine (1984)		1	149	2SK349
,500		0	10	35		0*	10												149	2SK350

		<u> </u>		T	1	最大	定札	咨(Ta	=25°C)		T			~~~		電	気 自	勺 特	性:	(Ta	=25°C)					
型	名	杜名	用 途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	V <sub>DSX</sub>	V <sub>GSO</sub>	IG	Pd	T <sub>i</sub>	Icss	max	I	oss (m	<b>A</b> )	,	GS(off),	Vth*(V	')		g <sub>m</sub> (m	S) μ*		g	os (mS	
					V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> ** (V)	I <sub>D</sub> *	Pch*	(°C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)		min	typ	max	V <sub>DS</sub> (V)	ID (mA)	r <sub>i)</sub> * typ	(Ω) max
2SK351		日立	高周波電力増幅 高速度電力SW	MOS		800*	± 20*	5A*	125W*	150*	±1μA	±20		1	640	1 *	5 *	10	1mA	1	(S) 2		10	3A		
2SK352	?	"	"	"		250*	±9*	300*	8W*	150*	±1μA	± 9		1	200	1	5	10	1mA	50	80		20	150		
2SK353	3	日電	C〜Kuバンド 低雑音増幅	GaAs		5	-6	120*	270	125*	-10μΑ	- 5	20	120	3	-0.5	-6	3	100	20	40	100	3	10		
2SK354		"	VHF〜Cバンド 低雑音増幅	"		5	6	150*	300	125*	-10μA	- 5	30	150	3	-0.8	-6	3	100	20	40	100	3	10		
2SK355		東芝	高速高電圧SW	Mos		150	± 20*	12A*	120W	150*	±100	± 20		1	150	1.5	3.5	10	1mA	3	(S) 6		10	10A		
2SK356	;	"	"	"		250	± 20*	12A*	120W	150*	±100	±20		1	250	1.5	3.5	10	1mA	3	(S) 6		10	10A		
2SK357		11	"	"		150	±20*	5A*	40W	150*	±100	± 20		1	150	1.5	3.5	10	1mA	0.8	(S) 1.8		10	3A		
2SK358		. "	"	"		250	±20*	5A*	40W	150*	±100	± 20		1	250	1.5	3.5	10	1mA	1	(S) 2.3		10	3A		
2SK359		日立	VHF, RF	"		20	±5	±1,30*	400*	150*	± 20	±5	4	12	10	0	-2	10	10	8	14		10	IDSS		
2SK360		"	"	"		20	±5	±1,30*	150*	150*	± 20	±5	4	12	10	0	-2	10	10	8	14		10	IDSS		
2SK361												antidation disputation to			and the second second second											
2SK362		東芝	低周波, アナログSW	J	-50			10	300	125	-1	-30	1.2	14	10	-0.25	-1.5	10	0.1	5	=5mA)   19		10	IDSS		
2SK363		"	"	"	-40			10	400	125	-1	-30	5	30	10	-0.3	-1.2	10	0.1	25	15mA) 60		10	"		
2SK364		"	"	"	40			10	400	125	-1	-30	2.6	20	10	-0.2	-1.5	10	0.1	(I <sub>DSS</sub> =	28		10	"		
2SK365		"	"	"	-50			10	200	125	-1	-30	1.2	14	10	-0.25	-1.5	10	0.1	5	=5mA) 19		10	"		
2SK366		11	"	"	-40			10	200	125	-1	-30	2.6	20	10	-0.2	-1.5	10	0.1	(I <sub>DSS</sub> = 12	=5mA) 28		10	"		
2SK367		"	低周波高電圧增幅 定電流回路	"	-100	4" men market e		10	200	125	-1	80	0.6	6.5	10	-0.4	-3.5	10	0.1	1.5	4.6		10	"		
2SK368		11	"	н	-100			10	150	125	-1	-80	0.6	6.5	10	-0.4	-3.5	10	0.1	1.5	4.6		10	"		
2SK369		"	低周波, 低雑音	11	-40			10	400	125	-1	-30	5	30	10	-0.3	-1.2	10	0.1	(I <sub>DSS</sub> = 25	40		10	"		
2SK370		"	"	"	-40			10	200	125	-1	-30	2.6	20	10	-0.2	-1.5	10	0.1	(IDSS =	22		10	"	0	-
2SK371		"	"	"	-40			10	200	125	-1	-30	5	30	10	-0.3	-1.5	10	0.1	$(l_{DSS} = 25)$	40		10	"		
2SK372		"	低周波, アナログSW	"	-40			10	200	125	-1_	-30	5	30	10	-0.3	-1.2	10	0.1	$(I_{DSS} = 25)$	15mA) 60		10	"		
2SK373		"	低周波高電圧增幅 低電流回路	"	-100			10	400	125	-1	-80	0.6	6.5	10	-0.4	-3.5	10	0.1	1.5	4.6		10	"		
2SK374		松下	低周波增幅,SW	"	-55*	55	-55	10,30*	200	125	-10	-30	1	20	10		-5	10	10	2.5	7.5		10	5		
2SK375		日 立	高周波電力増幅 高速度電力SW	MOS		300*	± 20°	1A*	10W*	150*	$\pm 1 \mu A$	± 20		1	240	1 *	5 *	10	1mA	200	400		10	500		

					促	Xi (	的 特	M:	(Ta=	25°C)		y		~	and last time -		化株品	外	
Cis	(pF)	The second second		C,,	(pF)			NF (f	= 1kHz, I	$R_{g} = 1M\Omega$	(dB)	NI	f (f=100	MHz) (	dB)	その他	型名		型名
typ	max	$V_{GS}(V)$ $I_D(mA)^*$	V <sub>DS</sub>	typ	max	$V_{GB}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	In (mA)	typ	max	$V_{DS}$ $(V)$	I <sub>D</sub> (mA)	A light services of Acids (1) a read of the distribution and an electric (1) a service and all the analysis and an electric and a service and	7: 11	形	
1,900	a married and a side of the	0	10	40		0 *	10		V	)S(()N)=9	Vmax ()	$I_D = 3A$ ,	$V_{GS} = 15$	V)				28B	2SK351
20		0	10	2.5		0.	10		VDS	S(ON) = 5 V	max (In	=100m	$V_{GS} =$	9V)				136	2SK352
	最大	発振周波:	数 90GF	lz typ								2.3	f=15GH 	z)   3	10	MAG=8dB typ (f=15GHz)		123	2SK353
	最大	発振周波	数 60GI	lz typ					and in the second			2	(f=8GHz	3	10	MAG=10dB typ (f=8GHz)		137	2SK354
1,600	2,200	0	10	350	600	0 *	10		Vos	(ON)=1.	8Vmax (	$I_0=40A$	$V_{GS} = 1$	0V)		Particular of Maria Control of Transport and Transport and Transport and Transport and Transport and Transport and Transport and Transport and Transport and Transport and Transport and Transport and Transport and Transport		134	2SK355
1,600	2,000	0	10	220	320	0 *	10		V <sub>DS</sub>	((ON)=2.	5Vmax (	$I_D = 30A$	$V_{GS} = 1$	0V)	and the second second second second	A description of the field of t		134	2SK356
260	350	0	10	50	100	0 *	10		VD	s(ON) = 9.	5 Vmax	$(I_D=8A,$	$V_{GS} = 1$	0V)			a year (generaling stage) of a debater of a produce of the first stage of the stage	138	2SK357
380	500	0	10	60	120	0.	10		V	s(ON) = 1	2Vmax (	$I_D = 8A$ ,	$V_{GS} = 10$	<b>V</b> )		A CONTROL OF THE PROPERTY OF T		138	2SK358
2.5		0	10	0.03		0 *	10			1	1	2	T	10	IDSS	PG=30dB typ (f=100MHz)		37A	2SK359
2.5	-	0	10	0.03		0 *	10					2	<b> </b>	10	IDSS	PG=30dB typ (f=100MHz)		87D	2SK360
													ga pagaman nga pagamanan			and the state of t			2SK361
13		0	10	3		-10	$I_D=0$						<del> </del>			$R_{DS(ON)}=80\Omega \text{ typ } \begin{pmatrix} V_{DS}=10\text{mV}, & V_{GS}=0 \\ I_{DSS}=5\text{mA} \end{pmatrix}$		82C	2SK362
75		0	10	15		-10	$I_D = 0$									$R_{DS(ON)}=20\Omega \text{ typ } \begin{pmatrix} V_{DS}=10\text{mV}, & V_{GS}=0 \\ I_{DSS}=15\text{mA} \end{pmatrix}$		82C	2SK363
30		0	10	6		-10	I <sub>D</sub> =0	F	LRDS(ON)=		$(V_{DS}=1)$	OmV, V	$c_{\text{GS}}=0$ , I	oss=5m	A)	2SJ104とコンプリメンタリ		82C	2SK364
13		0	10	3		-10	$I_D = 0$		T	<u> </u>	I	T				$R_{DS(ON)}=80\Omega \text{ typ } \begin{pmatrix} V_{DS}=10\text{mV}, & V_{GS}=0 \\ I_{DSS}=5\text{mA} \end{pmatrix}$		70B	2SK365
30		0	10	6		-10	$I_D=0$	F	ns(on)=		(Vps=1	1 0mV, V	$G_S = 0$ , I	ss=5m	A)	2SJ107とコンプリメンタリ		70B	2SK366
		0	10	3		I <sub>D</sub> =0	10	(f=	=100Hz,	$R_g = 100$	kΩ)	1	T					70A	2SK367
13		0	10	3		$I_{\rm D}=0$	10		100Hz,									105A	2SK368
13		0	10	15		-10	$I_D=0$		100Hz,	$\frac{10}{R_g = 100}$					<u> </u>			82C	2SK369
75			10	6		-10	$I_D=0$	(1	=10Hz,			ļ			1	2SJ108とコンプリメンタリ		70B	2SK370
30		0		15		-10	$I_D=0$	(f=	100Hz,	$\frac{10}{R_g=100}$	$(\Omega)$				ļ			70B	2SK371
75		0	10 10	15		-10	I <sub>D</sub> =0	5	10	10	5		-			$R_{DS(ON)}=20\Omega \text{ typ } \begin{pmatrix} V_{DS}=10\text{mV,} & V_{GS}=0 \\ I_{DSS}=15\text{mA} \end{pmatrix}$		70B	2SK372
75						$I_D=0$	10		100Hz,				<del> </del>			/1022—13my )		82B	2SK373
13		0	10	3				0.5 (f=	=100Hz,	$R_g = 100$	$I_{DSS}$		-					103A	2SK374
6.5		0	10	1.9		0 *	10	0.5	L	10	IDSS	[	Vac = 15	L	<u> </u>			150	2SK375
140		0	10	23		0.	10	<u> </u>	V	DS(ON)=4	vmax (.	ω=1A,	$V_{GS} = 15$	<b>v</b> /			L	L	

The same of the sa	***********					最 大	定	各 (Ta	=25°C)		T			·····		電	気 自	内 特	性	(Ta	=25°C)	'				
#Q	名	社名	用途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	Vosx	VGSO VGSS*	Ic	Pd	Ti	Icss	max	I	oss (m/	<b>A</b> )		VGS(off),	Vth*(V	<i>I</i> )		g <sub>m</sub> (m	S) μ*			gos (mS	
					V <sub>GDX</sub> ** (V)	VDSS*	V <sub>GSX</sub> ** (V)	I <sub>D</sub> *	Peh*	(°C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	I <sub>D</sub> (μA)	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	(Ω) max
2SK37	5	三洋	自コンデンサ・マイク	7 J	-20*	-		10	100	125			0.06	0.8	5											
2SK37	7	"	"	"	-20*			10	100	125			0.06	0.8	5											
2SK37	3	松	UHF 広帯域低雑音	GaAs		5	-4	1,130*	350	125	-80μA	-4	15	130	3		-4	3	500	40	75		3	30		
2SK379	)	"	SW電源 DC-DCコンバー:	Mos		400*	±20*	8A*	100W	150*	1			1	400	1.	5 *	VGS	1mA	2.5	(S)		25	5A		
2SK38	)	"	n n	"		450*	±20*	8A*	100W	150*				1	400	1*	5*	V <sub>G</sub> s	1mA	2.5	(S)		25	5A		
2SK381	l	三多	低周波電圧増幅 アナログSW	J	-50*			10	300	125*	-1	-30	0.3	12	10	-0.3	-6	10	10	1	3		10	IDSS		
2SK382	?	B Z	高周波電力増幅 高速度電力SW	MOS		500*	±20*	2A*	30W*	150*	±1μA	±20		1	400	2*	5 *	10	1mA	400	700		10	1A		
2SK383	3	"	"	"		100*	± 20*	10A*	50W*	150*	±1μA	±20		1	80	2 *	5 *	10	1mA	1.5	(S) 2.8		10	5A		
2SK384		"	11	"		500*	±20*	300*	10W*	150°	±1μA	±20		1	400	1.	5 *	10	1mA	60	100		10	200		
2SK385		東芝	高速高電圧SW	"		400	±20*	10A*	120W	150°	±100	±20		1	400	1.5	3.5	10	1mA	3	(S) 5		10	5A		
2SK386		"	"	"		450	± 20*	10A*	120W	150*	±100	± 20		1	450	1.5	3.5	10	1mA	3	(S) 5		10	5A		
2SK387		"	11	"		150	±20*	12A*	150W	150*	±100	±20		1	150	1.5	3.5	10	1mA	3	(S) 6		10	10A		
2SK388		"	11	"		250	±20°	12A*	150W	150*	±100	± 20		1	250	1.5	3.5	10	1mA	3	(S) 6		10	10A		
2SK389		"	低周波低雑音 差動增幅	J	-50			10	200	125	-1	-30	2.6	20	10	-0.15	-2	10	0.1	(I <sub>DSS</sub> =	=3mA) 20		10	I <sub>DSS</sub>		
2SK390																										
2SK391					7. 1																					
2SK392																										
2SK393						1 0			1			h	be- 1													
2SK394																										
2SK395																										
2SK396																										
2SK397															y						2		5,475.0	·		
2SK398		日 立	高周波電力増幅 高速度電力 S W	MOS		100*	± 20*	10A*	100W*	150*	±1μA	±20		1	80	2 *	5 *	10	1mA	1.5	(S) 2		10	5A		
2SK399		"	"	"		100*	± 20*	10A*	100W*	150*	±1μA	±20		1	80	2 *	5 *	10	1mA	1.5	(S) 2		10	5A		
2SK400		"	"	"		200*	± 20*	8A*	100W*	150*	±1μA	± 20		1	160	2 *	5 *	10	1mA	1	(S) 1.8		10	4A		

					T.	須 (	的 特	<u> </u>	(Ta=	25°C)	and a distance was a subface		.,					外	
Cis	(pF)	- man in an archite	and the state of t	C.,	(pF)		aga ma salahanaketeke	T	=1kHz, I	-	a) (dB)	NF	(f=100	MHz) (	dB)	その他	代替品		型名
typ	max	V <sub>GS</sub> (V) I <sub>D</sub> (mA)*	V <sub>DS</sub>	typ	max	V <sub>GD</sub> (V) V <sub>GS</sub> (V)*	V <sub>D\$</sub>	typ	max	V <sub>DS</sub>	I <sub>D</sub> (mA)	typ	max	V <sub>DS</sub>	I <sub>D</sub> (mA)		型名	形	
	Zin = 18N	dΩ min (	=1kHz	)					Vsc	,= -110	dBmax (	$V_{1N}=0$ )	or or or or or or or or or or or or or o			And the state of t		156	2SK376
		"								The second second second second second	"	· · · · · · · · · · · · · · · · · · ·	makantariak surtham saari 1999 (			The anticle of the complete open and a complete in the complete of the complet		127	2SK377
			ndern under reite, die den derkeinselbenk			-						(f	=800MH	z) 3	30	PG=10dBtyp (f=800MHz)	- Access to the second	91A	2SK378
800		0	20	30		0.	20		Ros	S(ON) = 1.	5Ω max (	$V_{GS} = 10$			1			140	2SK379
800		0	20	30		0.	20		Rı	DS(ON) = 2	Ω max (	V <sub>G</sub> s = 10	$V$ , $I_D = 5$	A)		the state of the s		140	2SK380
8	An again in the state of	0	10	1.5		0.	10		Roscon	N) = 250Ω	typ $\begin{pmatrix} f = V_{G} \end{pmatrix}$	$1kHz$ , $V_{s}=0$ , $I_{D}$	$I_{DS} = 10 \text{m}$ $s_S = 5 \text{mA}$	Vrms		2SJ40とコンプリメンタリ		151	2SK381
440		0	10	13		0 •	10				nax (I <sub>D</sub> =				the Market and the state of the			116B	2SK382
1,100		0	10	80		0.	10		VDS	ON)=0.9	Vmax (I	=5A,	$V_{GS} = 15$	7)				116B	2SK383
70		0	10	5		0.	10		V <sub>DS</sub> (	ON)=10V	max (ID:	=200mA	$V_{GS} =$	15V)				150	2SK384
,500	2,000	0	10	140	300	0.	10		VDS	ON)=7Vr	max (I <sub>D</sub> =	10A, V	$G_{GS} = 10V$	)				141	2SK385
,500	2,000	0	10	140	300	0.	10		V <sub>DS</sub> (	ON)=8Vr	nax (I <sub>D</sub> =	10A, V	cs=10V	)				141	2SK386
1,600	2,200	0	10	350	600	0.	10		VDS	ON)=1.8	Vmax (I	=10A,	$V_{GS} = 10$	V)				141	2SK387
1,600	2,000	0	10	220	320	0.	10		V <sub>DS</sub> (	ON)=2.5	Vmax (I	=10A,	$V_{GS} = 10$	V)				141	2SK388
25		0	10	5.5		-10	$I_D = 0$	0.5	$(R_g=1k\Omega)$	()   10	1	V <sub>G</sub> s	=20mV	max		2SJ109とコンプリメンタリ		148	2SK389
																			2SK390
																			2SK391
																			2SK392
																			2SK393
																			2SK394
																			2SK395
																			2SK396
							and and the second second second second												2SK397
800		0	10	70		0.	10		V <sub>DS</sub>	(ON)=1.	25Vmax (	$I_D=5A$ ,	V <sub>GS</sub> =1	5V)	L	2SJ112とコンプリメンタリ		28B	2SK398
800		0	10	70		0.	10									2SJ113とコンプリメンタリ		149	2SK399
750		0.	10	60		0.	10		V <sub>DS</sub>	(ON)=2.	8Vmax (I	D=4A,	V <sub>GS</sub> =15	v)		2SJ114とコンプリメンタリ		149	2SK400

	$\neg$					最 大	定析	} (Ta	=25°C)	- <del> </del>		the second day	Mary 005	***************************************		電	i 6'	) 特	性	(Ta	=25°C)					
型:	名	社 名	用 途	構造	V <sub>GDS</sub>	V <sub>DSX</sub>	V <sub>GSO</sub> V <sub>GSS</sub> *	IG	Pd	T <sub>j</sub>	Igss	max	In	ss (mA	7)	'	GS(off),	Vth*(V	7)		g <sub>m</sub> (m	S) μ*		g	., (mS	
.1.					V <sub>GDX</sub> **	V <sub>DSS</sub> *	V <sub>G</sub> sx**	I <sub>D</sub> *	Peh*	Teh* (*C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	Ι <sub>υ</sub> (μΑ)	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max
2SK401		日 立	高周波電力増幅 高速度電力SW	MOS		250*	±20*		100W*	150*	±1μΑ	±20		1	200	2 *	5 *	10	1mA	1.6	(S) 2.5		10	5A		
2SK402		"	"	"		400*	±20*	8A*	100W*	150*	±1μA	±20		1	320	2 *	5 <b>°</b>	10	1mA	1.2	(S) 1.7		10	4A		
2SK403		"	"	"		450°	±20*	8A*	100W*	150*	±1μA	±20		1	360	2 *	5 *	10	1mA	1.2	(S) 1.7		10	4A		
2SK404	:	三 洋	低周波, 高周波 増幅	J	-20	20*		10,20*	200	125	-1	-10	1.2	12	5		-2	5	10	5	10		5	Inss		
2SK405	]	東芝	低周波電力增幅	MOS		160*	±20*	8A*	100W	150	±1	±20				0.8	2.8	10	100mA	1	(S) 2		10	2A		
2SK406		日電	C〜Kuバンド 低雑音増幅	GaAs		5	- 6	120*	270	120*	-10μA	5	20	120	3	-0.5	-3.5	3	100	20	50	100	3	10		
2SK407		"	"	"		5	- 6	120*	270	120*	-10µA	-5	20	120	3	-0.5	-3.5	3	100	20	50	100	3	10		
2SK408		日 立	HF, VHF 電力増幅	MOS		180*	±20*	2A*	30W*	150*				1	140	0.5*	3 *	10	1mA	200	300		20	1A		
2SK409		"	"	"		180*	±20*	2A*	30W*	150*				1	140	0.5*	3 *	10	1mA	200	300		20	1A		
2SK410		"	"	"		180*	±20*	8A*	120W*	150*				1	140	0.5*	3 *	10	1mA	0.9	(S) 1.25		20	3A		
2SK411		"	高周波電力増幅 高速度電力 S W	"		600 <b>*</b>	±20*	5A*	100W*	150*	±1μA	± 20		11	500	2	5	10	1mA	1.5	(S) 2.3		10	3A		-
2SK412		"	11	"		250*	±20°	10A*	100W*	150*	±1μA	±20		1	200	2*	5 *	10	1mA	1.6	(S) 2.5		10	5A		
2SK413		"	"	"		140*	±20*	8A*	100W	150*	±1μA	±20		1	120	2 *	5 <b>*</b>	10	1mA	1	(S) 2		10	4A		
2SK414		"	"	"		160*	±20*	8A*	100W	150*	±1μA	± 20		1	140	2 *	5 <b>*</b>	10	1mA	1	(S) 2		10	4A		
2SK415		"	11	"		800*	± 20*	3A*	80W	150°	±1μA	±20		1	640	2 *	5 *	10	1mA	0.4	(S) 0.7		20	2A		
2SK416		n	11	"		40*	± 20°	2A*	10W	150*	±1μA	±20		1	35	1.	4 *	10	1mA	0.2	(S) 0.4		10	1A		
2SK417	j	東芝	高速大電流SW	"		60	± 20*	10A*	60W	150°	±100	±20		1	60	1.5	3.5	10	1mA	2	(S) 4		10	5A	and the same of th	
2SK418		"	高速度電圧SW	"		400	± 20*	2A*	50W	150°	±100	± 20	water and the same of the same	1	400	1.5	3.5	10	1mA	0.6	(S) 1.2		10	1A		
2SK419		"	"	"		450	± 20*	2A*	50W	150°	±100	± 20		1	450	1.5	3.5	10	1mA	0.6	(S) 1.2	and difference countries. Assess	10	1A		
2SK420		"	"	"		400	± 20*	5A*	60W	150°	±100	± 20	ally also associated and the second	1	400	1.5	3.5	10	1mA	1	(S) 2.5		10	3A		
2SK421		"	"	"		450	± 20°	5A*	60W	150*	±100	± 20		1	450	1.5	3.5	10	1mA	1	(S) 2.5	_	10	3A		and the same of th
2SK422		"	高速SW	"		60	± 20*	0.7A*	900	150°	±100	± 20		1	60	1.5*	3.5*	10	1mA	80	220		10	500		
2SK423		"	11	"		100	± 20*	0.5A*	900	150*	±100	± 20	accessor marks	1	100	1.5*	3.5*	10	1mA	50	150		10	300		enconnection of the Control
2SK424		日電	高耐圧大電流SW	,,		600°	± 20	3A*	100W	150*	±100	± 20		5	600	0.5	5	10	10mA	0.5	(S) 2	5	25	3A		
2SK425		"	低周波	J	<b>-50*</b>		50	10,30*	200	150	-1	- 20	1	18	10	-0.2	-1.2	10	10	7	9		10	1	Land	L

		T	_		Γ		最大	定 柞	各 (Ta	=25°C)							電	気 自	り 特	性	(Ta	=25°C)					
型	名	社:	名	用 途	構造	V <sub>GDS</sub>	Vosx	V <sub>G</sub> so V <sub>G</sub> ss*	Ic	Pa	T <sub>i</sub>	Igss	max	Iı	oss (m <i>A</i>	<b>A</b> )	'	/GS(off),	V <sub>th</sub> *(V	<b>'</b> )		g <sub>m</sub> (m	S) μ*		g	, (mS	
						V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> ** (V)	In* (mA)	Peh*	Tch* (*C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)		min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	(Ω) max
2SK426	5	В	電	低周波	J	-50*	50	-50	10,30*	200	150	-1	-20	1	18	10	-0.2	-1.2	10	10	7	9		10	1		
2SK427	7	Ξ	洋	AM チューナ RF	"	-15	15*		10,20*	200	125	-1	-10	1.2	12	5		-1.5	5	100	8	17		5	IDSS		
2SK428	3	В	立.	高速度電力SW 高周波電力増幅	MOS		60*	±20*	10A*	50W*	150°	±1μA	±20		1	50	2 *	5 *	10	1mA	1.5	(S) 2.2		10	5A		
2SK429	9	"		"	"		100*	±20*	3A*	20W*	150°	±1μA	±20		1	80	1 *	4 *	10	1mA	0.5	(S) 0.9		10	2A		
2SK430	)	"		"	"		150*	±20*	3A*	20W*	150°	±1μA	±20		1	120	1 *	4 *	10	1mA	0.5	(S) 0.9		10	2A		
2SK431	l	"		低周波低雑音	J		40	-40*	10, 30*	150*	150°	-10	-30	2.5	20	10	-0.13	-1.5	10	10	18	21		10	3		
2SK432	2			-					-																		
2SK433	3	Ξ :	菱	低周波電圧増幅 アナログSW	J	-50 <b>*</b>			10	150	125*	-1	-30	0.3	12	10	-0.3	-6	10	10	1	3		10	I <sub>DSS</sub>		
2SK434	ļ																										
2SK435	; 	日 :	立	低周波,高周波 増幅	J		22	-22	10,100	300*	150°	-10	-15	6	40	5		-2.5	5	10	20			5	10		
2SK436	; 	]= ;	#1	高周波,低周波 増幅	"	-15	15*		10,20*	150	125	-1	-10	1.2	12	5		-1.5	5	100	8	17		5	I <sub>DSS</sub>		
2SK437		松		SHF チューナ 低雑音増幅		-6*	5	-6	120*	270	125*	-10μA	-3	20	120	3		-3.5	3	100	20	50	100	3	10		
2SK438	3	"		"		-6*	6	-6	150	300	125*	-10μA	-3	20	120	3		-3.5	3	100	20	50	100	3	10		
2SK439	)	日 :	1	VHF, RF增幅	MOS		20	±5	±1,30	300*	150*	±20	±5	4	12	10	0	-2	10	10	8	14		10	Inss	***	ļ
2SK440	)	"		高速度電力SW 高周波電力増幅	"		200*	±20°	6A*	40W*	150*	±1μA	±20		1	160	2 *	5 <b>*</b>	10	1mA	1	(S) 1.8		10	3A		
2SK441		"		"	"		500*	± 20	300*	750*	150*	±1μA	±20		1	400	2 *	5 *	10	1mA	60	100		10	200		
2SK442		東	ِ خ	低周波電力増幅 高速SW	"		70*	±20°	10A*	30W	150	±1	± 20		1	70	1	3	5	1mA	1	(S) 1.9		5	2A	and the second of the second o	L
2SK443		三百	¥	ビデオカメラ初段	J	-15	15*		10,50*	200	125	-1	-10	5	38	5		-2	5	100	20	30		5	IDSS		
2SK444		"		"	"	-15	15*		10,50*	200	125	-1	-10	5	38	5		-2	5	100	20	30		5	"		
2SK445		"	1	"		-15	15*		10,50*	300	125	-1	-10	5	38	5		-2	5	100	20	30		5	"		A-45-5-5-5-
2SK446		日 1	1	SW	MOS		20*	±20*	±2A*	20W	150*	±100	±20		50μA	20	1.5	4	10	10mA	0.5	(S) 1.2		10	1A		
2SK447		東	اع	高速大電力SW モータドライブ			250°	±20°	±15A*	150W	150	±100	± 20	nderson - d'Olderson	1	250	1.5	3.5	10	1mA	4	(S) 7		10	15A	and the second s	
2SK448		日 1	E :	大電流SW	"		250°	±20*	±10A*	120W	150*	±100	±20		1	200	1	5	10	1mA	(S) 1			10	3A		
2SK449		"	_	"			450*	±20*	±8A*	120W	150*	±100	± 20	Avest Version	0.1	400	1	5	10	1mA	(S) 1			10	3A	arian provinces	- Committee of the Comm
2SK450																			And the last of the last of								

					T	从(	的 特	M:	(Ta=	25°C)							代替品	外	
Cis	(pF)			Crs	(pF)			NF (f	=1kHz, F	$R_{\pi} = 1M\Omega$	(dB)	NF	(f=100	MHz) (	dB)	その他	型名		型名
typ	max	V <sub>GS</sub> (V) I <sub>D</sub> (mA)*	V <sub>DS</sub> (V)	typ	max	$V_{GD}(V)$ $V_{GS}(V)^*$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max	V <sub>DS</sub>	I <sub>D</sub> (mA)		Y. A	形	and the second of the second o
13		0	10	3.2		0.	10	]	NV == 20m	ıV (max	)							78A	2SK426
7		0	5	2		0 *	5	1.5	(R <sub>g</sub> =	=1kΩ)   5	1					A Residence of Strategic and Strategic Strateg	the statement of controlling and color for the delice of the statement	157	2SK427
900		0	10	120		0.	10		Vos	(ON)=0.	75 Vmax	$(I_D=5A,$	$V_{GS} = 1$	5V)		2SJ122とコンプリメンタリ	No. of Concession, Name of Street, St. Street, St. Street, St. St.	116B	2SK428
280		0	10	24		0.	10		$V_{DS}$	(ON)=1.	4Vmax (	$I_D = 2A$ ,	$V_{GS} = 15$	(V)			And a strong sound of the strong stro	150	2SK429
260		0	10	14		0.	10		$V_{DS}$	(ON) = 2V	max (ID	=2A, V	$V_{GS} = 15V$	)				150	2SK430
28		0	10	5.6		0.	10				$e_n = 1n $	//√Hz	typ (VD	=10V,	$I_D = 3mA$	$A, R_g=0, f=1kHz)$		87E	2SK431
																7			2SK432
8		0	10	1.5		0.	10		Rosion	ι)=250Ω	typ (f=	1kHz, \ s=0, ID	$V_{DS} = 10n$ $O_{SS} = 5mA$	Vrms				152	2SK433
																,	*		2SK434
9	11	0	5	2.8	3.5	0.	5	0.5	(R <sub>g</sub> =	1 kΩ)	1							37B	2SK435
7		0	5	2	4	0 •	5	1.5	(R <sub>g</sub> =	1kΩ)	1							126A	2SK436
												1.8	f=12GH:	3	10	維音最小電力利得 10.5dB typ (f=12GHz)		103	2SK437
			AL ALL AND ALL													維音最小電力利得 10.5dB typ (f=12GHz)		103	2SK438
2.5		0	10	0.03		0.	10					2		10	IDSS	PG=30dB typ (f=100MHz)		8A	2SK439
750		0	10	60		0.	10		VDS	S(ON) = 1.	5Vmax (	$I_D=3A$	$V_{GS} = 1$	5V)				116B	2SK440
70		0	10	5		0.	10		RDS	s(ON)=50	Ω max (	$I_D=0.2A$	A, V <sub>GS</sub> =	15V)		And the second s		121B	2SK441
330		0	10	130		0.	10		VDS	S(ON) = 2.	8Vmax (	$I_D=7A$	$V_{GS} = 1$	5V)		2SJ123とコンプリメンタリ		138	2SK442
9		0	5	2.8		0.	5	1.5	(R <sub>g</sub> =	1kΩ) 5	1							126A	2SK443
9		0	5	2.8		0.	5	1.5	(R <sub>s</sub> =		1							157	2SK444
9	1	0	5	2.8		0.	5	1.5	(Rg=		1							57A	2SK445
150		0	10	150		0.	10									$R_{DS(ON)} = 0.4\Omega \text{ max } (V_{GS} = 12V, I_D = 1A)$	,	158	2SK446
2,000		0	10						Rosc	ON)=0.2	4Ω max	(I <sub>D</sub> =15A	, V <sub>GS</sub> =	10V)				141	2SK447
1,500	3,000	0	10	50		0.	10									$R_{DS(ON)} = 0.5\Omega \text{ max } (V_{GS} = 10V, I_D = 3A)$		108	2SK448
1,500	3,000	0	10	50		0.	10									$R_{DS(ON)} = 1.25\Omega \text{ max } (V_{GS} = 10V, I_D = 3A)$		108	2SK449
															1				2SK450

	· · · · · · · · · · · · · · · · · · ·		T				最 大	定 柞	各 (Ta	=25°C)							電	気 的	5 特	性	(Ta	=25°C)					
型	名	社名	í F	月 途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	Vosx	VGSO VGSS*	I <sub>G</sub>	Pd Pch*	T <sub>j</sub>	IGSS (nA)	max	I	oss (m <i>A</i>	<b>(</b> )	,	VGS(off),	Vth*(V	")		g <sub>m</sub> (m	S) μ*		g	os (mS	) (Ω)
						V <sub>GDX</sub> ** (V)	Voss*	V <sub>GSX</sub> **		(mW)	(°C)	(pA)*	V <sub>G</sub> s (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	I <sub>D</sub> (μA)	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max
2SK45	1																										
2SK45	2																										
2SK45	3	日 1	直高品	引波電力増幅	Mos		100*	±20*	10A*	120W	150*											(S) 1.8		7	3A		
2SK45	4	"		"	"		200*	±20*	8A*	120W	150*											(S) 1.5	<u> </u>	7	2A		ļ
2SK45	5	東	ェ コン イン	デンサ・マイク ピーダンス変換	J	-20*			10	100	125	(I <sub>G</sub>	-10	60 (µ	A)   500	5	-0.15	-0.8	5	0.1	0.5			5	IDSS		
2SK45	6	"		"	"	-20*			10	100	125	(I <sub>G</sub> -50	so) 10	60 60	A) 500	5	-0.15	-0.8	5	0.1	0.5	s = 200, 2	μΑ)	5	"		
2SK45	7	日 3	Z. SH 低杂	F, UHF 推音増幅	GaAs		6	+0.5 -6	100*	200*	125*	10μA	-5	30	100	5		-5	5	100		40		5	30		
2SK45	8	日 1	SW		Mos		150*	±20*	±1A*	16W	150*	±100	±20		50μΑ	100	1	5	10	1mA	0.5	(S) 0.6		10	0.5A		
2SK459	9	"	"		"		200*	±20*	±10A*	60W	150*	±100	±20		100μA	200	1	5	10	1mA	1	(S) 3		10	3A		
2SK460	0																										
2SK46	1			Charles and the Control of the Contr		_															(6)						
2SK462	2	日 1	£ sw		MOS		60*	±20*	±2A*	20W	150*	±100	±20		50μA	60	1	5	10	1mA	(S) 0.5			10	1A		
2SK463	3	"	"	and the second second	"		60*	±20*	±5A*	40W	150*	±100	±20		100μΑ	60	1	5	10	1mA	(S)			10	3A		
2SK464	4	"	"	attistic on which before the foreign at the first deal	"		60°	±20*	±8A*	50W	150*	±100	±20		50μA	60	1	5	10	1mA	(S) 1			10	4A		
2SK465	5			***************************************																							
2SK466	6			a again an ann ann an an aige air lite ann a									· *														
2SK467	7							Address reach the other Printers				-10000000000000000000000000000000000000									70)						
2SK468	3	日質	sw	TOUR WARE THE ANGEL OF	MOS		100*	±20*	±2A*	20W	150*	±100	±20		50μA	100	1	5	10	1mA	(S) 0.5			10	1A		
2SK469	9	nyer a ngapanan			a company																(6)						
2SK470	)	日旬	SW	CONTRACTOR TO THE REAL PROPERTY OF	MOS		100*	± 20°	±8A*	50W	150*	±100	±20		50µA	100	1	5	10	1mA	(S) 1			10	4A		
2SK471	l			resource o militale - many descriptions	and a supplement					and the second second						-			The same second district			ing water of consumer collect			***	Canada Service and Alexander	
2SK472	2	-	ļ	and the fall of the season of			- was come on the sec	- Appropriate to the state of			w   o  e=1 . o	ment lasts the	( (market)	- 1								e Bassaria Adama yina ani bir V	and the second s		page and the second second		
2SK473	3			their constitution for the delice control bloods			e <del>na</del> nanen da	and the same of the			AND THE TOTAL OF					and the second of the second of the					na ar Andrews (1990) (1990)	a named land nation of the constraint of the land of t	pané nyenye ndeloji ni ndenié te y			AL, VI JAMES MAN	
2SK474					and the second	-		-		and the same and			. 10 to 10 t	and the second second			ar the other		were transactive from the						AND THE REST		
2SK475	5																										

					Œ	汕	的特	M:	(Ta=	<b>25°</b> C)		Y		en diser independent			//\ kb	外	
Cis	( <b>pF</b> )			C <sub>r</sub> ,	(pF)			NF (f	=1kHz, l	$R_{\rm g} = 1M\Omega$	(dB)	NF	f (f=100	MHz) (	dB)	そ の 他	代替品		型名
typ	max		V <sub>DS</sub> (V)	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	In (mA)	typ	max	V <sub>DS</sub> (V)	In (mA)		型名	形	a programme de la compansión de principa de conferencia del conferencia de confer
							Ann. or a 111 \ m. o o o o							and the second second		South conductivities and the control of the control			2SK451
																The control of the co	an and a state of the State of		2SK452
350		0	10	10		-50,0*			Po	=120W t	yp $\begin{pmatrix} V_{DS} \\ f=1 \end{pmatrix}$	=50 V, 00MHz,	$P_{in} = 5W$ $I_{DD} = 0.$	1A)		$R_{ON} = 0.5\Omega \text{ max } (V_{GS} = 20 \text{ V}, I_D = 3 \text{ A})$		159	2SK453
350		0	10	10		-50,0*	the second secon		Po	=140W t	yp $\begin{pmatrix} V_{DS} \\ f=1 \end{pmatrix}$	=80V, 00MHz,	$P_{in} = 5W$ $I_{DD} = 0.$	1A)		$R_{ON}=1\Omega$ max $(V_{GS}=20V, I_D=2A)$		159	2SK454
7.2		0	5	2.3	A Phonometric Control on the Control of Control on the Control on	-5	$I_D = 0$				$V_N = 40n$	nVmax (	$V_{DD} = 5V$	$R_L=1$	kΩ, Av	$=80 dB, C_{g}=10 pF)$		160	2SK455
7.2		0	5	2.3		-5	$I_D = 0$		ionalministrability Worth 1					"				155	2SK456
	and the section of th											2.2	(f=3GHz 	)   5	10	PG=10dB typ (f=3GHz)		175B	2SK457
300		0	10	50		0 *	10									$R_{DS(ON)} = 1.5\Omega \text{ max } (V_{CS} = 10V, I_D = 0.5A)$	and the same of th	161	2SK458
900		0	10	60		0 *	10									$R_{DS(ON)} = 0.5\Omega \text{ max } (V_{GS} = 10V, I_D = 3A)$		162	2SK459
									-										2SK460
													***************************************						2SK461
300		0	10	100		0.	10									$R_{DS(ON)} = 0.5\Omega \text{ max } (V_{GS} = 10V, I_D = 1A)$		163	2SK462
500		0	10	100		0.	10									$R_{DS(ON)} = 0.3 \Omega \text{ max } (V_{GS} = 10V, I_D = 3A)$		164	2SK463
600		0	10	20		0.	10							***************************************		$R_{DS(ON)} = 0.2\Omega \text{ max } (V_{GS} = 10V, I_D = 4A)$		162	2SK464
					İ														2SK465
																			2SK466
																			2SK467
300		0	10	100		0.	10									$R_{DS(ON)}=1\Omega \text{ max } (V_{GS}=10V, I_D=1A)$		163	2SK468
																			2SK469
900		0	10	120		0.	10									$R_{DS(ON)}=0.3\Omega$ max $(V_{GS}=10V, I_D=4A)$		162	2SK470
				)															2SK471
																			2SK472
																			2SK473
																			2SK474
																			2SK475

						最 大	定相	各 (Ta	=25°C)							電	気 自	<b>的</b> 特	* 性	(Ta	=25°C)					
#9	名	社名	用 途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	Vosx	V <sub>GSO</sub> V <sub>GSS</sub> *	IG	Pa	T <sub>i</sub>	Icss	max	I	DSS (mA	()	,	VGS(off),	Vth*(V	7)		gm (m	S) μ*		g	os (mS	(Ω)
					V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> **	I <sub>D</sub> *	Pch*	(°C)	(nA) (pA)*	V <sub>G</sub> s (V)	miņ	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	$I_{D}$ $(\mu A)$	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max
2SK47	6														1			-								
2SK47	7	日質	sw	MOS		250*	±20*	±8A*	60W	150*	±100	±20		100µA	250	1	5	10	1mA	1	(S) 3		10	3A		
2SK47	8					(3)																				
2SK47	9																									
2SK48	0																									
2SK48	1																			(0)			-			
2SK48	2	日電	SW	MOS		450*	±20*	±5A*	50W	150*	±100	±20		100μΑ	450	1	5	10	1mA	(S)			10	2A		
2SK48	3	-																								
2SK48	4																ļ					ļ				
2SK48	5															ļ										
2SK48	6																									
2SK487	7																									
2SK488	8																									
2SK489	9														and the first special and the second		·		ļ							
2SK490	0														<del>-</del> -		-									
2SK491			Id this has been booked										white walking or water													
2SK492			低周波電圧増幅 アナログSW	1	-50*	and the second second second		10	150	125*	-1	-30	1	12	10		-3	10	10	6	15		10	IDSS		
2SK493	3	三洋	ビデオカメラ初段	"	-15	15*	-	10,50*	300	125	-1	-10	5	38	5		-2.2	5	100	15	27	N	5	"		
2SK494		日立	低周波高周波增幅	"		22	-22	10, 100*	300*	150*	-10	-15	6	40	5		-2.5	5	10	20			5	10		
2SK495	5										man differential for Con-															
2SK496						~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~	andreas and the later of										-				*					
2SK497	<b>'</b>	Not the same time									Security out of the last							and the same of th		us provincements						
2SK498			and the second second second second		r gan tidar sing ian and		( Table 1 )									Million of the control of	all the control of the control	and the stay to the state of								
2SK499	)		and the second s										graph allegas (1800)			a mandan marin and Mandala		To consideration while a light control		automata des Printessadio And	arkinikani dali di					
2SK500	)			<u> </u>													<u>L</u>									

					電	须(	的特	i 11:	(Ta=	25°C)		n a water water					//b ++ //	外	
Cia	( <b>pF</b> )			С.,	(pF)			NF (f	=1kHz, R	$R_g = 1M\Omega$	) (dB)	NF	(f=100	MHz) (	dB)	その他	代替品		型名
typ	max	$\begin{bmatrix} V_{GS}(V) \\ I_{D}(mA)^{\bullet} \end{bmatrix}$	V <sub>DS</sub> (V)	typ	max	$V_{GB}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	In (mA)	typ	max	V <sub>DS</sub> (V)	ID (mA)		型名	Ħ∌	
																			2SK476
600		0	10	40		0 *	10									$R_{DS(ON)} = 0.8\Omega$ max $(V_{GS} = 10V, I_D = 3A)$		162	2SK477
and the second second																			2SK478
		e impresser e de origeneere e		Andrew Ver. Section S. 1986 Pro-							The second second second	- American	The second secon						2SK479
							en Marke religi kalayay Marke a			and the same of th	Control of Control					And worked to the contribution of the language of the contribution			2SK480
										ar algebrasia, en estado en estado en estado en estado en estado en estado en estado en estado en estado en es			Promocilianole (III Alvilla) - 174						2SK481
600		0	10	20		0.	10									$R_{DS(ON)} = 2\Omega \text{ max } (V_{GS} = 10 \text{ V}, I_D = 2 \text{ A})$		162	2SK482
		To lines distances																	2SK483
				Market Balley (A) Bulley										-					2SK484
													-						2SK485
														11					2SK486
																			2SK487
																			2SK488
																			2SK489
																			2SK490
																			2SK491
20		0	10					1 (f:	= 100Hz,	R <sub>g</sub> =1k9	Ω)					$R_{DS(ON)}=70\Omega \text{ typ } \begin{pmatrix} f=1\text{kHz}, & V_{DS}=10\text{mVrms} \\ V_{GS}=0, & I_{DSS}=5\text{mA} \end{pmatrix}$		152	2SK492
7		0	5	2		0.	5	1.5	$R_g = 1k\Omega$	5	1							165	2SK493
9	11	0	5	2.8	3.5	0.	5	0.5	$R_{\bullet} = 1k\Omega$	5	1							8B	2SK494
																		- 1	2SK495
	ADDRESS OF STREET																		2SK496
																			2SK497
																			2SK498
										774									2SK499
																	a delata de la completa del la completa del la completa del la completa de la completa de la completa de la completa de la completa de la completa de la completa de la completa de la completa del la completa del la completa del la completa del la completa del l	La Carrier Prop	2SK500

				1		最 大	定札	各 (Ta	=25°C)							電	気 自	勺 特	性	(Ta	=25°C)					
型	名	社 名	用途	構造	V <sub>GDS</sub>	V <sub>DSX</sub>	VGSO VGSS*	IG	Pd	Ti	Icss	max	I	DSS (m/	<b>A</b> )		VGS(off),	$V_{th}^*($	V)		gm (m	s) μ*			gos (mS	) (O)
					V <sub>GDX</sub> **	V <sub>DSS</sub> *	V <sub>GSX</sub> **	I <sub>D</sub> *	Pch*	(°C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	$I_D$ $(\mu A)$	min	typ	max	V <sub>D</sub> s (V)	I <sub>D</sub> (mA)	typ	max
2SK501																										
2SK502								-																		
2SK503											ļ															
2SK504																										
2SK505		日電	ビデオ帯, 高馬 波増幅	J	15*	15	-15	5, 50*	400	125	-1	-10	10	50	5	-0.6	-3.5	5	10	14	26		5	IDSS		
2SK506																										
2SK507	I	日電	ビデオ帯, 高周 波増幅	J	-15*	15	-15	5, 50*	350	150	-1	-10	10	50	5	-0.6	-3.5	5	10	14	26		5	IDSS		
2SK508		"	"	"	-15*	15	-15	5, 50*	200	150	-1	-10	10	50	5	-0.6	-3.5	5	10	14	26		5	IDSS		T Y
2SK509												-														
2SK510		4																								
2SK511	E	立	高速度電力 SW 高周波電力増幅	MOS		250*	±9*	300*	8W*	150*	±1μA	±9		1	200	1 *	5 *	10	1mA	50	80		20	500		
2SK512			高速度電力SW	"		500*	±20*	12A*	125W*	150*	±1μA	± 20		1	400	2 *	4 *	10	1mA	2.5	(S) 3.5		10	6A		
2SK513		n	高速度電力SW 高周波電力増幅	"	******	800*	±20	3A*	60W*	150*	±1μA	± 20		1	640	2 *	4 *	10	1mA	0.4	(S) 0.7		20	2A		
2SK514										encountral transition little liberature	The state of the s															
2SK515			endert ettungsakuludedi on Sanaskansoniide							And the Parket of the Control of the																-
2SK516																										
2SK517			apeniar in Marian de Labora de Maria (n. 1886). Para de Carrella (n. 1886).										APT 4 PT Access 64 To 1							Andrewson March 18 and						
2SK518	E	電電	高周波増幅	J	-30*	30	-30	10, 50*	400	150	-1	- 20	30	110	10	-1.5	-9	10	10		22		10	Inss	and the second	
2SK519		"	"	,,	-30*	30	-30	10, 50*	350	150	-1	-20	30	110	10	-1.5	-9	10	10		22		10	Iuss		
2SK520		"	"	"	-30*	30	-30	10, 50*	200	150	-1	-20	30	110	10	-1.5	-9	10	10	THE SECURITION OF SPICE	22		10	IDSS		
2SK521			aging published and approximate the second agreement agreement and an approximate the second agreement agr														nn - danud ma . arii						4		Araba Arrasa	
2SK522			gar ngaya shigiri sar shigang gabag bilak difficulta (i) ngaying basil sibir s				ang makan bilandik da						-F					a surfal terretory	e en a completito de a d	Maria A. S. P. Miller and	and the second section of the				Transport Committee Committee	And the second of the second of the second
2SK523			gala diagram and property and being all and an arrivery of management	and the second			ant abilities du l'embrer es en le le V		STATE STATE OF STREET	adaptahan melangan sa	and moving per or		a all hadronic di li dalam di li ma	AT LOSS SELF WHEN	ando un de medica e Trac	erinerinenna araitti			and the second of	No. of the second						genter riteration and a transfer
2SK524	7						***************************************			age construction of the	arture or en	n) 14/27 64			er blouwer op i vite farmene van v			an al Più - America America	-Maryal TVs India are a	terruptuser entrettini	- which is a second of the se	mark de major militar	ally on marking		L. CORNEL PROPERTY	
2SK525	Я	泛芝	DC-DC コンバータ	MOS		150*		10A*	40W		**********	Ourgoure or to	retirence una		water # #* - 4 W	(V 1.5	' <sub>th</sub> )   3.5		1mA		(S) 4	and the second of the second	10	5A	una como ne tras per muelto.	ARCHES - No. 10 to 8

F)	$V_{GS}(V)$ $I_{D}(mA)^{*}$	V <sub>DS</sub>		(pF)			ME (C.											代替品		
max	$V_{GS}(V)$ $I_D(mA)^*$	V <sub>DS</sub>	_				MP (I	= [kHz, F	$R_{g} = 1M\Omega$	(dB)	NF	(f=100	MHz) (	dB)	そ	Ø	他	1511		型名
			typ	max	$\begin{bmatrix} V_{GD}(V) \\ V_{GS}(V)^{\bullet} \end{bmatrix}$	V <sub>DS</sub>	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max	V <sub>DS</sub> (V)	In (mA)	enhana ann a na she shekhilin sa kulturi.			型名	彤	time the state of
												and the second second	anna an an an an an an an an an an an an		and the second s	nama ya Madili ilifi i an'angka a kata a akkila sika lan				2SK501
															Alexander of the second of the second of the second of the second of the second of the second of the second of	and the control that they also apply the control of	an may recover a la company management destruction and distance			2SK502
			of the state of th													,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,				2SK503
			in the many residency decreased and the																	2SK504
	10*	5	1.6	Assemble and the second second	10mA	5						211111111111111111111111111111111111111							53B	2SK505
									-						and the state of t					2SK506
	10*	5	1.6		10mA	5	Anna and the second and the second			Annual Control of the Control of the Control	Commission of the				and the second s				104B	2SK507
	10*	5	1.6		10mA	5				Mr. San Marian (Thinks of San Asia V						an an an ann an Aire ann an Aire an Aire an Aire an Aire an Aire an Aire an Aire an Aire an Aire an Aire an Ai	photo die desire del proposition de la company de la compa		78A	2SK508
																				2SK509
								***************************************									and the same of th			2SK510
	0	10	2.5		0 *	10			VDS(ON)	=5Vmax	$(I_D=10$	0mA, V	GS=9V)						136	2SK511
	0	10	50		0 *	10	<u> </u>		VDS(ON)	=3.9Vm	ax (I <sub>D</sub> =	6A, V <sub>G</sub>	=15V)		and the second s				28B	2SK512
	0	10	22		0.	10		R	s(ON)=6	Ω max (I	D=2A	$V_{GS} = 15$	V)		- International Control of the Contr				116B	2SK513
															-					2SK514
																				2SK515
																				2SK516
															the state of the s					2SK517
	10*	10	2		10mA	10							No. 20. 20. 20. 2						53A	2SK518
	+									And the second second second second									104B	2SK519
																			78A	2SK520
					1															2SK521
						-									-					2SK522
																and the same of the same of	V			2SK523
									ensembritish billionek Kironey dir 🗝											2SK524
								n		L	(In — E A	Va = -	01/)	L	or non-life and describe and a second second second			1		2SK525
		10*	10° 5 10° 5 10° 5  0 10 0 10 0 10 10 10° 10	10° 5 1.6  10° 5 1.6  10° 5 1.6  0 10 2.5  0 10 50  0 10 22  10° 10 2  10° 10 2	10° 5 1.6  10° 5 1.6  10° 5 1.6  0 10 2.5  0 10 50  0 10 22  10° 10 2  10° 10 2	10° 5 1.6 10mA 10° 5 1.6 10mA  0 10 2.5 0° 0 10 50 0° 0 10 22 0°  10° 10 2 10mA  10° 10 2 10mA	10° 5 1.6 10mA 5 10° 5 1.6 10mA 5  10° 5 1.6 10mA 5  0 10 2.5 0° 10  0 10 50 0° 10  0 10 22 0° 10  10° 10 2 10mA 10  10° 10 2 10mA 10	10° 5 1.6 10mA 5 10° 5 1.6 10mA 5  10° 5 1.6 10mA 5  0 10 2.5 0° 10  0 10 50 0° 10  0 10 22 0° 10  10° 10 2 10mA 10  10° 10 2 10mA 10	10° 5 1.6 10mA 5  10° 5 1.6 10mA 5  0 10 2.5 0° 10  0 10 50 0° 10  0 10 22 0° 10  Ref. 10° 10 2 10mA 10  10° 10 2 10mA 10  10° 10 2 10mA 10	10* 5 1.6 10mA 5  10* 5 1.6 10mA 5  0 10 2.5 0 * 10 Vosioni 0 10 50 0 * 10 Vosioni 0 10 22 0 * 10 Rosioni=6  10* 10 2 10mA 10  10* 10 2 10mA 10  10* 10 2 10mA 10	10° 5 1.6 10mA 5  10° 5 1.6 10mA 5  0 10 2.5 0° 10 V <sub>DS(ON)</sub> =5V <sub>max</sub> 0 10 50 0° 10 V <sub>DS(ON)</sub> =3.9V <sub>m</sub> 0 10 22 0° 10 R <sub>DS(ON)</sub> =6Ω max (1  10° 10 2 10mA 10  10° 10 2 10mA 10  10° 10 2 10mA 10	10° 5 1.6 10mA 5  10° 5 1.6 10mA 5  0 10 2.5 0° 10 V <sub>DS(ON)</sub> =5Vmax (I <sub>D</sub> =10  0 10 50 0° 10 V <sub>DS(ON)</sub> =3.9Vmax (I <sub>D</sub> =2A,  0 10 22 0° 10 R <sub>DS(ON)</sub> =6Ω max (I <sub>D</sub> =2A,  10° 10 2 10mA 10  10° 10 2 10mA 10  10° 10 2 10mA 10	10° 5 1.6 10mA 5  10° 5 1.6 10mA 5  0 10 2.5 0° 10 V <sub>DS(ON)</sub> =5Vmax (I <sub>D</sub> =100mA, V <sub>OS(ON)</sub> =3.9Vmax (I <sub>D</sub> =6A, V <sub>OS(ON)</sub> =6Ω max (I <sub>D</sub> =2A, V <sub>OS</sub> =15)  10° 10 2 10mA 10  10° 10 2 10mA 10  10° 10 2 10mA 10	10° 5 1.6 10mA 5  10° 5 1.6 10mA 5  0 10 2.5 0° 10 V <sub>DS(ON)</sub> =5Vmax (I <sub>D</sub> =100mA, V <sub>CS</sub> =9V)  0 10 50 0° 10 V <sub>DS(ON)</sub> =3.9Vmax (I <sub>D</sub> =6A, V <sub>CS</sub> =15V)  0 10 22 0° 10 R <sub>DS(ON)</sub> =6Ω max (I <sub>D</sub> =2A, V <sub>CS</sub> =15V)  10° 10 2 10mA 10  10° 10 2 10mA 10	10° 5 1.6 10mA 5 10° 5 1.6 10mA 5 10° 10 V <sub>DS(ON)=5</sub> Vmax (I <sub>D</sub> =100mA, V <sub>GS</sub> =9V) 0 10 50 0° 10 V <sub>DS(ON)=6</sub> Ω max (I <sub>D</sub> =2A, V <sub>GS</sub> =15V) 0 10 22 0° 10 R <sub>DS(ON)=6</sub> Ω max (I <sub>D</sub> =2A, V <sub>GS</sub> =15V) 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10	10° 5 1.6 10mA 5 10mA 5 10mA 5 10mA 5 10mA 5 10mA 5 10mA 5 10mA 5 10mA 5 10mA 5 10mA 5 10mA 5 10mA 5 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10 2 10mA 10 10° 10° 10° 10° 10° 10° 10° 10° 10°	10° 5 1.6 10mA 5  10° 5 1.6 10mA 5  10° 5 1.6 10mA 5  0 10 2.5 0° 10 Vosions=5Vmax (ID=100mA, Vcs=9V)  0 10 50 0° 10 Vosions=3.9Vmax (ID=6A, Vcs=15V)  0 10 22 0° 10 Rosions=6Q max (ID=2A, Vcs=15V)  10° 10 2 10mA 10  10° 10 2 10mA 10  10° 10 2 10mA 10	10° 5 1.6 10mA 5  10° 5 1.6 10mA 5  0 10 2.5 0° 10 Vosion=SVmax (Io=100mA, Vos=9V)  0 10 50 0° 10 Vosion=3.9Vmax (Io=6A, Vos=15V)  0 10 22 0° 10 Rosion=6Ω max (Io=2A, Vos=15V)  10° 10 2 10mA 10  10° 10 2 10mA 10  10° 10 2 10mA 10	10° 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 5 1.6 10mA 10 10° 10 2 10mA 10 10° 10° 10° 10° 10° 10° 10° 10° 10°	10

			1	T	T	最 大	定析	各(Ta	=25°C)		<u> </u>					電気	i ś	特	性	(Ta	=25°C)					
型 :	名	社名	用途	構造	V <sub>GDS</sub>	V <sub>DSX</sub>	V <sub>GSO</sub>	IG	Pd	T <sub>i</sub>	IGSS	max	Iı	oss (mA	1)	V	GS(off),	Vth*(V	7)		g <sub>m</sub> (m	S) μ*		g	os (mS r <sub>D</sub> *	) (0)
					V <sub>GDX</sub> **	Voss*	Vgss* Vgsx** (V)	ID* (mA)	Pch*	Tch* (*C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub>	Ι <sub>D</sub> (μΑ)	min	typ	max	$V_{DS}$ $(V)$	I <sub>D</sub> (mA)	typ	max
2SK526		東芝	DC-DCコンバー	9 MOS		250*		10A*	40W							(V <sub>1</sub>	1h) 3.5		1mA		(S) 4		10	5A		
2SK527	-	"	"	"		60*		10A*	40W							(V <sub>1</sub>	ւհ) 3.5		1mA		(S) 4		10	5A		
2SK528		"	SWレギュレー	9 "		400*		2A*	30 W							(V <sub>0</sub>	3.5		1mA		(S) 1		10	1A		
2SK529		"	"	"		450*		2A*	30W							(V <sub>1</sub>	3.5		1mA		(S) 1		10	1A		
2SK530		"	"	"		400*		5A*	40W							( V <sub>i</sub>	3.5		1mA		(S) 2.5		10	3A		
2SK531		"	"	"		450*		5A*	40W							(V <sub>1</sub>	3.5		1mA		(S) 2.5		10	3A		
2SK532		"	"	"		60*		12A*	40W							1.5	3.5		1mA		(S) 5		10	6A		
2SK533											-										(2)					
2SK534		日立	高速度電力SV	w Mos		800*	± 20*	5A*	100W*	150°	±1μA	± 20		1	640	2 *	4 *	10	1mA	0.8	(S) 1.2		20	3A		
2SK535		"	"	"		400*	± 20*	1.5A*	20W*	150*	±1μA	±20		0.1	320	2 *	4 *	10	1mA	0.2	(S) 0.4		20	1A		
2SK536																					(0)					
2SK537		東芝	SWレギュレー	9 MOS		900*		1A*	60 W							(V <sub>1</sub>	3.5		1mA		(S) 0.45		10	0.5A		
2SK538		"	"	"		900*		3A*	100W							1.5	3.5		1mA		(S) 1		10	1.5A		
2SK539		"	"	"		900*		5A*	150W							1.5	3.5		1mA		(S) 2		10	3A		
2SK540				j kali									<u> </u>													
2SK541																										
2SK542																										
2SK543															Labora & Marth (Michigan)											
2SK544														and the second second second												
2SK545								and the second s																		
2SK546						n Marie van de Visco														er seremente						
2SK547								anne de service de service de service de service de service de service de service de service de service de ser		and the state of t			A													
2SK548			and the second s			e estatula apparado a esta esta e				all lands on the same		y arvan canada ante milio			gar vegeta jihandi at un sijatini		***********									Accessor for a
2SK549						The same and the same of the s						an de Maria Maria (aleman)	**************	and the second second				or a shellowing table .			According to the Parket				******	or at a transmission.
2SK550																										

		NOTES CARGO PETERS SEE		Printed Artistant Co. No. of the Web To	T	X (	的 特	1	( Ta =		and the state of	T							代标品	外	
Cis	(pF)			Crs	( <b>pF</b> )			NF (f	= 1kHz, 1	$R_{g} = 1MC$	1) (dB)	NF	f=100	MHz) (	dB)	そ	Ø	他	型名		型名
typ	max	$V_{GS}(V)$ $I_D(mA)^*$	(V)	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	Vos (V)	typ	max	V <sub>DS</sub>	ID (mA)	typ	max	V <sub>DS</sub>	In (mA)	a sina a disabasii yiki dhawad a dhisiistiin da dha ilibad	name a company and distributed from second	rated Militaria i Brookly on the Wall St.	15 11	形	
				-		na diamana na isi Mondho di Alban	and a section		Rose	ON) = 0.6	Ω max (	$I_D = 5A$ ,	$V_{GS} = 10$	V)		nen Sannin d. f. bir dağı mağladırını dilik den bir ildi.					2SK526
									Rose	on)=0.1	4Ω max	$(I_D = 5A,$	$V_{GS} = 1$	0V)		Value of the last section					2SK527
									Rose	on = 2.2	Ω max ()	$I_D=1A$ ,	$V_{GS} = 10$	V)							2SK528
									Rose	on) = 2.5	Ω max (	$I_D = 1A$ ,	$V_{GS} = 10$	V)							2SK529
		A CONTRACTOR OF THE CONTRACTOR							Rose	on)=1.4	Ω max (	$I_D = 3A$ ,	$V_{GS} = 10$	V)							2SK530
							and the second second second		Rose	on)=1.6	Ω max (	$I_D = 3A$ ,	$V_{GS} = 10$	V)							2SK531
							The second section of		Rose	on)=0.0	7Ω max	$(I_D=6A,$	$V_{GS} = 1$	0A)							2SK532
																					2SK533
850		0	10	40		0.	10		Vı	os(ON) = 1	2Vmax (	$I_D = 3A$ ,	$V_{GS} = 1$	)V)						149	2SK534
250		0	10	10		0.	10		$V_{DS(ON)} = 12V_{max} (I_D = 3A, V_{GS} = 10V)$ $V_{DS(ON)} = 6V_{max} (I_D = 1A, V_{GS} = 15V)$											150	2SK535
																					2SK536
									Rose	ον)=9Ω	max (I <sub>D</sub> :	=0.5A,	V <sub>GS</sub> = 10	V)							2SK537
	and the second s								Rose	ON)=4.5	Ω max (]	$I_D = 1.5A$	, V <sub>GS</sub> =	10V)	Andrew State Control of the Control		-				2SK538
									Rose	ON)=2.5	Ωmax (]	$I_D=3A$ ,	$V_{GS} = 10$	V)							2SK539
																					2SK540
																					2SK541
										-											2SK542
																					2SK543
																					2SK544
																					2SK545
														J. T. J. J. J. J. J. J. J. J. J. J. J. J. J.							2SK546
																					2SK547
																					2SK548
																					2SK549
																					2SK550

		T		the second state of the second section of the section of the	1		最大	定す	各 (Ta	=25°C	)						電	気 !	的 特	产性	(Ta	=25°C)					
型	名	社名	用用	途	構造	V <sub>GDS</sub>	VDSX	V <sub>GSO</sub> V <sub>GSS</sub> *	IG	Pd	T <sub>i</sub>	Igss	max	I	DSS (m/	<b>A</b> )	'	Jascoff),	V <sub>th</sub> * (\	<b>J</b> )		gm (m	S) μ*			gos (mS	3)
						V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSS</sub> * V <sub>GSX</sub> ** (V)	I <sub>D</sub> *	Pch*	(°C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	$I_D$ $(\mu A)$	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	(Ω) max
2SK55	1																										
2SK55	2																										
2SK55	3																										- 2
2SK55	4																										
2SK55	5																										
2SK556	6																										
2SK55	7																										
2SK558	8																										
2SK559	9															*											
2SK560	0																										
2SK561	1																										
2SK562	2							*																			
2SK563	3																										
2SK564	1																										
2SK565	5										-0													-			
2SK566	5																										
2SK567	,																	- Pro-William Paradiana									
2SK568	3									VII. II . 180 VII. III.		- Parameter Comments and a second															
2SK569	)																										
2SK570	)			Total Control of the			***************************************					4-5-4-4															
2SK571																		and the second							- 1		
2SK572	:	東芝	DC-DC =	ンバータ	моѕ		150°			100W	r when an order a sakel a						1.5*	3.5*	May see a landstrange and	1mA		(S 6.	5	10	10A		
2SK573	A Producer vacan	"	"	en ambama della artara a barrer	"		250°			100W						. 2004. 1.00	1.5*	3.5*		1mA		(S 6.	)	10	10A		
2SK574			THE STREET STREET			maker of encourage of																					
2SK575			Manager - Manager Transporter and							er ander authorize	According to the second																

		And the second of the second of	A		Æ	気 (	的 特	; <u>†</u>	(Ta=	25°C)									/h th =	外	
Cis	(pF)			Crs	(pF)			NF (f	=1kHz, 1	$R_s = 1M\Omega$	(dB)	NF	(f=100	MHz) (	dB)	7	Ø	他	代替品		型名
typ	max	$V_{GS}(V)$ $I_{D}(mA)^{*}$	V <sub>DS</sub>	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub>	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)			and a supplicable (Salahilla supplicable should show a source source).	型名	形	
	2000																				2SK551
			- American American																		2SK552
																					2SK553
		e per interessor was elected			THE RESERVE OF THE PERSON OF T		-														2SK554
				productive extraorresiste in a file in Superior								and the following support of the				Anna Marka M					2SK555
			The second secon			the second															2SK556
and the second second						na a naiseanna air i meann air i n ann a	a (Sparing para Assignar) para maharan														2SK557
																					2SK558
																					2SK559
																					2SK560
																	-				2SK561
																					2SK562
																					2SK563
																	- A - 1712 - J - AN - AND - AN				2SK564
																ann der namme and an Oliver an Abrahabababababababababababababababababab					2SK565
																Annual science and the Section of th		-			2SK566
																					2SK567
																					2SK568
																					2SK569
																	THE RESERVE OF THE PERSON NAMED IN COLUMN TWO IS NOT THE PERSON NAMED IN COLUMN TWO IS NAMED IN THE PERSON NAMED IN THE PERSON NAMED IN THE PERSON NAMED IN THE PERSON NAMED IN THE PERSON NAMED IN THE PERSON NAMED IN THE PERSON NAMED IN THE PERSON NAMED IN THE PERSON NAMED IN THE PERSON NAMED IN TH				2SK570
																A The second second second second second second second second second second second second second second second		.,			2SK571
								Rds(ON)	=0.18Ω	max (ID	=10A, \	/cs=10	l V)	,							2SK572
							-				=10A, V					and the second section of the second section of the second section section section section section section sec					2SK573
														170							2SK574
																			<u> </u>		2SK575

	1		Π		最 大	定 柞	杏 (Ta	=25°C)							電	気 的	5 特	性	(Ta	=25°C)			γ		
型名	社名	用 途	構造	V <sub>GDS</sub>	Vosx	V <sub>GSO</sub>	Ic	Pa	T <sub>i</sub>	IGSS	max	Iı	oss (mA	()	. v	GS(off),	Vth*(V	) .		g <sub>m</sub> (m	S) μ*		g	。 (mS	(Ω)
				V <sub>GDX</sub> **	V <sub>DSS</sub> *	V <sub>GSX</sub> ** (V)	ID* (mA)	Pch*	Tch*	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	Ι <sub>D</sub> (μΑ)	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max
2SK109A	三菱	低周波, 低雑音	J	-50*			10,20*	150 unit	125	-1	-30	1	12	10		-3	10	10	6	15		10	IDSS		
2SK127A	松下	低周波	"	-80			10,20*	250	125			0.5	-12	10					3			10	"		
2SK130A	日電	低周波, 低雑音	,,	-30°	30	-30	10,50*	250	125	-1	-20	5	30	5	,	-1.5	5	10	28	9		5	"		
2SK134®	日立	高速度電力SW	Mos		140	±15°	7A	100W*	150°						0.15	1.45	10	100mA	0.7	(S)	1.4	10	3A		
≥SK135®	<b> </b> "	"	"		160	±14°	7A*	100W*	150*						0.15	1.45	10	100mA	0.7	(S)	1.4	10	3A		
2SK160A	日電	低周波, VHF	J	-50°		50	10,20*	150	125	-1	-30	0.5	12	5	-0.25	-4.5	5	10	1.5	2.1		5	0.5		
2SK176⊕	日立	高周波電力増幅 高速度電力 SW	Mos		200*	± 20	8A*.	125W	150		-		3	160	0.55*	3*	10	100mA	0.7	(S)	1.4	10	3A		
2SK192A	東芝	FM, VHF	J	-18*			10	200	125	-10	-1	3	24	10	-1.2		10	1		7		10	I <sub>DSS</sub>		
2SK214®	日立	高周波電力増幅 高速度電力SW	MOS		160	±15°	500°	30W*	150°						0.2*	1.5*	10	10mA	20	40		20	10		
2SK216®	"	"	"		216	±15°	500°	30W*	150°						0.2*	1.5*	10	10mA	20	40		20	10		
2SK293A	日電	高耐圧高速度 大電流 SW	"		300*	± 20*	7A*	100W	150°	±100	± 20		1	300	0.4	3	10	50mA	0.6	(S) 1		10	3A		
FLC08ME	富士通	Cパンド高出力	GaAs		15	-5		3W	175*				450	5	-2		3	10mA		100		5	160		
FLC15ME	"	"	"		15	-5		6W	175*				900	5	-2		3	20mA		200		5	300		
FLC30ME	"	"	,,		15	-5		11.5W	175*				1.8A	5	-2		3	40mA		400		5	600		
FLC081WF	"	"	"		15	-5		3.3W	175*				550	5	-2		3	10mA		130		5	200		
FLC151WF	"	"	"		15	-5		6.5W	175*				1.1A	5	-2		3	20mA		250		5	400		
FLC301MG-4	"	II .	"		15	-5		15W	175*				2.2A	5	-2		3	40mA		500		5	800		
FLC301MG-6	"	ı,	"		15	-5		15W	175*				2.2A	5	-2		3	40mA		500		5	800		
FLC301MG-8	"	"	"		15	-5		15W	175*				2.2A	5	-2		3	40mA		500		5	800		
FLM3742-3	"	"	"		15	-5		18.8W	175*				2.4A	5	-2		3	50mA		500		5	800		
FLM3742-5	"	"	"		15	-5		26.3W	175*				4.4A	5	-2		3	80mA		(S) 1		5	1.6A		
FLM4450-3	"	"	"		15	-5	~	18.8W	175*				2.4A	5	-2		3	50mA		500		5	800		
FLM4450-5	"	"	" .		15	-5		26.3W	175*				4.4A	5	-2		3	80mA		(S) 1		5	1.6A		
FLM5964-3	"	"	"		15	-5		18.8W	175*				2.4A	5	-2		3	50mA		500		5	800		
FLM5964-5	"	11	"		15	- 5		26.3W	175*				4.48	8	-2		3	80mA		(S)		5	1.6A		

	- mar Districtives				Œ	な ロ	的特	11:	(Ta = 25°C	C)		**************************************								外		٦
Cit	(pF)			C,	(pF)			NF (f=1	kHz, R <sub>e</sub> =	1MΩ)	(dB)	NF	(f=100	MHz) (	dB)	ŧ	Ø	他	代替品		型名	١
typ	max	$V_{GS}(V)$ $I_D(mA)^{\bullet}$	V <sub>DS</sub>	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max (	Vos V)	ID (mA)	typ	max	Vos (V)	In (mA)				型名	形		
20		0	10					(f=100H 1	$     \begin{array}{ccc}       z, & R_{R} = 1 \\       2.5 &   \\     \end{array} $	kΩ) 10	1			<b>∆</b> V <sub>GS</sub> :	= 30mVm	$nax (V_{DS} = 10V,$	$I_D = 1 mA$ )			84	2SK109A	
	A COLUMN TO SERVICE THE SERVIC							NV	/=80mVm	nax (V	os=10\	$V$ , $I_D = 1$	mA, Rg	=100kΩ	)					80	2SK127A	
55		5 *	10	10		5mA	10	(R <sub>g</sub> :	$=100\Omega$ )	5	5					NF=3dB max	$ \begin{pmatrix} V_{DS} = 5V, \\ f = 100Hz, \end{pmatrix} $	$R_g = 5mA$ $R_g = 100\Omega$		53A	2SK130A	
600		5	10	10		-5*	10		V <sub>DS(s</sub>	· • t) = 12	2Vmax	$(I_D=7A$	, V <sub>GD</sub> =(	)		2SJ49⑪とコン	プリメンタリ	)		28A	2SK134®	, .
600		-5	10	10		-5*	10				/	,				2SJ50⑪とコン	イプリメンタリ	)		28A	2SK135@	, .
4.1		0	10	0.9		0.	10													78A	2SK160A	
800		5	10					ton=60n	s typ, toff	r == 200n	ns typ (	$I_D=2A$	$V_{GS} = 1$	5V, R <sub>L</sub> :	=15Ω)					28A	2SK176@	)
					0.65	-10						2	3.5	$\begin{pmatrix} 10 \\ (V_{DD}) \end{pmatrix}$		PG=20dBtyp	(f=100MHz	)		88	2SK192Λ	ŀ
90		10*	10	2.2		10mA	10		VDS(sa	(t)=2Vr	max (I	n=10mA	, V <sub>GD</sub> =	0)						116A	2SK214®	,
90		10*	10	2.2		10mA	10				"									116A	2SK216⊕	,
950	1,500	-5	10	10		5 <b>*</b>	10	V <sub>DS(ON)</sub> =	=5.2Vma	x, Ros	s(on) == 1	.3Ωmax	$(V_{GS} = )$	5V, I <sub>D</sub> =	=4A)					108	2SK293A	
			Pout =	28dBm t	yp, Gp=	9dB typ	( V <sub>E</sub>	s=8.5V,	I <sub>DS</sub> ≃I <sub>DSS/</sub>	/2, f=	4GHz,	$P_{in} = 1$	9dBm)							145	FLC08ME	
			Pout=	31dBm t	ур, Ср=	7.5dB ty	/p (V	s=8.5V,	I <sub>DS</sub> ≃I <sub>DSS</sub> ,	/2, f=	4GHz,	Pin=2	3.5dBm)							145	FLC15ME	
			Pout =	34dBm t	ур, Gp=	6.5dB ty	p (V <sub>D</sub>	s = 8.5V, 1	I <sub>DS</sub> ≃I <sub>DSS</sub>	/2, f=	4GHz,	Pin=2	7.5dBm)							145	FLC30ME	;
			Pout=	28.5dBm	typ, Gr	=6.5dB	typ (VD	s=10V, In	os≃Ioss/2	2, f=8	BGHz,	Pin = 220	dBm)							143	FLC081WF	
			Pout=	30.5dBm	typ, Gr	=5.5dB	typ (VD	s=10V, I <sub>D</sub>	s=I <sub>DSS</sub> /2	2, f=8	BGHz,	Pin=25	dBm)							143	FLC151WF	
		**************************************	Pout=	33dBm ty	/p, Gp=	8dB typ	(V <sub>D</sub>	s=10V, I <sub>D</sub>	os≃I <sub>DSS</sub> /2	2, f=4	.2GHz	, Pin=	25dBm)			A Committee of the Comm			-	144	FLC301MG-	4
			Pout=	33dBm ty	p, Gp=	7dB typ	(V <sub>D</sub>	$s=10V$ , $I_D$	os≃I <sub>DSS</sub> /2	2, f=7	.2GHz	, Pin=	26dBm)							144	FLC301MG-6	5
			Pout=	33dBm ty	p, Gp=	6dB typ	(V <sub>D</sub>	s=10V, I <sub>D</sub>	s≃I <sub>DSS</sub> /2	2, f=8	3.5GHz,	, Pin=	27dBm)							144	FLC301MG-8	8
			Pout=	35dBm ty	p	The Providence of the Association of the Associatio	(V <sub>D</sub>	s=10V, I <sub>D</sub>	s≃I <sub>DSS</sub> /2	2, f=3	3.7~4.	2GHz,	Pin=28.	5dBm)						146	FLM3742-3	
		and the submidient in the submidient of the subm	Pout=	37dBm ty	rp q		(V <sub>D</sub>	s=10V, I <sub>D</sub>	s=I <sub>DSS</sub> /2	2, f=3	3.7~4.	2GHz,	Pin=28.	5dBm)						146	FLM3742-5	1
			Pout=	35dBm ty	'p		(V <sub>D</sub>	s=10V, I <sub>D</sub>	s≃I <sub>DSS</sub> /2	2, f=4	.4~5.	0GHz,	Pin = 29d	Bm)						146	FLM4450-3	
			Pout=	37dBm ty	'P		(V <sub>D</sub>	$s = 10V$ , $I_D$	s≃I <sub>DSS</sub> /2	2, f=4	.4~5.	0GHz,	Pin=29d	Bm)						146	FLM4450-5	1
			Pout=	35dBm ty	p		(V <sub>D</sub>	s=10V, ID	s≃I <sub>DSS</sub> /2	2, f=5	.9~6.	4GHz,	Pin=30d	Bm)		a ad Casandan saucht nur Manten Manhamman han All Cashall (Casha)				146	FLM5964-3	1
			Pout =	37dBm ty	'p		(VD	s=10V I <sub>D</sub>	s≃I <sub>DSS</sub> /2	2, f=5	.9~6.	4GHz,	Pin=31d	Bm)				CONTRACTOR AND AND AND AND AND AND AND AND AND AND		146	FLM5964-5	

		T		<u> </u>		最 大	定札	各 (Ta	=25°C)							電	気 自	勺 特	性	(Ta	=25°C)					
	型 名	杜名	用 途	構造	V <sub>GDS</sub>	V <sub>DSX</sub>	V <sub>GSO</sub> V <sub>GSS</sub> *	Ic	Pd	T <sub>i</sub>	Icss	max	I	oss (m <i>P</i>	<b>(</b> )	,	VGS(off),	Vth*(V	7)		gm (m	S) μ*		g	gos (mS	(Ω)
					V <sub>GDX</sub> **	V <sub>DSS</sub> *	V <sub>GSX</sub> **	I <sub>D</sub> *	Pch*	Tch* (*C)	(nA) (pA)*	V <sub>GS</sub> (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	Ι <sub>D</sub> (μΑ)	min	typ	max	V <sub>DS</sub> (V)	ID (mA)	typ	max
	FLM6472-5	富士通	Cバンド,高出力	GaAs		15	-5		26.3W	175*				4.4A	5	-2		3	80mA		(S) 1		5	1.6A		
	FLM7177-5	"	"	"		15	-5		26.3W	175*				4.4A	5	-2		3	80mA		(S) 1		5	1.6A		
	FLM7785-4	"	"	"		15	-5		26.3W	175*				4.4A	5	-2		3	80mA		(S) 1		5	1.6A		
*	FLS02W	"	Sバンド,高出力	GaAs SB		12	-5		1.5W	175°		***************************************		250	5	-2		3	1mA	22	50		5	50		
Ì	FLS09	"	"	"		15	-5		3W	175*				450	5	-2		3	10mA	45	90		5	160		
	FLS09ME	"	"	GaAs		15	-5		3W	175*				450	5	-2		3	10mA		90		5	160		
	FLS16	"	"	"		15	-5		6W	175*				900	5	-2		3	20mA		180		5	300		
	FLS16ME	"	"	"		15	-5		6W	175*				900	5	2		3	20mA		180		5	300		
	FLS31	"	"	"		15	5		11.5W	175*				1.8A	5	-2		3	40mA		350		5	600		
	FLS31ME	"	"	"		15	-5	-	11.5W	175*				1.8A	5	-2		3	40mA		350		5	600		
	FLS50	"	"	GaAs SB		15	-5		15W	175*				2400	5	-2		3	50mA	250	500		5	800		
	FLS50ME	"	11	GaAs		15	-5		15W	175*				2.4A	5	-2		3	50mA		500		5	800		
	FLX03MB	"	X バンド 高出力, 発振	"		12	5		2.5W	175*			ty 29	р 90	5						80		5	150		
	FLX06MB	"	11	"		12	5		5W	175*			ty 65	р 50	5						150		5	300		
	FLX12MB	"	"	"		12	-5		8.8W	175*			ty 15		5						300		5	700		
*	FLX30MB	"	"	"		12	-5		15W	175*			t y 25	р 00	5						500		5	1200		
	FSX51W/WF	"	Sバンド,低雑音	"		5	-5		1W	175*			30	120	3	-1	-5	3	1mA	10	25		3	30		
1	FSX52W/WF	"	Cバンド, 低雑音	"		12	-5		1.5W	175*			100	220	3	-2		3	2mA		50		3	60		
	FSX53W/WF	"	"			12	-5		3W	175*			200	450	3	-2		3	5mA		100		3	120		
	M47F	松下	低周波, 低雑音	J	-30	30	-30	30*	250	125	-1	-20	0.5	20	10	-0.1	-2	10	10	4	8		10	1		
	MGF1202	三 菱	比惟日相	GaAs	-6*	8	-6	100*	300	150*	- 10μA	-3	30	100	3	-0.5	-5	3	100	25	35		3	30	maga in against change beaut	. services
	MGF1402	"	S帯~X帯 低雑音増幅		-6*	8	-6	100°	300	150*	-10μA	-3	30	100	3	-0.3	-5	3	100	25	35	-	3	30	******	
	MGF1403	"	S帯~Ku帯 低雑音増幅		-6*	6	-6	80*	200	150*	-10μA	-3	20	80	3	-0.3	-5	3	100	20	30		3	30		
	MGF1404	"	"	"	-6*	6	-6	80*	200	150*	-10μA	-3	15	80	3	-0.3	-5	3	100	20	30		3	15		
L	MGF1412	"	S 带~X 带 低雑音増幅	"	-6*	8	-6	100*	300	150*	-10μΑ	-3	30	100	3	-0.3	-5	3	100	25	35		3	30		

	電 気 的 特 性 (Ta=25°C)	. 外	
Cis (pF)	$C_{rs}$ (pF) $\left  \begin{array}{c c} NF & \left  \begin{array}{c c} F = 1kHz, R_g = 1M\Omega \end{array} \right  & NF & \left  \begin{array}{c c} F = 100MHz \end{array} \right  & dB \end{array} \right $ を 他	ļ	型名
	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	形	
	$P_{out} = 37dBm \text{ typ}$ $(V_{DS} = 10V, I_{DS} \simeq I_{DSS}/2, f = 6.4 \sim 7.2 \text{GHz}, P_{in} = 32dBm)$	146	FLM6472-5
	$P_{out} = 37dBm \text{ typ}$ (VDS = 10V, IDS = IDSS/2, f=7.1~7.7GHz, $P_{in} = 33dBm$ )	146	FLM7177-5
*	P <sub>out</sub> =36dBm typ (V <sub>DS</sub> =10V, I <sub>DS</sub> ≃I <sub>DSS</sub> /2, f=7.7~8.5GHz, P <sub>in</sub> =32dBm)	146	FLM7785-4
	$P_{out} = 22dBm min, Gp = 12dB typ$ ( $V_{DS} = 10V, I_D = 1/2 I_{DSS}, f = 4GHz, P_{in} = 11dBm$ )	93	FLS02W
	$P_{out} = 28dBm \text{ typ, } Gp = 9dB \text{ typ} \qquad (V_{DS} = 10V, I_{D} \approx 1/2 I_{DSS}, f = 4GHz, P_{in} = 19dBm)$	94	FLS09
	$P_{out}=28dBm \text{ typ, } Gp=9dB \text{ typ} \qquad (V_{DS}=10V, I_{DS}\simeq I_{DSS}/2, f=4GHz, P_{in}=19dBm)$	145	FLS09ME
	$P_{out}=31dBm \text{ typ}, Gp=7.5dB \text{ typ} $ ( $V_{DS}=10V, I_{DS}\simeq I_{DSS}/2, f=4GHz, P_{in}=23.5dBm$ )	94	FLS16
	P <sub>out</sub> =31dBm typ, Gp=7.5dB typ (V <sub>DS</sub> =10V, I <sub>DS</sub> ≃I <sub>DSS</sub> /2, f=4GHz, P <sub>in</sub> =23.5dBm)	145	FLS16ME
Annual State of the State of th	$P_{out} = 34dBm \text{ typ}, Gp = 6.5dB \text{ typ}  (V_{DS} = 10V, I_{DS} \simeq I_{DSS}/2, f = 4GHz, P_{in} = 27.5dBm)$	94	FLS31
	P <sub>out</sub> =34dBm typ, Gp=6.5dB typ (V <sub>DS</sub> =10V, I <sub>DS</sub> ≃I <sub>DSS</sub> /2, f=4GHz, P <sub>in</sub> =27.5dBm)	145	FLS31ME
	P <sub>out</sub> =36dBm typ, Gp=5.5dB typ (V <sub>DS</sub> =10V, I <sub>D</sub> =1/2 I <sub>DSS</sub> , f=4GHz, P <sub>in</sub> =30.5dBm)	94	FLS50
	P <sub>out</sub> =36dBm typ, Gp=5.5dB typ (V <sub>DS</sub> =10V, I <sub>DS</sub> =1 <sub>DSS</sub> /2, f=4GHz, P <sub>in</sub> =30.5dBm)	145	FLS50ME
	Pout = 23dBm min, Gp = 8dB typ (V <sub>DS</sub> = 10V, I <sub>D</sub> = 1/2 I <sub>DSS</sub> , f=12GHz, P <sub>in</sub> =16dBm)	95	FLX03MB
	Pout = 26dBm min, Gp = 7dB typ (V <sub>DS</sub> = 10V, I <sub>D</sub> = 1/2 I <sub>DSS</sub> , f = 12GHz, P <sub>in</sub> = 20dBm)	95	FLX06MB
	Pout = 29.5dBm min, Gp = 5.5dB typ (V <sub>DS</sub> = 10V, I <sub>D</sub> = 1/2 I <sub>DSS</sub> , f = 12GHz, P <sub>in</sub> = 25dBm)	95	FLX12MB
		95	FLX30MB
			FSX51W/WF
		96 (W)	FSX52W/WF
		130 (WF	
		38	M47F
	$e_n=1.9 \text{nV}/\sqrt{\text{Hz}} \text{ typ (VDs}=10 \text{V, } I_D=1 \text{mA, } f=1 \text{kHz})$ $   (f=4 \text{GHz})   3   10   \text{Gs}=11 \text{dB typ (} f=4 \text{GHz}) $	166	
	1.4 1.0 (f=4GHz) (4.001)	122	MGF1402
	1.1 1.4 (f=19CH <sub>2</sub> )	122	
	1.8   2.3   3   10   05=10.3db typ (1=120H2)	122	
	1.6   1.7   3   10   05-10.3db typ (1-12012)	122	-
	最大発振周波数 70GHz typ	122	MGF 1412

.

			T		T	Γ	最 大	定	格(Ta	=25°C)		T	-		*****		電	気 É	内 特	* 性	(Ta	=25°C)				***************************************	-
	型	名	社名	用途	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	V <sub>DSX</sub>	V <sub>GSO</sub> V <sub>GSS</sub> *	IG	Pd	Ti	Icss	max	]	DSS (m	<b>A</b> )		VGS(off),	Vth*(	7)		g <sub>m</sub> (m	S) μ*			gos (mS	
						VGDX**	V <sub>DSS</sub> *	VGSX**	I <sub>D</sub> *	P <sub>ch</sub> *	Tch*	(nA) (pA)*	V <sub>GS</sub>	min	max	V <sub>DS</sub>	min	max	V <sub>DS</sub>	$I_D$ $(\mu A)$	min	typ	max	V <sub>DS</sub>	I <sub>D</sub> (mA)	r <sub>D</sub> *	(Ω) max
ı	MGF18	01	三参	S帯~X帯 中電力増幅	GaAs		8	-8	250*	1W	150*	-20μA	<del> </del>	150	250	3	-1.5	-6	3	100	70	90	T T	3	100		Γ
ı	MGF18	02	,,	C帯~X帯 中電力増幅	"		8	-8	250*	1.5W	150*		<del> </del>	150	250	3	-2	-6	3	100	70	90		3	100		
l	MGF21	16	"	S帯~X帯 中電力増幅	"		11	-10	550*	3W	150*			300	550	3	-2	-7	3	1mA		175		3	200		-
ı	MGF21	17	,,	C帯~X帯 中電力増幅	"		11	-10	550*	3W	150*		<b> </b>	300	550	3	-2	-7	3	1mA		175		3	200		
ı	MGF21	24	"	C帯~Ku帯 電力増幅	"		11	-11	800*	4.2W	150°			450	800	3	-2	-7	3	1mA	180	250		3	300		
I	MGF21	24F	"	~Ku帯 電力増幅	"		11	-11	800*	4W	150*			450	800	3	-2	-7	3	1mA	180	250		3	300		
ı	MGF21	24G	"	"	"		11	-11	800*	4W	150°			450	800	3	-2	-7	3	1mA	180	250		3	300		
Ī	MGF21	48	"	C帯~Ku帯 電力増幅	"		11	-11	1.6A*	8.3W	150*			0.9	A)   1.6	3	-2	-7	3	1mA	360	500		3	600		
	MGF21	48F	"	~Ku 帯 電力増幅	"		11	-11	1.6A*	8W	150*			0.9	A)   1.6	3	-2	-7	3	1mA	360	500	*****	3	600		
	MGF21	48G	"	"	"		11	-11	1.6A*	8W	150°			0.9	A)   1.6	3	-2	-7	3	1mA	360	500		3	600		
	MGF21	72	11	S帯~X帯 電力増幅	"		11	-11	2.3A*	12.5W	150*			1.5	A)   2.3	3	-2	-7	3	1mA	540	750		3	900		
	MGF22	05	"	S帯~C帯 電力増幅	"		11	-11	3.6A*	12.5W	150°			2	A) 3.6	3	-2	-7	3	10mA		800		3	1.4A		
	MGF-X	34M	"	10GHz 電力増幅	"		11	-11	2.3A*	12.5W	150°			1.5	A)   2.3	3	-2	-7	3	1mA	540	750		3	900		
٠Ĺ	MK10		11	DC~VHF	J	-30°	20	-10	10,20*	150	125	-100	-10	1	20	10		-8	10	10	1.9	4		10	IDSS	0.05	
*	μPA50A		日電	低周波	"	-60°	60	±60	10,20*	200 unit	150	-10	-10	(Q <sub>1</sub> , 1.5	Q <sub>2</sub> )	10	-0.3	-2.4	10	10	2	4	8	10	1		
	μPA60A		"	差動増幅	"	-40°	40	-40	50	250 unit	175	-0.1	- 20	0.5	5	10	-0.2	-2.5	10	10	1	2		10	0.5	0.015	
ŀ	μPA61A		"	11	"	-40°	40	-40	50	250 unit	175	-0.1	- 20	0.5	5	10	-0.2	-2.5	10	10	1	2		10	0.5	0.015	- 10
	μPA62C		"	差動増幅 バランス MIX	"	-20*		-10	10,32*	350	125	-50	-8	8	32	10	-0.35	-2.2	10	10	12.5	15		10	3		
1	µPA63H		"	低周波	"	-60°	60	-60	10,30°	250 unit	125	-1	-20	1.5	20	10	-0.3	-4.2	10	10	2	4	8	10	1		
1	μPA68H		"	低周波, 低雑音	"	-50°	50	-50	10,30*	250 unit	125	-1	-20	1	18	10	-0.15	-2.5	10	10	5	7		10	1		N commence benefits
1	uPA70A		11	DC	"	-40*	40	-40	50	250	175	-0.1	- 20	0.5	5	10	-0.2	-2.5	.10	10	1	2		10	0.5	4	
1	μPA71A		"	"	"	-40°	40	-40	50	250	175	-0.1	-20	0.5	5	10	-0.2	-2.5	10	10	1	2		10	0.5	4	Samuelierole de ristan
												A. r. year being al		and grade and grade and						<del>.,,</del> ,,,,					and the second second		
1	2SK4370	BD	松下	SHF チューナ 低雑音増幅		-6.	5	-6	120*	270	125*	−10µA	-3	20	120	3		-3.5	3	100	20	50	100	3	10		
L	2SK354/	`	日覧	VHF〜Cバンド 低雑音増幅	GaAs	-6.	5	-6	150°	300	125*	-10μA	-5	30	100	3	-0.8	-6	3	100	20	40	100	3	10		ngles ligngelyana

\*

					U	Ά I	的特	i 11:	(Ta=	25°C)	elikasikat kanalan di kanalan di kanalan di kanalan di kanalan di kanalan di kanalan di kanalan di kanalan di k						/h	外	
Cis	(p <b>F</b> )			Cr.	(pF)			NF (f	=1kHz, 1	$R_{\kappa} = 1M\Omega$	a) (dB)	NF	(f=100	MHz) (	dB)	その他	代替品		型名
typ	max	$V_{GS}(V)$ $I_{D}(mA)$	Vos (V)	typ	max	$V_{GB}(V)$ $V_{GS}(V)$		typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)		型名	形	
					最大	発振周波	数 <b>45</b> G	Hz typ								Gp=9dB typ (f=8GHz)		167	MGF1801
	W. P. S. S. S. S. S. S. S. S. S. S. S. S. S.		and the second s	-	T											Gp=7dB typ (f=12GHz)		170	MGF1802
					最大	発振周波	数 40G	Hz typ								Gp=7dB typ (f=12GHz)		169	MGF2116
								1								Gp=7dB typ (f=12GHz)		170	MGF2117
					最大	発振周波:	数 35G	Hz typ		Annual County of Street						Gp=6dB typ (f=12GHz)		124	MGF2124
																Gp=5.5dB typ (f=14GHz)	and the second s	171	MGF2124E
										<u> </u>		and the second s				Gp=5.5dB typ (f=14GHz)		172	MGF21240
					最大	上 発振周波:	数 30G	Hz typ	<b></b>							Gp=5dB typ (f=12GHz)		124	MGF2148
	•															Gp=4.7dB typ (f=14GHz)		171	MGF2148F
																Gp=4.7dB typ (f=14GHz)		172	MGF21480
					最大	 発振周波	数 25G	Hz typ	L							Gp=5.5dB typ (f=8GHz)		124	MGF2172
								1								Gp=6.5dB typ (f=6GHz)		173	MGF2205
										<u> </u>						Gp=6dB typ (f=9.6~10.2GHz)		174	MGF-X34M
				1.3				2		10	0.5	3.0		10	5	PG=20dB typ (f=100MHz)		9	MK10
(Q <sub>1</sub> ,	Q <sub>2</sub> )	1.	10	(Q <sub>1</sub> , 1.3	Q <sub>2</sub> )	1mA	10		Iz)60nV / √Hz	10	1	⊿I <sub>DSS</sub>	=10%m	ax (V <sub>DS</sub>	=10V)			44	μPA50A
2.5	5	0	10	0.5	1.5	0.	10					⊿V <sub>GS</sub> =	=5mVma	$x \begin{pmatrix} V_{DS} = 0 \\ I_D = 0 \end{pmatrix}$	=10V .2mA)			111	μPA60A
2.5	5	0	10	0.5	1.5	0*	10					⊿V <sub>GS</sub> =	=40mVma					111	μPA61A
7.5		3*	10	2.5		3mA	10						=400MH		3	PG=12dB typ (f=400MHz)		76	μPA62C
6	8	1.	10	1.6	2.5	1mA	10	(f=1)	0Hz, nV	√Hz)   10	1	⊿V <sub>GS</sub> =	=60mVma	$x \begin{pmatrix} V_{DS} \\ I_{D} = \end{pmatrix}$	=10V)			66	μPA63H
15		0	10	3		0.					nax (VDI Vmax (V	0=15V, /Gs=10V						66	μPA68H
	5	0	10		1.5	0*	10				Marian Million Marian	s=10V,				$e_n = 10 \text{nV} \sqrt{\text{Hz}} \text{ max}$ (V <sub>DS</sub> = 10V, I <sub>D</sub> = 200 $\mu$ A, f=1kHz)		77	μΡΑ70Α
	5	0	10		1.5	0.	10		⊿V <sub>G</sub>	s=40mV	max (Vi	os=10V,	I <sub>D</sub> =200	μA)		$e_n = 20 \text{nV} \sqrt{\text{Hz}} \text{ max}$ $(V_{DS} = 10 \text{V}, I_D = 200 \mu \text{A}, f = 10 \text{Hz})$		77	μΡΑ71Α
										<u> </u>									
												1.6	(f=12		1 10	雑音最小電力利得 10.5dB typ (f=12GHz)		103	2SK437®
							.,		NF	=2dB ty	/p (f=80	· · · · · · · · · · · · · · · · · · ·		·		MAG=10dB typ (f=8GHz), 7.5dB typ (f=12GHz)		9	2SK354A

		-		T		最大	定札	子 (Ta	=25°C)				~			電	気 自	勺 特	性	(Ta	=25°C	)				
型 名		社 名	用 途	構造	V <sub>GDS</sub>	VDSX	V <sub>GSO</sub> V <sub>GSS</sub> *	I <sub>G</sub>	Pd Pch*	T <sub>j</sub>	IGSS	max	I	DSS (mA	<b>A</b> )	,	VGS(off),	Vth*(V	<i>I</i> )		gm (n	nS) μ*			gos (mS	( <b>Ω</b> )
					V <sub>GDX</sub> ** (V)	V <sub>DSS</sub> *	V <sub>GSX</sub> ** (V)	(mA)	(mW)	(*C)	(nA) (pA)*	V <sub>G</sub> s (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub> (V)	$I_D$ $(\mu A)$	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	ma
3SJ11	1	日電	スイッチング	Mos		-30*	-30 <b>*</b>	-10*	100	100*	-100	-10		-0.1μA	-10	-3.0	-6.5	-10	-10		0.8		-10	-10V (V <sub>GS</sub> )		
3SJ11A	1	"	DC スイッチング	"		-30 <b>*</b>	±40*	-50 <b>*</b>	225*	75*	-10*	-10		-10µA	-10	-1.5	-3.5	-10	-10	0.5	1		-10	-1	0.07	
35K11⊕		日 立	小信号增幅	"																						
35K12®	1	"	チョッパ	"																						
35K13®		"	DC	"																						
3SK14	1	日電	DC、チョッパ	"		20	±30*	10*	100	100*	2 *	10		3	10		-5	10	10	0.5	0.8		10	-1	0.01	
3SK15	=	三菱	DC	"		25	+2 -10	10*	100	100*	-10*	-10		10	6		-9	6	10	0.5	1.0		6	1	0.04	
3SK15A	1	"	"	"		25	+2 -10	10*	100	100*	-10*	-10		10	6		-9	6	10	0.5	1.0		6	1	0.04	
3SK16		"	チョッパ スイッチング	"		25	+2 -10	10*	100	100*	-10*	-10		10	6		-9	6	1	0.5	1.0		6	1	0.04	
3SK17		"	低周波	"		25	+2 -10	10*	100	100*	-1	10		10	6		-9	6	10	0.5	1.0		6	1	0.04	
3SK18		"	チョッパ スイッチング	"		15	±10*	10*	100	100*	-10 <b>*</b>	-10		5	6		-6	6	10	0.5	1.0		6	1		0.
3SK19		"	VHF	"		15	±10°	10*	100	100*	-10*	-10		5	6		-6	6	10	0.5	1.0		0	1	0.05	0.
3SK20⊕	E	立.	DC, 低周波	"		20	+5** -20	10*	100*	150*	-1*	-6	0.4	5.0	6		-3.5	6	10	0.4			6	IDSS		0.1
3SK21⊕		"	チョッパ	"		20	+5** -20	10*	100*	150*	-1*	-6	3	16	6		6	6	10	2.5			6	"		
3SK22	¥	更 芝	FM, VHF	J	-18*			10	200	150	-100	-10	3	24	10	-1.2		10	1		7.0		10	"		
35K23		n	ビジコンカメラ ヘッドアンプ	"	-15 <b>*</b>			10	200	150	-100	-10	6	24	10	-1.8		-5.5	1	6		12	10			
3SK24	札	2 下		MOS																						
3SK25		"		"																						
3SK28	東	芝芝	ビデオ, VHF	J	-18			10	200	150	-10	-15	3.7	22	10	-1.2	-5.5	10	1	4.5		13.0	10	loss		
3SK29	E	電	低周波	MOS		20	± 30*	10*	80	100*	10*	10	1 (1	yp)	. 10		-5	10	10	0.5	0.8		10	1	0.01	
3SK30	E		FM/AM RF, MIX	J			- 15*	10	200*	150*	-100	- 10	3	20	10		-5	10	20	4	7.5		10	IDSS		
3SK30A		"	"	"			-18*	10	200*	150*	- 100	-10	3	20	10		-6	10	20	4	7.5		10	"		
38K33	E	電	FM, VHF	MOS		25	± 30*	20*	250	150*	-1	10	4	15	10		-4	10	50	4	6		10	5		
3SK38	身	( 芝	チョッパ	"	10	20*	10*	10*	200	125	200	10		50nA	6	0.	3 *	6	50nA	0.35			6	3 (V <sub>GS</sub> )		
35K38A		"	"	"	±12	20*	±12°	10*	200	125	± 25	±12		50nA	6	0 •	3 •	6	50nA	0.35			6	3 (V <sub>C1S</sub> )		

					兀	気 (	的 特	÷ 11:	(Ta=	25°C)					e josenski stem stom		代替品	外	
Cis	(pF)			Cn	(pF)			NF (f	=1kHz, F	$R_{\rm g} = 1 M\Omega$	(dB)	NF	(f=100		dB)	その他	型 名		型名
typ	max	$V_{GS}(V)$ $I_{D}(mA)^{\bullet}$	$V_{DS}$ (V)	typ	max	$V_{GD}(V)$ $V_{GS}(V)$	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	ID (mA)	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)		W Zi	形	
5		-10						Ron=	lkΩ max	$(V_{DS} = -$	-1V, V	s = -10	V) tph()	$_{(N)} = 0.4$ $_{(FF)} = 0.$	μs typ 4μs typ		3SJ11A	23	3SJ11
8		0	-10						Ron	=500Ωm	ax (Vos	=-1V,	$V_{GS} = -$	-10V)				23	3SJ11A
																	3SK20⊕	26	3SK11®
			natural electric addition of the control of the con														3SK21®	26	3SK12@
																	3SK20⊕	26	3SK13®
3		0	10					5		10	1							23	3SK14
4		0	0															24	3SK15
4		0	0	* All Many														24	3SK15A
4		0	0					Ron=1	kΩmax(¹	$V_{\rm DS} = 0.1$	V, V <sub>GS</sub>	=0), Ro	off = 10M	IΩmin(V	$v_{\text{DS}} = 0.1$	$V$ , $V_{GS} = -6V$ )		24	3SK16
4		0	0															24	3SK17
0.3		1*	6	0.1		1mA	6	Ron=1	. 2kΩmax	$(V_{DS} = 0)$	).1V, Vo	15 = V <sub>G2</sub>	s=0) to	N = 20ns FF = 25n	max s max			25	3SK18
0.3		1*	6	0.1		1mA	6					(200 4	MHz)	6	1	PG=20dBtyp (f=200MHz)		25	3SK19
5		0	6															26	3SK201
5		0	6					Ros	ı=300Ωπ	nax (V <sub>D</sub>	s=0.1V	$V_{G1S} =$	$V_{G2S} = 0$	, Roff	=100MΩ	$\lim_{\Omega \text{min } (V_{DS}=0.1V, V_{G1S}=-6V, V_{G2S}=0)}$		26	3SK211
					0.6	-10						2	3.5	10 (V <sub>DD</sub> )		PG=20dBtyp (f=100MHz)		27	3SK22
	3	0	0	0.4		-10											3S K28	27	3SK23
																		39	3SK24
																		39	3SK25
	6	0	10	-	0.6	-10			2.5	10	IDSS		2.5	10 (V <sub>DD</sub> )		PG=17dBmin (f=100MHz)		27	3SK28
3		0	10															23	3SK29
5		0	10	0.4	0.6	0*	10					2.0	3.5	10 (V <sub>DD</sub> )		PG=17dBtyp (f=100MHz)	2SK54	29	3SK30
5		0	10	0.4	0.6	0*	10					2.0	3.5	10 (V <sub>DD</sub> )		PG=17dBtyp (f=100MHz)	2SK55	29	3SK30A
3		5*	10		0.3	5m A	10						3	10	5	PG=15dBmin (f=100MHz)		30	3SK33
	4.5	0	0		4.5	0	0	Ron=5	00Ωmax	$(V_{DS}=1)$	0mV, Vo	s = 3V),	Roff=	100MΩn	nin (V <sub>DS</sub>	$s = \pm 10 \text{nV}, V_{\text{GS}} = 0$	3SK38A	31	3SK38
	2.5	0	0		2.5	0*	0	⊿C <sub>G</sub> =0	.3pFmax	k, Rosion	n=500Ωr	nax (VDS	=10mV	V <sub>G1S</sub> =3	3V, V <sub>G2S</sub>	=0)		31	3SK38A

				I	最 大	定格	3 (Ta	=25°C)		<u> </u>		<del></del>			電	気 的	り 特	性	(Ta	=25°C)					
型名	社名	用 逸	構造	V <sub>GDS</sub> V <sub>GDO</sub> *	V <sub>DSX</sub> V <sub>DSS</sub> *	V <sub>GSO</sub> V <sub>GSS</sub> *	I <sub>G</sub>	Pd Pch*	T <sub>j</sub> T <sub>ch</sub> *	Igss (nA)	max	Iı	oss (mA		,	VGS(off),		,		g <sub>m</sub> (m	S) μ*			չ <sub>օ</sub> , (mS լ բ <sub>լյ</sub> *	) (Ω)
	ļ			V <sub>GDX</sub> ** (V)	(V)	V <sub>G</sub> sx** (V)		(mW)	(°C)	(pA)*	V <sub>G</sub> s (V)	min	max	V <sub>DS</sub> (V)	min	max	V <sub>DS</sub>	I <sub>D</sub> (μA)	min	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max
3SK71	日電	エレクトレット コンデンサ・マイク	J		20		5,10*	150	125				I <sub>D</sub> 0.5	(V <sub>DD</sub> ) 5					Av1 == -	-10.5dI	3 min(V	DD=5V,	Cin = 1	0pF, f=	=1kHz)
μРА33Α	"	DC、チョッパ	Mos		-30°	±30*	-20* unit	100 unit	100	-10	-10				-2.5	-5.5	-10	-10	1	2		-10	-1		
μPA34A	"	"	"		20*	±30*	10* unit	100	75	10*	10		2.5	10		-5	10	50	0.3	0.6		10	IDSS		
TX-429D	ソニー	可変抵抗	"	(V <sub>DB</sub> ) -25	-20	(V <sub>GB</sub> ) -25	±15°	100	80	-0.2μA	-5	-6		-2	(V -0.4	tho)   -2.5	-1	-1		0.8		-1			
PM1210B	日立	高速度電力SW	11		120*	±20*	10A*	50W*	150°	±1μA	± 20		1	100	1 *	4.5*	10	1mA	1.5	(S) 2		10	5A		
PM1220B	"	"	"		120*	±20*	20A*	80W*	150*	±1μA	±20		1	100	1 *	4.5*	10	1mA	2.5	(S) 4		10	10A		
PM4550C	n	11	"		450°	±20°	50A*	350W*	150*	±1μA	±20		1	350	2 *	4 *	10	1mA	8	(S) 12		10	25A		
																		-							
						*																			
							and the comment of the state of																		
	-																								
			*************																						
			****																						
			~																						
														-											
					and sometime of													TTY	Combines (		P = 1				
***************************************		n de la sette de la companya del la companya de la	-										are and the section of the section o												
althorough a second paragraph of												n di akasabangan samboro					man distribution to				de engage de de la constant				
										.											and the second s				
··········															artendro Minerale telleri			*							
						السبب	لــــــــــــــــــــــــــــــــــــــ		لتسسيا							لسسسا					سسسيا			لتستمسم	-

					電	気	的特	性.	(Ta=	25°C)		againe is a second second second					· · · · · · · · · · · · · · · · · · ·	~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~		外	<u> </u>
Ci. (	pF)			Crs	(pF)			NF (f	=1kHz, 1	$R_{\epsilon} = 1M\Omega$	a) (dB)	NF	(f=100)	MHz) (	dB)	7	Ø	他	代替品		型名
typ	max	$\begin{bmatrix} V_{GS}(V) \\ I_{D}(mA)^{\bullet} \end{bmatrix}$	V <sub>DS</sub> (V)	typ	max	V <sub>GD</sub> (V) V <sub>GS</sub> (V)	V <sub>DS</sub> (V)	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	typ	max	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)		No all the control of the land	Alarahan dalah Magarita (2000) - Makadan dalah sebagai da 1970	型名	形	a Liverando de Servicio de Caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de caración (1877) de servicio de cara
			was united the second	<b>~***</b>				agada ( Man manda Manash M							<b>4</b>				and the second s	112	3SK71
15	20	0	0	Ron=	500Ωma:	$x \begin{pmatrix} V_{DS} = V_{GS}$	-6V)	1Vth=0.	$2V \begin{pmatrix} V_{DS} \\ I_{D} = 0 \end{pmatrix}$	$= -10V$ $-10\mu A$	) ⊿g <sub>m</sub> =	10%max	$\begin{pmatrix} V_{DS} = - \\ I_{D} = - \end{pmatrix}$	-10V)						22	μPA33A
4		0	10					ΔI	pss=0.1	mAmax	$\begin{pmatrix} V_{DS} = 1 \\ V_{G1S} = 0 \end{pmatrix}$	0V)								22	μPA34A
												~300Ω (		$t_{\text{the}} = -1$	00V, Vs	$=0, V_{BG}=10V,$	$V_{DS} = -1V)$			68	TX-429D
1,130	***	0	10	80		0.	10		Ros	(ON)=0.	3Ω max	$(I_D=5A,$	$V_{GS}=1$	5V)	· •					133	PM1210B
2,200		0	10	200		0 *	10		Ros	(ON) = 0.	15Ω max	$(I_D=10A$	VGS=	=15V)	•					133	PM1220B
7,500		0	10	175		0 *	10		Ros	(ON)=0.	18Ω max	$(I_D=25A$	, V <sub>G</sub> s=	=15V)				-		36	PM4550C
				-																	
																		0			
																an an air an air an air an an an an an an an an an an an an an					
																	,				
											18										
													******************								
													~								

		T					最 大	定札	各 (Ta	=25°C)				•			電	気 的	5 特	性	(Ta	=25°C)			····		
	型名	٤	社 名	用 途	構造	V <sub>GDS</sub>	VDS	VGSO	ΙD	Pd	Tch	Iciss	max	IDSS	(mA)	V <sub>DS</sub>	V <sub>P1</sub> (V)	V <sub>DS</sub> (V)	V <sub>P2</sub> (V)	V <sub>DS</sub> (V)	. 1	gm (mS)	)	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	gos (	(mS)
						( <b>v</b> )	(V)	( <b>v</b> )	(mA)	(mW)	(.c)	IG2SS (nA)	V <sub>GS</sub> (V)	min	max	V <sub>G2S</sub>	max	V <sub>G2S</sub>	max	V <sub>G1S</sub> (V)	min	typ	max	V <sub>G2S</sub> (V)	V <sub>G1S</sub> *	typ	max
*	(デュアルゲー 3SK32	-H)	松下	A STATE OF THE STA	MOS																4. <u>-</u> 1.0					-	
*	3SK35	]	東芝	VHF, RF, MIX	"		20	± 6	30	300	150	±100	±6	3	24	15 4	-4	15 4	-2	15 0		10		15	10		
	3SK37	1	ソニー	VHF, RF/MIX	"		20	± 8	25	230	120	±100	±8	4	20	10	-3	10	-3	10	7.5	9.5		10	5	(200) 0.5	MHz)
	3SK39, 39	)Ø 1	松 下	11	"		20	± 8	24	250	150	±20	±8	1	24	10	-3	10	-3	10	7		18	10	5	The second second second second second second second second second second second second second second second se	
	3SK40	1	日電	11	"		20	± 7	25	250	150	±100	±5	4	25	10	-4	15	-4	15 0	8	10		15	5	and which was the second to the second	
*	3SK41		"	"	"		20	± 7	25	250	150	±100	±5	4	25	10	-4	15	-4	15 0	8	10		15 4	5		
*	3SK44	3	東芝	"	"		20	± 6	45	300	150	±100	±6	3	40	15	-3.3	15	-3.3	15 0		13		15 4	10	and the same of the Basis of the same	
	3SK45	ı	日立	VHF, RF, MIX	"		22	± 7	35	330	150	±20	±7	4	32	15	-3	15	-2	15 0		14		15 4	10		
	3SK47	I	日電	VHF, RF, MIX 可変抵抗用	"		20	± 7	25	300	150	±100	±5	4	25	10	-3	10	-3	10	8	16		10	5	e angrej aktobere, ge aktobre	
	3SK48	,	ノニー	UHF, RF/MIX	"		18	+ 6 - 4	30	240	110	±1μA	+6 -4	2	11	10 5	-3	10 5	-3	10	a a terramina de constituir	11	and a section of the section of	10 5	10		
	3SK49	ŧ.	公 下	VHF, RF/MIX	"		20	± 8	30	350	150	±20	±8	2.5	30	10 5	-3	10 5	-3	10		15		10	5		
	3SK49NC		"	11	"		20	± 8	30	350	150	± 20	±8	2.5	30	10	-3	10	-2	10	8	15		10 5	5		
	3SK49②		"	"	"		20	± 8	30	350	150	± 20	±8	2.5	30	10 5	-3	10 5	-3	10 0	8		18	10 5	5		
	3SK51	E	立.	VHF, RF, MIX	"		20	± 7	35	330	150	±20	±7	7	25	15 4	-3	15 4	-2.5	15 0		17		15 4	10		
	3SK53		"	UHF, RF	"		15	± 8	33	330	150	±20	±8	0.1	30	10 5	-1.7	10 5	-1.1	10 0	11			10 5	20		
*	3SK55	東	芝	VHF, RF, MIX	"		20	± 9	30	300	150	±50	±7	3	24	15 4	-2.5	15 4	-2.5	15 0		16		15 4	10		
	3SK59		n	"	"		20	± 9	30	300	150	±50	±7	3	24	15 4	-2.5	15 4	-2.5	15 0		20		15 4	10		
	3SK60	E	立.	VHF, RF	"		15	± 8	33	330	150	± 20	±8		12	6 3	-1.7	10 3	-1.1	10 3	11	16		6	10		
	3SK61	ץ	ノニー	VHF, RF/MIX	"		20	± 8	25	230	120	±100	±8	4	20	10 5	-3	10 5	-3	10 0		9.5		10 5	5		
	3SK63	東	(芝	VHF, RF	"		20	± 9	30	300	150	±50	±7	3	24	15 4	-2.5	15 4	-2.5	15 0		20		15 4	10		Develope -
	3SK66	杠	不	UHF, RF	"		20	± 8	30	350	150	± 20	±8	0.5	12	10 5	3	10 5	-3	10 0	8			10 5	10		
	3SK70	E	立.	"	"		20	± 8	50	360	150	± 20	±5	1	20	15 4	-3	15 4	-3	15 0	7	12		15 4	7		
	3SK72	松	工	VHF, RF	"		20	± 8	30	350	135	± 20	±8	2.5	80	10 5	-3	10 5	-3	10	8	12	18	10 5	5		
	3SK73	東	(芝	VHF, RF/MIX	"		20	± 9	30	300	125	±50	±7	3	14	15 4	-2.5	15 4	-2.5	15 0		20		15 4	10		allerines quin
	3SK74	В	電	11	"		20	± 10	25	200	125	± 100	± 10	7	25	6 3	-3	6	-3	6	17	20		6 3	10		

Γ				T	<del></del>	T		最大	定析	各(Ta	=25°C)							電	気 的	勺 特	性	(Ta	=25°C)					
#	ŤĮ.	名	社名	用	途	構造	V <sub>GDS</sub>	V <sub>DS</sub>	V <sub>G</sub> so	ID	Pd	Tch	Igiss	max	Inss	(mA)	V <sub>DS</sub> (V)	V <sub>P1</sub> (V)	V <sub>DS</sub> (V)	V <sub>P2</sub> (V)	V <sub>DS</sub> (V)	1	gm (mS	)	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	gos (	mS)
							( <b>v</b> )	(V)	(V)	(mA)	(mW)	( <b>°C</b> )	IG2SS (nA)	V <sub>G</sub> s (V)	min	max	V <sub>G2S</sub> (V)	max	V <sub>G2</sub> S (V)	max	V <sub>G1S</sub> (V)	min	typ	max	V <sub>G2S</sub> (V)	V <sub>G1S</sub> * (V)	typ	max
35	K76															A												
35	K77		東芝	VHF,	RF	MOS		20	±9	30	300	125	±50	±7	3	24	15 4	-2.5	15 4	-2.5	15 0		20		15 4	10		
35	K78	<del></del>	"	UHF,	RF	"		20	±9	30	300	150	±50	±7	3	24	15 4	-3.5	15 4	-3.5	15 0	8			15 4	10		
3S	K79	an Mahamadalka di	松丁	-	"	"		20	±8	30	350	135						-3	10 5	-3	10 0	8			10 5	10		
35	K80		日立	- '	7	"		20	±8	50	200	125	±20	±5	1	20	15 4	-3	15 4	-3	15 0	7			15 4	7		
35	K81		"	VHF,	RF	"		20	±8	35	200	125	±50	±8	5	25	15 4	-3	15 4	-2	15 0	8			15 4	10		
35	K82		"	UHF,	RF	"		15	±8	33	200	125	±20	±8		20	6 3	-1.7	10	-1.1	10 3	13			3	10		
35	K83		"	VHF,	RF	"		15	±8	33	200	125	±20	±8		20	6 3	-1.7	10 3	-1.1	10 3	13			6 3	10		
35	K84																											
351	K85		日立	VHF	RF	MOS		22	±8	35	200	125	±50	±8	4	32	15 4	-3	15 4	-2	15 0	10			15 4	10		
351	K86																											
351	K87		日复	UHF,	RF	Mos		20	±10	25	200	125	±100	±10	0.5	8	10	-2	10	-0.7	10	18	22		10	10		
351	K88		"	,	,	"		20	±10	25	200	125	± 20	±10	0.01	6	10	-2	10	-0.7	10	14	17		10	10		
351	K89																											
351	K90																											
351	K91																											
351	K92																											
351	K93															and the same of th		*********									and the state of t	- was a mirror as
351	K94			ļ	والمراجعة المراجعة ا														10		10	a designation with making symbols	araba watani a far					
351	K95		日立	UHF,	RF	MOS	an year opposite and	15	±10	35	200	125	±100	±8		20	6 8	-2	10 3	-2	10 3	14	peed i tradi Adi' er sursus soor si'd		6 3	10	with the last of t	
351	K96		"	VHF,	RF	"	-7	15	±8	35	200	125	±100	±8		30	6 3	-2	10 3	-2	10 3	15			6 3 5	10	and the second s	a com landado norallo
351	K97		松下	UHF,	RF	GaAs		13	-6	80	350	125	– 20μA	6	8.5	45	5 0	-6	5 0	-6	5 0	10	20		2	10	, as were an experience and	Alle Australiane - Acc.
351	K98						me o do a manda menos			and the second s		o alka astro set e to e e	e, et 140 m et 200 - et 1	an orași and a san an				**************************************							· (Marijano) - alia and and and and		proper fragment our management of the last	and the state of the state of
351	K99						-	***************************************		angga gala banan dalam 1997 d		water at the s	was a second or the second or the second or the second or the second or the second or the second or the second	leson vi	The state of the s				10			<b>–</b>					** at	1 TO 1 THE COURSE OF SERVICE
351	K100		松下	UHF 低雑音	下高利得 F增幅	Mos		15	±8	30	250	125	± 20	±8	0.5	8	10	-3	10 4	-1.3	10 4	8	12.5		10 4	10		

					T	%	的特	11:	(Ta=	25°C)								and the second second second second		外		
Ci.	(pF)	ID (mA)	(V)	C,,	(pF)	In (mA)	V <sub>DS</sub> (V)					NF (200	(dB) MHz)	V <sub>DS</sub> (V)	In (mA)	7	Ø	他	代替品		型名	名
typ	max	V <sub>G1S</sub> *	V <sub>G2S</sub> (V)	typ	max	V <sub>G1S</sub> * (V)	V <sub>G2S</sub> (V)					typ	max	V <sub>G2S</sub> (V)	V <sub>G1S</sub> * (V)				型名	形		
	and the second second second																				3SK76	-
4.25		10	15 4	0.03	0.05	10	15 4					2.2	3.2	V <sub>DD</sub> =	= 15V	PG=20dB typ	(f=200MHz)	Walter Allin & Ballet	Committee of the commit	92	3SK77	
					0.03	10	15 4					(f=80 4.5	0MHz)   5.5	15	10	PG=16dB typ	(f=800MHz)	Ober de collection (1) - 18 pp. Proposition (1	3SK102, 115	93	3SK78	
						100000000000000000000000000000000000000				A COLUMN TABLE		(f=80	0MHz)   5	15 10	10	PG=10dB min	(f=800MHz)			91	3SK79	
	5	7	15 4	0.02		7	15 4					(f=90	0MHz)   6	15 4	7	PG=10dB min	(f=900MHz)			115	3SK80	
5		10	15 4	0.03		10	15 4						3.3	15 4	10	PG=17dB min	(f=200MHz)			115	3SK81	
	5	10	6 3	0.02		10	6 3				And Andrews Control of the Control o	(f=90	0MHz)   5.5	6 3	10	PG=10dB min	(f=900MHz)			115	3SK82	
	5	10	6 3	0.02		10	6 3						3	6 3	10	PG=20dB min	(f=200MHz)			115	3SK83	
					A COMMENT OF THE REAL PROPERTY.																3SK84	
3.3		10	15	0.03		10	15 4	arradical Asia (Asia Asia Asia Asia Asia Asia Asia Asia					3.2	15 4	10	PG=18dB typ	(f=200MHz)			115	3SK85	
											A A STATE OF THE S	madeline to the second									3SK86	
2.5	3.5	10	10	0.02	0.03	10	10 4					(f=90 3.8	0MHz)   5.5	10 4	10	PG=18dB typ (	(f=900MHz)			114	3SK87	
2.0	2.5	10	10	0.02	0.03	10	10 4					(f=90 3.8	0MHz)   5.5	10 4	10	PG=16dB typ (	(f=900MHz)			114	3SK88	
																					3SK89	
																					3SK90	
																					3SK91	
																					3SK92	
																			1		3SK93	
																					3SK94	
2.6		10	6 3	0.02		10	6 3					(f=900	0MHz) 5.5	6 3	10	PG=10dB min (	f=900MHz)			115	3SK95	
4.5		10	6	0.03		10	6 3	1 7					3	6 3	10	PG=22dB min (	f=200MHz)		۲	115	3SK96	
1.2	2	-6*	5 -6	0.02	0.04	-6 <b>*</b>	5 -6					(f=1 1.7	GHz) 2.8	5 2	10	PG=16dB typ (	f=1GHz)			91B	3SK97	
																					3SK98	
																					3SK99	
1.6	2.5	-5*	10 -5	0.02		-5*	10 -5					(f=800 2.6	MHz) 4	10	10	PG=14.5dB typ	(f=800MHz)			91B	3SK100	

\*

					<u> </u>	最大	定相	子 (Ta	=25°C)		<u> </u>					電	気 自	勺 特	性	(Ta	=25°C)					
型	名	社名	用途	構造	V <sub>GDS</sub>	Vos	VGSO	Īρ	Pd	Tch	Igiss	max	Inss	(mA)	V <sub>DS</sub> (V)	(V)	V <sub>DS</sub> (V)	(V <sub>P2</sub>	V <sub>DS</sub> (V)	1	gm (mS	)	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	gos (	mS)
					( <b>v</b> )	( <b>v</b> )	( <b>v</b> )	(mA)	(mW)	(°C)	I <sub>G2SS</sub> (nA)	V <sub>G</sub> s (V)	min	max	V <sub>G2S</sub> (V)	max	V <sub>G2S</sub> (V)	max	V <sub>G1S</sub> (V)	min	typ	max	V <sub>G2S</sub> (V)	V <sub>G1S</sub> * (V)	typ	max
3SK10	1	東芝	VHF, RF, MIX	моѕ		20	±9	30	200	125	±50	±7	3	24	15 4	-2.5	15 4	-2.5	15 0		20		15 4	10		
3SK10	2	11	"	"		20	±9	30	200	125	±50	±7	3	24	15 4	-3.5	15 4	-3.5	15 0	8			15 4	10		
3SK103	3	日立	UHF, RF	"		15	±10	35	200	125	±100	±8	_	10	6 3	-1	10 3	-1	10 3	10	15		6 3	10		
3SK104	4	"	UHF, TVチューナ RF	"		15	±10	35	200	125	±100	±8		20	6 3	-2	10 3	-2	10 3	14			6 3	10		
3SK10	5																									
3SK106	5																									
3SK107	7	三洋	VHF, RF	MOS		20	±7	30	250	125	±50	±7	2.5	24	10	-3	10	-2.5	10 0		17		10	10		
3SK108	3	"	II .	"		20	±15	30	250	125	50	V <sub>G1</sub> s5V V <sub>G2</sub> s10V	I <sub>DSX</sub> (V <sub>0</sub>	1s=2V) 21	10	1.5	10	1.5	10 5	11	15		10 10	10		
3SK109	9																									
3SK110	)		100 - 100 -																							
3SK111	1																			-					ļ	
3SK112	2																									
3SK113	3	日 立.	UHF, TVチューナ RF			12	±0.5 -6	80	200	125	- 20μA	-6	10	80	5	-6	5 0	-6	0	10			5	10		
3SK114	<b>.</b>	東芝	TV, FMチューナ VHF, RF, MIX	MOS		15	±9	30	200	125	±50	±7	0	6	3	-1	6 3	-0.5	3	13	20		3	10		
3SK115	5	"	TVチューナ UHF, RF, MIX	"		15	±8	30	200	125	±50	±6	0	6	6 3	-1.5	3	-1	6 3		17		6 3	10		
3SK116	5	松下	VHF, RF	"		20	±8	30	200	125	± 20	±8	2.5	30	10 5	-3	10 5	-3	10 0	8	15		10 5	5		
3SK117																										
3SK118	3	an in the same and the same and the same and the same and the same and the same and the same and the same and	analo, e, analoja jostovski stava i stav voje s																							
3SK119																		and the same of the same of								
3SK120			mır		Mar. 1880 1981 1881 1881						a anamaran	manyon of the trade of a decoding		and - delegate de desire	F		E		E .	. manusing medition			5			
3SK121		東芝	TV+1-+ UHF, RF, MIX	GaAs		10	-6	50	200	125	- 20μA	-5	20	45	5 0	-4	5 0	-4	5 0	maisan ni Min 1818 Menj	17		0	10		
3SK122			THE PART							e canada com destructura de composito de com				Jan Managara Bankara d	10		10		10				10			-
3SK123	3	日電	UHF, TVチューナ RF	MOS		18	±10	25	200	125	± 20	±8	0.01	6	10 4	-2	4	-0.7	4	14	18		4	10		
3SK124			mak ay haran o maka kerapanan bahasar Pendad I		and the second s	ana Saa	#1 74 B. MARLEMENT						ar eleganis Amerik										makapini kanan nga matika manan nda			agagi anga malina .
3SK125			X (1.44 - 4.44 -																							

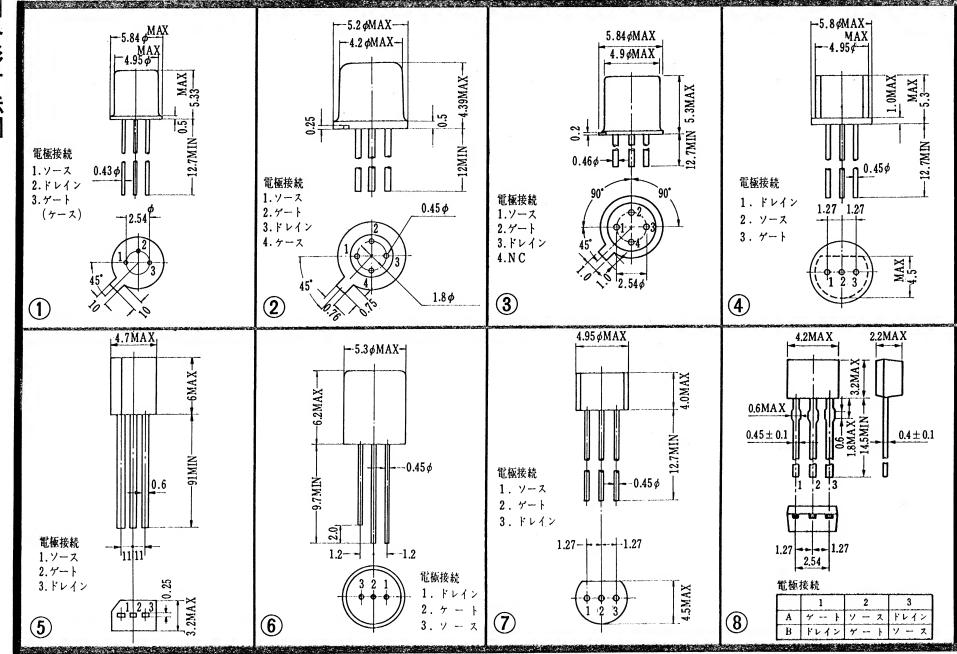
				<del></del>	Æ	須	的特	M:	(Ta=	25°C)	 								外	
Cia	(pF)	In (mA)	V <sub>DS</sub> (V)	Crs	(pF)	ID (mA)	(V)				NF (200	(dB) MHz)	V <sub>DS</sub> (V)	-I <sub>D</sub> (mA)	そ	Ø	他	代替品		型名
typ	max	V <sub>G1S</sub> * (V)	V <sub>G2S</sub> (V)	typ	max	V <sub>G1S</sub> *	V <sub>G2S</sub>	a)		*	typ	max	V <sub>G2S</sub> (V)	V <sub>G1S</sub> * (V)				型名	形	
4.25	gagarando el as literas en custoso	10	15 4	0.03	0.05	10	15 4				2.2	3.2	V <sub>DD</sub> =	=15V	PG=20dB typ (	(f=200MHz)			125	3SK101
1.7	-	10	15 4	10° 00000 00 00 00 00 00	0.03	10	15 4		angene an elizabet net a		 (f=8)	00MHz)	15 4	10	PG=16dB typ (	(f=800MHz)	AND AND AND AND AND AND AND AND AND AND		125	3SK102
2		10	6	0.02		10	6 3			and the second second second	 (f=90	00MHz)   5	6 3	10	PG=10dB min (	(f=900MHz)	acceptant of military scare from the property and the filter		115	3SK103
2.6		10	6	0.02		10	6		-		(f=90	00MHz)   5	6 3	10	PG=10dB min (	(f=900MHz)			175A	3SK104
																				3SK105
				-																3SK106
5.5		0.	10	0.02	0.05	0.	10				(f=10 2.2	00MHz)   3.5	10 4	10	PG=20dB min (	(f=100MHz)			128	3SK107
3		0.	10	0.02	0.05	0.	10 10				(f=10 1.8	00MHz)   2.5	10 10	10	PG=23dB min (	(f=100MHz)			128	3SK108
	and The State of t												Total Control of the							3SK109
			,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,																	3SK110
										alternative tradesia.										3SK111
																				3SK112
1.2		-6*	5 -6	0.02		-6*	5 -6				(f=90 1.5	00MHz)   3	5 0	10	PG=15dB typ (	(f=900MHz)			175A	3SK113
4.25	5.5	10	6	0.03	0.05	10	6 3				1.4	2.8	6 3	10	PG=25dB typ (	(f=200MHz)			125	3SK114
2		10	6	0.02		10	6				(f=80 3.2	00MHz)	6	10	PG=16dB typ (	f=800MHz)			125	3SK115
4		-8*	10 -8	0.01		-8*	10 -8			,	2	3	15 7		PG=20dB typ (	f=200MHz)			147A	3SK116
																				3SK117
																				3SK118
															and the second s					3SK119
									-		 		era e de montalido e 14 de					-		3SK120
0.9	2	10	5	0.02	0.05	10	5				(f=80 1.5	0MHz) 2.5	5 1	10	PG=20.5dB typ	(f=800MHz)			125	3SK121
																				3SK122
1.9	2.5	10	10	0.02	0.03	10	10 4				(f=90 2.8	0MHz)   4.5	10	10	PG=17dB typ (	f=900MHz)			114	3SK123
						-														3SK124
																				3SK125

			Τ				最 大	定札	各 (Ta	=25°C)							電	気 白	勺 特	性	(Ta	=25°C)					
型	名	社名	;	用 途	構造	V <sub>GDS</sub>	V <sub>DS</sub>	VGSO	ΙD	Pa	Teh	Igiss	max	Inss	(mA)	V <sub>DS</sub> (V)	(V)	V <sub>DS</sub> (V)	(V)	V <sub>DS</sub> (V)		gm (mS)	)	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	g., (	mS)
						( <b>v</b> )	(V)	(V)	(mA)	(mW)	(.c)	IG2SS (nA)	V <sub>GS</sub> (V)	min	max	V <sub>G2S</sub> (V)	max	V <sub>G2S</sub> (V)	max	V <sub>G1S</sub> (V)	min	typ	max	V <sub>G2S</sub> (V)	V <sub>G1S</sub> * (V)	typ	max
3SK126		東芝	į T V	V, FM+2-+ VHF, RF, MIX	моѕ		15	±9	30	150	125	±50	±7	0	6	6	-1	6	-0.5	6 3	13	20		6	10		
3SK127		"	U	JHF, TVチューナ RF, MIX	"		15	±8	30	150	125	±50	±6	0	6	<u>6</u> 3	-1.5	6	-1	6 3		17		6 3	10		
3SK128																											
3SK129		松下	Fυ	JHF, RF	GaAs		13	-3.5	50	350	125	±20	±3.5	8.5	40	5 0	-3.5	5	-3.5	5 0	18	25		5 1.5	10		
3SK130																											
3SK131		日和		THF, TVチューナ RF, MIX	MOS		20	±8	25	200	125	±20	±8	7	25	6 3	-2	8	-1.5	8 0	22	28		6 3	10		
3SK132		"	U	HF <i>+</i> 2-+ RF	"		20	±10	25	200	125	±20	±10	0.5	8	10 4	-2	10	-0.7	10 4	18	22		10 4	10		
3SK133		"		HF, TV+1-+ F	"		20	±10	25	200	125	±20	±10	0.01	6	10	-2	10	-0.7	10 4	14	17		10 4	10		*
3SK134																											
3SK135																											
3SK136		日立	- R	HF, TV+ューナ F	MOS		20	±8	35	150	125	±100	±8	5	25	15 4	-3	15 4	-2	15 0	8			15 4	10		
3SK137		"	U R	HF, TVチューナ F	"		15	±10	35	150	125	±100	±8		20	3	-2	3	-2	10 3	14			6 3	10		
3SK138		"	U R	HF, TV+1-+ F	"		15	±10	35	150	125	±100	±8		10	6 3	-1	10 3	-1	10 3	10	15		6 3	10		
3SK139											organia a serving s				ominen a uce cel												
3SK140		東芝		Vチューナ HFRF, MIX	GaAs		10	-6	50	150	125	−20µA	-5	20	45	5 0	-4	0	-4	5 0		17		5 0	10		
3SK141		松下	U	HF, RF	"		13	-3.5	50	200	125	±20	±3.5	8.5	40	5 0	-3.5	5 0	-3.5	5 0	18	25		5 1.5	10		
3SK144																											
3SK145		東芝	U	Vチューナ HFRF, MIX	MOS		13.5	±8	30	200	125	±50	±6	0	6	6 3	-1.5	6 3	-1	3		16		6 3	10		
3SK146		"		11	"		13.5	±8	30	150	125	±50	±6	0	6	6 3	-1.5	6 3	-1	6 3		16		6 3	10		
3SK147			$\perp$																-								
3SK148																	~~~~~										
3SK149			_																								
3SK150	]	東芝	U	Vチューナ HFRF, MIX	MOS		15	±8	30	200	125	±50	±6	3	14	3	-1.5	6 3	-1	6 0	22	27		3	10		
3SK104	v	日立	R		"	-	15	±10	35	200	125	±100	±8		20	6 3	-2	10 3	-2	10 3	14			6 3	10		
MGF110	0 .	三菱	U 低	HF, SHF :雑音増幅	GaAs		8	-6	60	150	150			15	60	3 0	-5	3 0	-5	3 0	10	15		3 0	15		

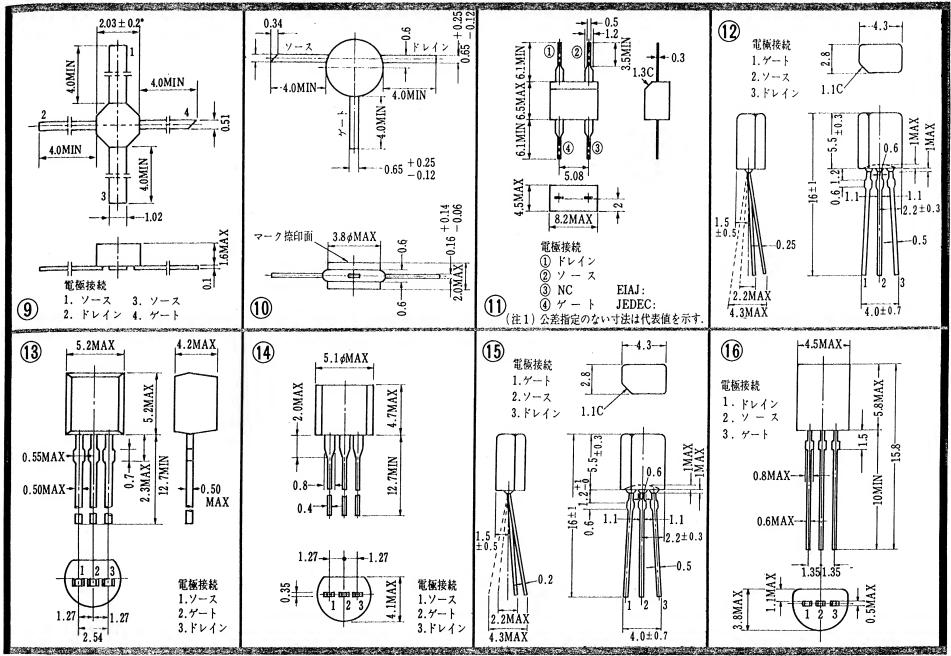
					U	须	的特	性	(Ta=	=25°C)								//>	外	
Ci. (	(p <b>F</b> )	In (mA)	V <sub>DS</sub> (V)	C <sub>r</sub>	(pF)	ID (mA)	V <sub>DS</sub> (V)					NF (200	(dB) MHz)	Vos (V)	I <sub>D</sub> (mA)	₹ <b>0</b>	他	代替品		型名
typ	max	V <sub>G1S</sub> *	V <sub>G2S</sub>	typ	max	V <sub>G1S</sub> * (V)	V <sub>G2S</sub> (V)					typ	max	V <sub>G2S</sub> (V)	V <sub>G1S</sub> * (V)			型名	形	
4.25	5.5	10	6	0.03	0.05	10	6 3	and the second section of				1.4	2.8	6 3	10	PG = 25dB typ (f = 200MH	z)		176	3SK126
2		10	6 3	a di Lagrand Characago (Characago (Characago (Characago (Characago (Characago (Characago (Characago (Characago	0.03	10	6					(f=80 3.2	OMHz)	6 3	10	PG=16dB typ (f=800MH	z)		176	3SK127
				<b>**</b> **********************************						****										3SK128
0.6	1.5	-3.5*	5 -3.5	0.02	0.04	-3.5*	5 -3.5		-	The second section of the section of the sect		(f=1 1.2	IGHz)	5 1.5	10	PG=17dB typ (f=1GHz)			91B	3SK129
																				3SK130
5	6.5	10	6	0.05	0.08	10	6 3		İ			1.3	2.5	10 5	10	PG = 24dB typ (f = 200MH	z)		177	3SK131
2.5	3.5	10	10	0.02	0.03	10	10						00MHz)   5.5	10	10	PG=18dB typ (f=900MH	z)		177	3SK132
2	2.5	10	10	0.02	0.03	10	10			a promise and described			00MHz)   5.5	10	10	PG=16dB typ (f=900MH	z)		177	3SK133
																				3SK134
																				3SK135
5		10	15 4	0.03		10	15 4						3.3	15 4	10	PG=17dB min (f=200MH	z)		176	3SK136
2.6		10	6	0.02		10	6 3					(f=90	00MHz)	6	10	PG=10dB min (f=900MH	z)		176	3SK137
2		10	6 3	0.02	-	10	6					(f=90	00MHz)	6	10	PG=10dB min (f=900MH	z)		176	3SK138
				************																3SK139
0.9	2	10	5 0	0.02	0.05	10	5			<u> </u>			00MHz) 2.5	5	10	PG=20.5dB typ (f=800)	íHz)		176	3SK140
0.6	1.5	-3.5*	5 -3.5	0.02	0.04	-3.5*	5 -3.5			1			IGHz)	5 1.5	10	PG=17dB typ (f=1GHz)			147B	3SK141
			_3.5				0.0										Michael Carlotte Control of the Cont			3SK144
1.8		10	6 3	0.02	0.03	10	6 3					(f=80 2.6	00MHz)	6	10	PG=17.5dB typ (f=800N	IHz)		125	3SK145
1.8		10	6 3	0.02	0.03	10	6 3						00MHz)	6	10	PG=17.5dB typ (f=800N	IHz)		176	3SK146
			9																	3SK147
																				3SK148
																	,			3SK149
2.7	3.6	10	6 3	0.025	0.04	10	6	変換雑	音指数	NFcs=5	.5dB max	(200/2	45MHz)			変換利得 Gcs=24.5dB typ	(200/245MHz)		125	3SK150
2.6		10	6	0.02		10	6 3						3	6 3	10	PG=20dB min (f=200MH	z)		175A	3SK104V
			<u> </u>									(f=4 2.5	GHz)   3.3	3	10	Gs=9dB typ (f=4GHz)		1	168	MGF1100

		Τ					最 大	定析	(Ta	=25°C)								気 的		性	(Ta	=25°C)					
型	名	社	名	用 途	構造	V <sub>GDS</sub>	V <sub>D</sub> s	V <sub>GSO</sub>	ΙD	Pd	Teh	Igiss		IDSS	(mA)	V <sub>DS</sub>	(V)	V <sub>DS</sub>	V <sub>P2</sub> (V)	V <sub>DS</sub>	1	gm (mS	)	V <sub>DS</sub> (V)	I <sub>D</sub> (mA)	gos (	(mS)
						( <b>v</b> )	( <b>v</b> )	( <b>v</b> )	(mA)	(mW)	(°C)	IG2SS (nA)	V <sub>G</sub> s (V)	min	max	V <sub>G2S</sub> (V)	max	V <sub>G2S</sub> (V)	max	V <sub>G1S</sub> (V)	l	typ	max	V <sub>G2S</sub> (V)	V <sub>G1S</sub> * (V)	typ	max
3SK15	1	東	芝	TVチューナ VHFRF, MIX	MOS		.15	±8	30	150	125	±50	±6	3	14	6 3	-1.5	6 3	-1	6 0	22	27		6 3	10		
													:														
		*																									
			_																								
			-						and the second																		
			_																								
			_																								
																											and the second second
ļ																											
ļ																		AND A STATE OF THE	nas desar urrentino della co	Name of the Control of Taxable							
							****							<b>_</b>								i vanadi ari i a ari basai i					
		r #8#81#	_														and an amount of the	······································									

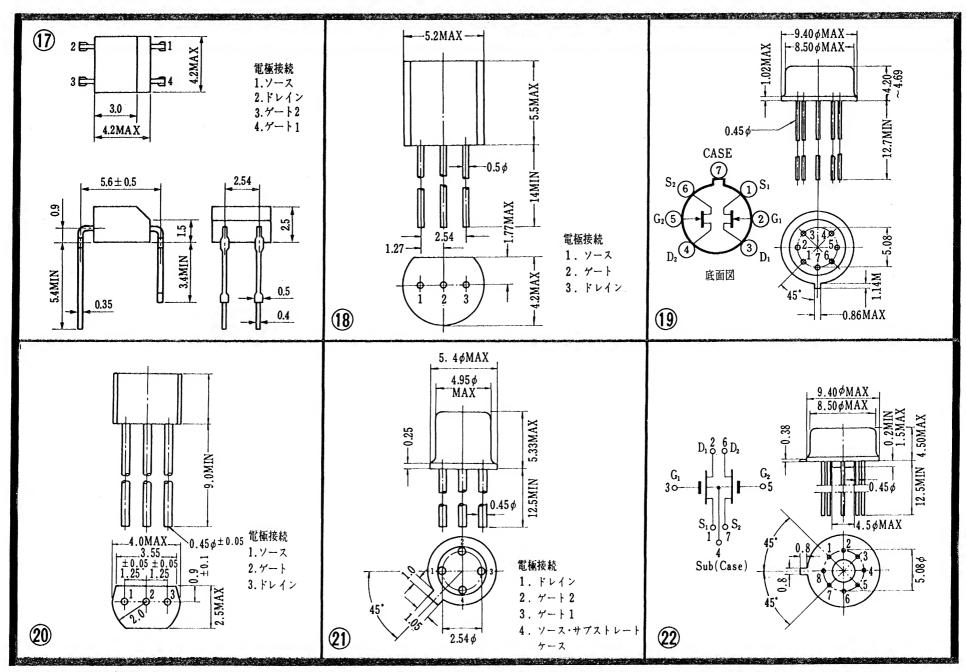
		4400 Table & Colored & Col			兀	気	的特	性	( Ta =	25°C)							and the second s			外	
Cis		ID (mA) VG1S* (V)	V <sub>DS</sub> (V) V <sub>G2S</sub> (V)	Crs		$\begin{bmatrix} I_D \\ (mA) \\ V_{G1S} \\ (V) \end{bmatrix}$	V <sub>DS</sub> (V) V <sub>G2S</sub> (V)					NF (200 typ	(dB) MHz) max	V <sub>DS</sub> (V) V <sub>G2S</sub> (V)	ID (mA) VG1S* (V)	₹	Ø	他	代替品型 名	形	型名
typ	max	(V)	(V) 6 3	0.025	max 0.04	10	6 3	亦換雑	音指数 N	IFce=5	5dR may			(V)	(V)	変換利得 Gcs=2	24 5dB tvn(20	00/245MHz)		176	3SK151
2.7	3.6	10	3	0.025	0.04	10	3	<b>支</b> 1矢和:	E 18 40 1	ir cs=3.	. 3015 11187	200/2	43/41727	I	T	Z1X1111-7 OCS - 2		JU/ 24JM112 /		170	33K131
							and the second section of the section	and the second section of the con-				er meljanera, av til dir Va	and the second s				ar deline met dir relief in the letter and an indicate with the	Kalifornia andrea in para de la compansión de la compansión de la compansión de la compansión de la compansión			
	and the second second second		en la compressión de la compressión de la compressión de la compressión de la compressión de la compressión de			en Carlos III	Variety is Different or									Consider the course to the constant of the con		gypnografia (n. 1845). Angeles ann a 1850 d'Albert 1871 (n. 1874). Se ann a 1870 d'Albert 1871 (n. 1874). Se a			
									The contact that the second factor is	The same and the same			<b></b>			New York and the second					
			-																		
					-																
	elter merenderiget et e										ļ										ar are a construct the fact that the
																The second secon					
		and the state of t																			
														AND THE RESERVE AND THE PARTY OF THE PARTY O	and the same of	and the state of t		1			
						and the same of th											and the second of the second o				
																					AND THE THE PARTY AND THE PART
					-						and the state of t										
																			· · · · · · · · · · · · · · · · · · ·		
																					-



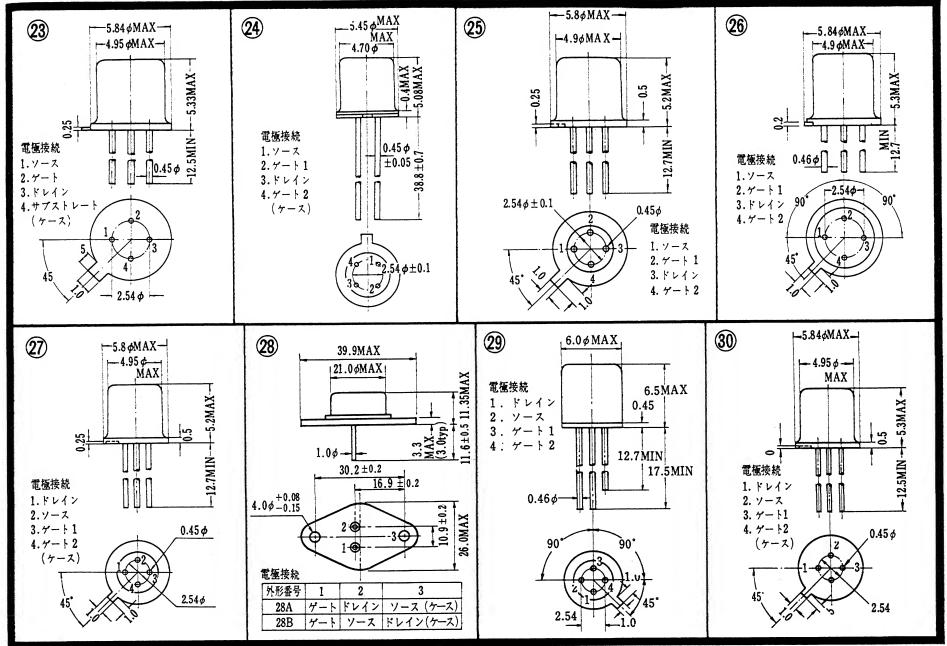
《寸法図単位:mm》



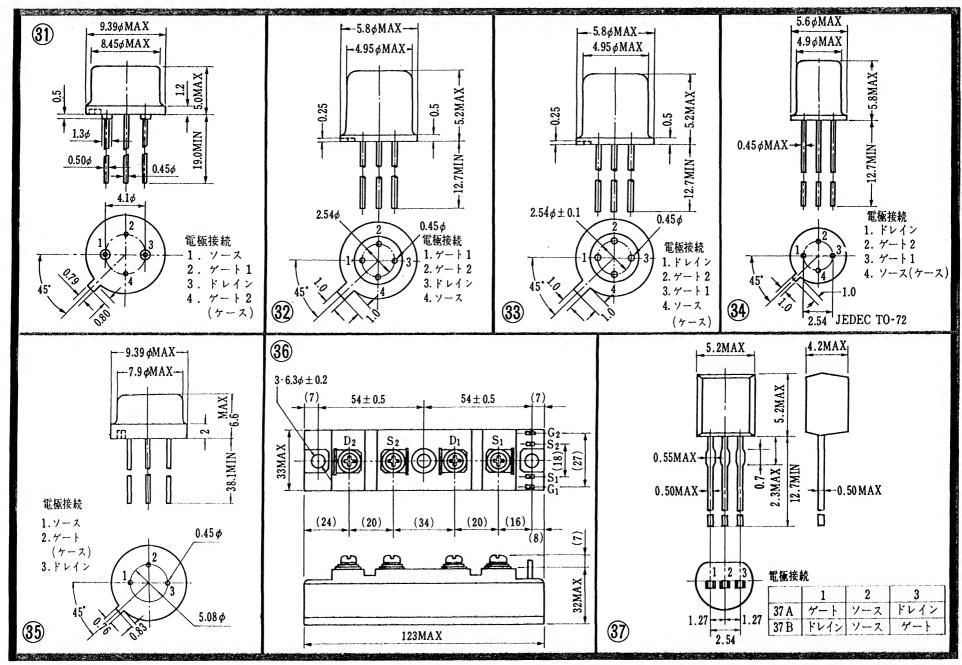
〈寸法図単位:mm〉



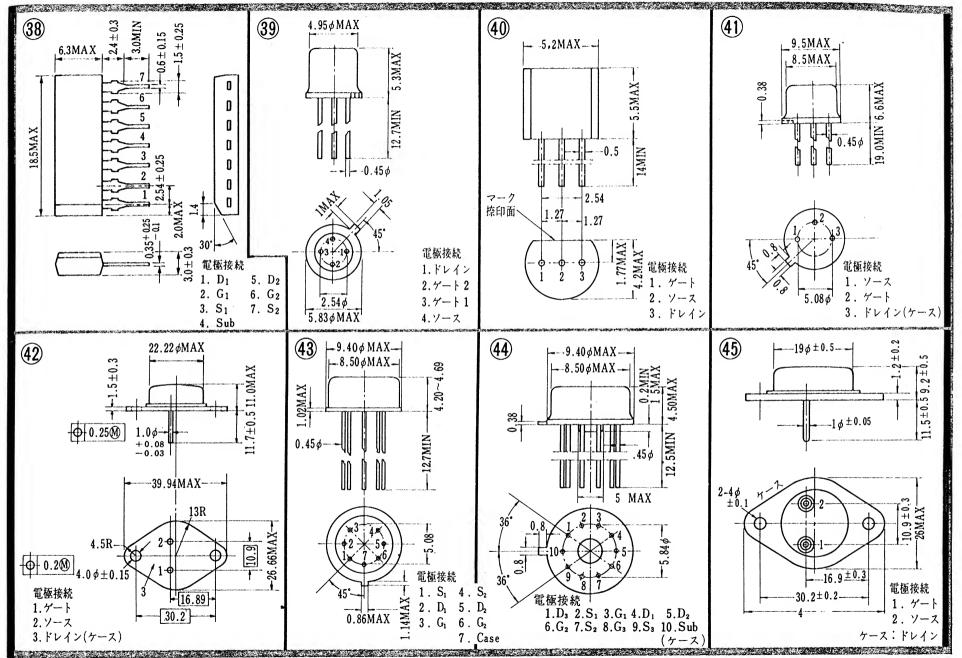
〈寸法図単位:mm〉



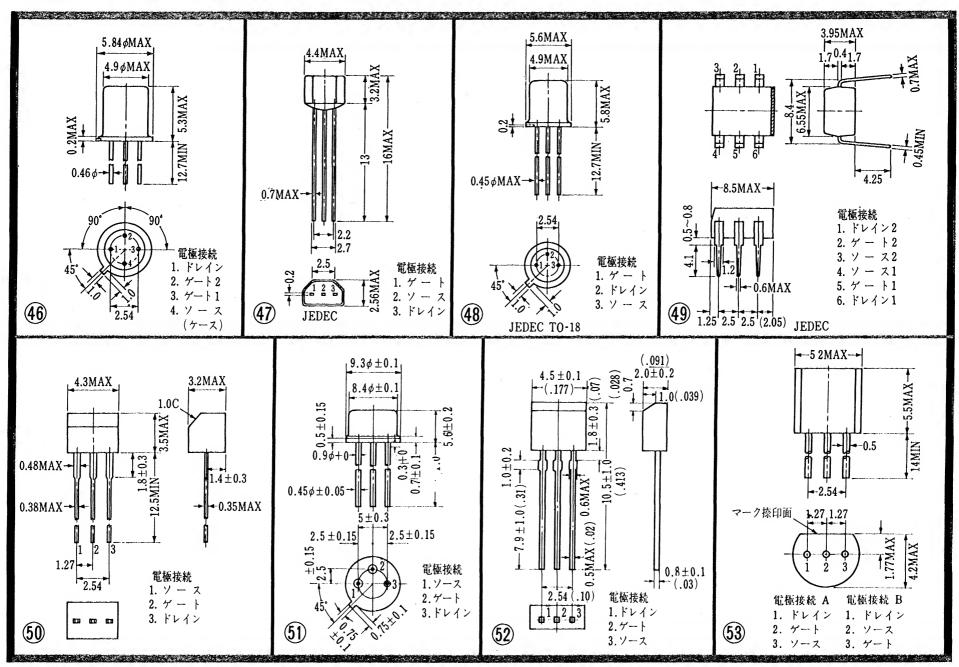
〈寸法図単位:mm〉



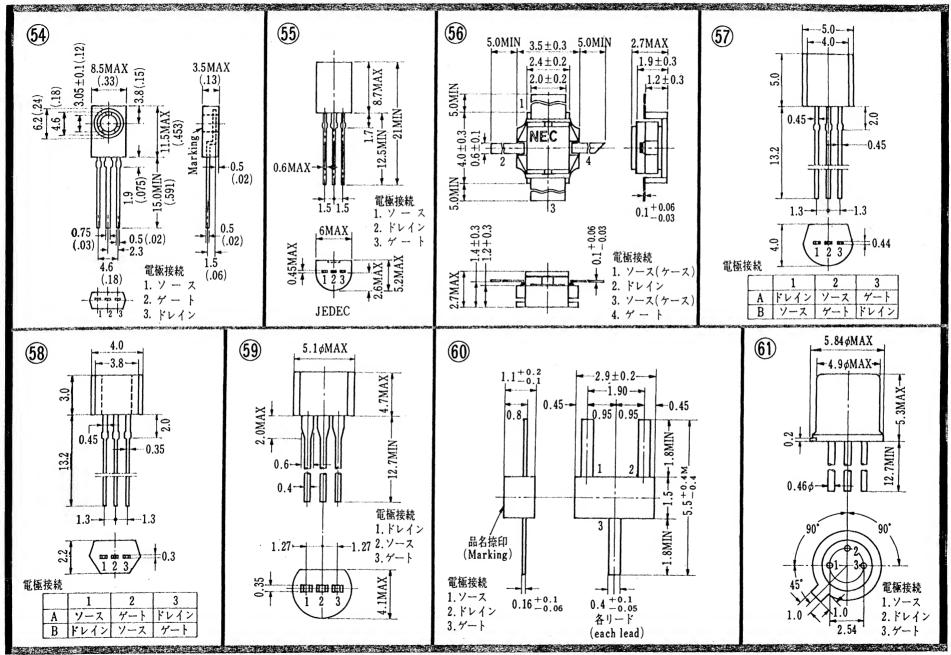
《寸法図単位:mm》



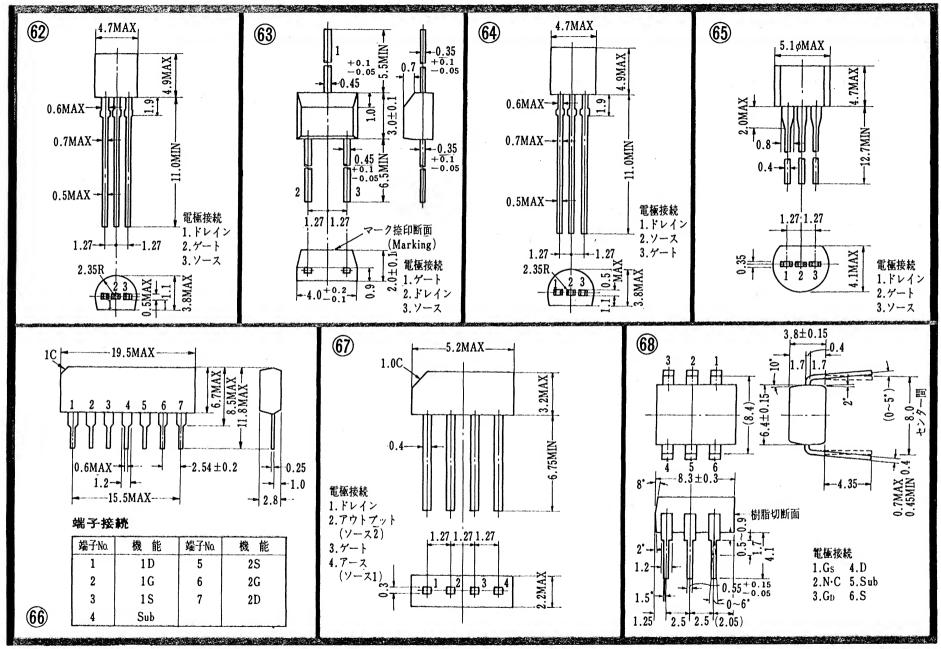
〈寸法図単位:mm〉



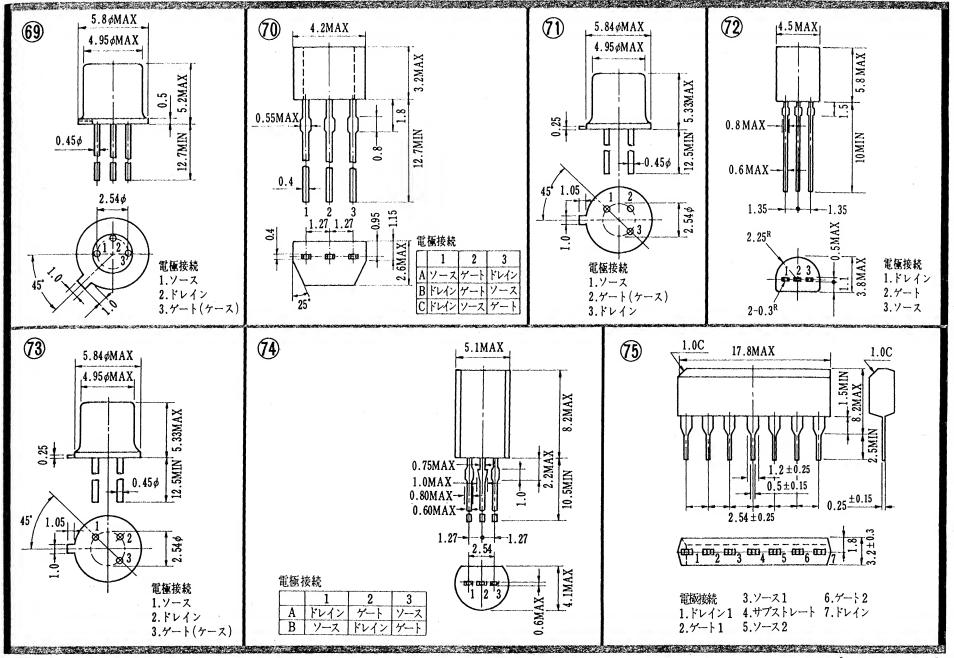
《寸法図单位:mm》



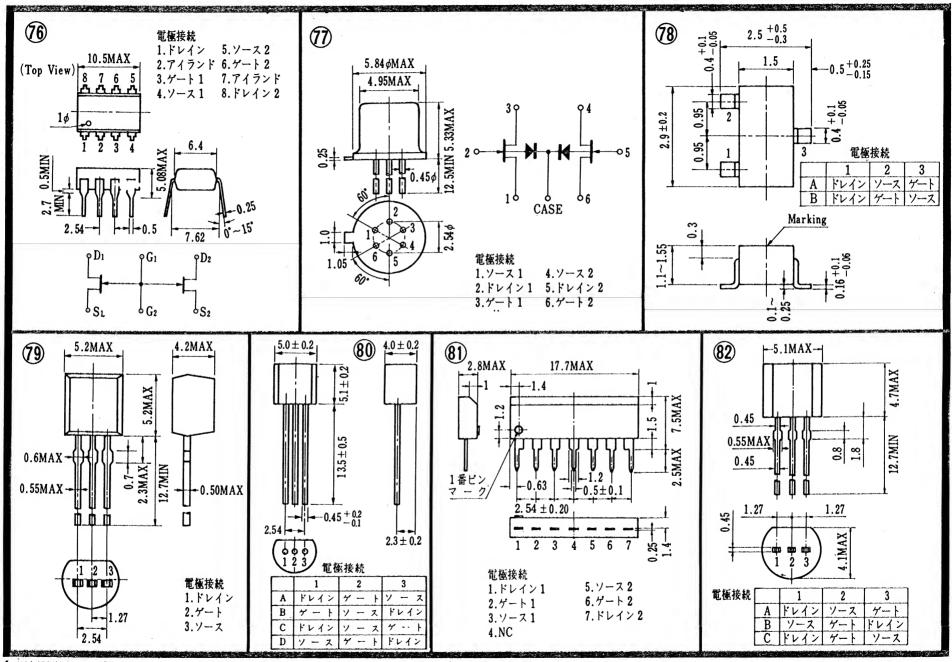
〈寸法図単位:mm〉



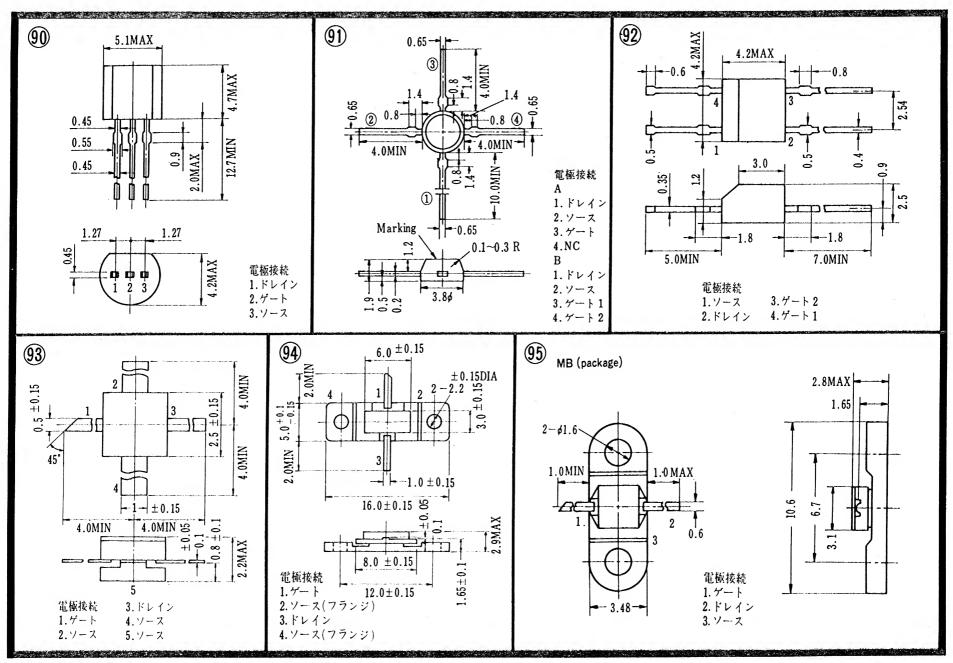
《 小法国对单位: mm<sup>3</sup>



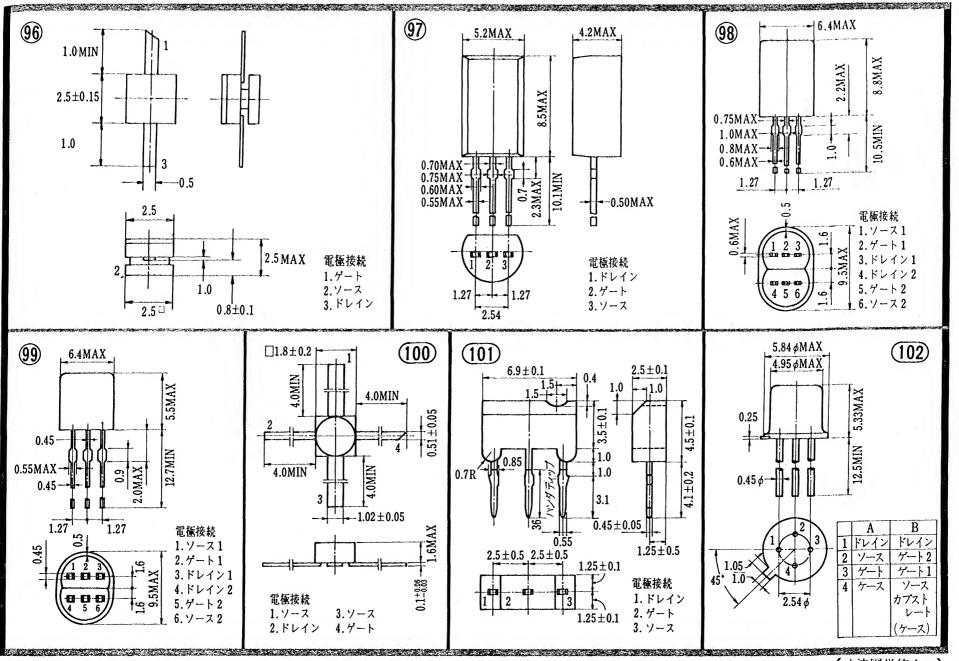
〈寸法図単位:mm〉



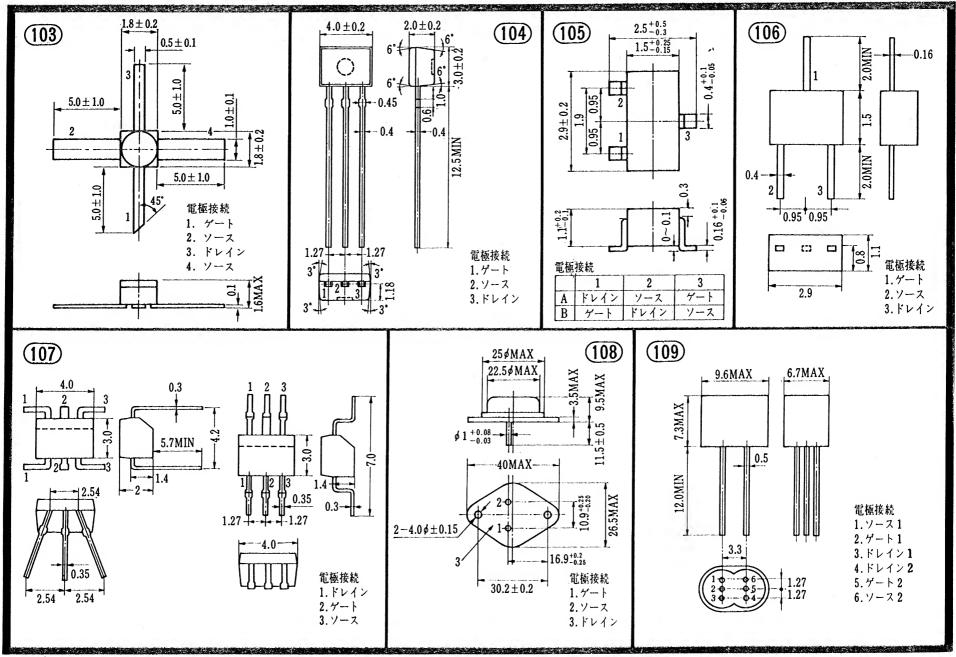
〈寸法図単位:mm〉



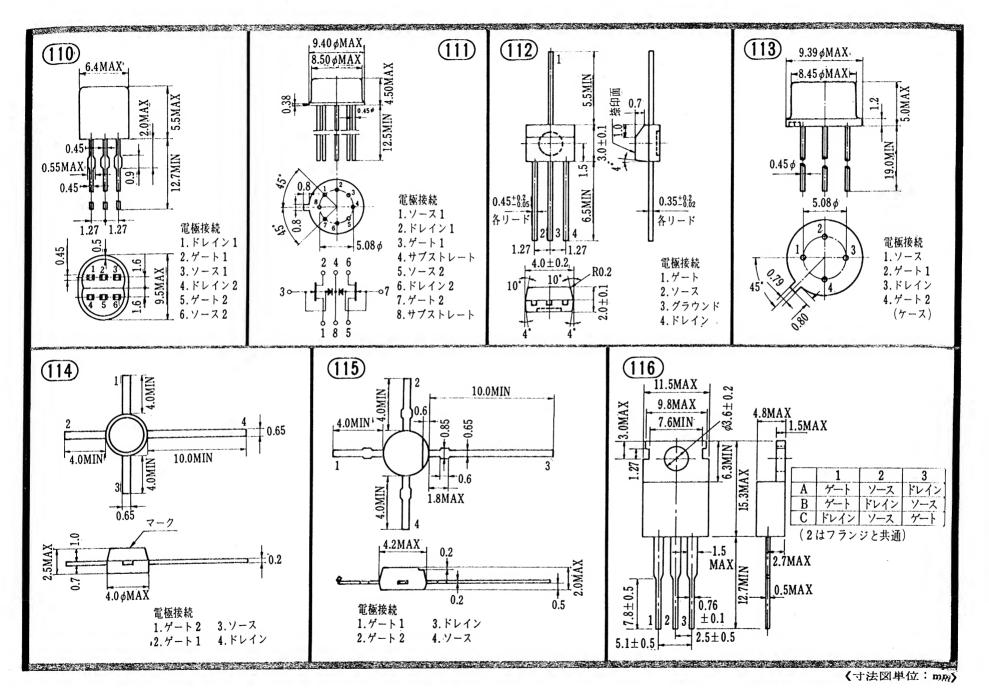
《 寸法|図単位: mm》

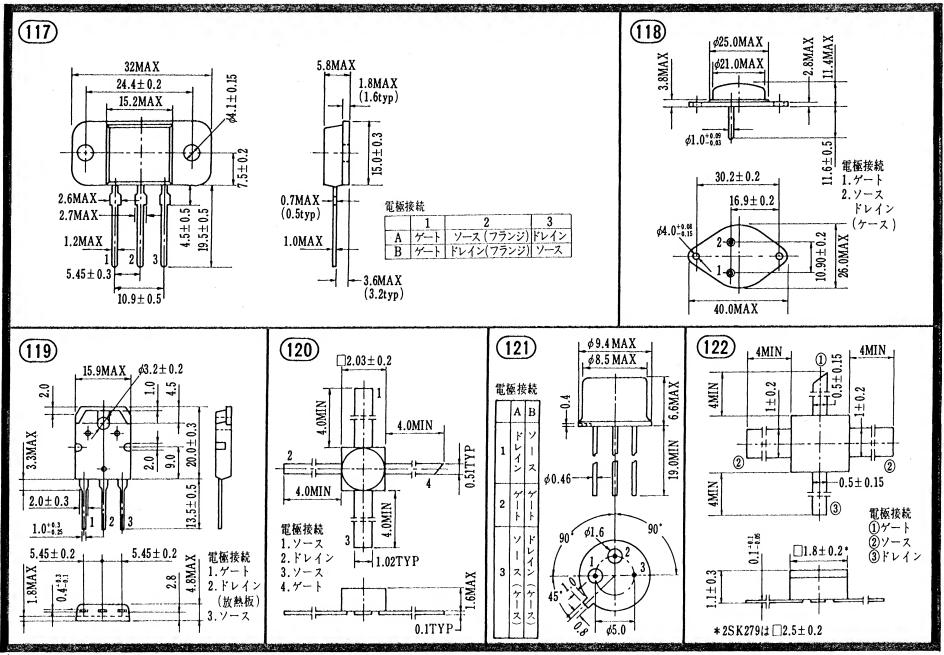


〈寸法冈单位:mm〉

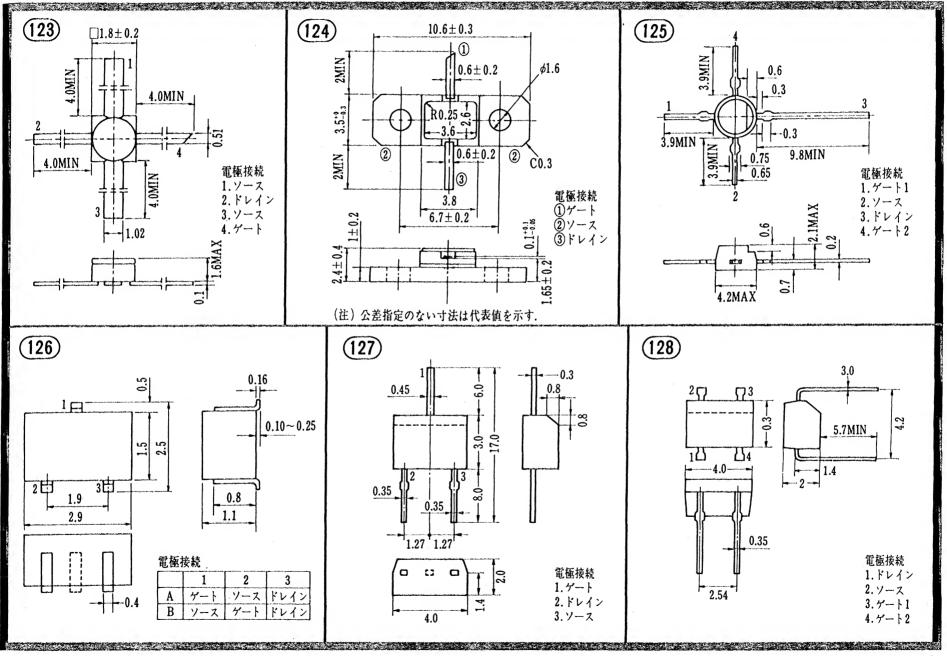


《寸法図単位:mm》

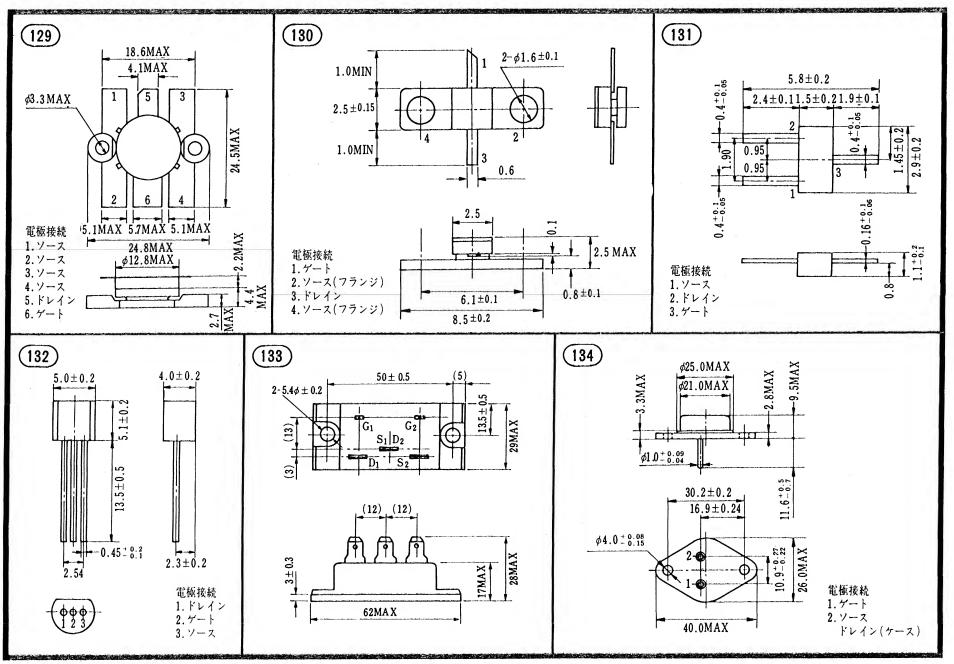




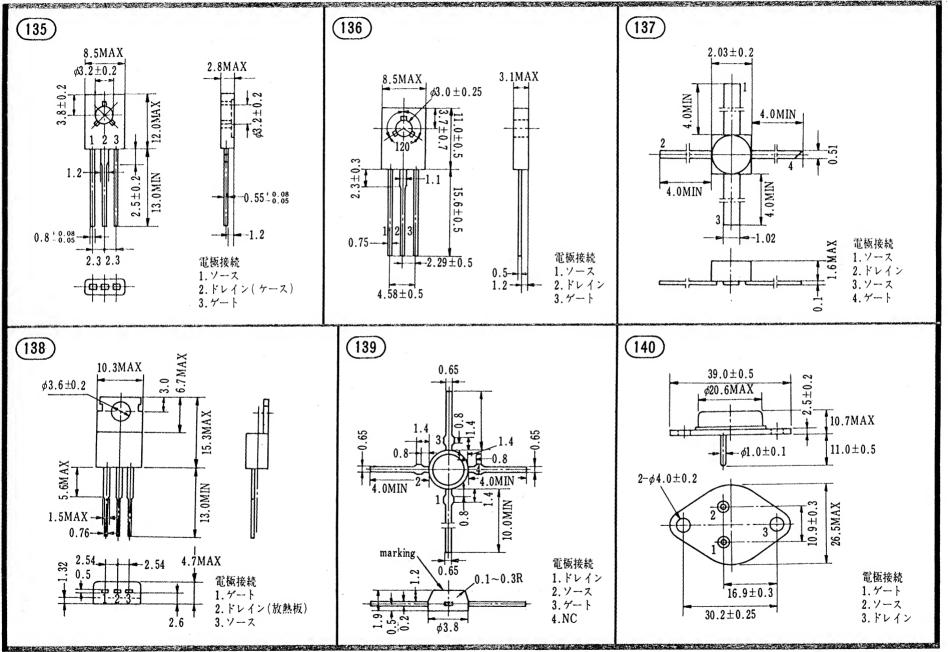
〈寸法図単位:mm》



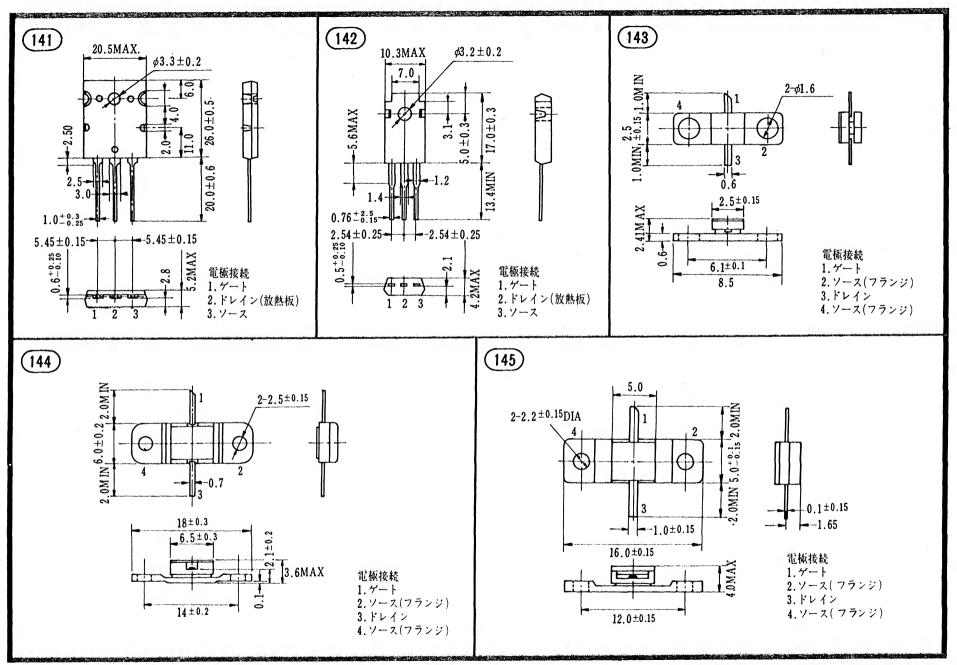
〈寸法図単位:mm〉



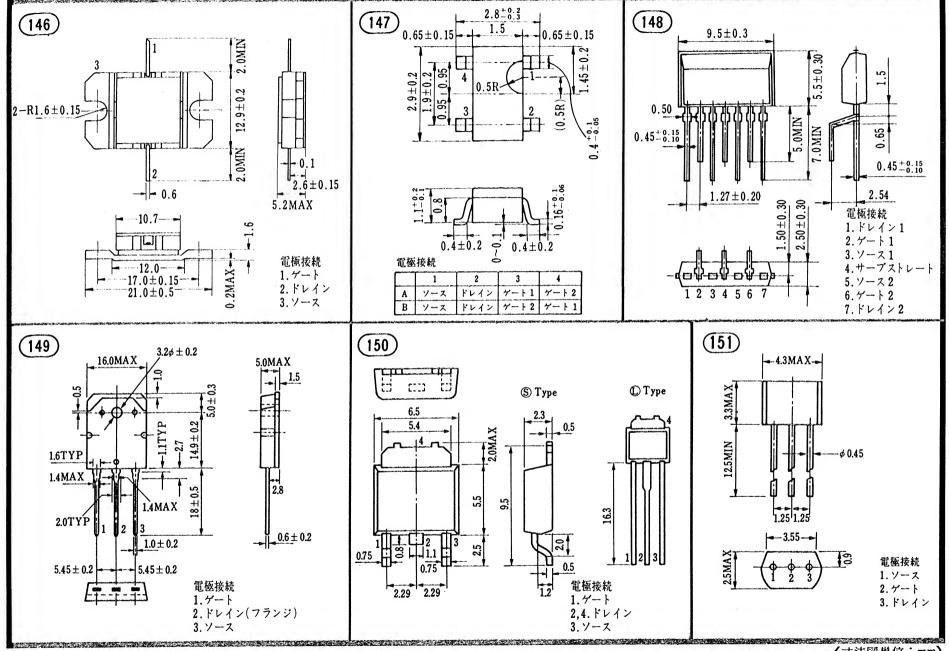
〈寸法図単位:mm〉



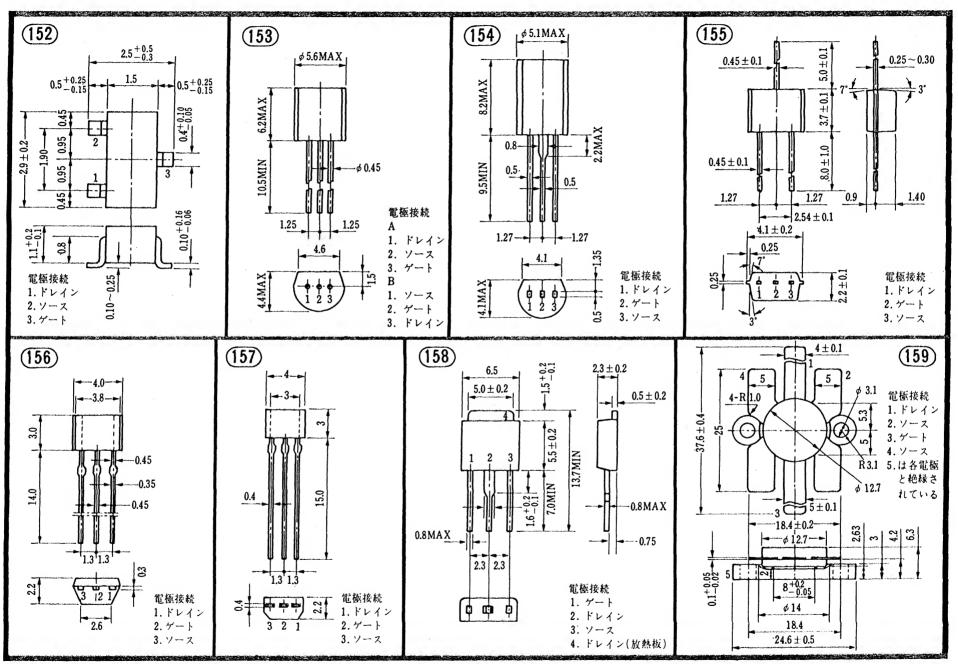
〈寸法図単位:mm〉



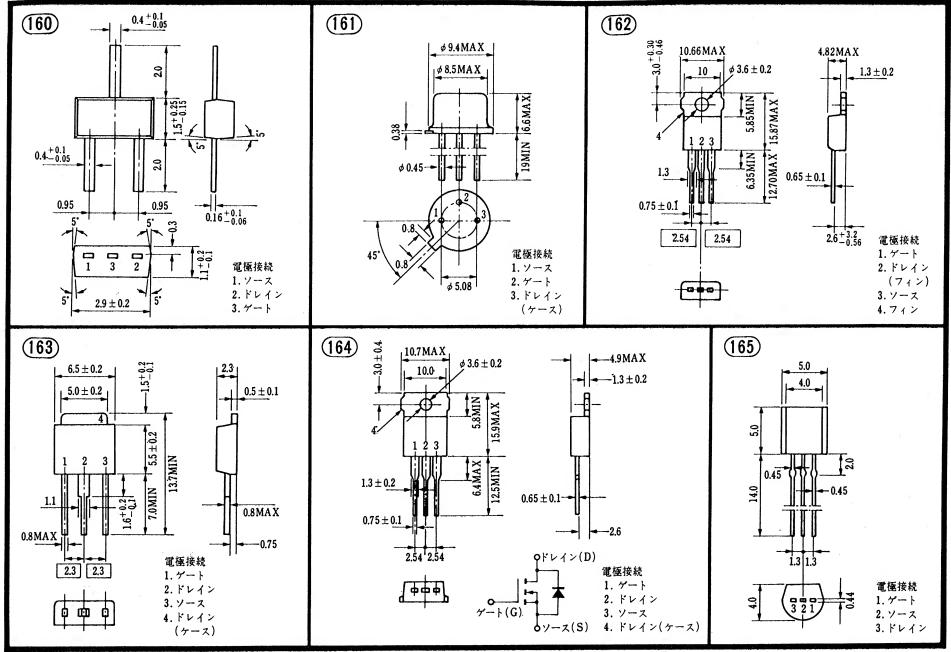
(寸法図単位:mm)



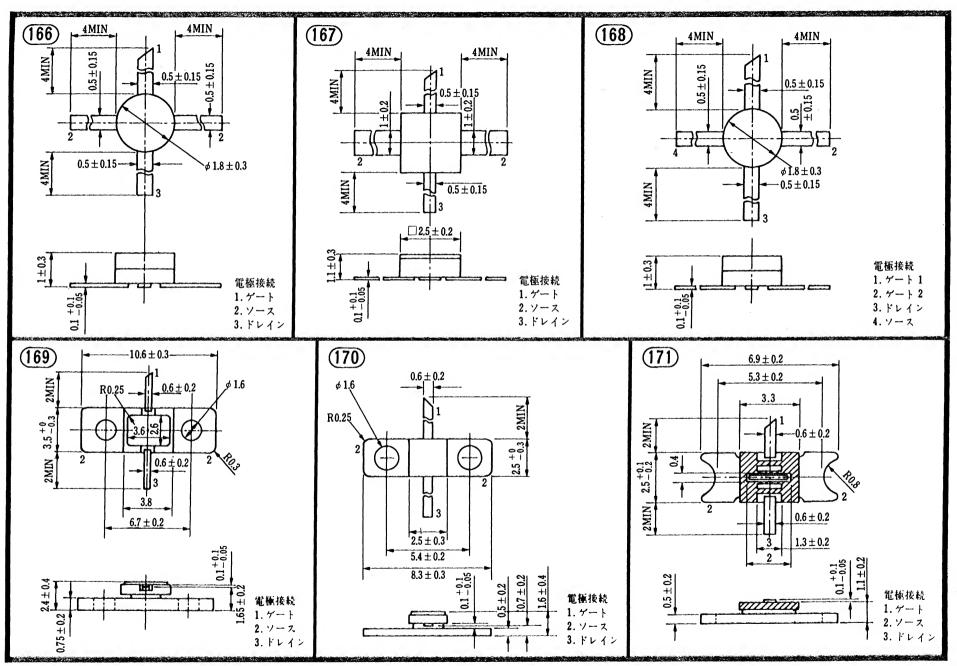
〈寸法図単位:mm〉



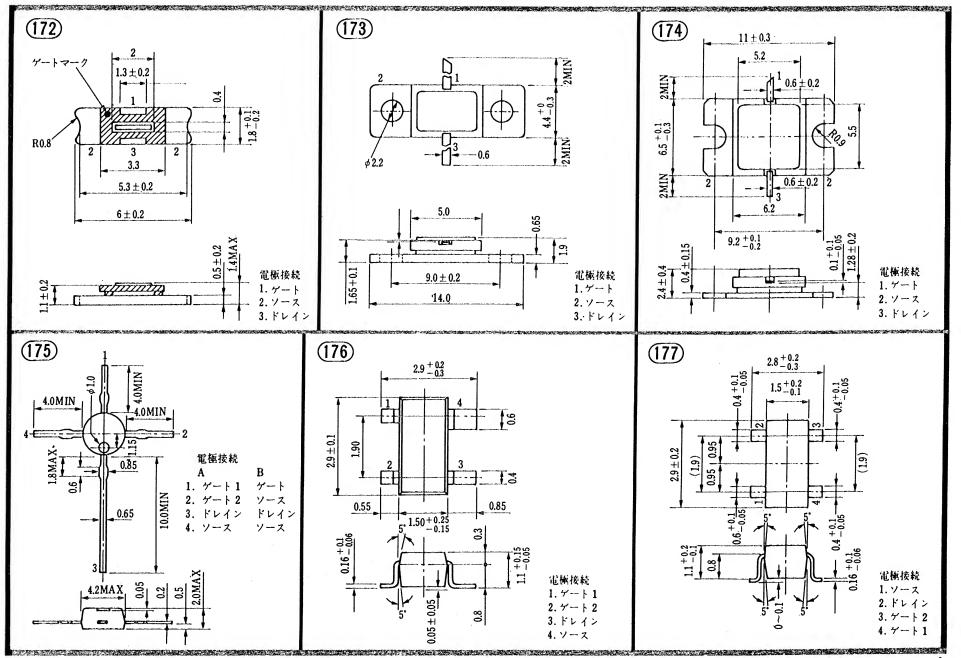
〈寸法図単位:mm〉



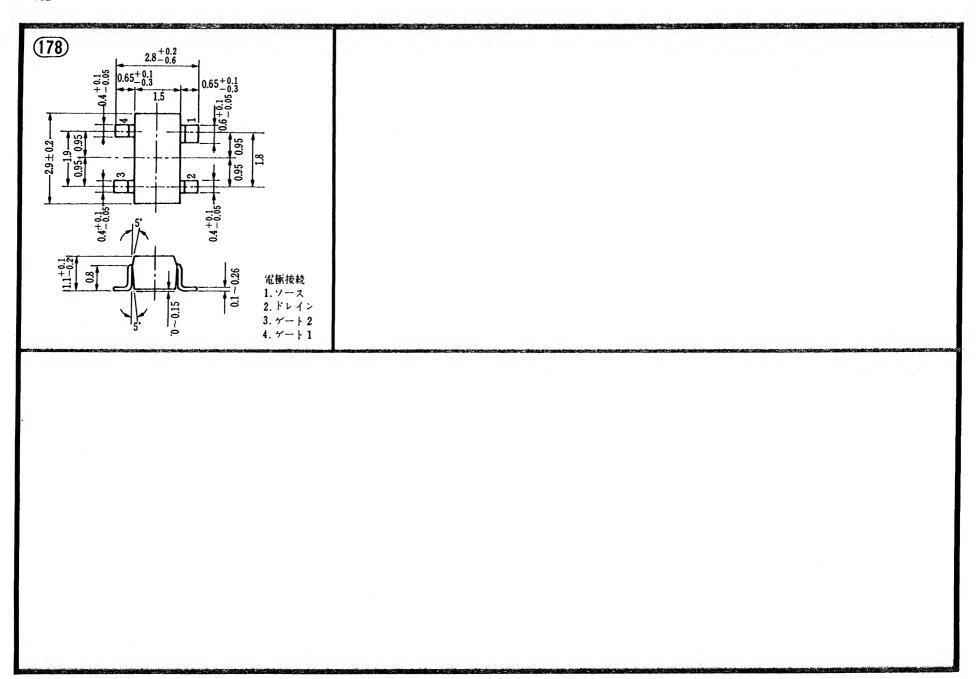
〈寸法図単位:mm〉



〈寸法図単位:mm〉



〈寸法図単位:mm〉





個別特性図

アイテム

C

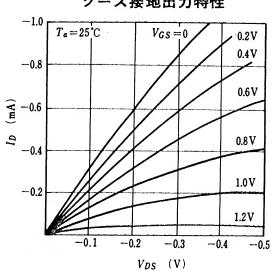
 $I_{DSS}$  (mA) | 1.0~3.0 | 2.5~6.0 | 5.0~

D

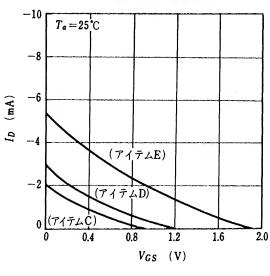
## ソース接地出力特性

12		

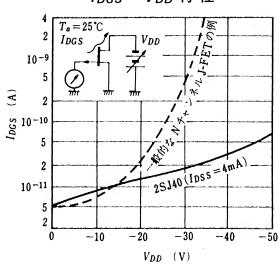
E

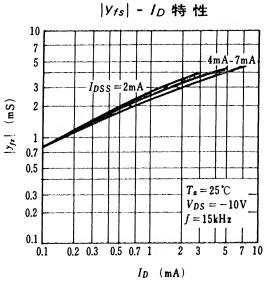


## ソース接地伝達特性

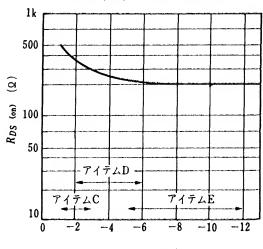


IDGS - VDD 特性





Ros(on) - loss 特性



IDSS (mA)

2SJ43

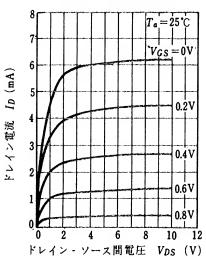
# Si 接合型 Pチャンネル

松

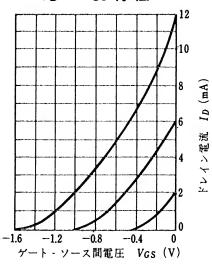
IDSS ランク分類

Class	P	Q	R
IDSS (mA)	0.5~3	2~6	4~12

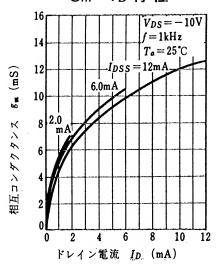
10 - Vos 特性



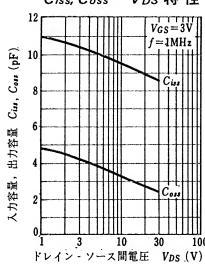
1p - VGS 特性



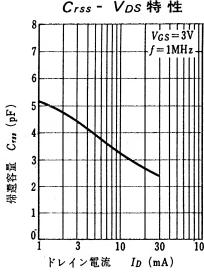
8m-1D特性



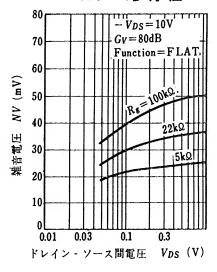
Ciss, Coss - VDS 特性



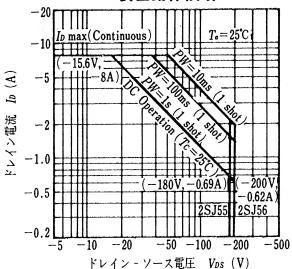
Crss - Vos 特性



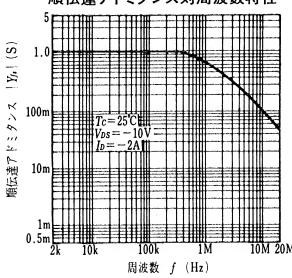
NV - 10 特性



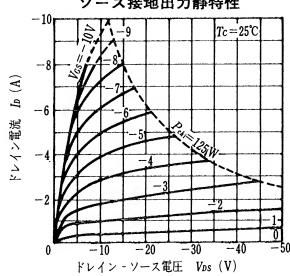
#### 安全動作領域



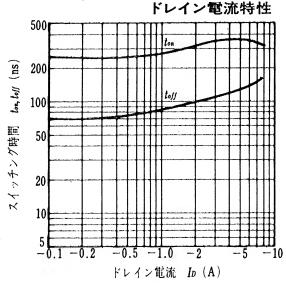
## 順伝達アドミタンス対周波数特性

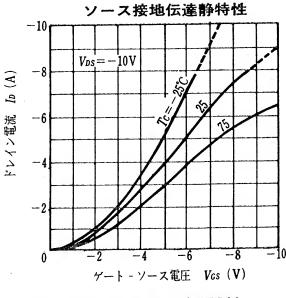


# ソース接地出力静特性

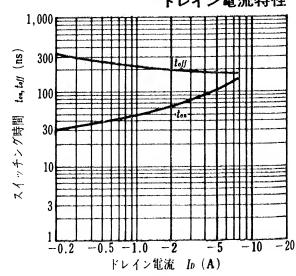


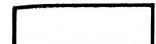
2SJ55,56 スイッチング時間対





2SJ56円 スイッチング時間対 ドレイン電流特性

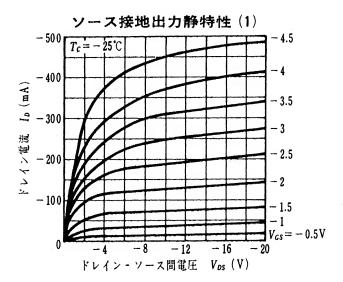


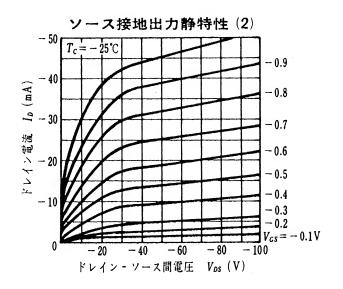


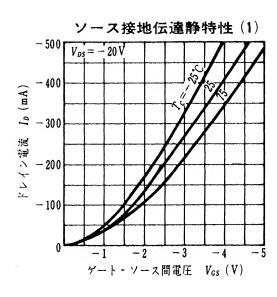
2SJ76,77,77成,78,79,79成 Si MOS型 Pチャンネル

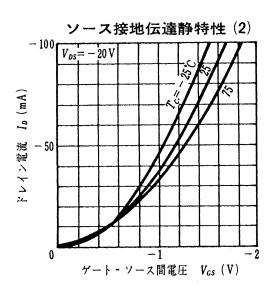
日

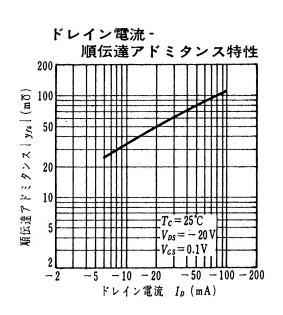
立

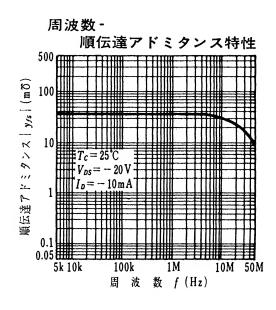












下

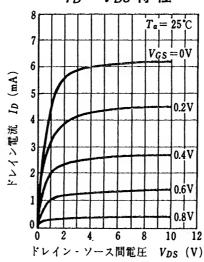
## Ipss ランク分類

Class	P	Q	R
IDSS (mA)	0.5~3	2~6	4~12
Marking Symbol	1MP	1MQ	1MR

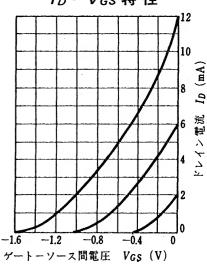
## 10 - Vos 特性

Si 接合型

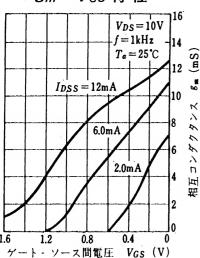
Pチャンネル



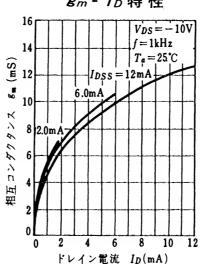
/D - VGS 特性



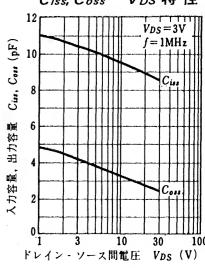
## gm - Vgs特性



8m-1D特性



Ciss, Coss - VDS 特性

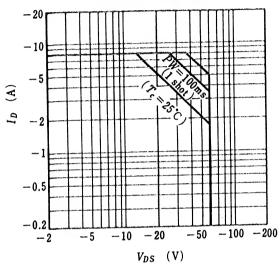


2SJ96

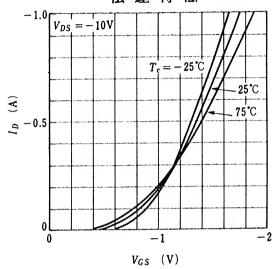
# Si MOS型 Pチャンネル

日 立

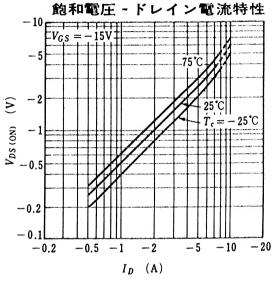




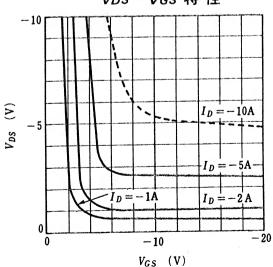
#### 伝 達 特 性



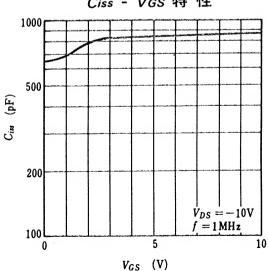
ドレイン - ソース間



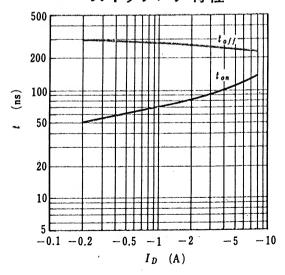
## Vos - Vgs 特性



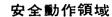
## Ciss - VGS 特性

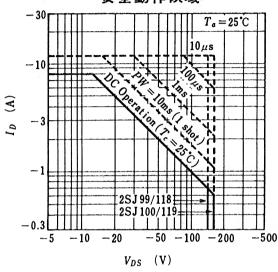


## スイッチング 特性

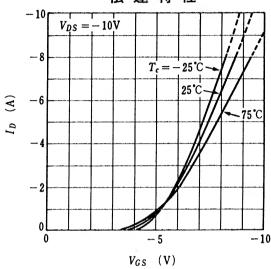


日 立

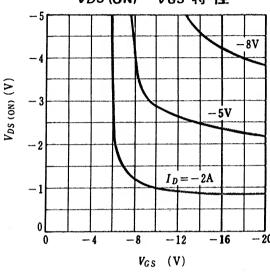




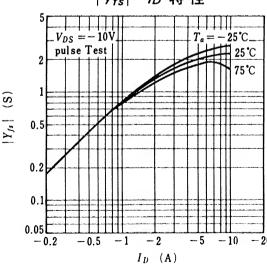
## 伝 達 特 性



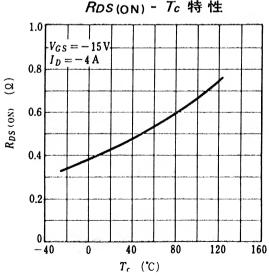
VDS (ON) - VGS 特性



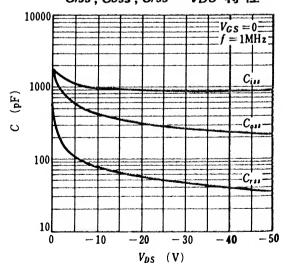
# | Yfs | - ID 特性



RDS(ON) - Tc 特性



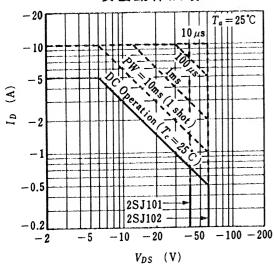
Ciss, Coss, Crss - VDS 特性

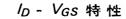


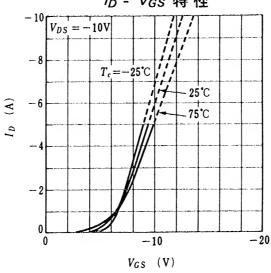
2SJ101,102

Si MOS型 Pチャンネル E 立

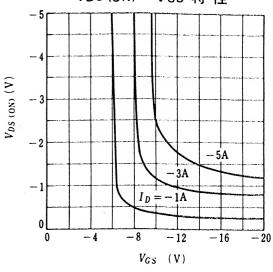




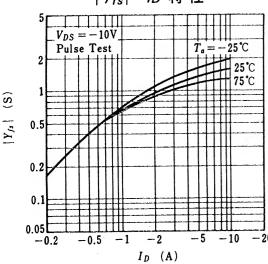




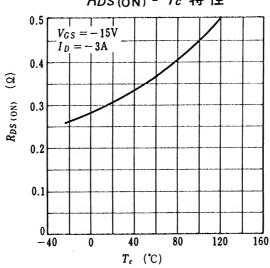
Vos (ON) - VGS 特性



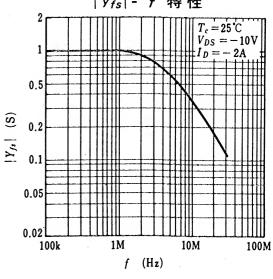
## | Yfs | - ID 特性



RDS(ON) - Tc 特性

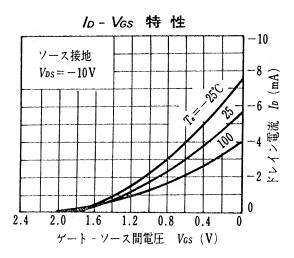


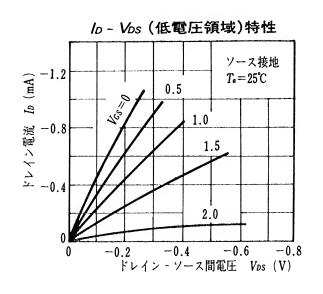
|Yfs|- f 特性

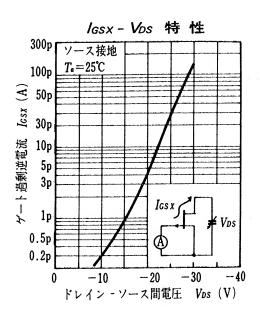


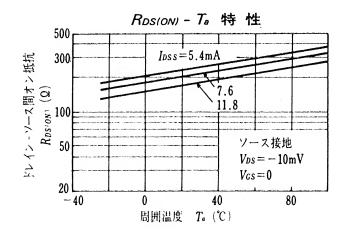
IDSS分類 Y:-1.2~-3.0mA

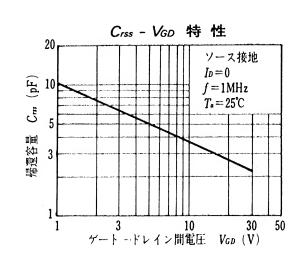
GR:  $-2.6 \sim -6.5 \text{mA}$ BL:  $-6 \sim -14 \text{mA}$ 

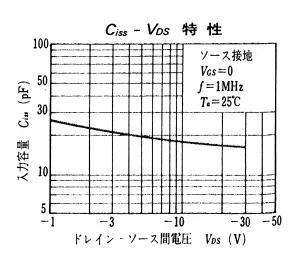










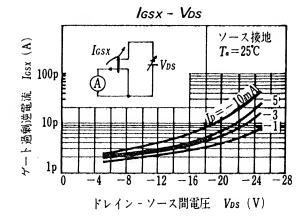


芝

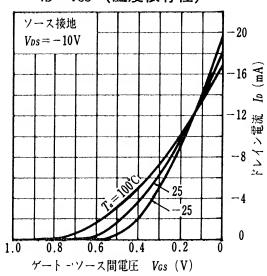
東

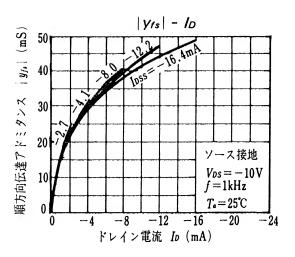
# Si 接合型 Pチャンネル

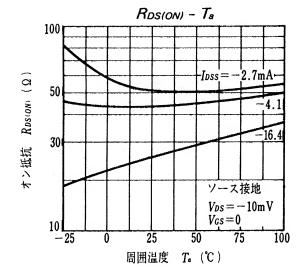
 $I_{DSS}$ 分類 GR:  $-2.6\sim-6.5$ , BL:  $-6\sim-12$ , V:  $-10\sim-20$ 

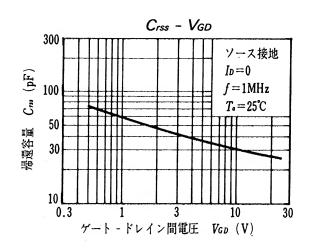


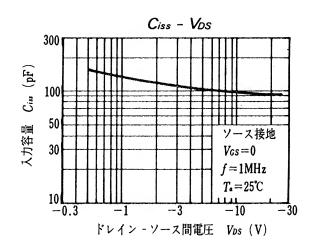
In - Vas (温度依存性)



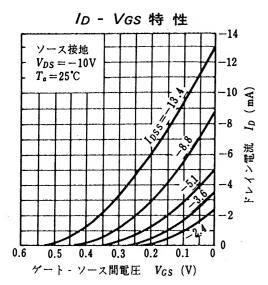


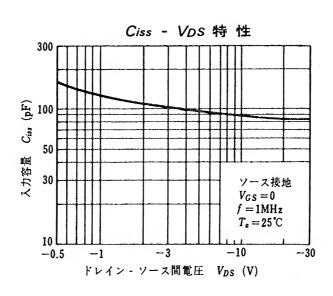


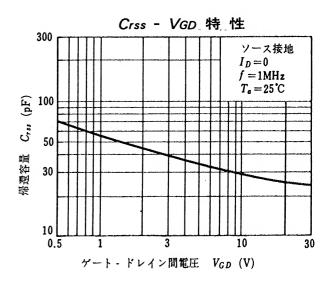


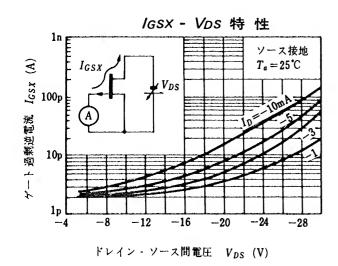


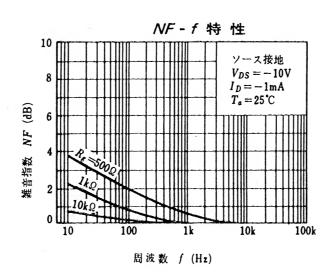
Si 接合型 Pチャンネル

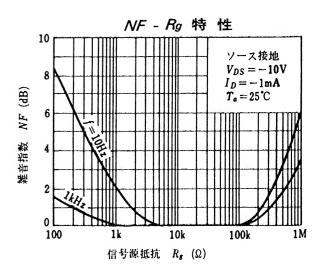




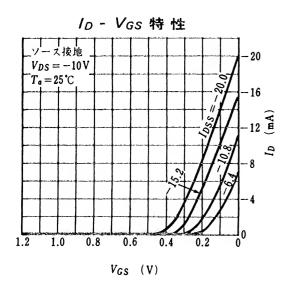


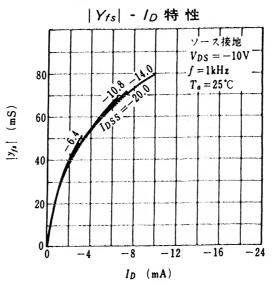


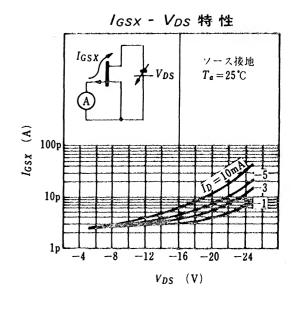




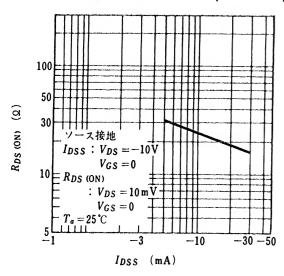
IDSS 分類 GR: -5.0~-10.0, BL: -8.0~-16.0, V: -14.0~-30.0

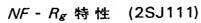


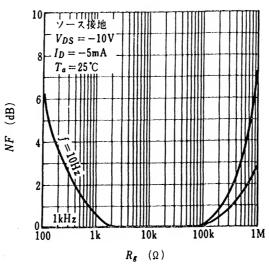




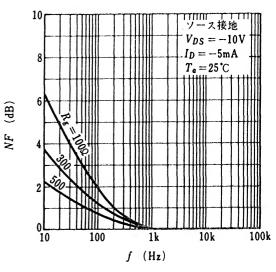
RDS (ON) - IDSS 特性 (2SJ110)



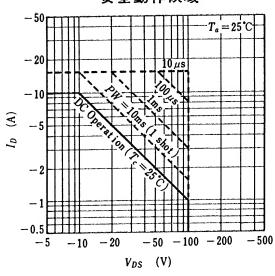




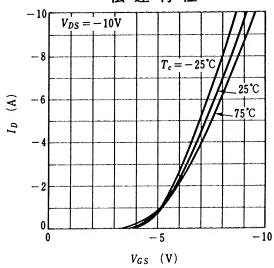
NF - f 特性 (2SJ111)



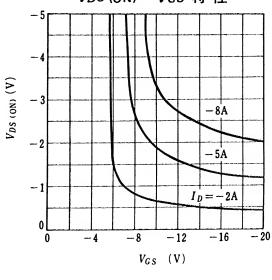
#### 安全動作領域



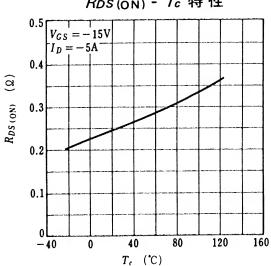
#### 伝達特性



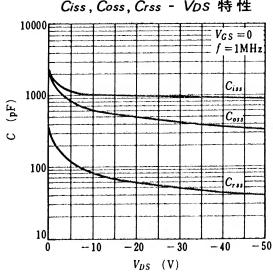
VDS (ON) - VGS 特性



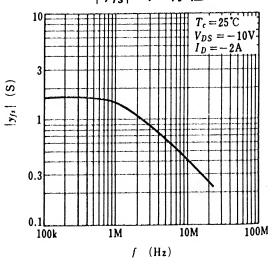
#### RDS(ON) - Tc 特性



Ciss, Coss, Crss - VDS 特性

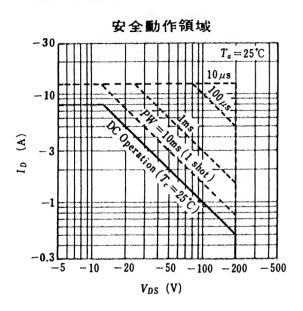


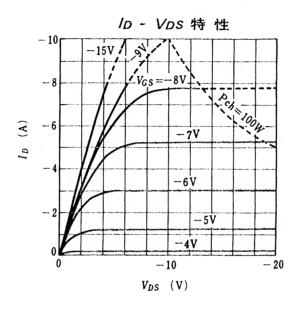
| Yfs | - f 特性

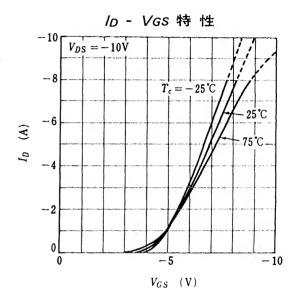


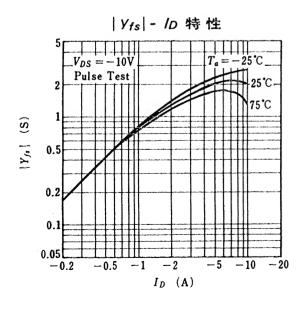
## Si MOS型 Pチャンネル

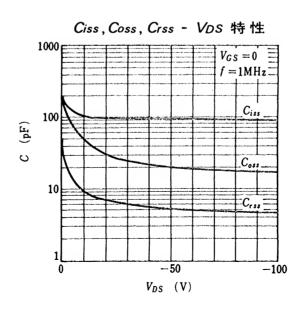
日 立

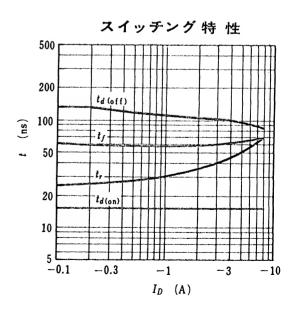






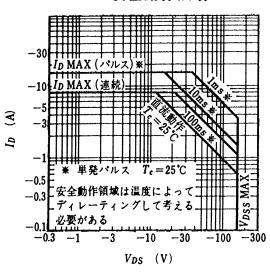




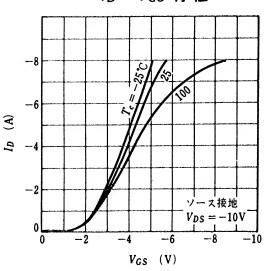


Si MOS型 \_ Pチャンネル 東芝

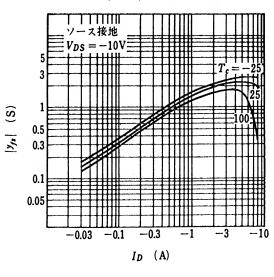
#### 安全動作領域



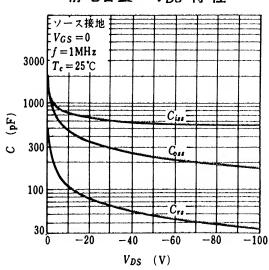
In - Vas 特性



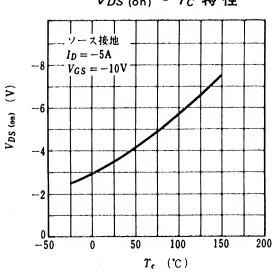
|Yfs| - ID 特性



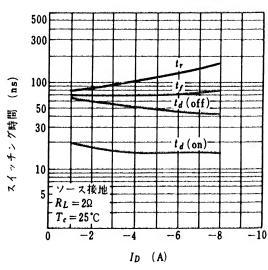
静電容量 - Vps 特性



Vos (on) - Tc 特性

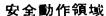


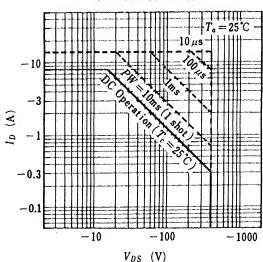
スイッチング特性



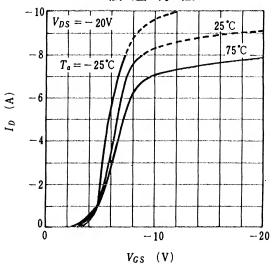
### Si MOS型 Pチャンネル

日 立

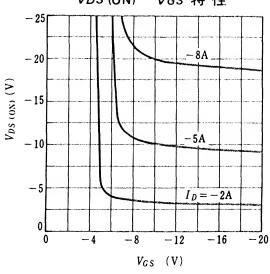




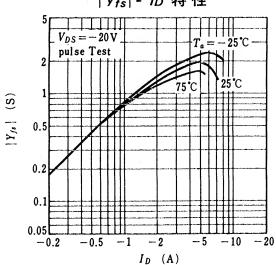
伝 達 特 性



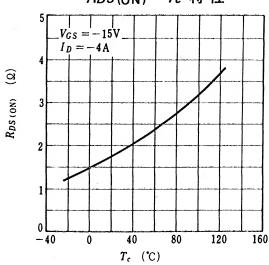
VDS (ON) - VGS 特性



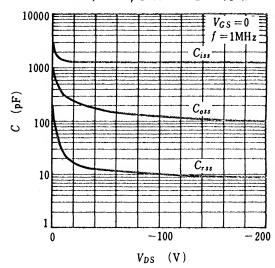
| Yfs | - ID 特性



RDS(ON) - Tc 特性

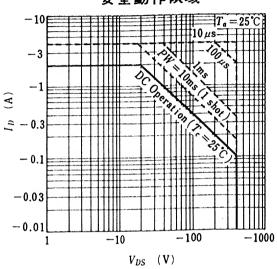


Ciss, Coss, Crss - VDS 特性

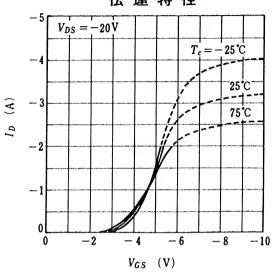


Si MOS型 Pチャンネル 日 立

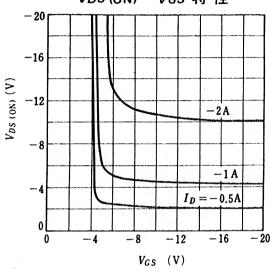
### 安全動作領域



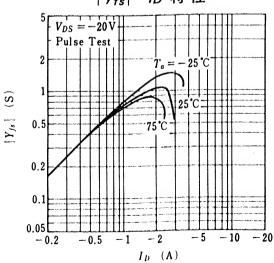


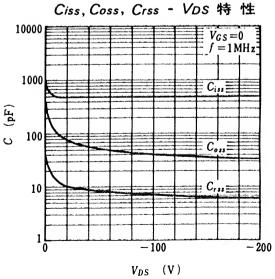


VDS (ON) - VGS 特性

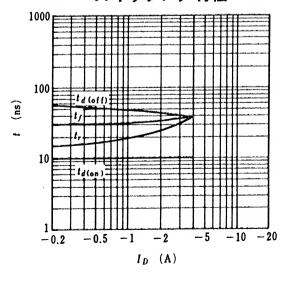


| Yfs | - ID 特性

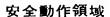


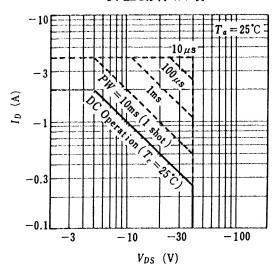


スイッチング 特性

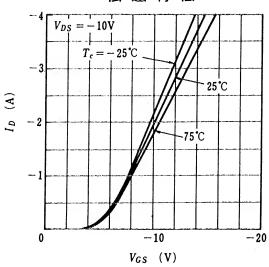


Si MOS型 日 立 Pチャンネル

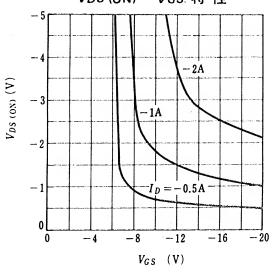




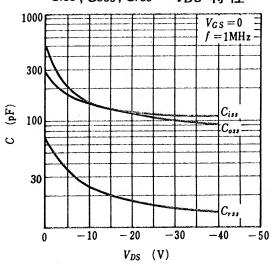
伝達特性



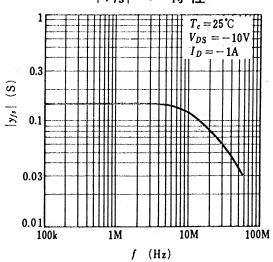
Vos (ON) - Vgs. 特性



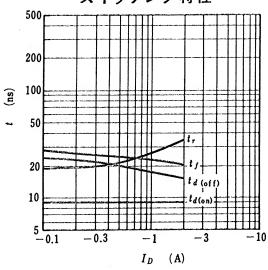
Ciss, Coss, Crss - VDS 特性



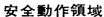
|Y<sub>fs</sub>|-f 特性

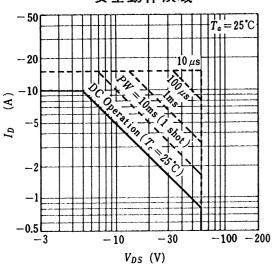


スイッチング特性

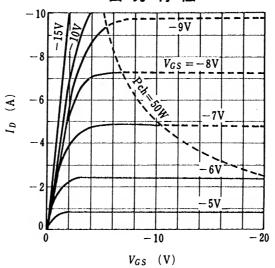


Si MOS型 Pチャンネル 日 立

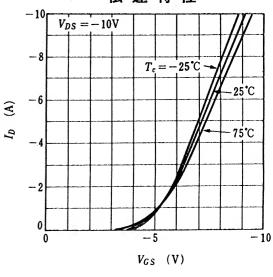




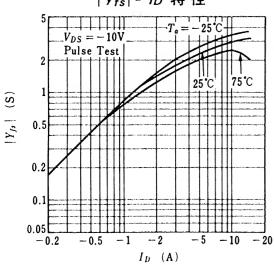




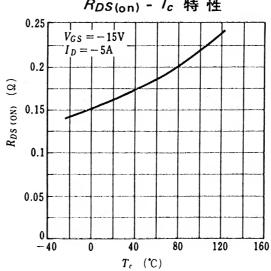
伝 達 特 性



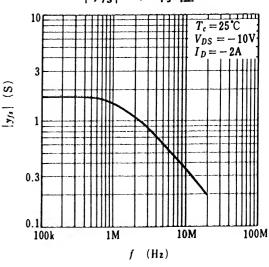
### | Yfs | - ID 特性



RDS(on) - Tc 特性

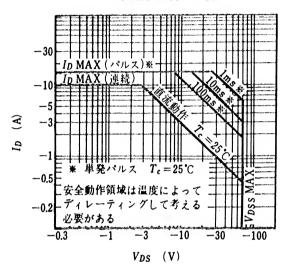


|Yfs|-f 特性

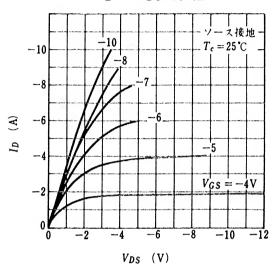


Si MOS型 Nチャンネル 東 芝

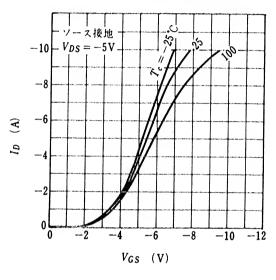
安全動作領域



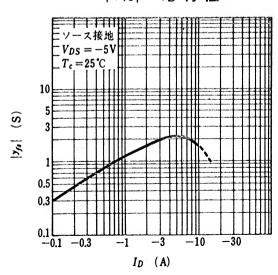
/p - Vps 特性



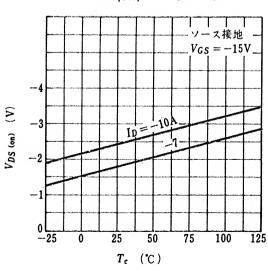
/D - VGS 特性



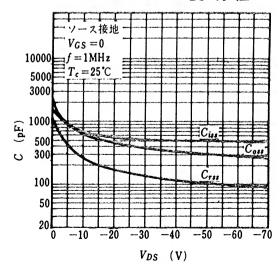
|Yfs| - ID 特性



Vos (on) - Tc 特性

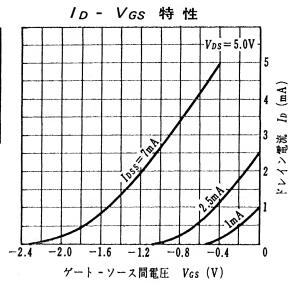


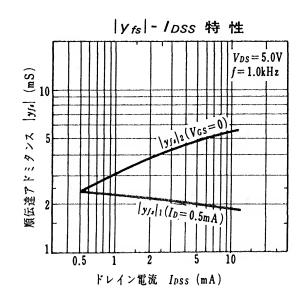
静電容量 - Vos 特性

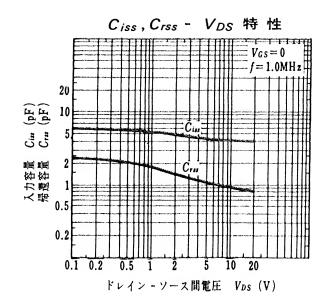


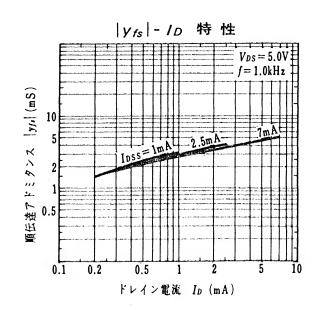
## 2SK105, 2SK160, 160A Si接合型 Nチャンネルー

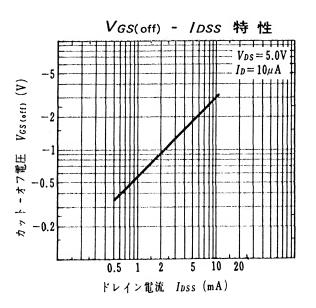
Ioss区分	0.5~1.5	1.0~3.0	2.0~6.0	4.0~12
2SK105	E	F	Н	J
2SK160	K4	K5	K6	K7
2SK160A	K24	K25	K26	K27











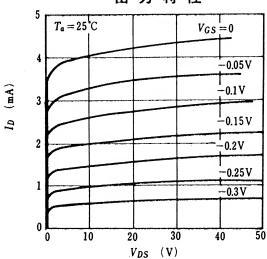
2SK108,492

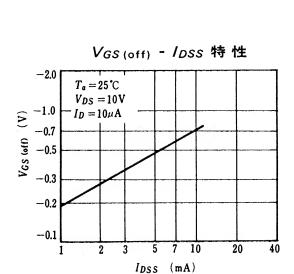
## Si 接合型 N チャンネル

菱

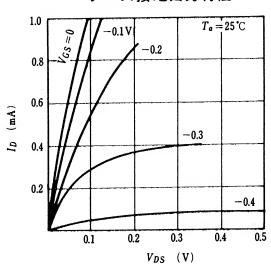
アイテム	С	D	Е
I <sub>DSS</sub> (mA)	1~3	2.5~6	5~12



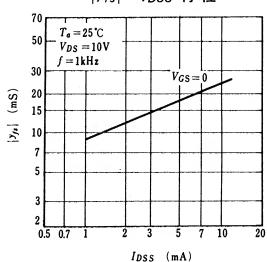




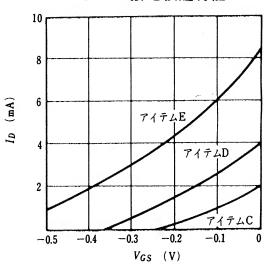
#### ソース接地出力特性



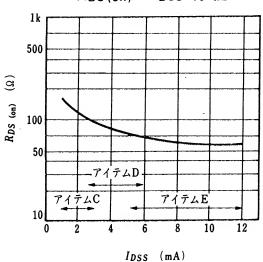
|Yfs| - IDSS 特性



#### ソース接地伝達特性

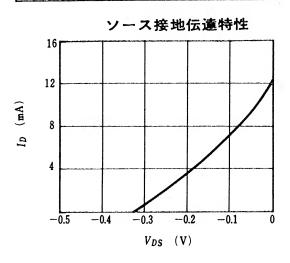


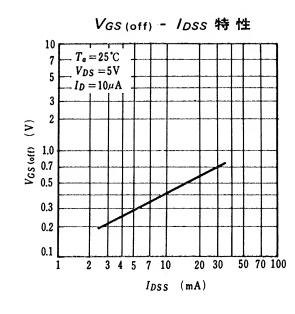
RDS(on) - IDSS 特性

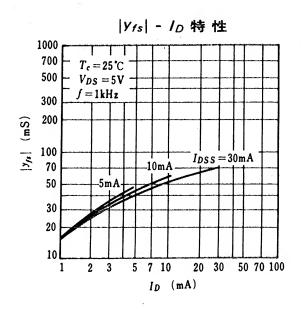


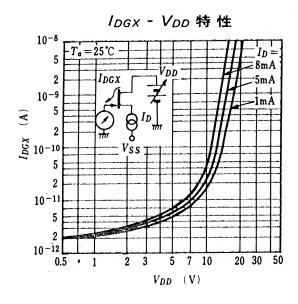
## Si 接合型 N チャンネル

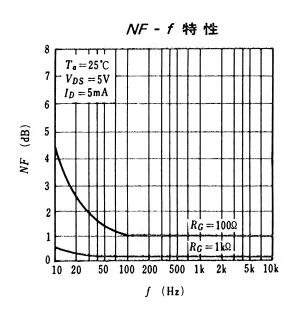
アイテム	D	E	F	G
IDSS (mA)	2.5~6	5~12	10~20	17~36

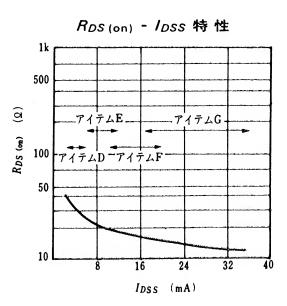






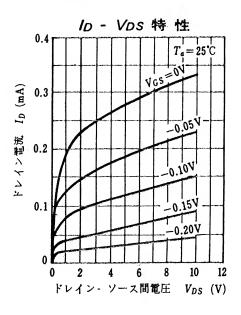


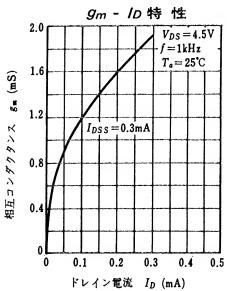


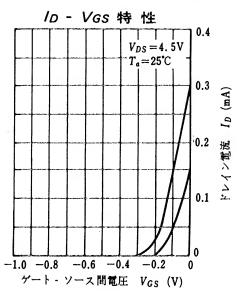


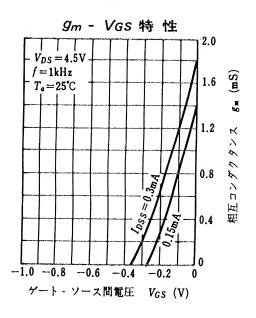
## Si 接合型 Nチャンネル

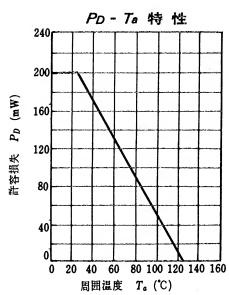
松 下







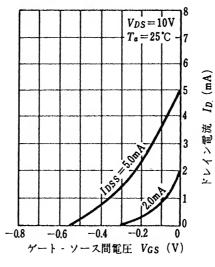




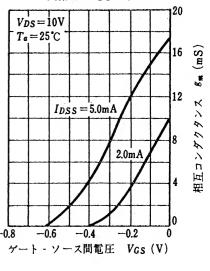
IDSS ランク分類

Class	P	Q	R
IDSS (mA)	0.5~3	2~6	4~12

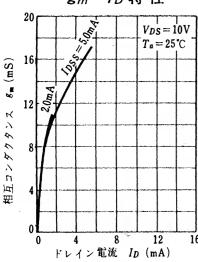
Ip - Vgs 特性



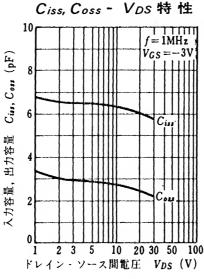
gm - VGS 特性



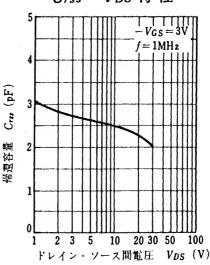
gm - 10特性



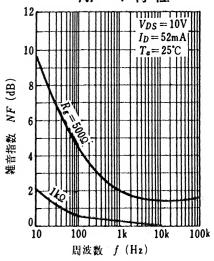
Ciss, Coss - VDS 特性

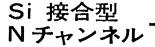


Crss - VDS 特性



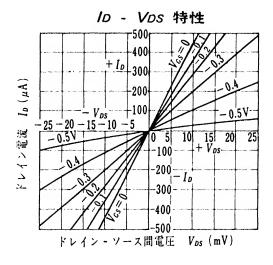
NF - f 特性

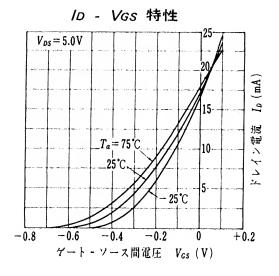


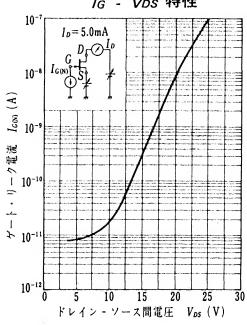


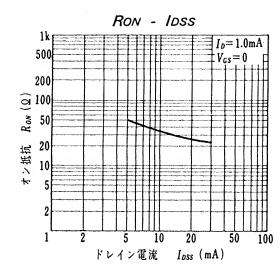
#### 日 電

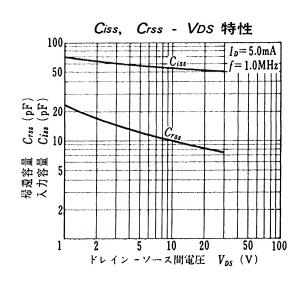
IG - Vos 特性









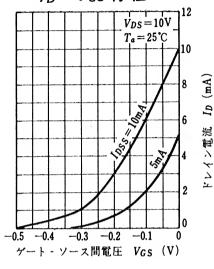


## Si 接合型 Nテャンネル

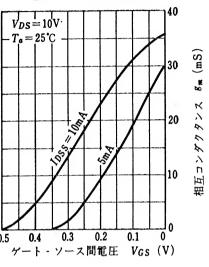
IDSS ランク分類

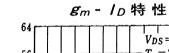
Class	P	Q	R	S
IDSS (mA)	0.5~3	2~6	4~12	10~20

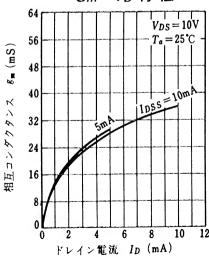
In - Vas 特性



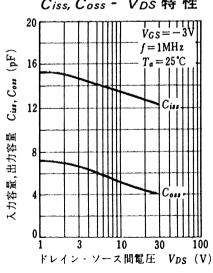
gm - Vgs 特性



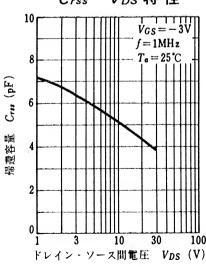




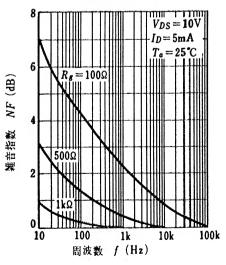
Ciss, Coss - VDS 特性



Crss - VDS 特性



NF - f 特性

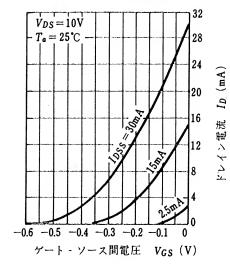


下

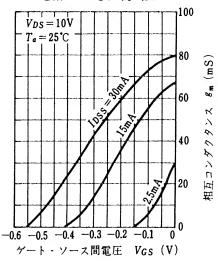
IDSS ランク分類

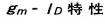
ſ	Class	Р	Q	R	S	Т
	IDSS (mA)	0.5~4	2~6	4~12	10~20	18~30

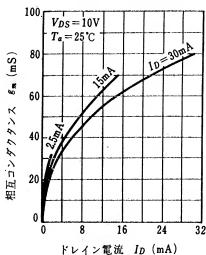
10 - Vgs 特性



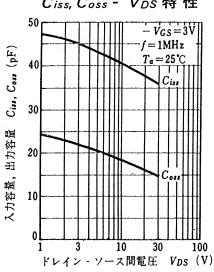
gm - Vgs特性



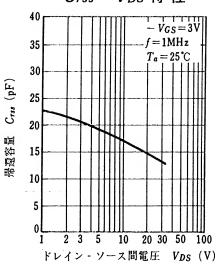




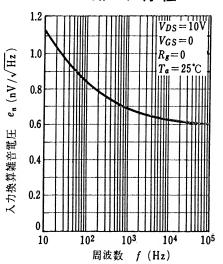
Ciss, Coss - VDS 特性



Crss - VDS 特性



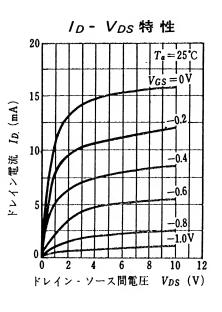
en - f 特性

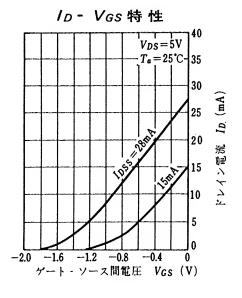


IDSS ランク分類

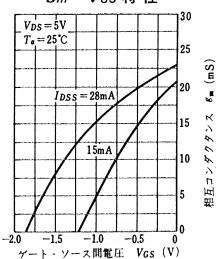
Class	P	Q	R
IDSS (mA)	8~16	14~24	20~32

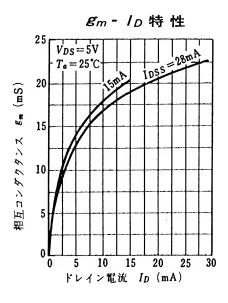
Si 接合型 Nチャンネル



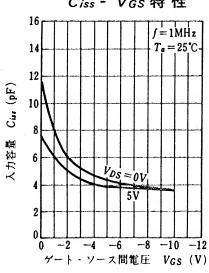


gm - Vgs特性

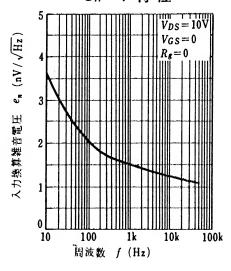




Ciss - VGS 特性



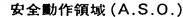
en-f特性

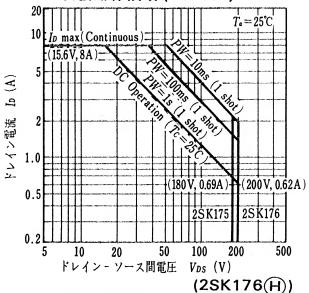


2SK175, 176, 176(H)

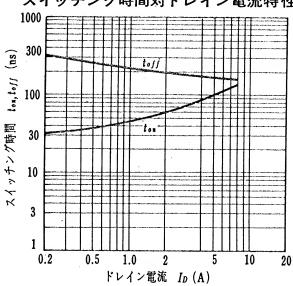
### Si MOS型 Nチャンネル

日 立

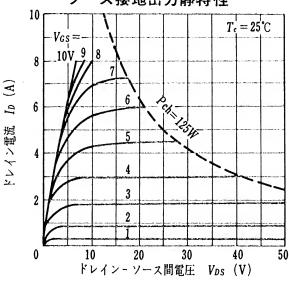




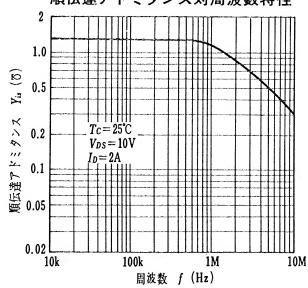
### スイッチング時間対ドレイン電流特性



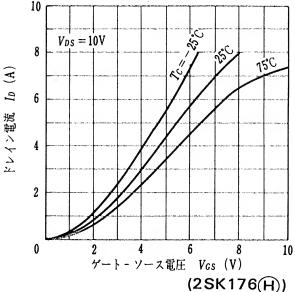
#### ソース接地出力静特性



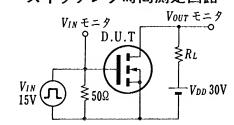
#### 順伝達アドミタンス対周波数特性



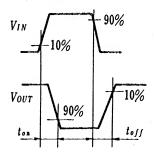
#### ソース接地伝達静特性



### スイッチング時間測定回路



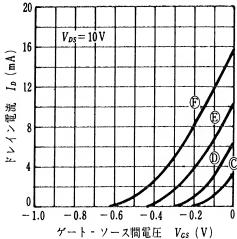
#### 応答波形



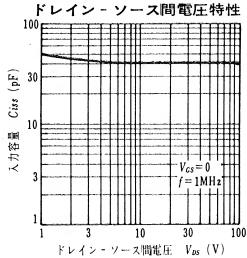
#### Ipssの値により下記のように4区分し、現品に表示してある.

©	<b>(</b>	Œ	Ē
2.5~ 5	4~8	6~12	10~20

#### ソース接地伝達静特性



#### 入力容量対

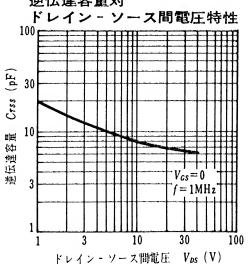


## Si 接合型 N チャンネル

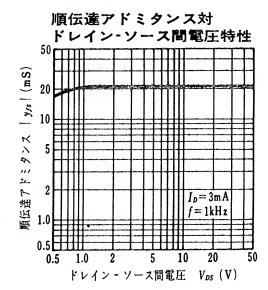
# 順伝達アドミタンス -ドレイン電流特性 200 (S m) - s/k - メハル - f = 1kHz

#### 逆伝達容量対

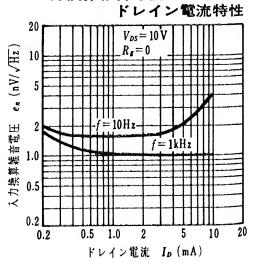
0.5 1.0



ドレイン電流 I<sub>D</sub> (mA)

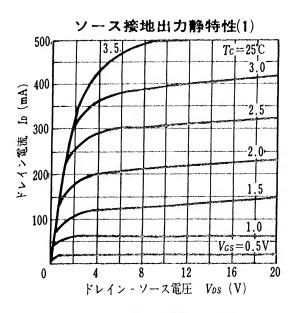


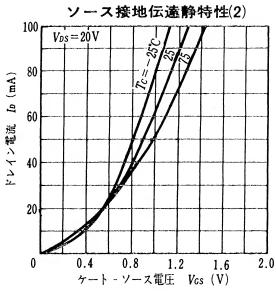
#### 入力換算雜音電圧 -

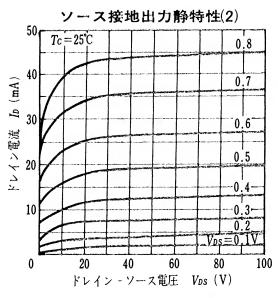


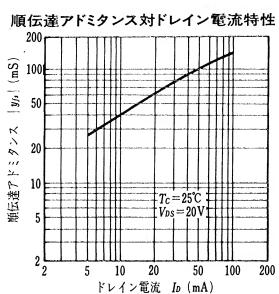
## 2SK213,214,214(K),215,216,216(K) Si MOS型 Nチャンネル

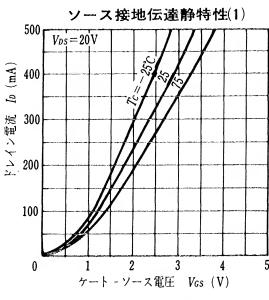
日 工

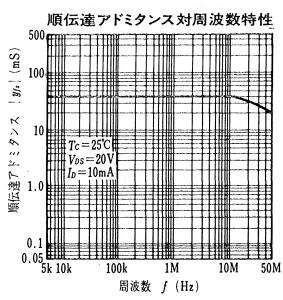










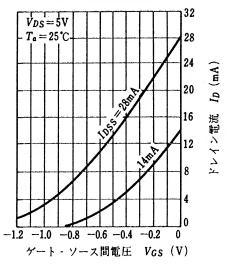


## Si 接合型 Nチャンネル

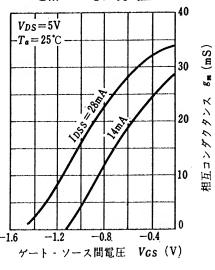
IDSS ランク分類

Class	P	Q	R	S
IDSS (mA)	5~16	14~24	20~32	28~42

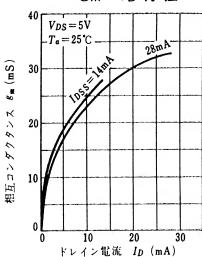
/p - V<sub>GS</sub> 特性

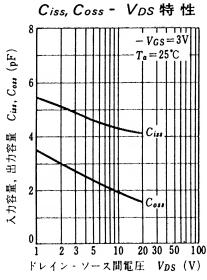


gm - Vgs 特性

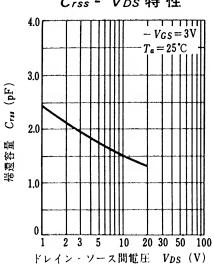


gm - 1D特性

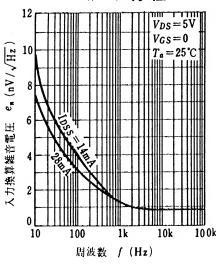




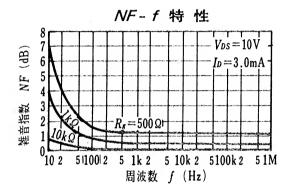
Crss - Vos 特性

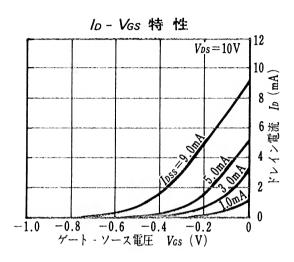


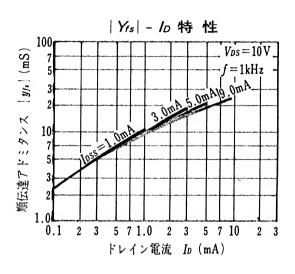
en-f特性

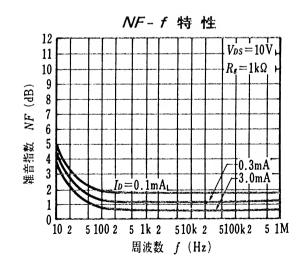


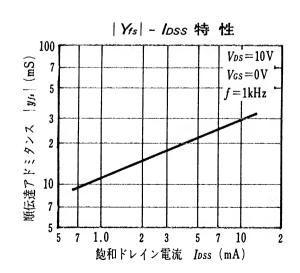
IDSSにより次のように分類している。(単位 mA)
0.6 C 1.5 1.2 D 3.0 2.5 E 6.0 5.0 F 12.0

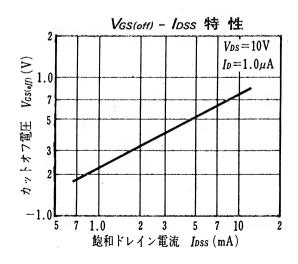


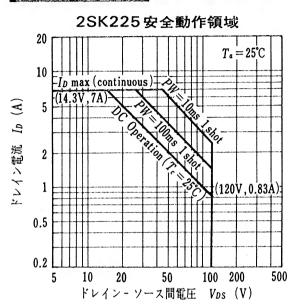


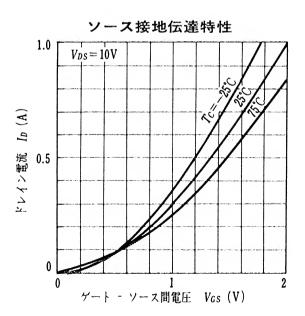


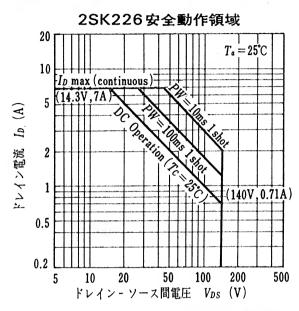


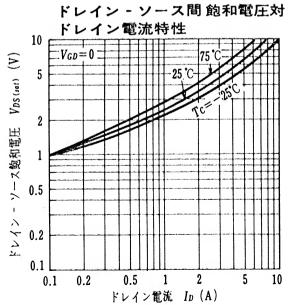


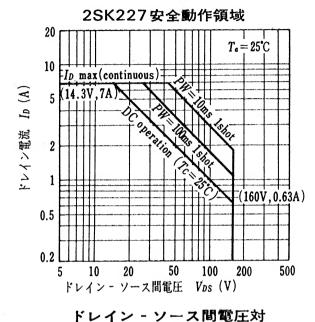


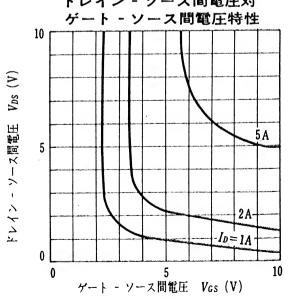










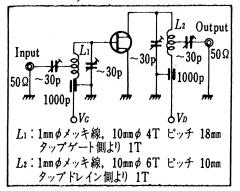


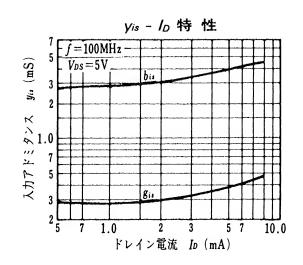
## Si 接合型 Nチャンネル

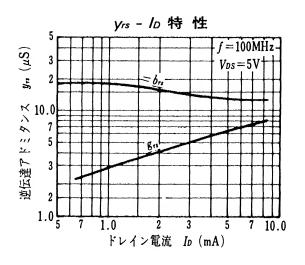
三 洋

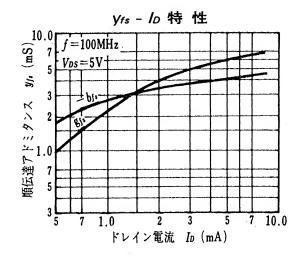
IDSSにより次のように分類している.(単位 mA)
0.6 C 1.5 1.2 D 3.0 2.5 E 6.0 5.0 F 12.0

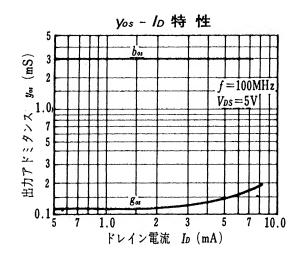
PG, NF 測定回路

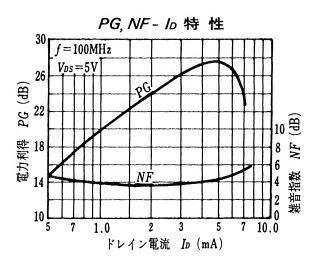








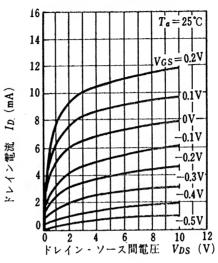




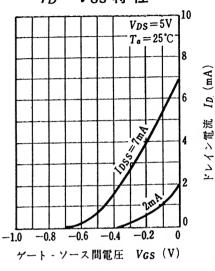
IDSS ランク分類

Class	·P	Q	R	S
IDSS (mA)	0.5~1.5	1~3	2~6	4~12

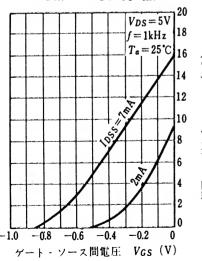
In - Vps 特性



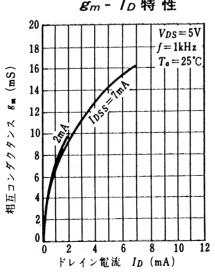
Ip - VGS 特性



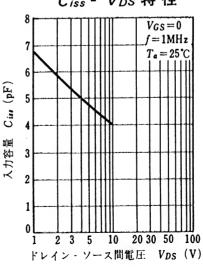
gm - VGS特性



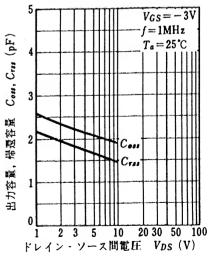
gm - 1D特性

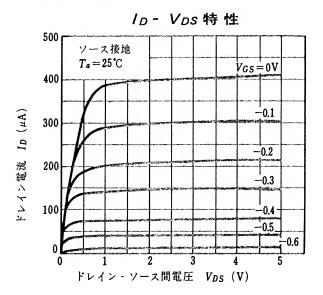


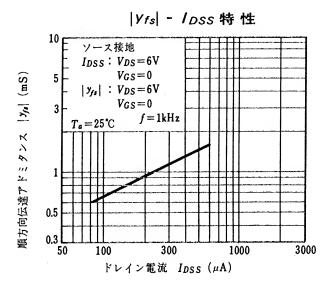
Ciss - VDS 特性



Coss, Crss - VDS 特性

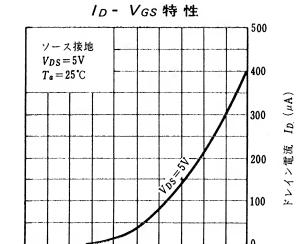






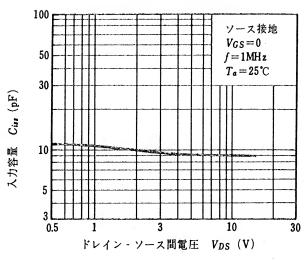
## Si 接合型 Nチャンネル

## 東芝





ゲート - ソース間電圧 VGS (V)

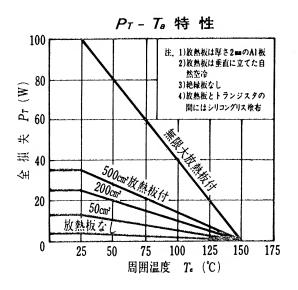


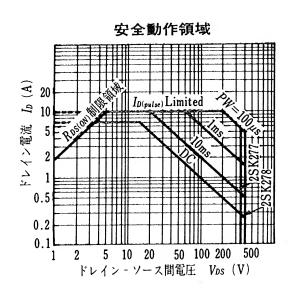
-1.0

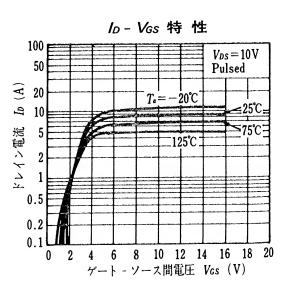
-0.8

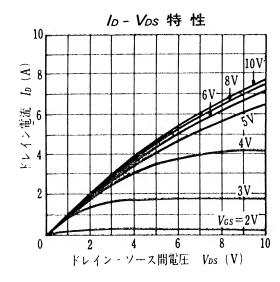
-0.6

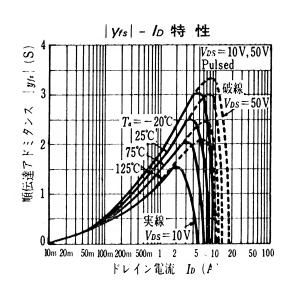
## 2SK277, 278

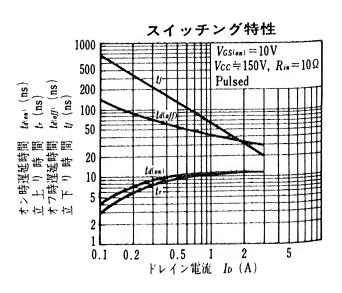




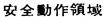


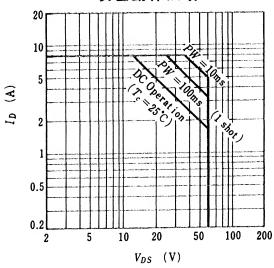




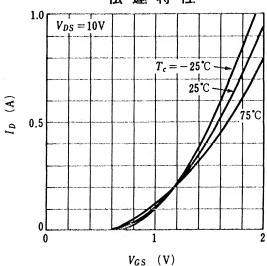


Si MOS型 Nチャンネル 日立

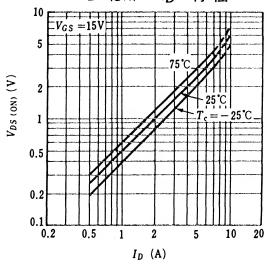




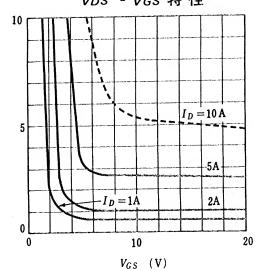




Vos (ON) - 10 特性

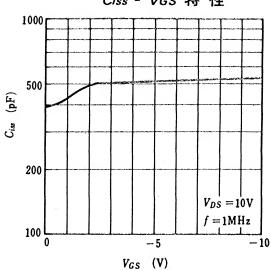


#### Vos - VGs 特性

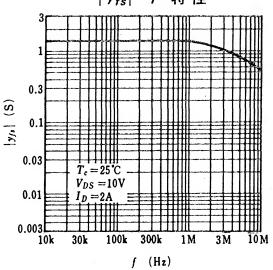


 $\widehat{\mathbf{S}}$ 

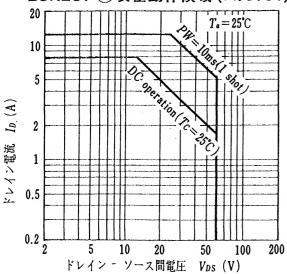
#### Ciss - VGS 特性



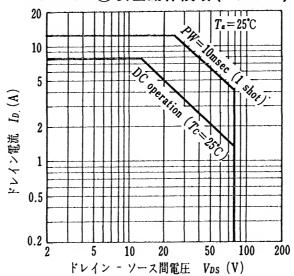
#### |Y<sub>fs</sub>|-f 特性



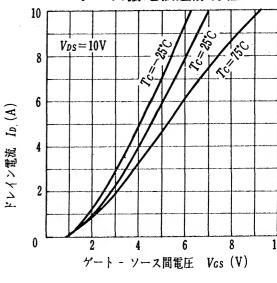




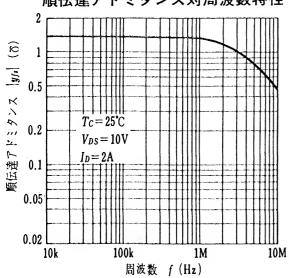
#### 2SK288 🛭 安全動作領域 (A.S.O.)



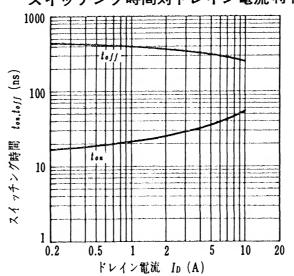
ソース接地伝達静特性



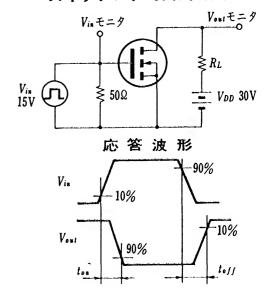
#### 順伝達アドミタンス対周波数特性



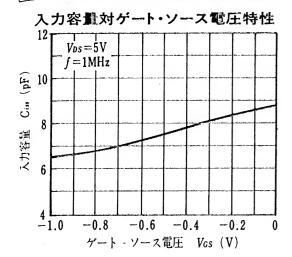
#### スイッチング時間対ドレイン電流特性

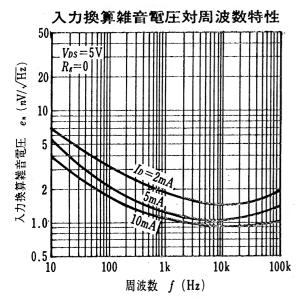


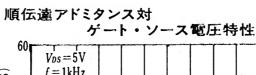
#### スイッチング時間測定回路

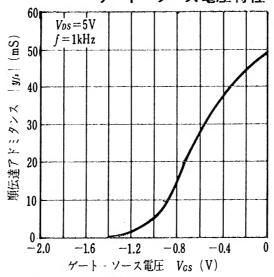


IDSS区分	gradus business and disagradus participates and the	ga anany mpanggapa ny ny mpanggapa ny mpangg	y man and an and the support operations as
E	F	G	Н
6~12	10~20	16~32	25~50

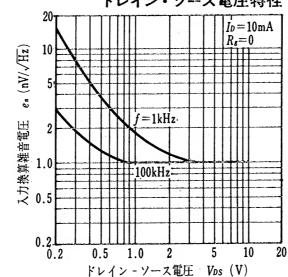




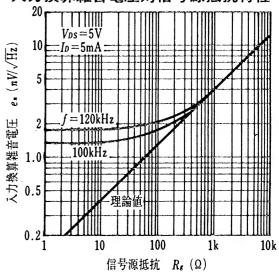




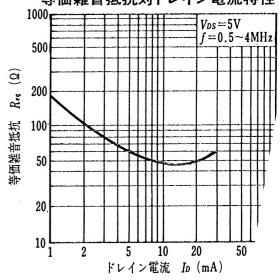
入力換算雑音電圧対 ドレイン・ソース電圧特性



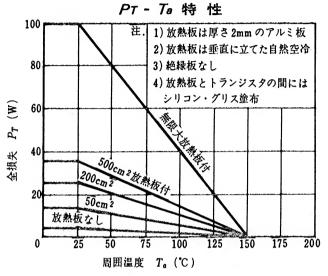
入力換算雜音電圧対信号源抵抗特性



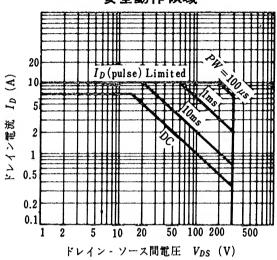
#### 等価雑音抵抗対ドレイン電流特性



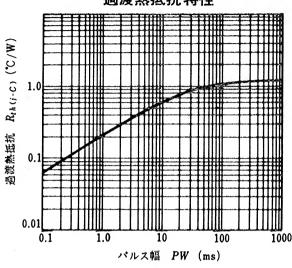




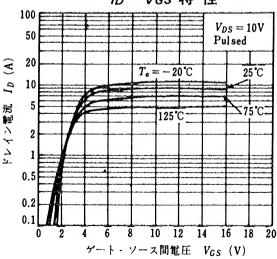
#### 安全動作領域

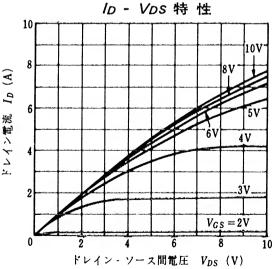


#### 過渡熱抵抗特性

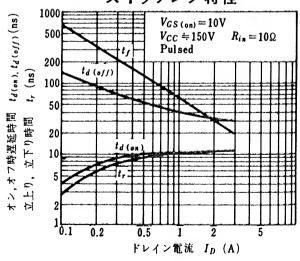


#### ID - VGS 特性





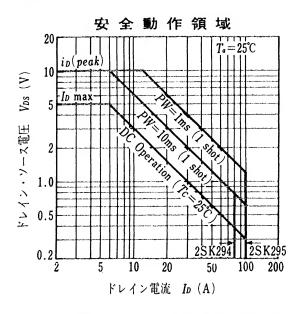
スイッチング特性

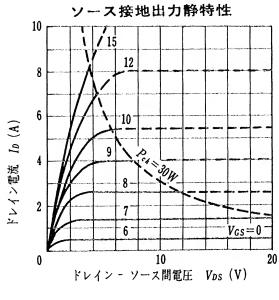


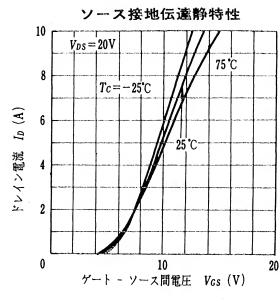
2SK294, 295

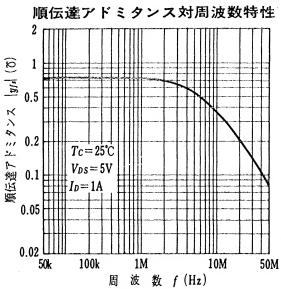
## Si MOS型 \_ Nチャンネル

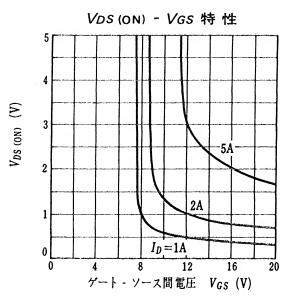
日 立

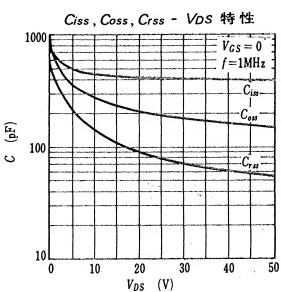


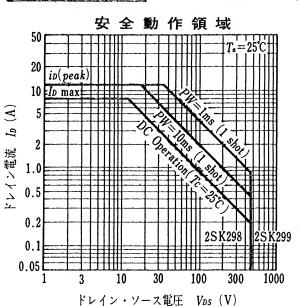


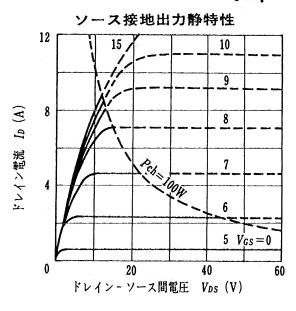


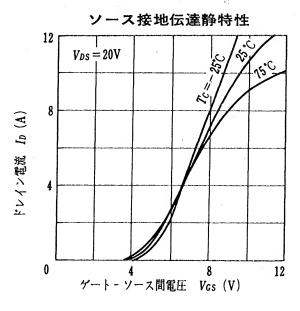


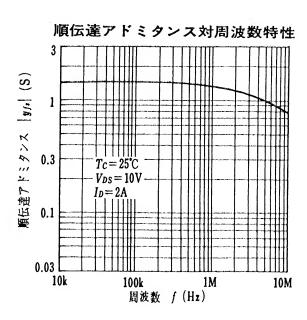


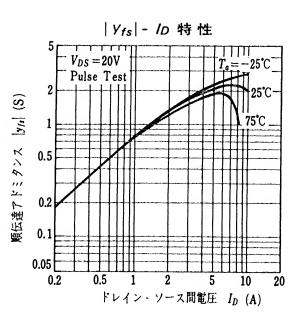


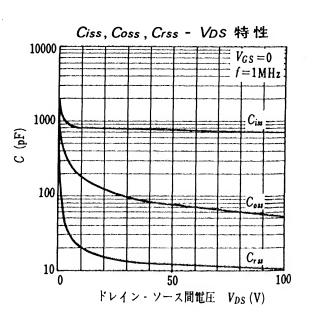








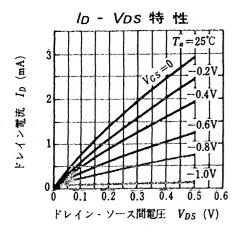


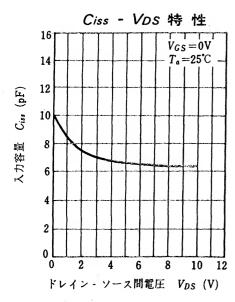


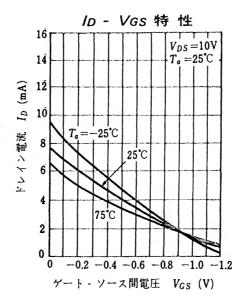
## Si 接合型 Nチャンネル

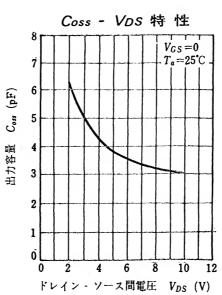
IDSS ランク分類

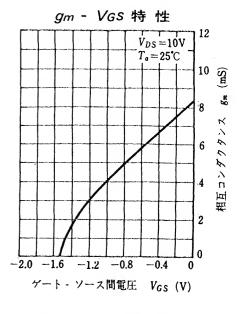
and the second s	P	Q	R	S
IDSS (mA)	1~3	2~6.5	5~12	10~20

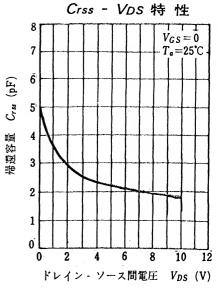






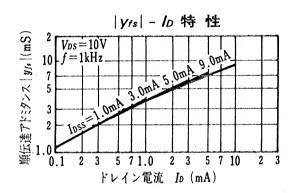


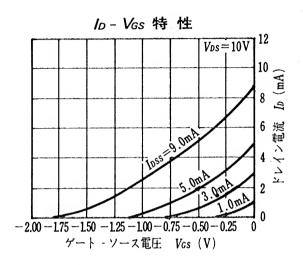


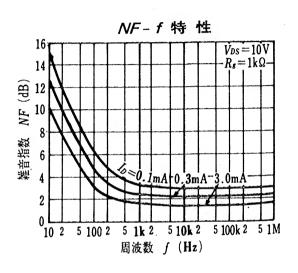


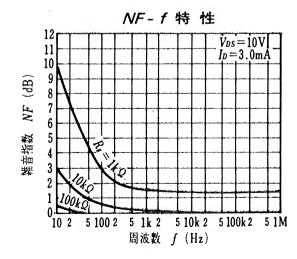
Ipssにより次のように分類している。(単位 mA)

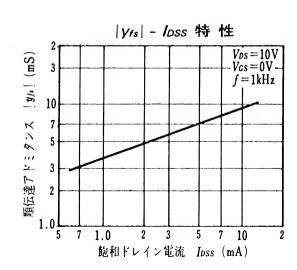
0.6 C 1.5 1.2 D 3.0 2.5 E 6.0 5.0 F 12.0

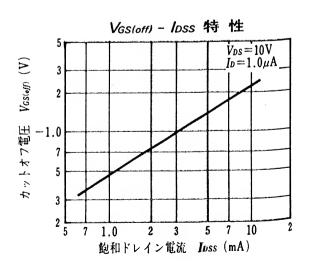








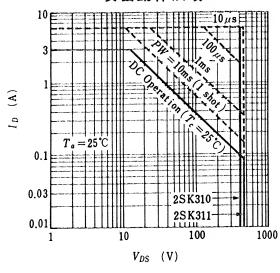




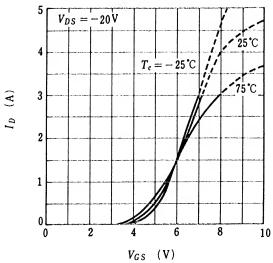
2SK310,311

Si MOS型 Nチャンネル 日 立

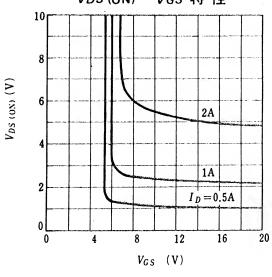




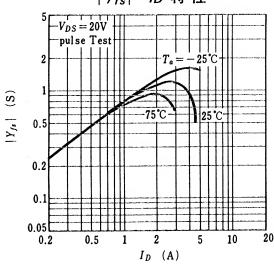
# 伝 遠 特 性



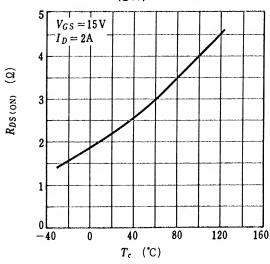
Vos (ON) - VGS 特性



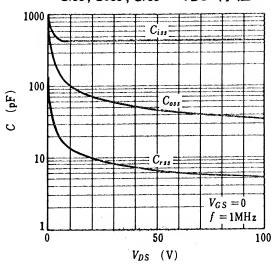
# | Yfs | - ID 特性



# RDS(ON) - Tc 特性

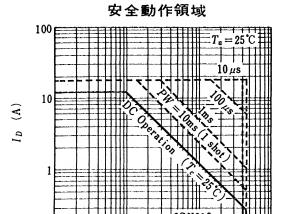


Ciss, Coss, Crss - VDS 特性



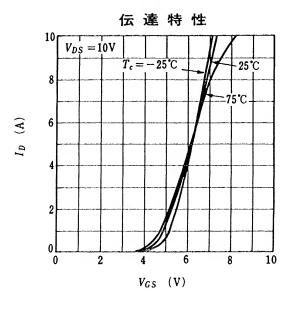
100

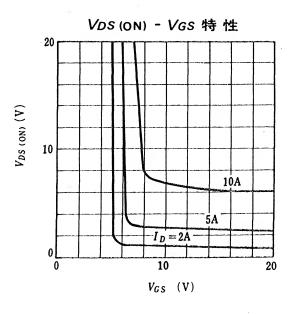
1000

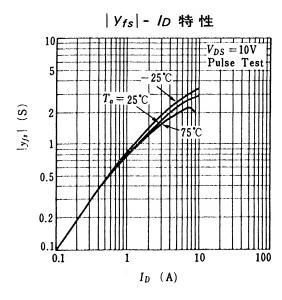


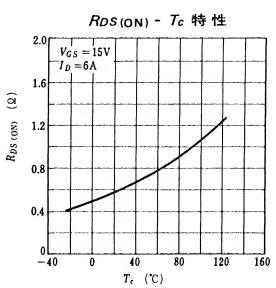
10

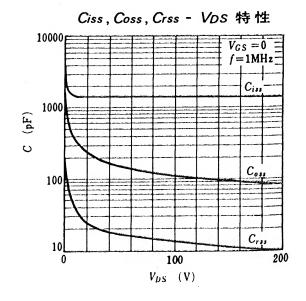
 $V_{DS}$  (V)







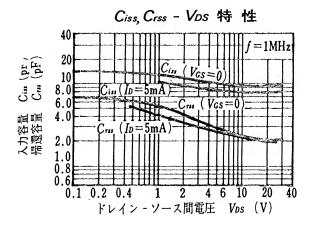


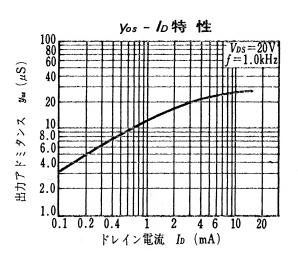


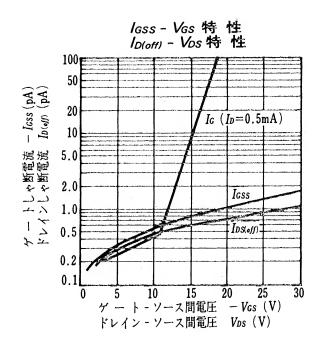
H

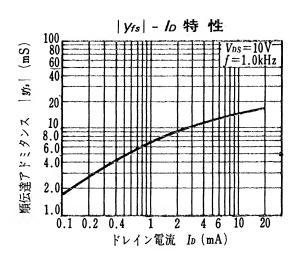
# 2SK314

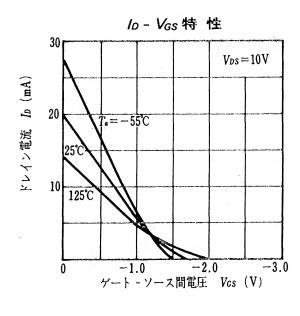
IDSS区分 K:5~12mA L:11~18mA M:17~24mA N:23~30mA

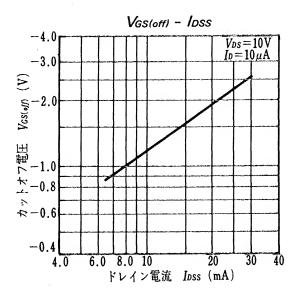




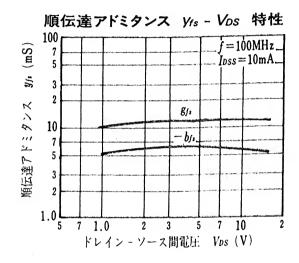


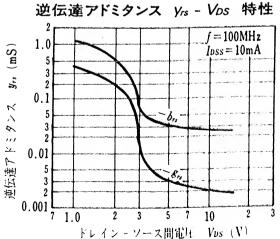


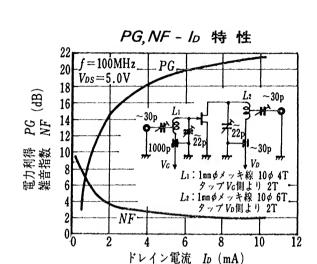




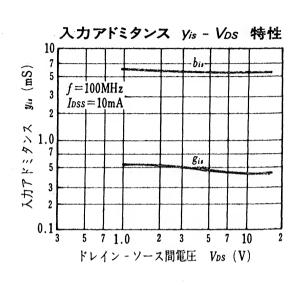
Iossにより次のように分類している。(単位 mA) 2.5 E 6.0 5.0 F 12.0 10.0 G 24.0

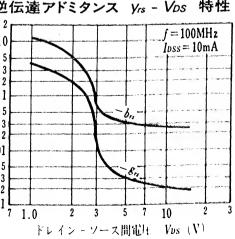


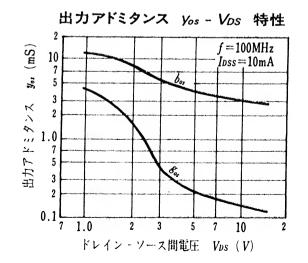




Si 接合型 Nチャンネル



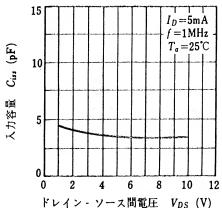




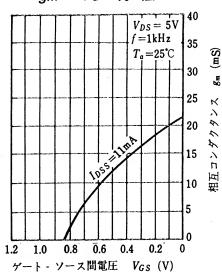
IDSS ランク分類

	P	Q	
$I_{DSS}(mA)$	5~16	14~24	

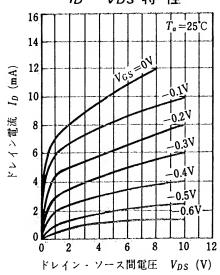
Ciss - Vos 特性



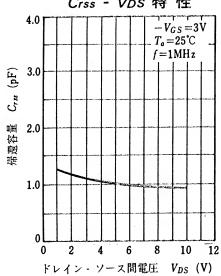
gm - VGS 特性



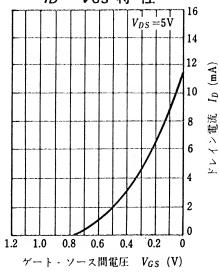
ID - VDS 特性



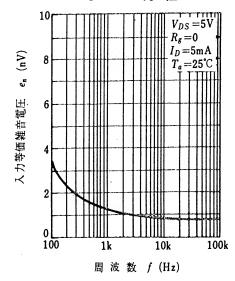
Crss - VDS 特性



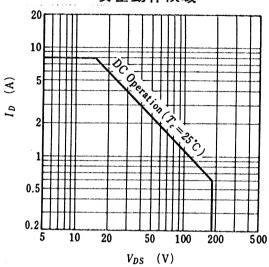
ID - VGs 特性



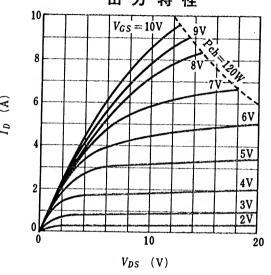
en - f 特 性



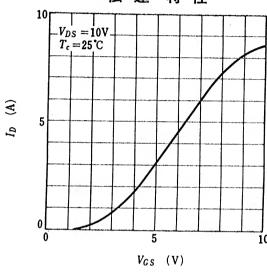




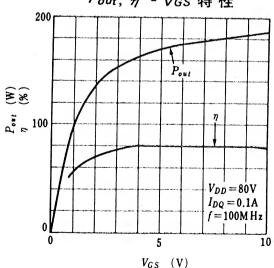
### 出力特性



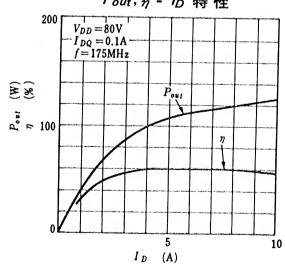
伝 達 特性



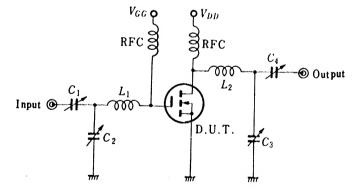
# Pout, n - VGS 特性



# Pout, n - 10 特性



### 電力測定回路



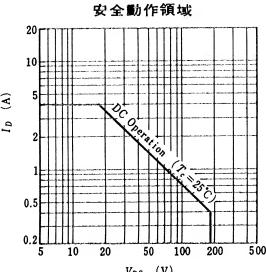
 $C_1 = 22pF$ ,  $C_2 = 33pF$ ,  $C_3 = 10pF$ ,  $C_4 = 22pF$  $L_1$ ,  $L_2$ ; ID=6mm, d=1mm

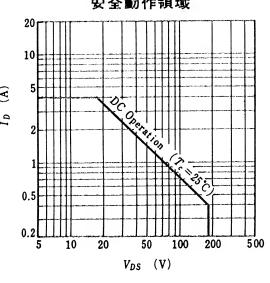
f = 100 MHz;  $L_1 = 3\text{T}$ ,  $L_2 = 6\text{T}$ 

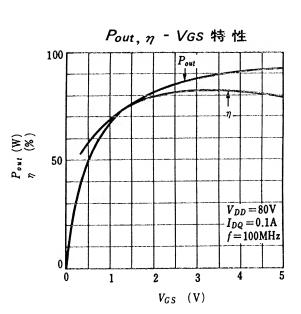
f = 175 MHz;  $L_1 = 1 \text{T}$ ,  $L_2 = 3 \text{T}$ 

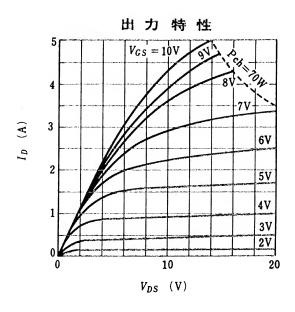


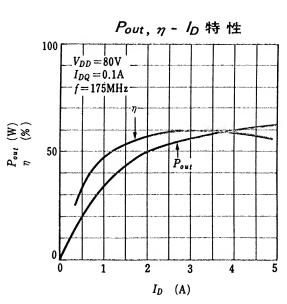
電力測定回路

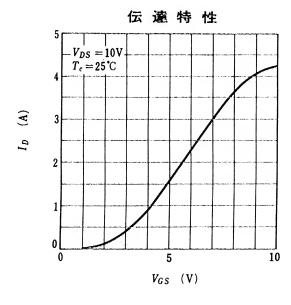


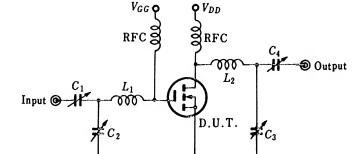


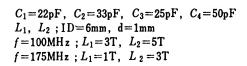


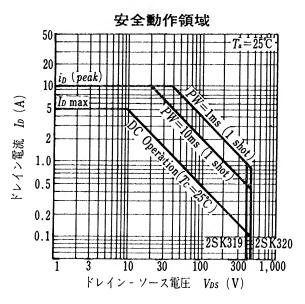


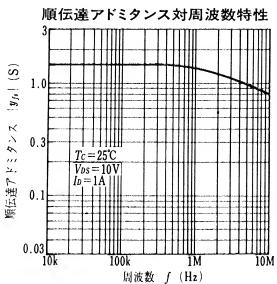


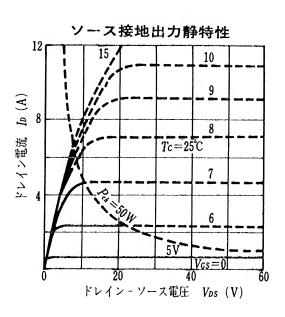


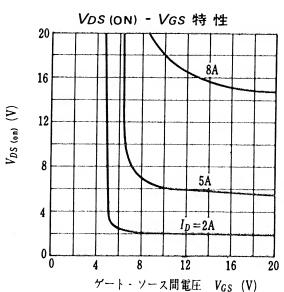


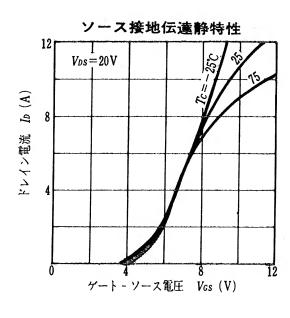


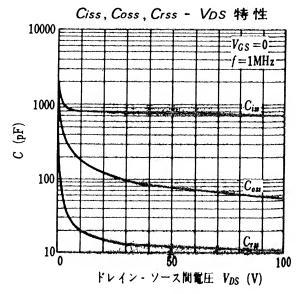








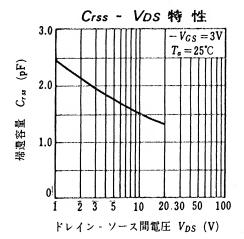


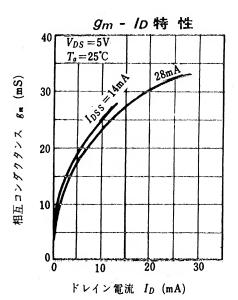


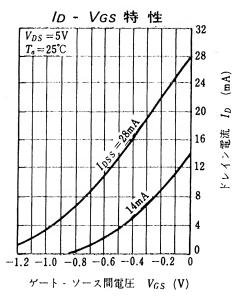
下

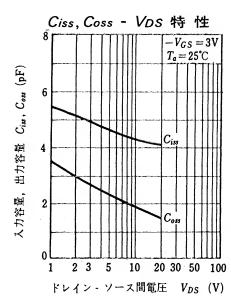
IDSS ランク分類

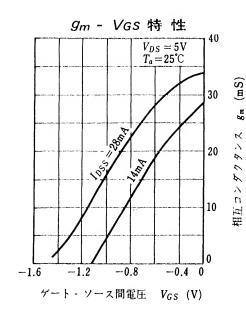
	P	Q	R	S
$I_{DSS}$ (mA)	5~16	14~24	20~32	28~42

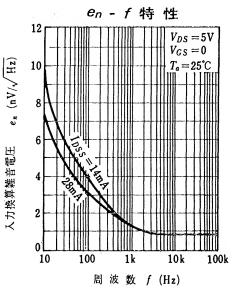










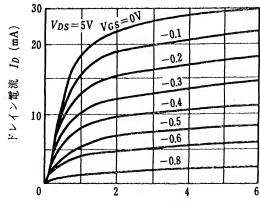


# Si 接合型 Nチャンネル

#### IDSS ランク分類

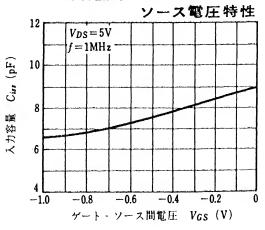
Grade	P	Q	R	S	Т
Mark	WP	WQ	WR	WS	WT
IDSS	5~16	14~24	20~32	28~42	36~50

### ソース接地出力静特性

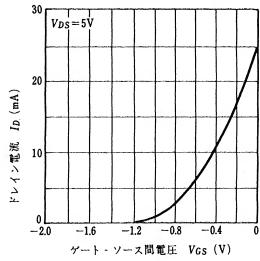


ドレイン・ソース間電圧 VDS (V)

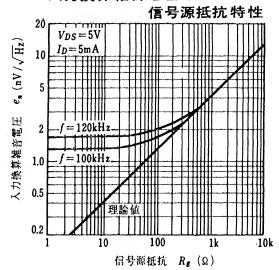
### 入力容量対ゲート -



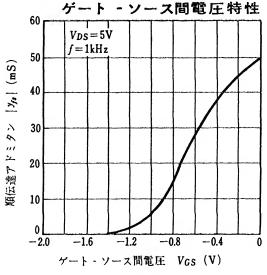
# ソース接地伝達静特性



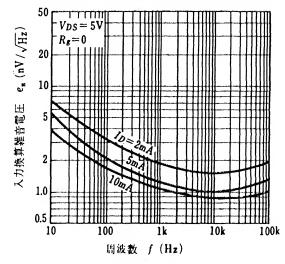
入力換算雑音電圧対



# 順伝達アドミタンス対



### 入力換算雑音電圧対周波数特性





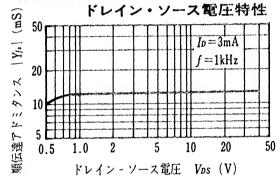
# Si 接合型 Nチャンネル

日 立

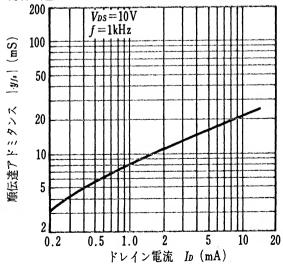
IDSS	X	分	
------	---	---	--

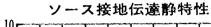
-	Grade	В	С	D	Е
	Mark	КВ	КC	K D	KE
	IDSS	1.6~3.2	2.5~5	4~8	6~12

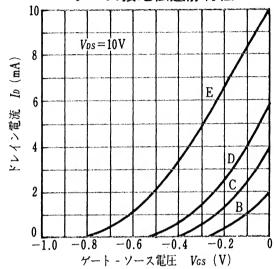
### 順伝達アドミタンス対



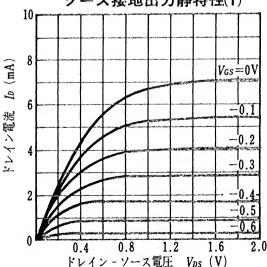
# 順伝達アドミタンス対ドレイン電流特性



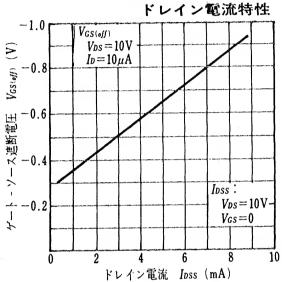




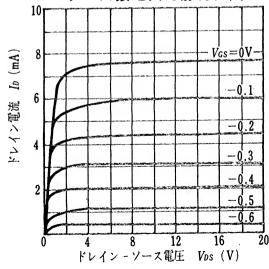
# ソース接地出力静特性(1)



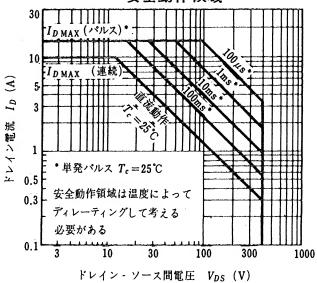
# ゲート・ソース遮断電圧対



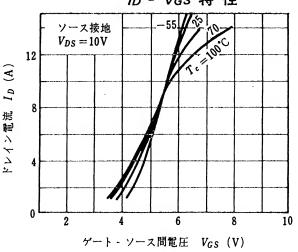
### ソース接地出力静特性(2)



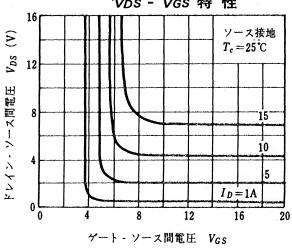


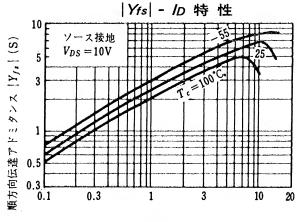


ID - VGS 特性

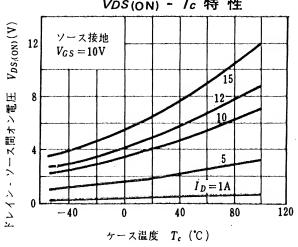


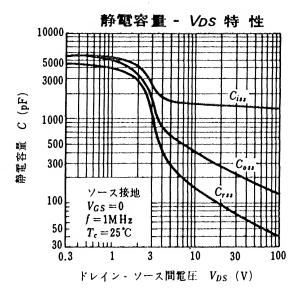
Vos - Vos 特性





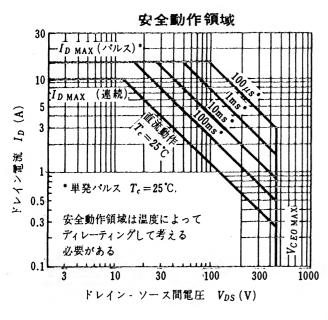
VDS(ON) - Tc 特性

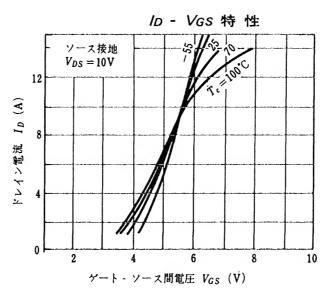


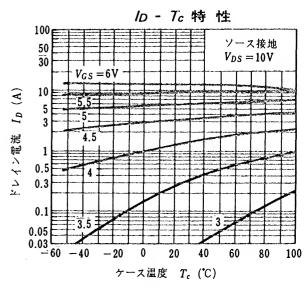


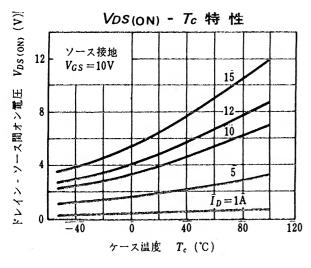
ドレイン電流 I<sub>D</sub>(A)

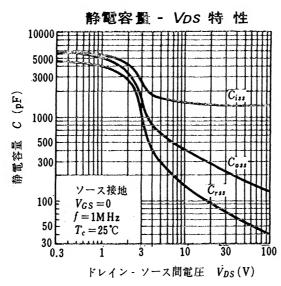
Si MOS型 N チャンネル 東 芝

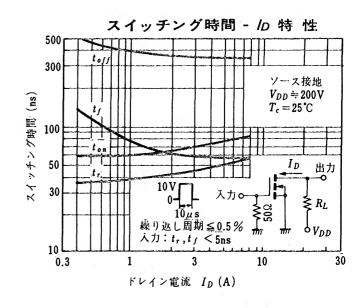






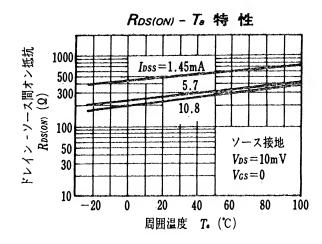


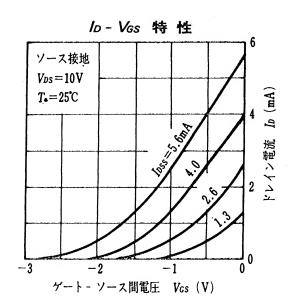


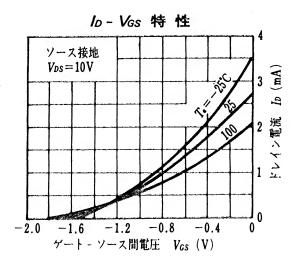


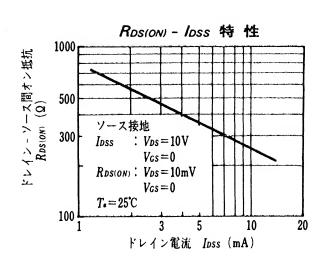
# Si 接合型 Nチャンネル

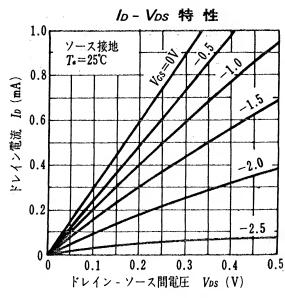
IDSS分類 Y:1.2~3.0mA, GR:2.6~6.5mA, BL:6~14mA

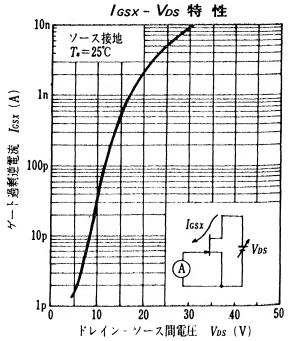










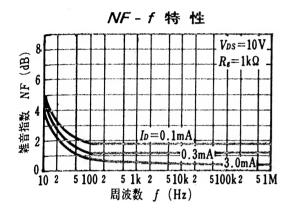


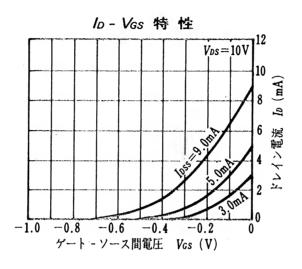
# Si 接合型 複合Nチャンネル

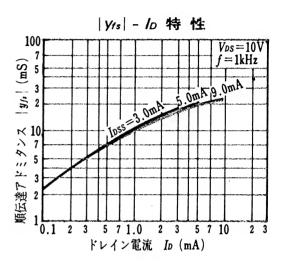
三洋

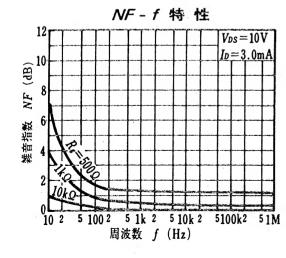
Inssにより次のように分類している.(単位 mA)

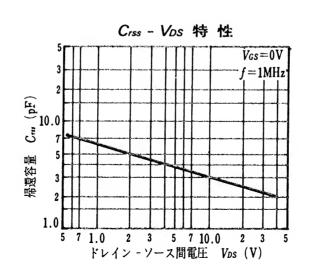
1.2 D 3.0 2.5 E 6.0 5.0 F 12.0

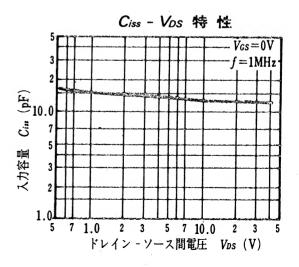






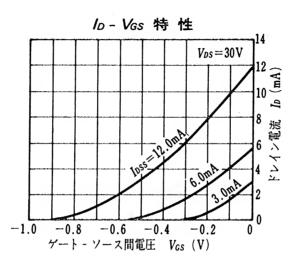


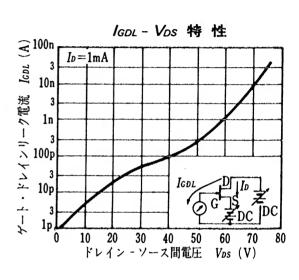


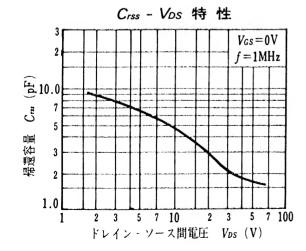


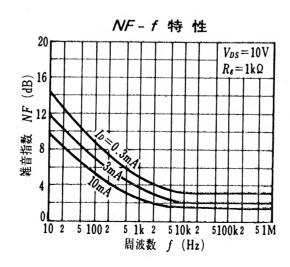
IDSSにより次のように分類している。(単位 mA)

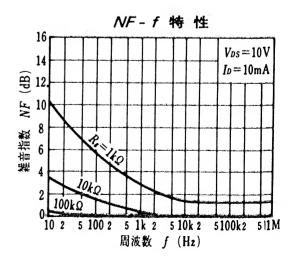
				-				
1.2	D	3.0	2.5	E	6.0	5.0	F	12.0

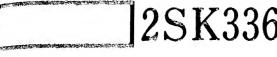


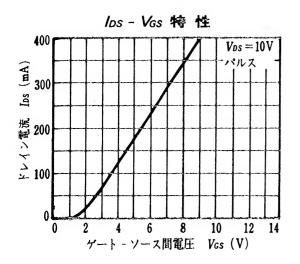


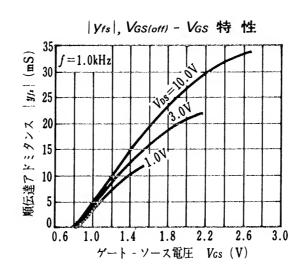


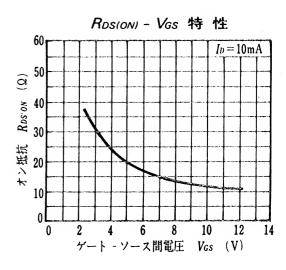


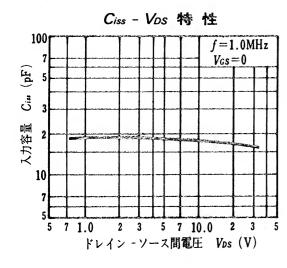


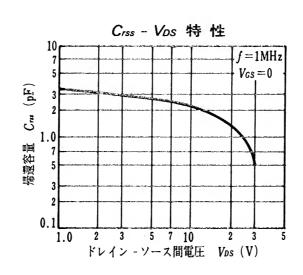


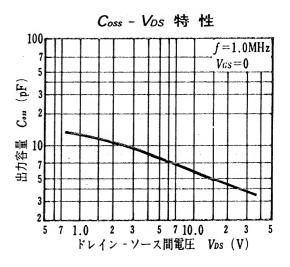


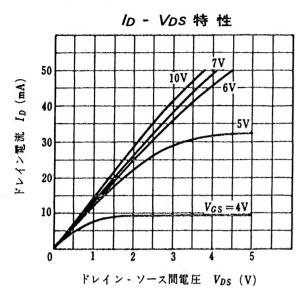


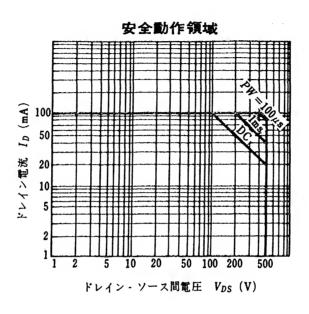


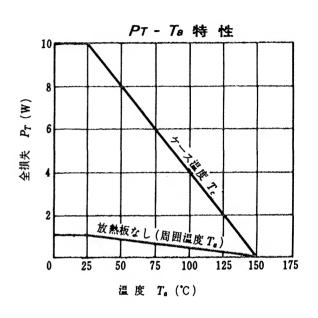


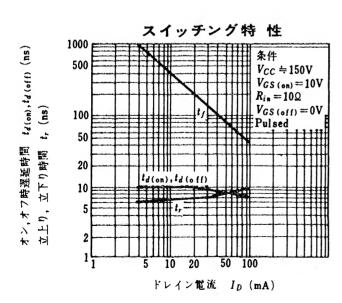


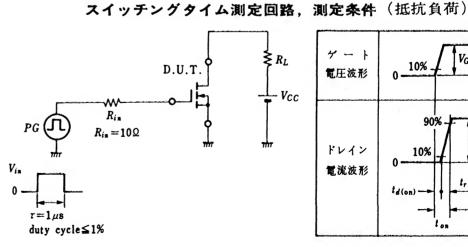


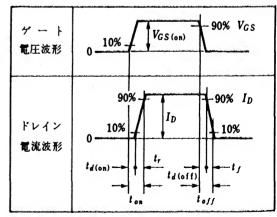








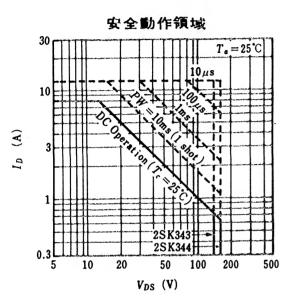


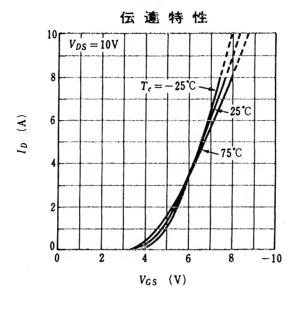


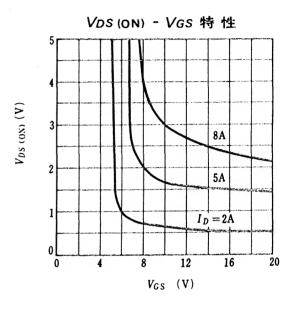
2SK343,344

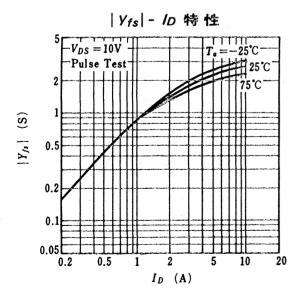
# Si MOS型 Nチャンネル

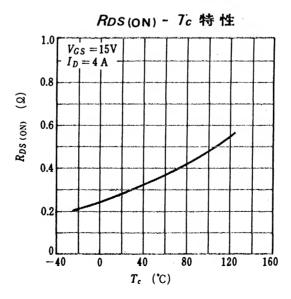
日立

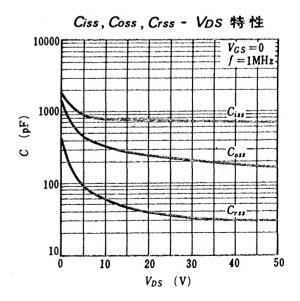


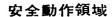


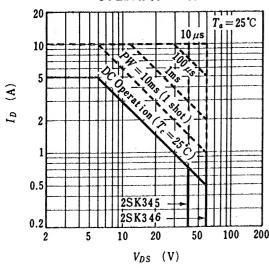




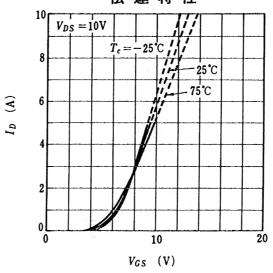




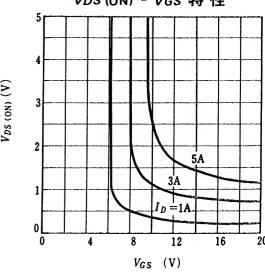




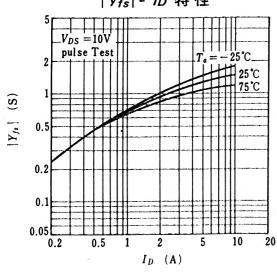
伝達特性



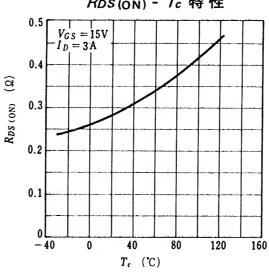
Vos (ON) - Vgs 特性



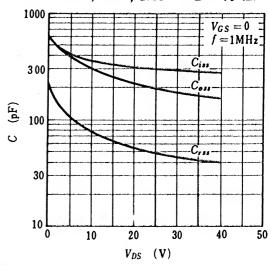
| Yfs | - ID 特性



RDS(ON) - Tc 特性

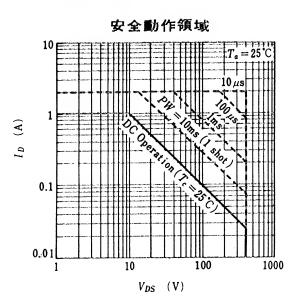


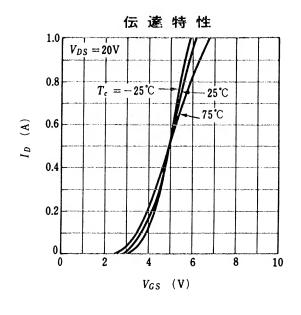
Ciss, Coss, Crss - VDS 特性

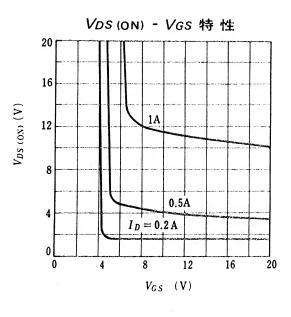


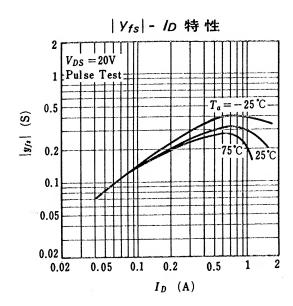
# Si MOS型 Nチャンネル

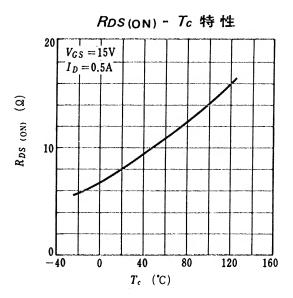
日 立

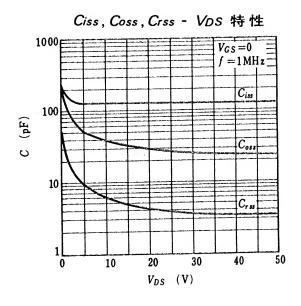






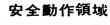


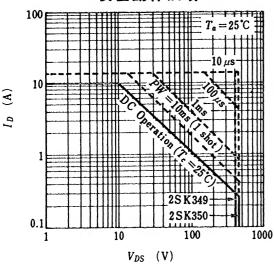




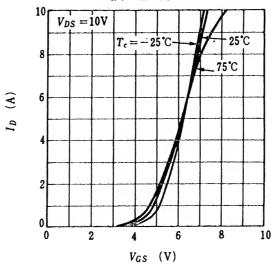
2SK349,350

Si MOS型 日 立 Nチャンネル

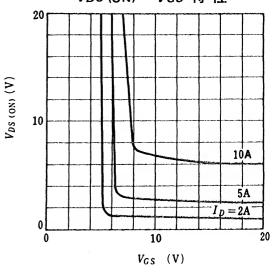




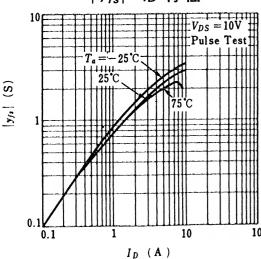




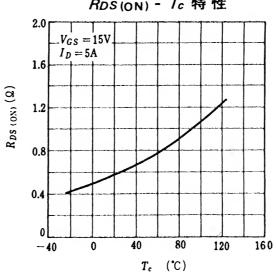
VDS (ON) - VGS 特性



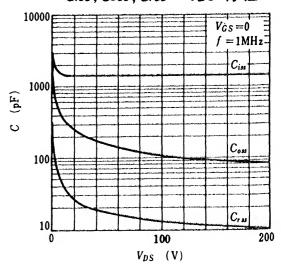
# |Yfs| - ID 特性



RDS(ON) - Tc 特性



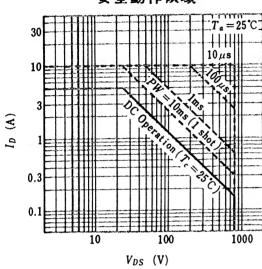
Ciss, Coss, Crss - VDS 特性



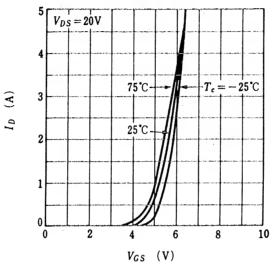
# Si MOS 型 Nチャンネル

日立

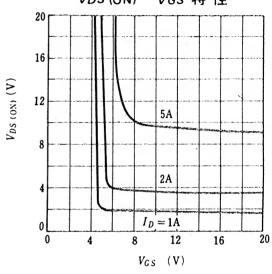




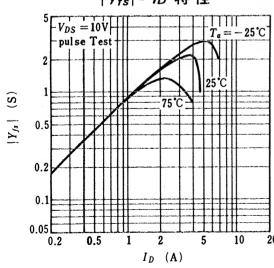




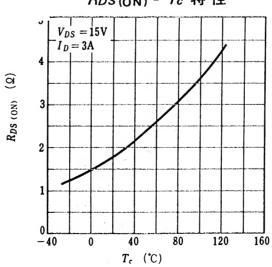




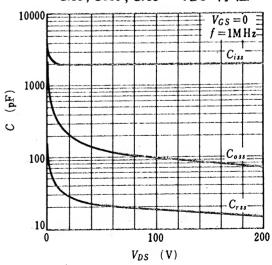
# | Yfs | - ID 特性



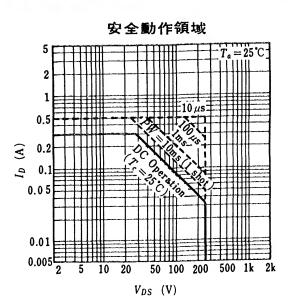
RDS(ON) - Tc 特性

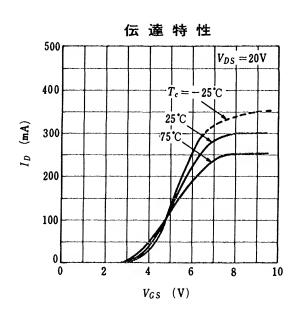


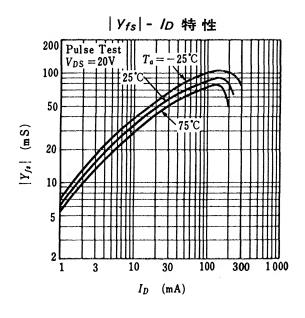
Ciss, Coss, Crss - VDS 特性

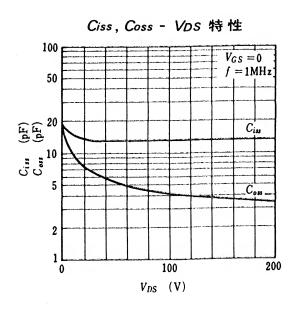


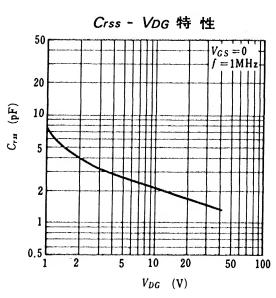
Si MOS型 日立 Nチャンネル

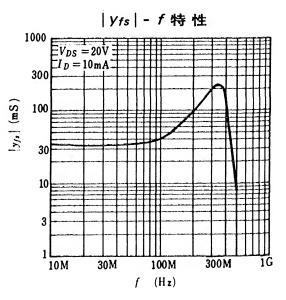






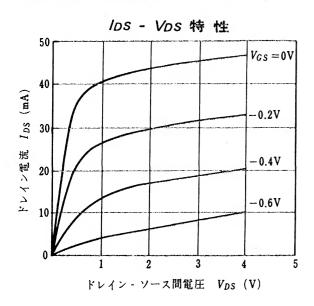


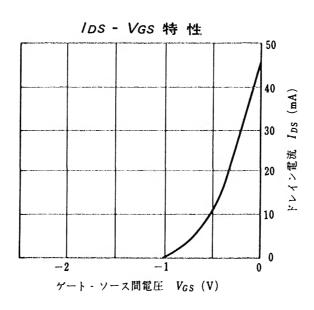


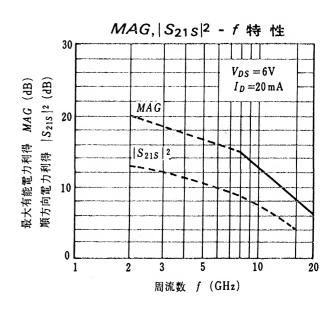


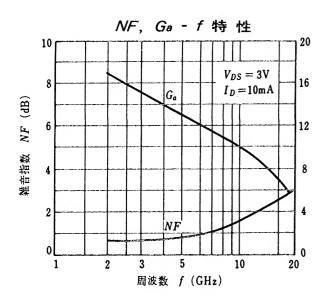


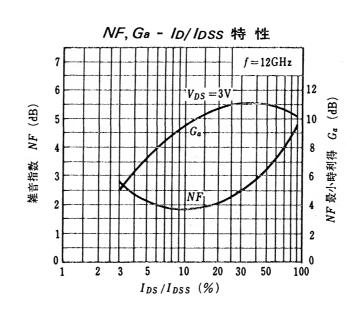


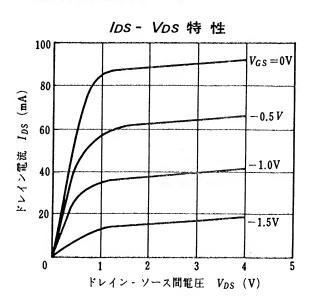


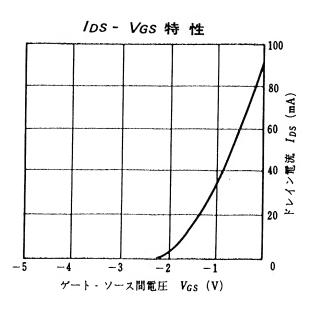


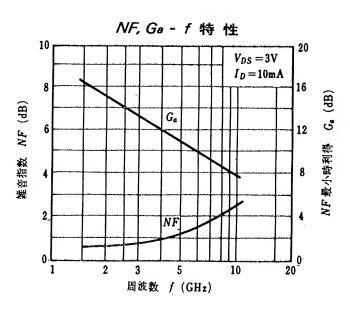


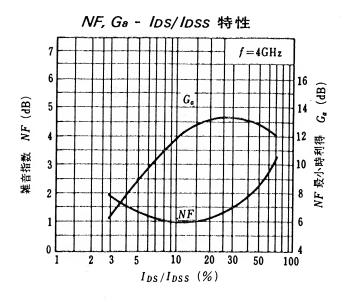


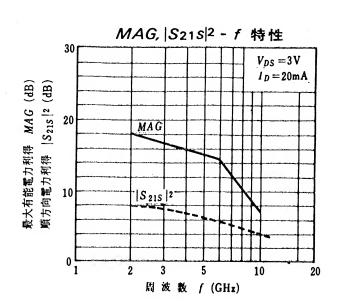








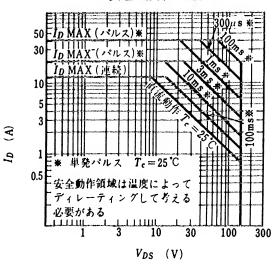




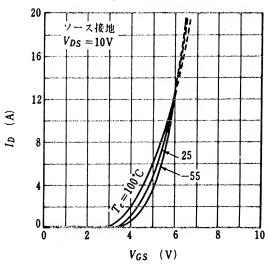
# Si MOS型 Pチャンネル

東芝

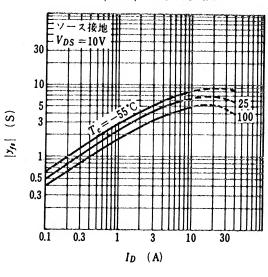
安全動作領域



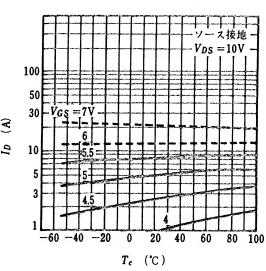
1p - VGS 特性



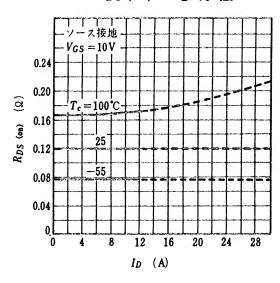
|Yfs| - 10 特性



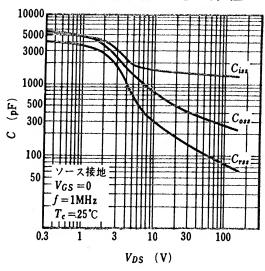
10 - Tc 特性



RDS (on) - ID 特性

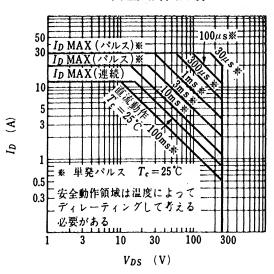


静電容量 - Vos 特性

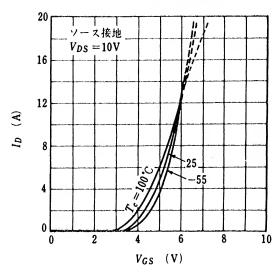


Si MOS型 Nチャンネル 東 芝

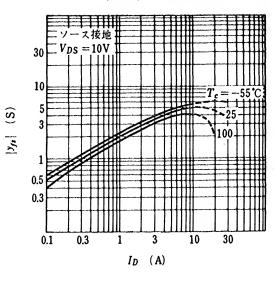
### 安全動作領域



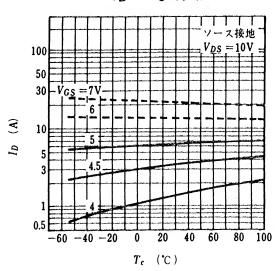
/D - VGS 特性



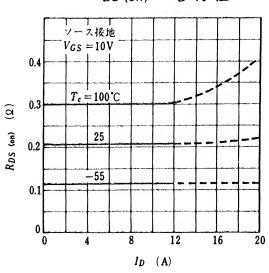
|Yfs| - ID 特性



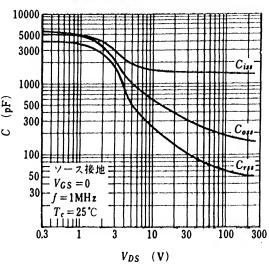
1D - Tc 特性



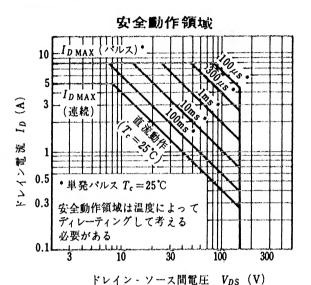
RDS (on) - ID 特性

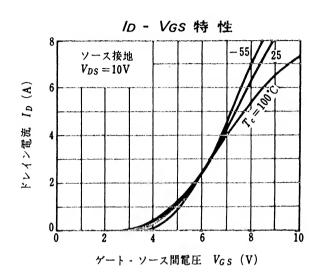


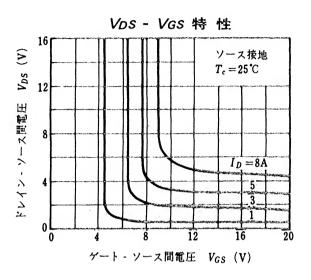
静電容量 - Vos 特性

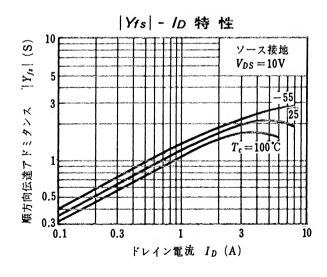


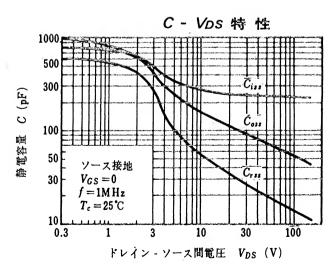
Si MOS型 \_ Nチャンネル 東 芝

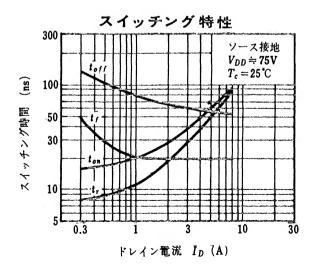




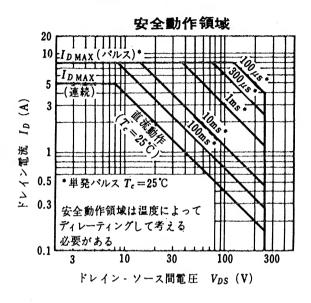


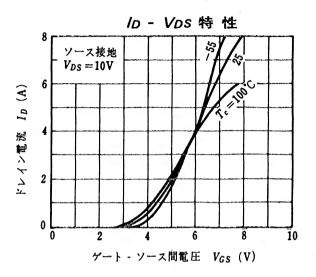


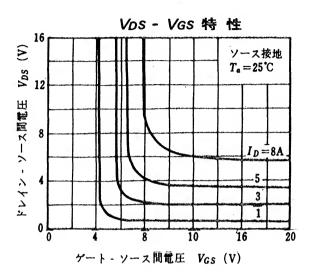


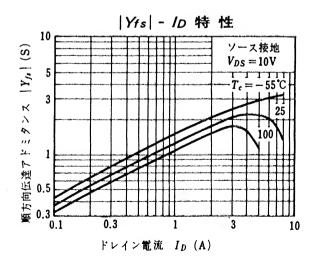


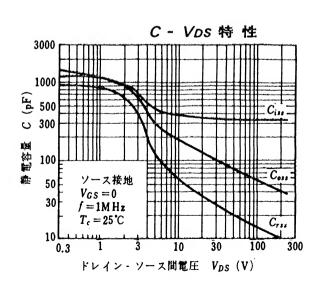


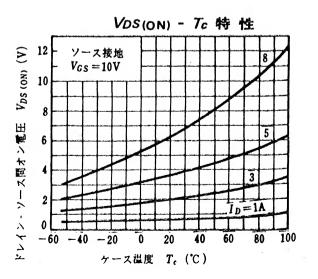












2SK359,360,439

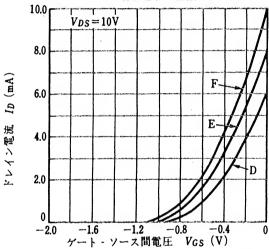
# Si MOS型 Nチャンネル

日 立

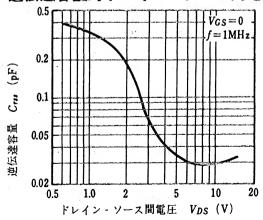
### 2SC360/439 IDSS 分類

	D	E	F
IDSS (mA)	4~8	6~10	8~12

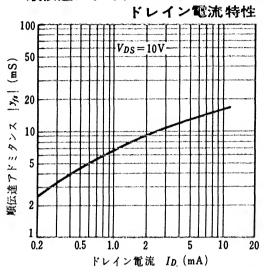
### ソース接地伝達静特性



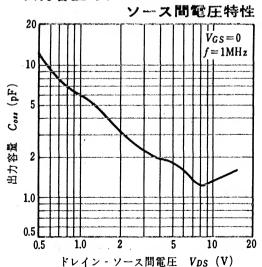
# 逆伝適容置対ドレイン・ソース間電圧特性



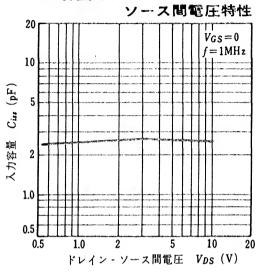
### 順伝達アドミタンス対



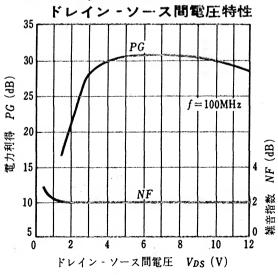
### 出力容量対ドレイン-



### 入力容量対ドレイン -

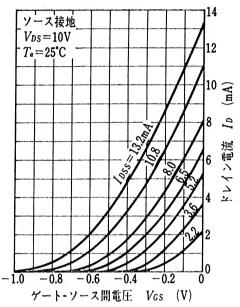


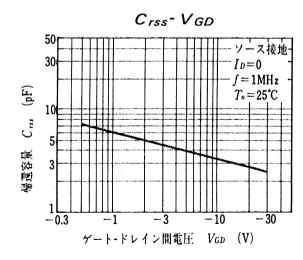
### 電力利得, 雑音指数对



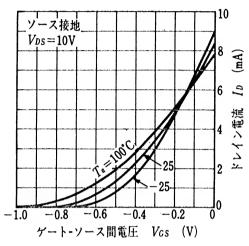
IDSS分類 Y:1.2~3.0, GR:2.6~6.5, BL:6~14



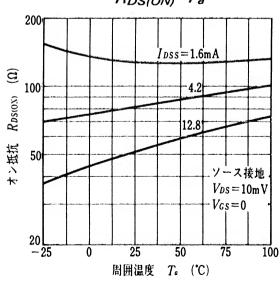




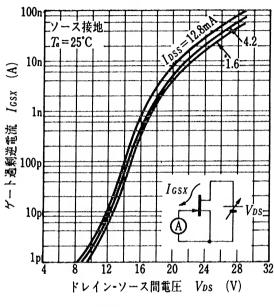
# /D-V<sub>GS</sub>(温度依存性/



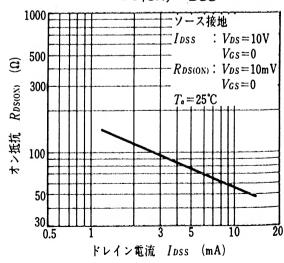
RDS(ON)- Ta



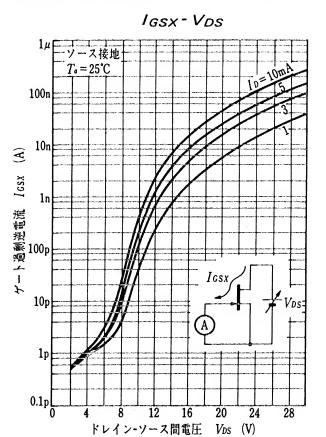
### IGSX-VDS



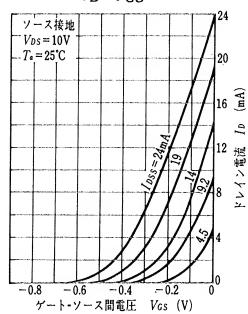
# R'DS(ON)-1DSS



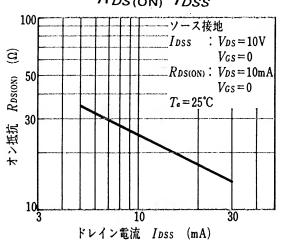
IDSS分類 GR: 5.0~10.0, BL: 8.0~16.0, V: 14.0~30.0



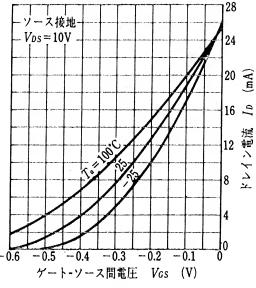
1D-VGS



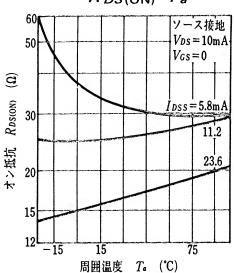
RDS(ON)-1DSS



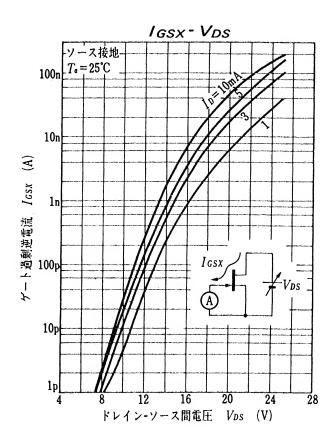
10-VGS (温度依存性)

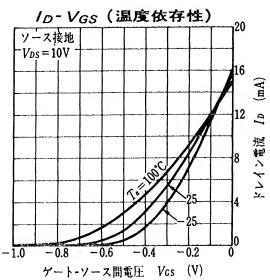


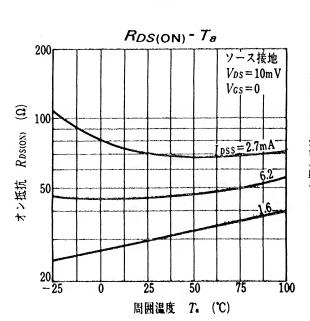
RDS(ON)-Ta

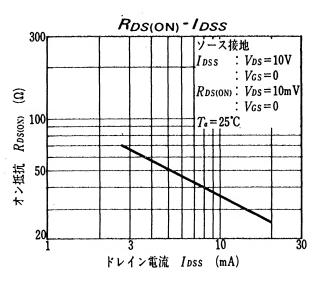


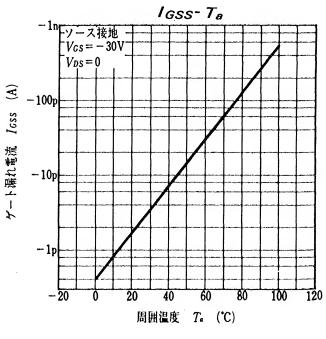
IDSS分類 GR: 2.6~6.5, BL: 6~12, V:10~20



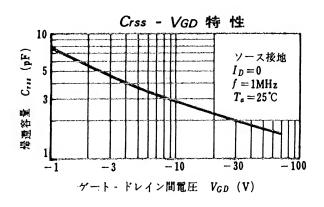


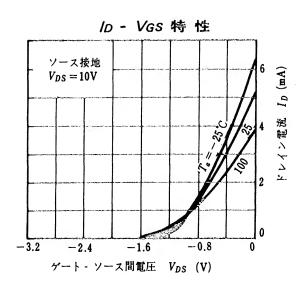


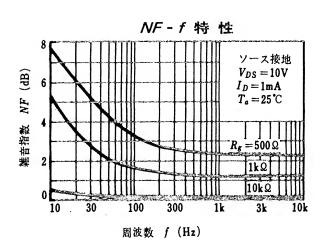


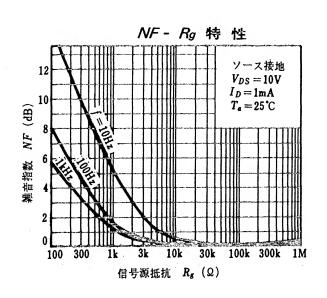


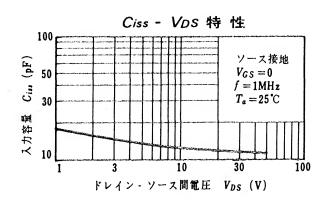
IDSS 分類 O: 0.6~1.4, Y: 1.2~3.0, GR: 2.6~6.5 (mA)

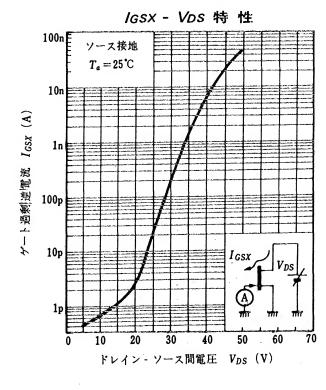












IDSS 分類 O:0.6~1.4mA, Y:1.2~3.0mA, GR:2.6~6.5mA

Ciss - VDS 特性

ソース接地

VGS = 0

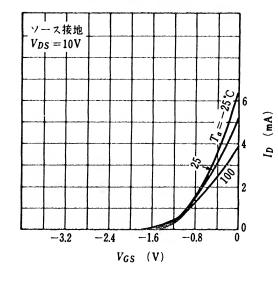
「= 1MHz

Ta = 25°C

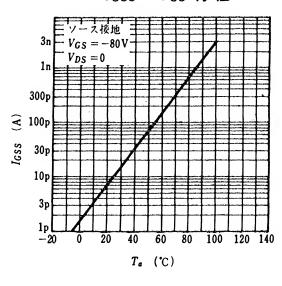
30

VDS (V)

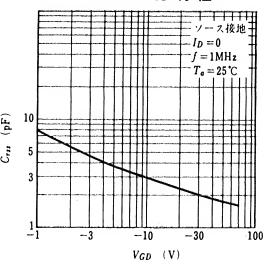
1<sub>D</sub> - V<sub>GS</sub> 特性



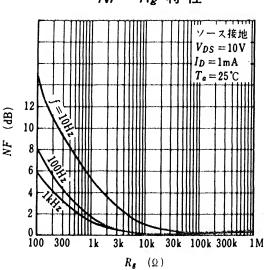
Igss - Vgs 特性



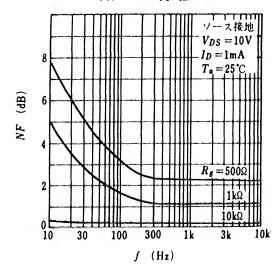
Crss - VGD 特性



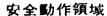
NF - Rg 特性

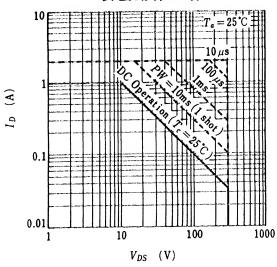


NF - f 特性

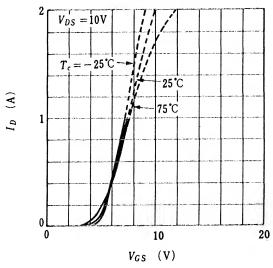


Si MOS型 Nチャンネル E 立

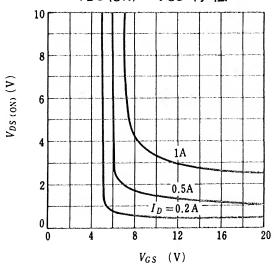




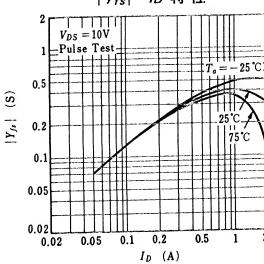




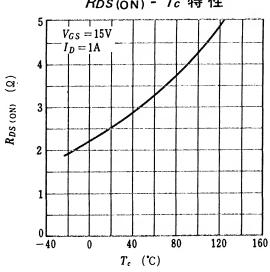
VDS (ON) - VGS 特性



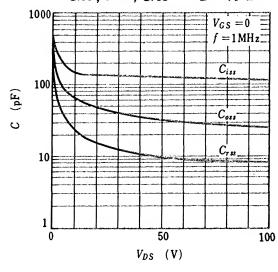
### | Yfs | - ID 特性



#### RDS(ON) - Tc 特性



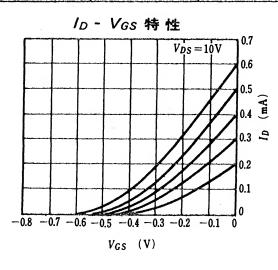
#### Ciss, Coss, Crss - VDS 特性

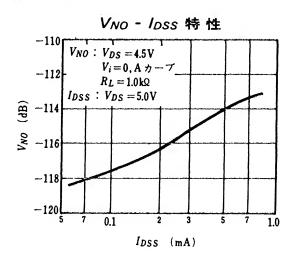


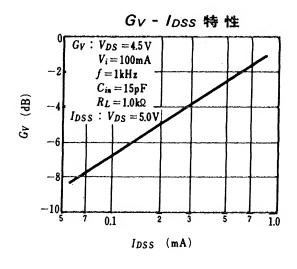
Si 接合型 N チャンネル 三 洋

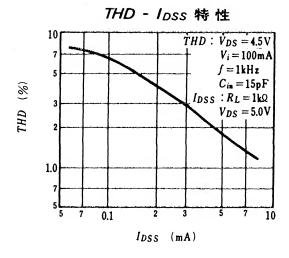
IDSS により次のように分類する(単位:µA)

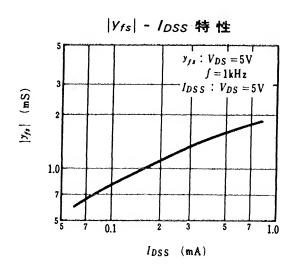
		60	J	180				250					800
--	--	----	---	-----	--	--	--	-----	--	--	--	--	-----

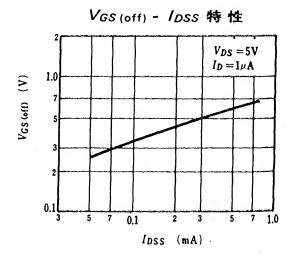




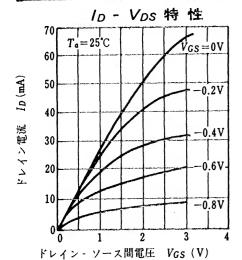






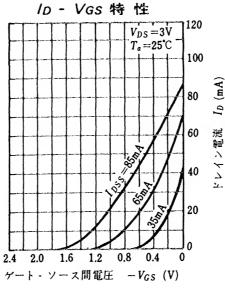


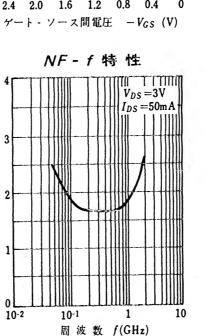
# $I_{DSS}$ ランク分類 P Q R $I_{DSS}$ (mA) $15\sim50$ 40 $\sim80$ 70 $\sim$ 130



## GaAs 型 Nテャンネル



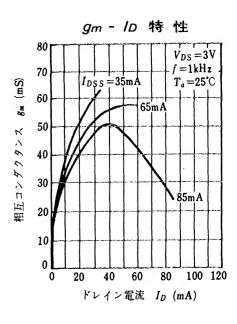


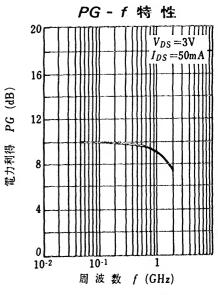


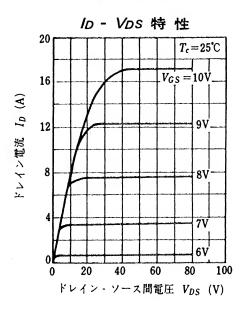
(dB)

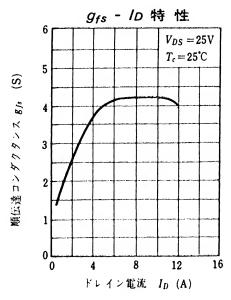
NF

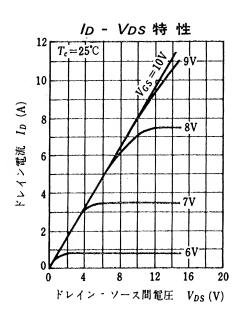
維音指数

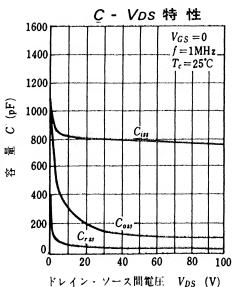


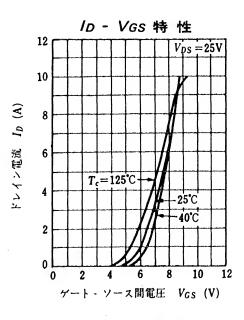


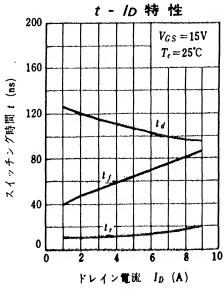






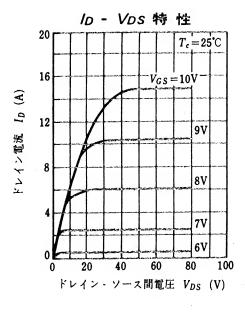


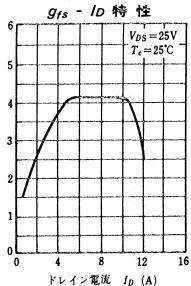




## Si MOS型 Nチャンネル

松下





 $\widehat{\mathbf{s}}$ 

813

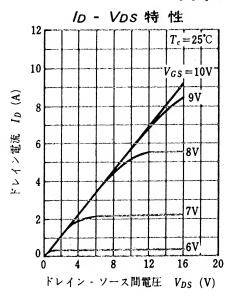
K

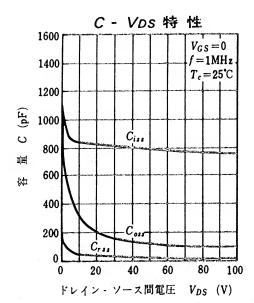
 $\lambda$ 

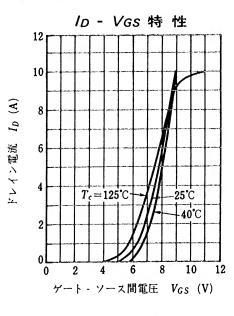
\*

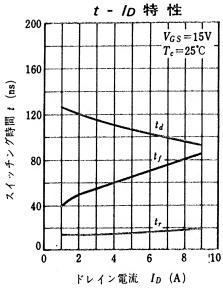
47

順伝達コン





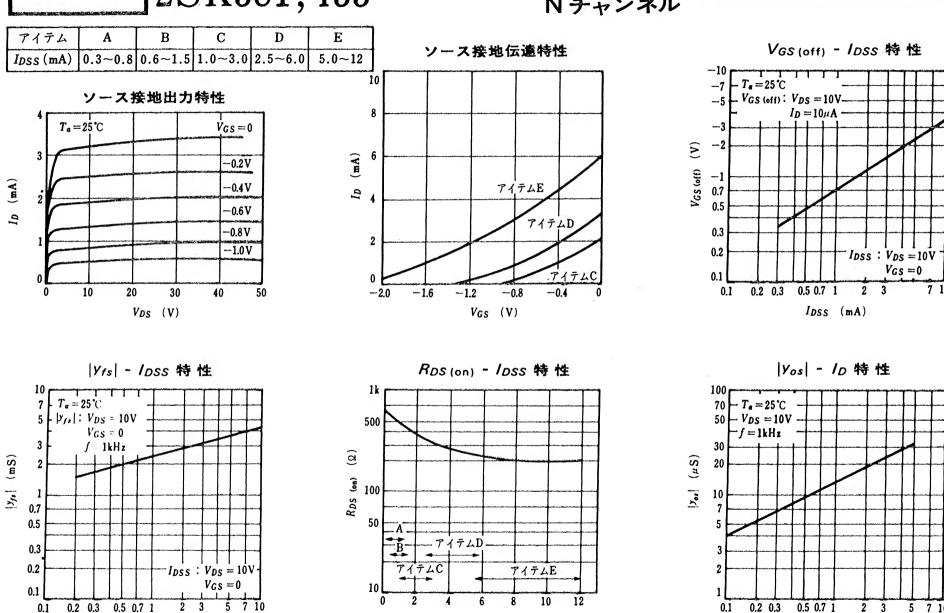




 $I_D$  (mA)

IDSS (mA)

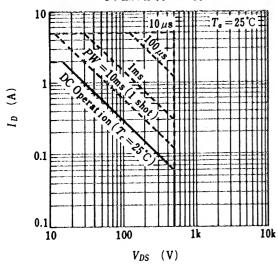
## Si 接合型 N チャンネル



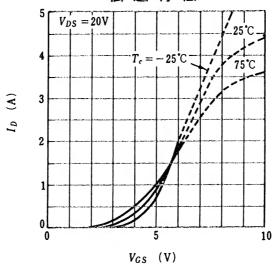
IDSS (mA)

Si MOS型 Nチャンネル 日 立

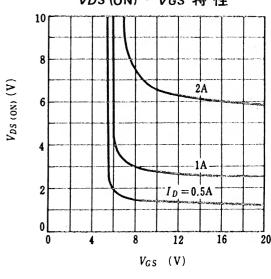




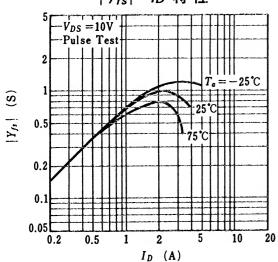
#### 伝道特性



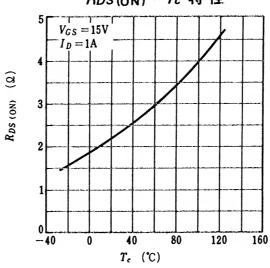
Vos (ON) - Vgs 特性



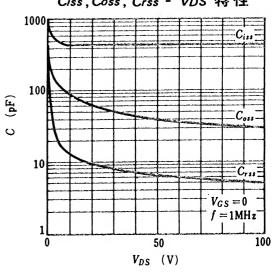
#### | Yfs | - ID 特性



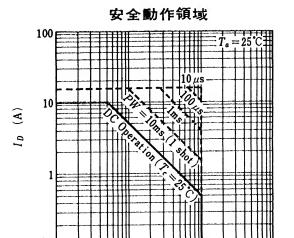
#### RDS(ON) - Tc 特性



#### Ciss, Coss, Crss - VDS 特性



Si MOS型 日立 Nチャンネル

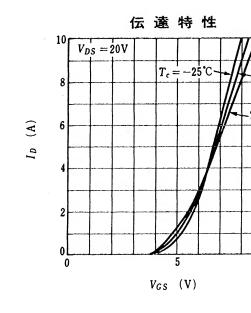


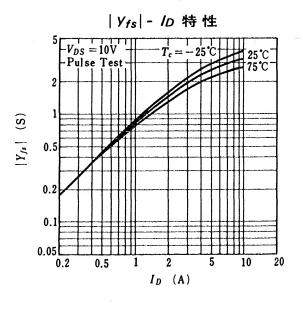
10

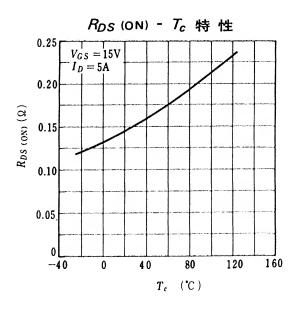
 $V_{DS}$  (V)

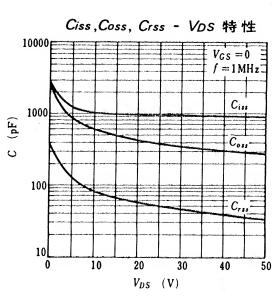
100

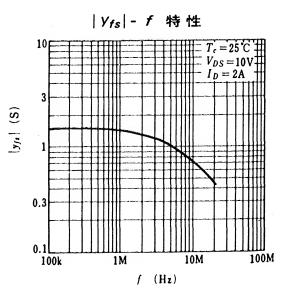
1000





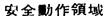


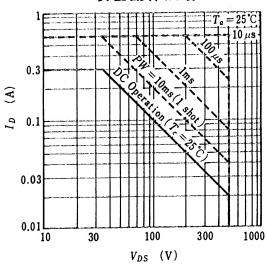




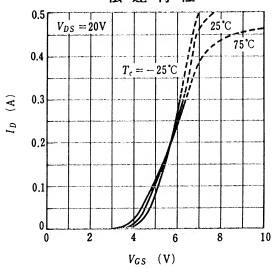
## Si MOS型 Nチャンネル

日立

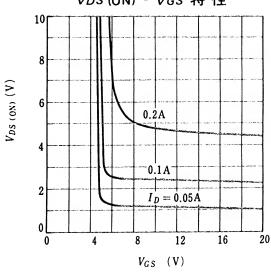




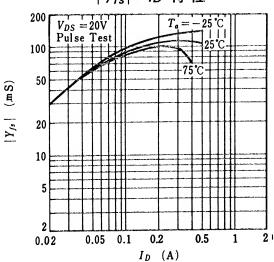
伝 遠 特 性



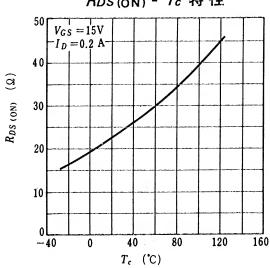
Vos (on) - Vgs 特性



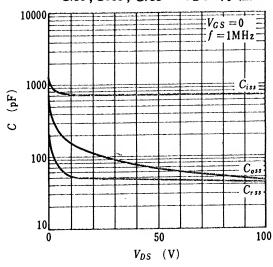
| Yfs | - ID 特性



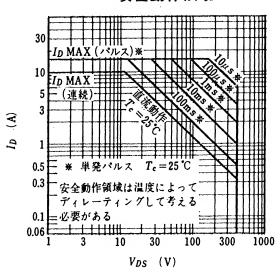
RDS(ON) - Tc 特性



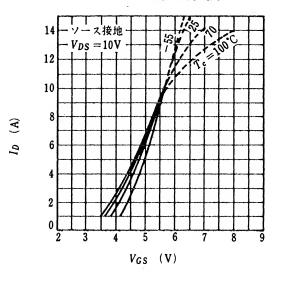
Ciss, Coss, Crss - VDS 特性



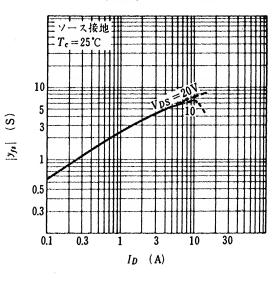
Si MOS型 Nチャンネル 東芝



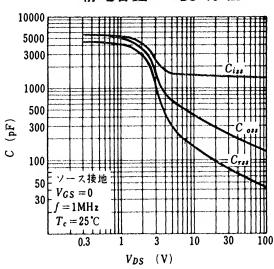
/p - VGS 特性



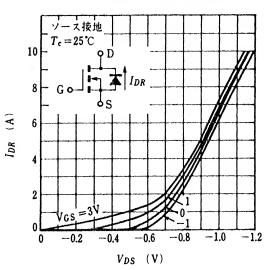
|Yfs| - ID 特性



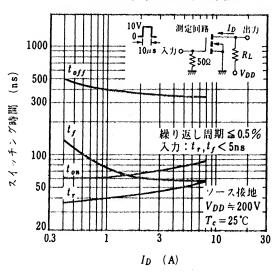
静電容量 - Vos 特性



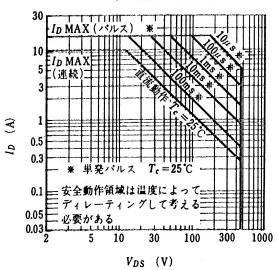
IDR - VDS 特性



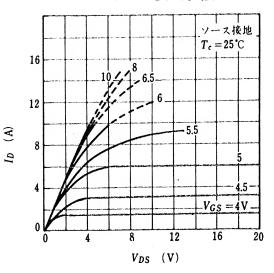
スイッチング特性



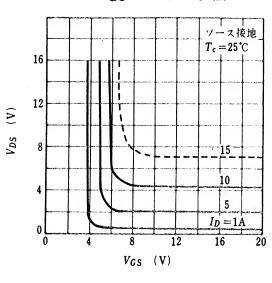
Si MOS型 Nチャンネル 東 芝



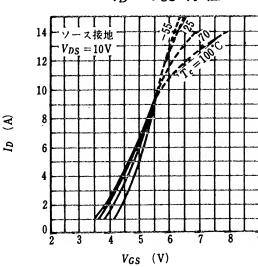
1p - Vps 特性



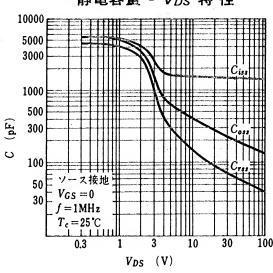
VDS - VGS 特性



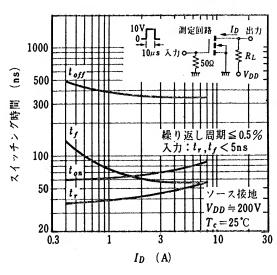
In - Vgs 特性



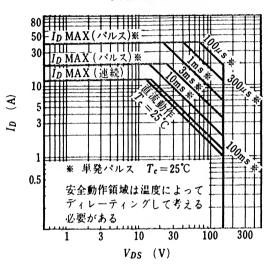
静電容量 - Vos 特性



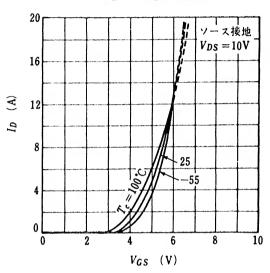
スイッチング特性



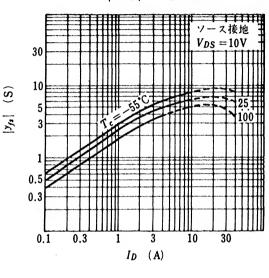
Si MOS型 Nチャンネル 東 芝



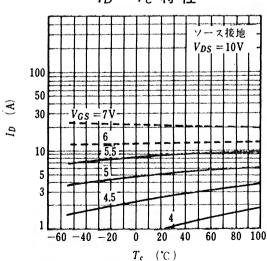
Ip - VGS 特性



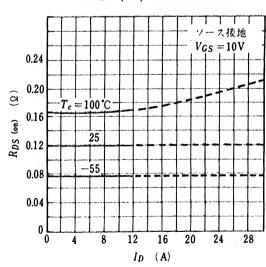
|Yfs| - ID 特性



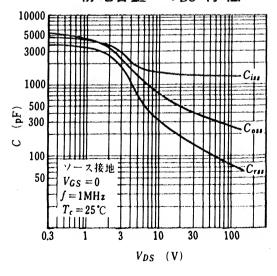
/<sub>D</sub> - T<sub>C</sub> 特性



RDS (on) - ID 特性



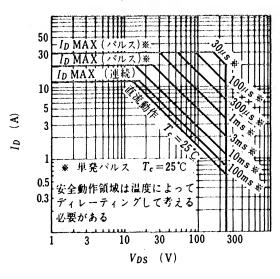
静電容量 - Vos 特性



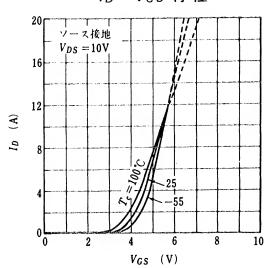
## Si MOS型 \_ Nチャンネル

東 芝

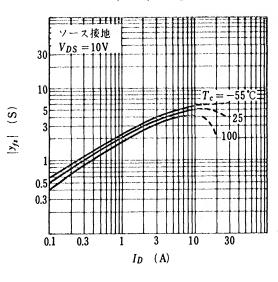
安全動作領域



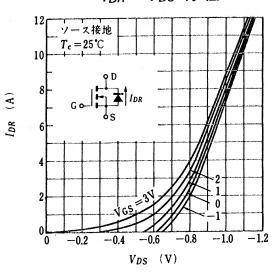
ID - VGS 特性



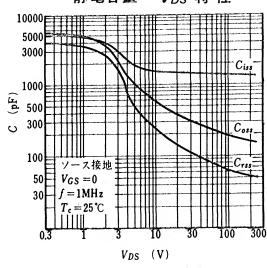
|Yfs| - ID 特性



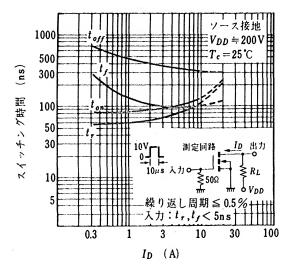
IDR - VDS 特性



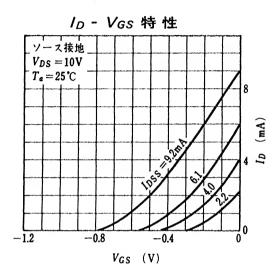
静電容量 - Vos 特性

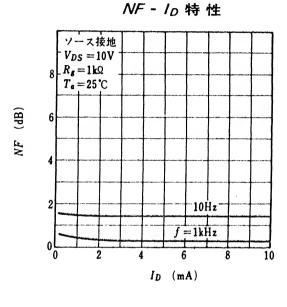


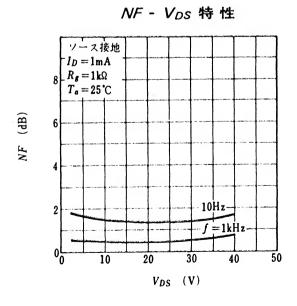
スイッチング特性

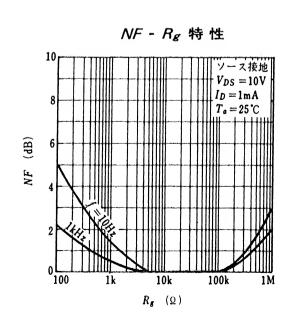


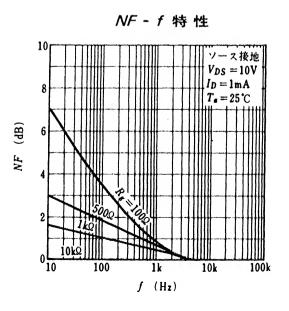
IDSS 分類: GR=2.6~6.5mA, BL=6~12mA, V=10~20mA





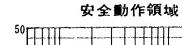


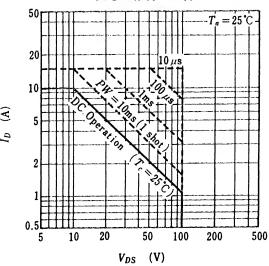




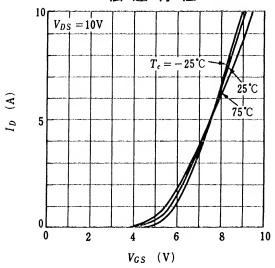
## Si MOS型 Nチャンネル

E 亚

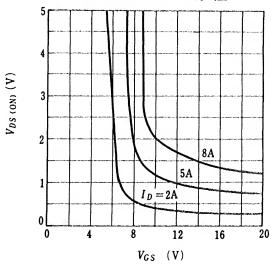




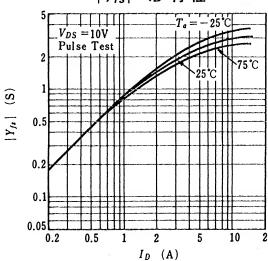
伝達特性



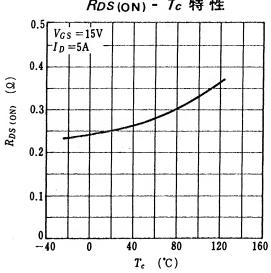
VDS (ON) - VGS 特性



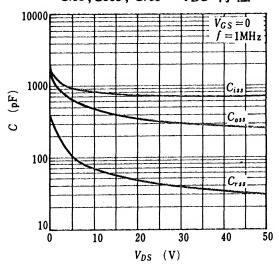
|Yfs|- ID 特性



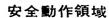
RDS(ON) - Tc 特性

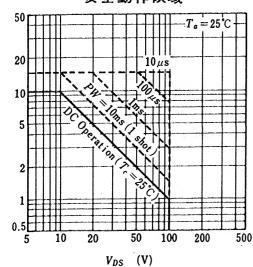


Ciss, Coss, Crss - VDS 特性

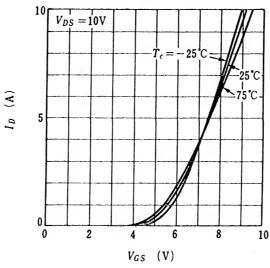


Si MOS型 Nチャンネル 日 立

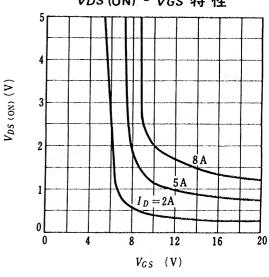




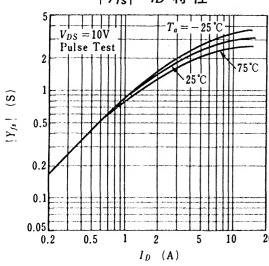
#### 伝達特性



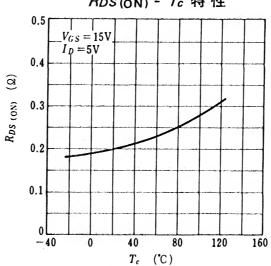
Vos (ON) - Vgs 特性



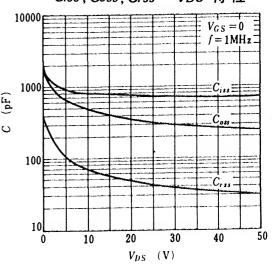
#### | Yfs | - ID 特性



RDS(ON) - Tc 特性

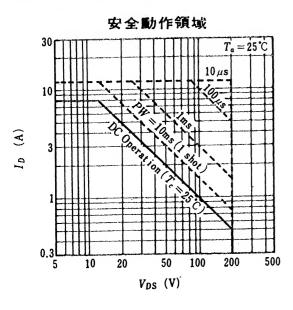


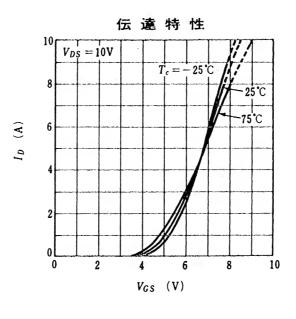
Ciss, Coss, Crss - VDS 特性

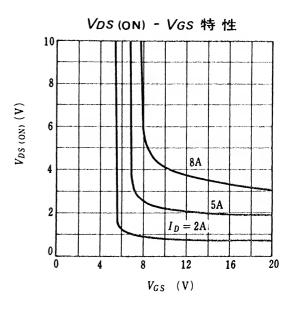


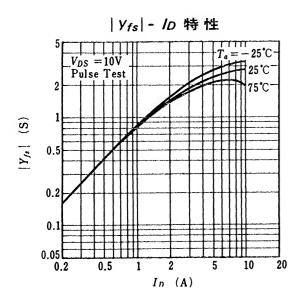
## Si MOS型 Nチャンネル

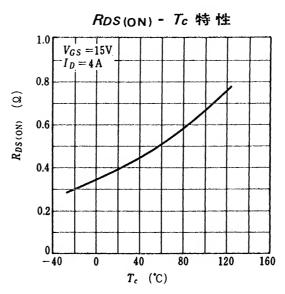
且 立

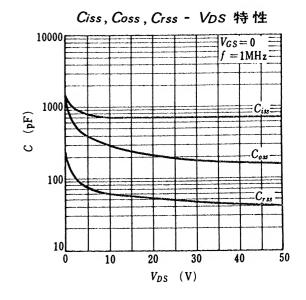




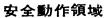


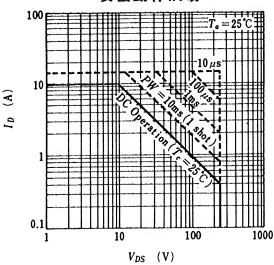




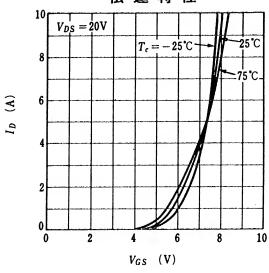


Si MOS型 Nチャンネル B 立

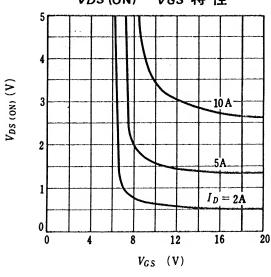




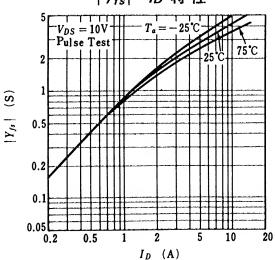




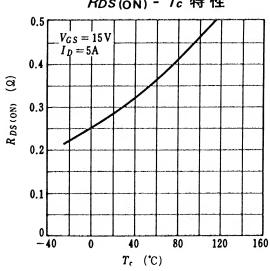
VDS (ON) - VGS 特性



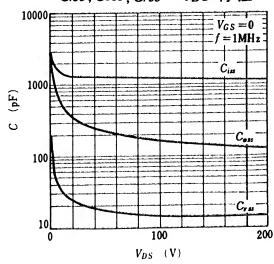
#### | Yfs | - ID 特性



RDS(ON) - Tc 特性

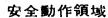


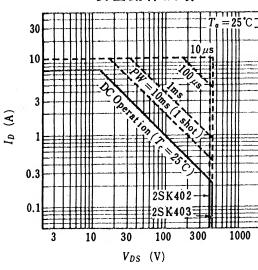
Ciss, Coss, Crss - VDS 特性



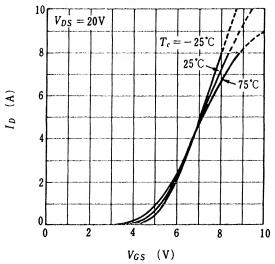
2SK402,403

Si MOS型 Nチャンネル 日 立

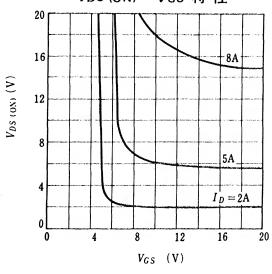




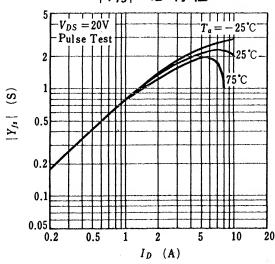
伝 遠 特 性



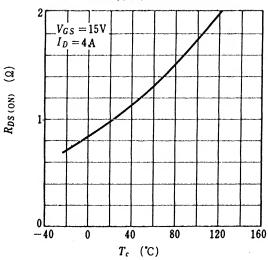
VDS (ON) - VGS 特性



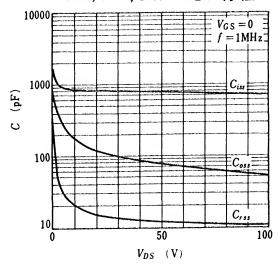
| Yfs | - ID 特性



RDS(ON) - Tc 特性

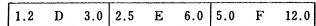


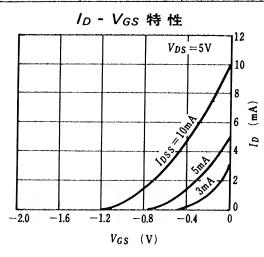
Ciss, Coss, Crss - VDS 特性

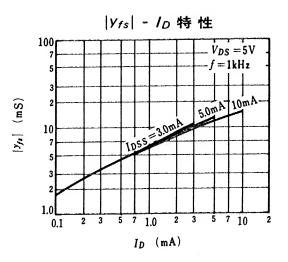


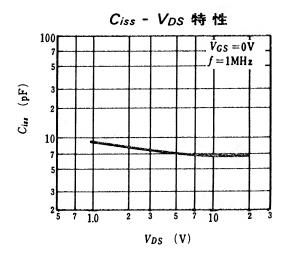
Si 接合型 N チャンネル 三 洋

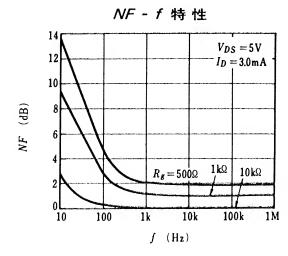
Vps=5V により次のように分類している.

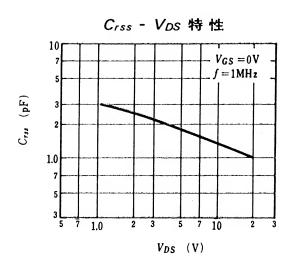


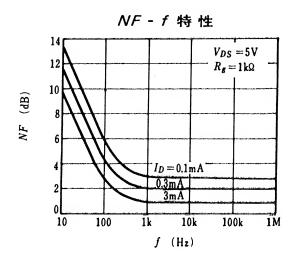








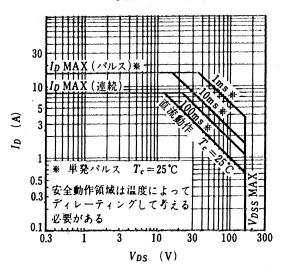




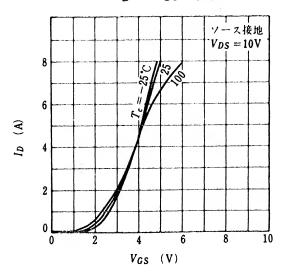
## Si MOS型 Nチャンネル

東 芝

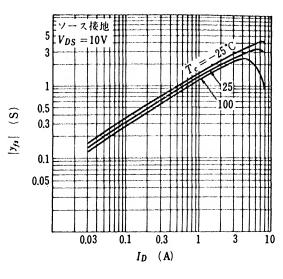
安全動作領域



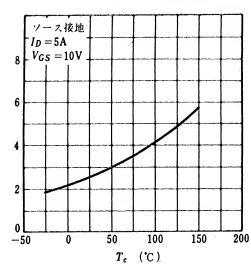
1p - VGS 特性



|Yfs| - ID 特性



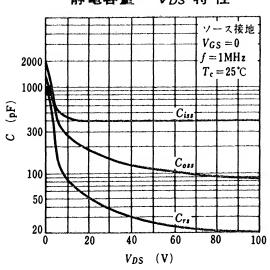
VDS (on) - Tc 特性



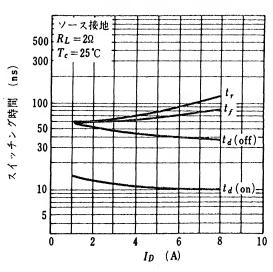
 $\widehat{\mathbf{S}}$ 

VDS (on)

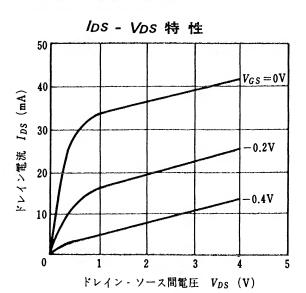
静電容量 - Vos 特性

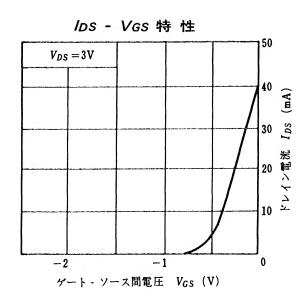


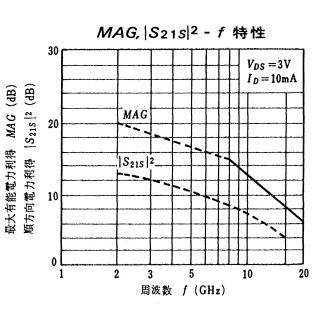
スイッチング特性

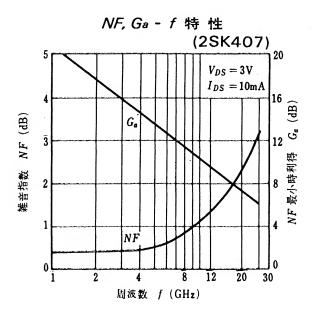


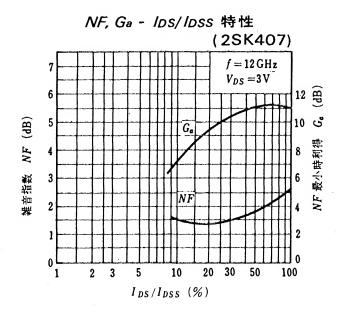
日









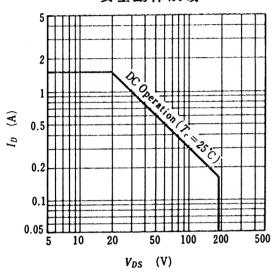


]2SK408,409

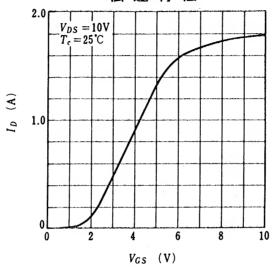
## Si MOS型 Nチャンネル

日 立

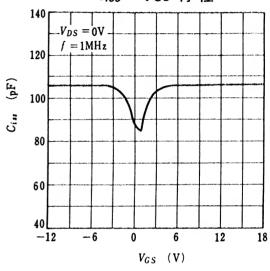
安全動作領域



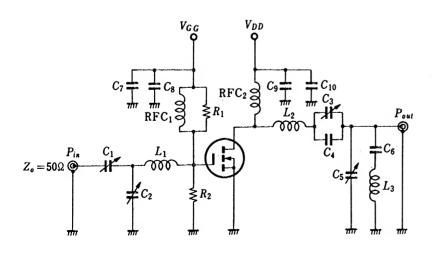
伝遵特性



Ciss - VGS 特性



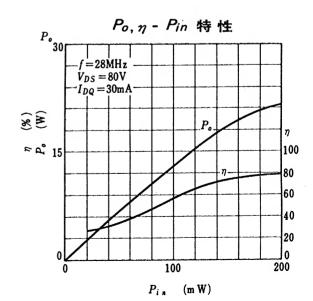
#### 28MHz 電力測定回路



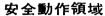
 $C_1$ ,  $C_2$ ,  $C_3 = \sim 50 \text{pF}$   $C_4 = 68 \text{pF}$   $C_5 = \sim 20 \text{pF}$   $C_6 = 1.5 \text{pF}$   $C_7$ ,  $C_9 = 0.1 \mu\text{F}$   $C_8 = 4.7 \mu\text{F}$  $C_{10} = 22 \mu\text{F}$ 

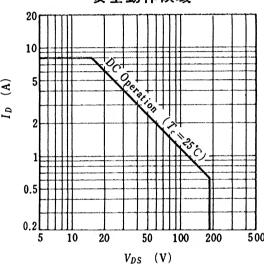
 $L_1: ID=12mm, d=1.5mm, T=6T$  $L_2: ID=12mm, d=1.5mm, T=9T$ 

 $L_3: ID=12mm, d=1.5mm, T=5T$ 

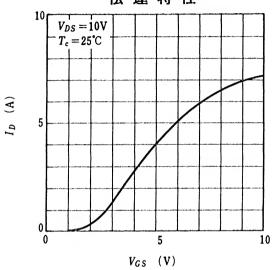


Si MOS型 Nチャンネル 日 立

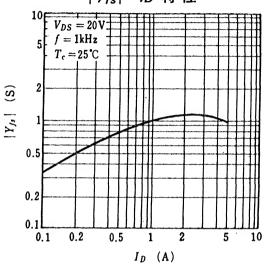




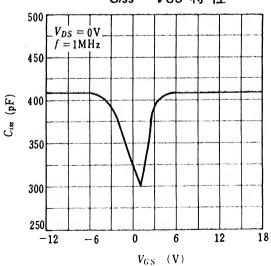
#### 伝達特性



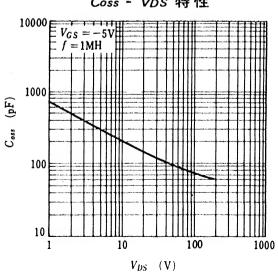
| Yfs | - ID 特性



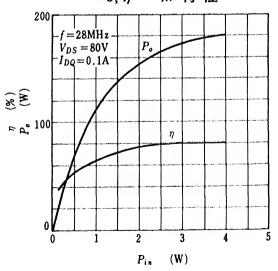
#### Ciss - VGS 特性



Coss - Vos 特性

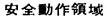


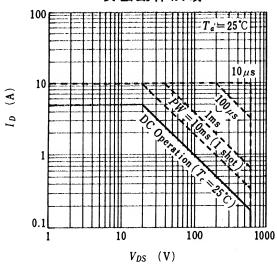
Po, η - Pin 特性



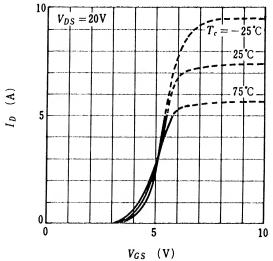
## Si MOS型 Nチャンネル

日 立

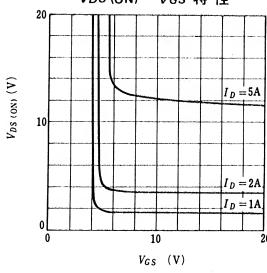




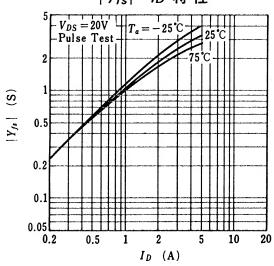




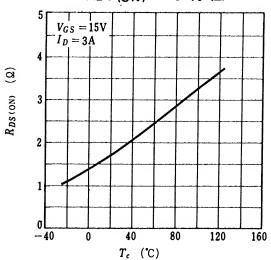
Vos (on) - Vgs 特性



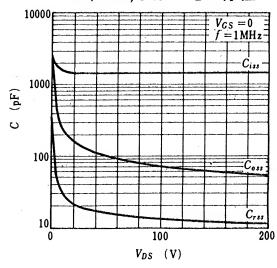
#### |Yfs| - ID 特性



Ros(ON) - Tc 特性

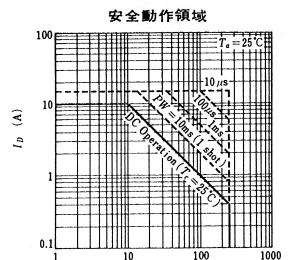


Ciss, Coss, Crss - VDS 特性

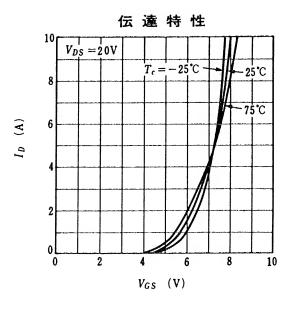


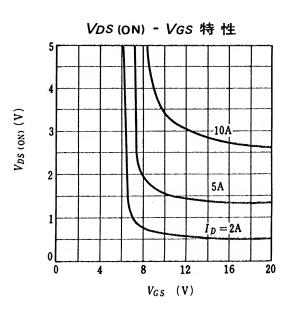
Si MOS型 Nチャンネル

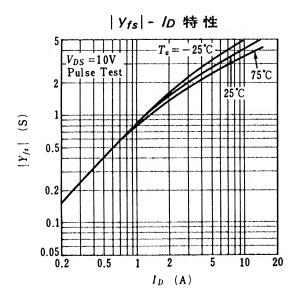
日 立

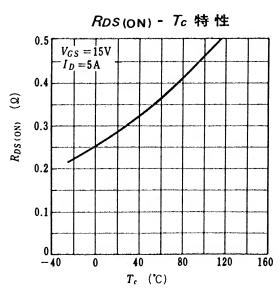


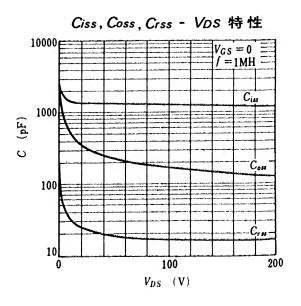
 $V_{DS}$  (V)





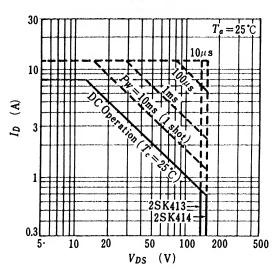




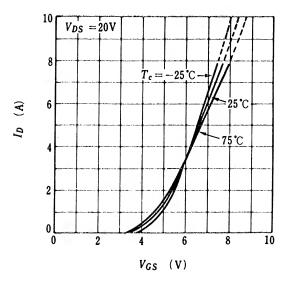


2SK413,414

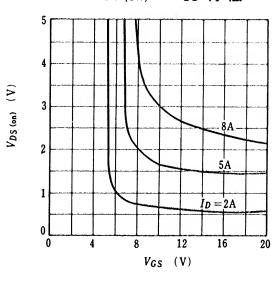
Si MOS型 Nチャンネル 日立



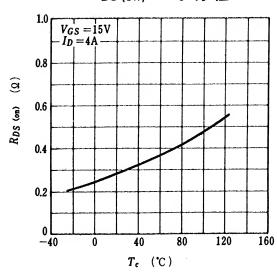
1D - VGS 特性



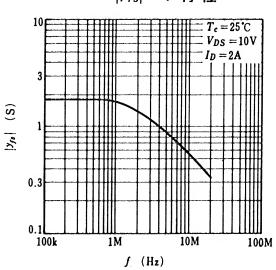
VDS (on) - VGS 特性



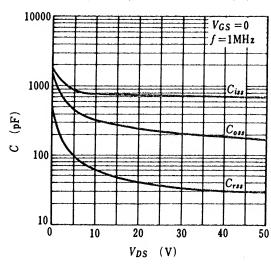
PDS (on) - Tc 特性

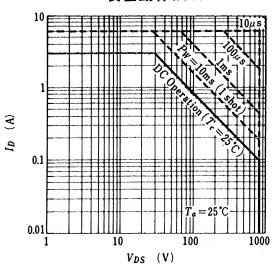


|Yfs| - f 特性

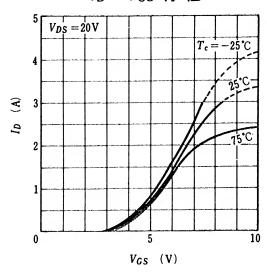


Ciss, Coss, Crss - VDS 特性

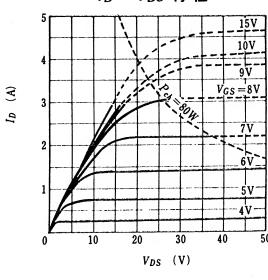




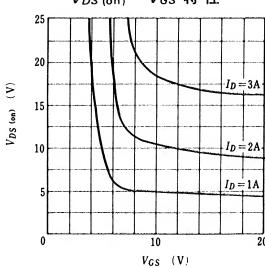
ID - VGS 特性



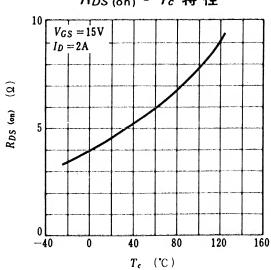
Ip - Vps 特性



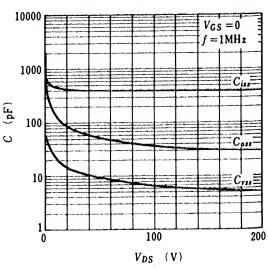
VDS (on) - VGS 特性



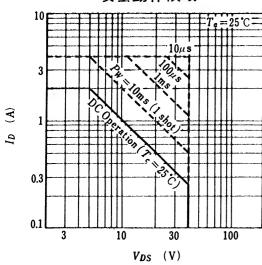
RDS (on) - Tc 特性



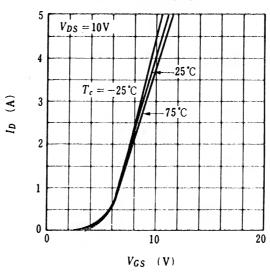
Ciss, Coss, Crss - VDS 特性



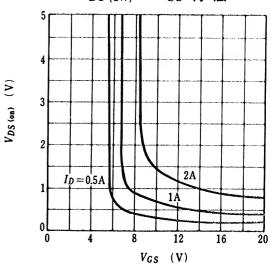
Si MOS型 Nチャンネル 日 立



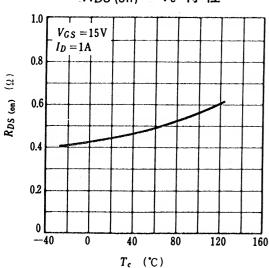
1o - VGS 特性



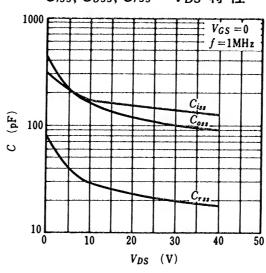
VDS (on) - VGS 特性



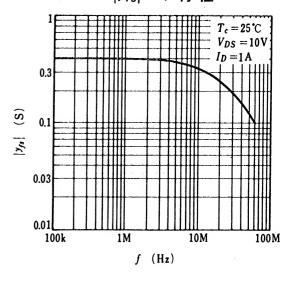
RDS (on) - Tc 特性



Ciss, Coss, Crss - VDS 特性

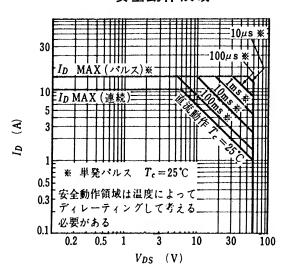


|Yfs| - f 特性

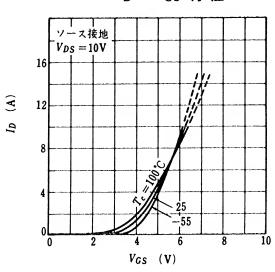


Si MOS型 Nチャンネル 東 芝

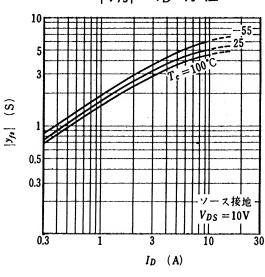
安全動作領域



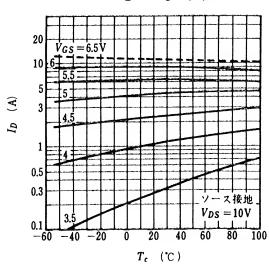
/p - V<sub>GS</sub> 特性



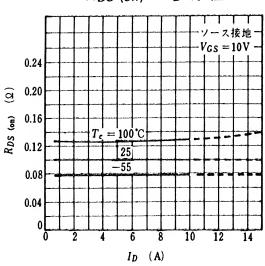
|Yfs| - ID 特性



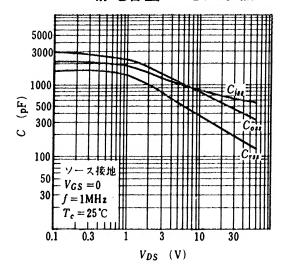
/D - Tc 特性



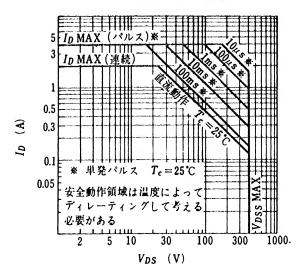
R<sub>DS</sub> (on) - I<sub>D</sub> 特性



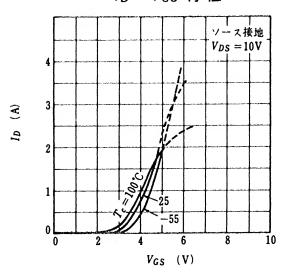
静電容量 - Vos 特性



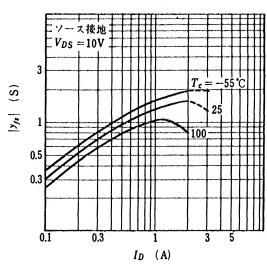
Si MOS型 Nチャンネル 東 芝



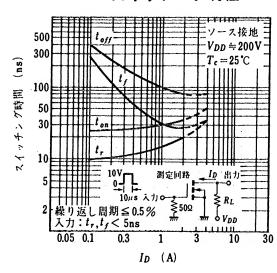
10 - VGS 特性



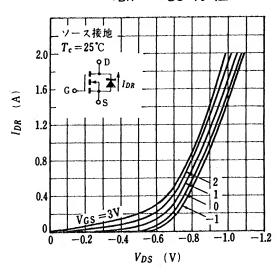
|Yfs| - ID 特性



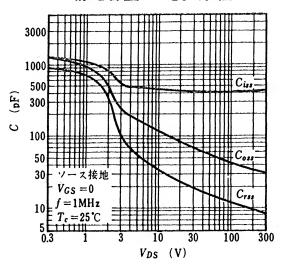
スイッチング特性



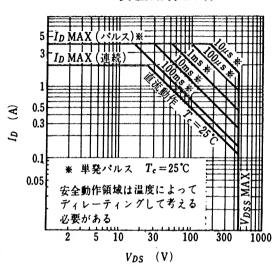
IDR - VDS 特性



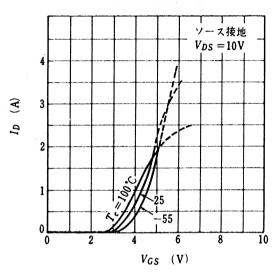
静電容量 - Vos 特性



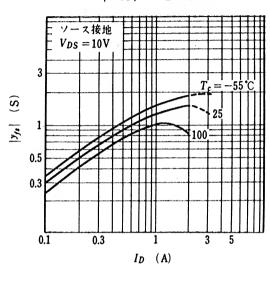
Si MOS型 Nチャンネル 東芝



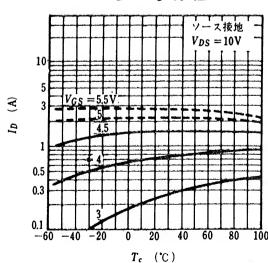
ID - VGS 特性



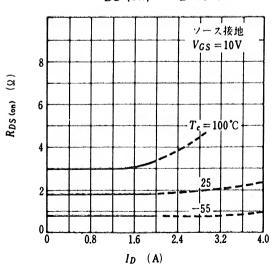
|Yfs| - ID 特性



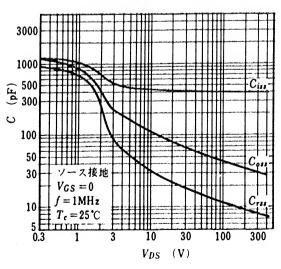
10 - Tc 特性



RDS (on) - ID 特性

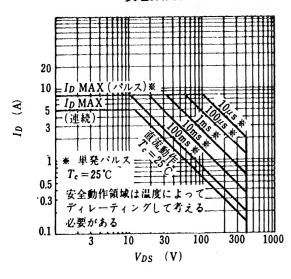


静電容量 - Vps 特性

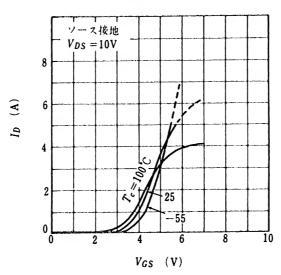


Si MOS型 \_ Nチャンネル 東 芝

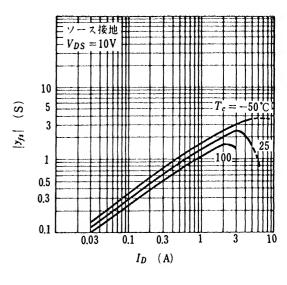
安全動作領域



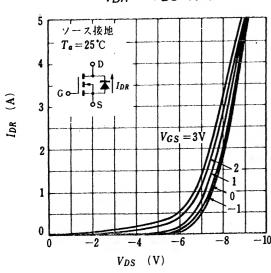
1D - VGS 特性



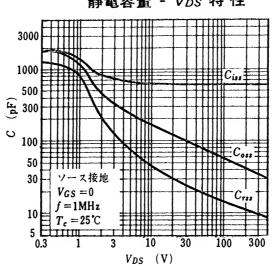
|Yfs| - ID 特性



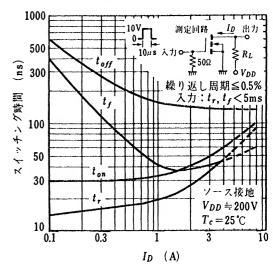
IDR - VDS 特性



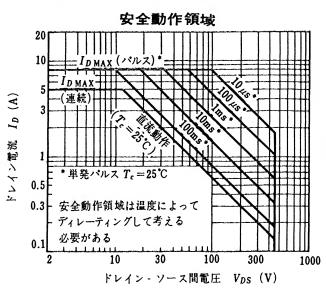
静電容量 - Vps 特性

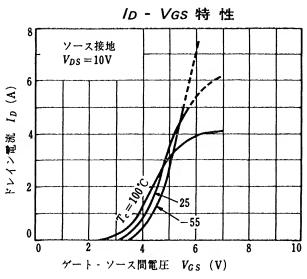


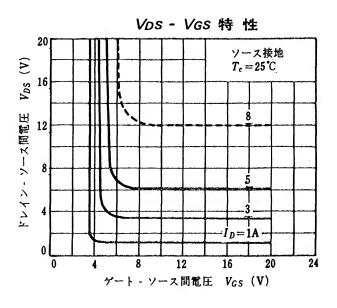
スイッチング特性

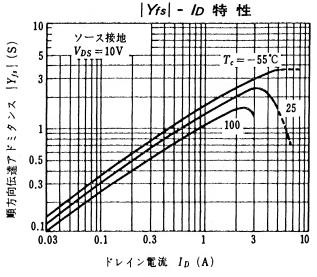


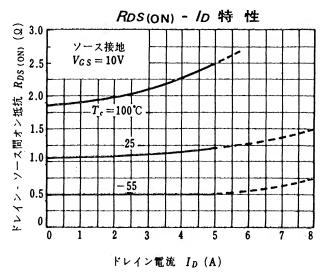
Si MOS型 Nチャンネル 東 芝

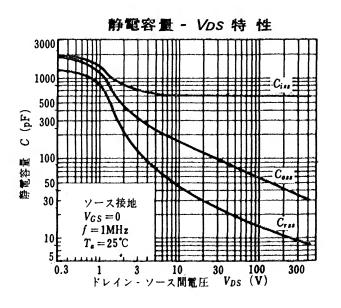




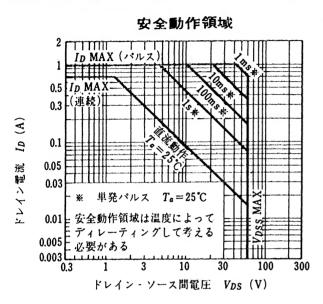


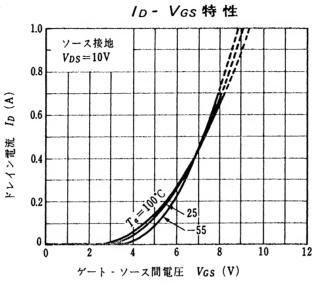


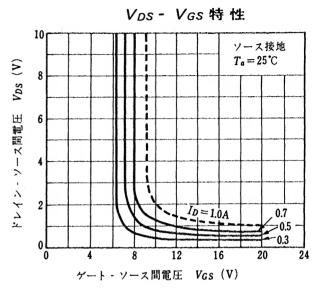


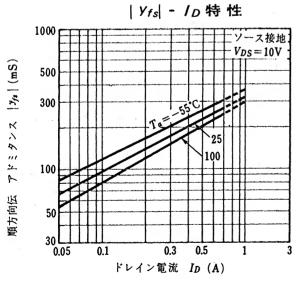


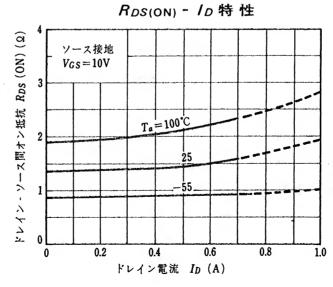
Si MOS型 Nチャンネル 東芝

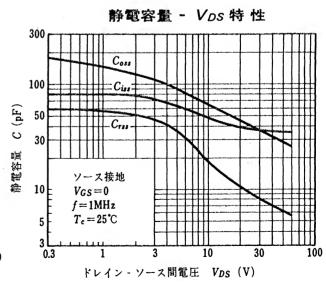




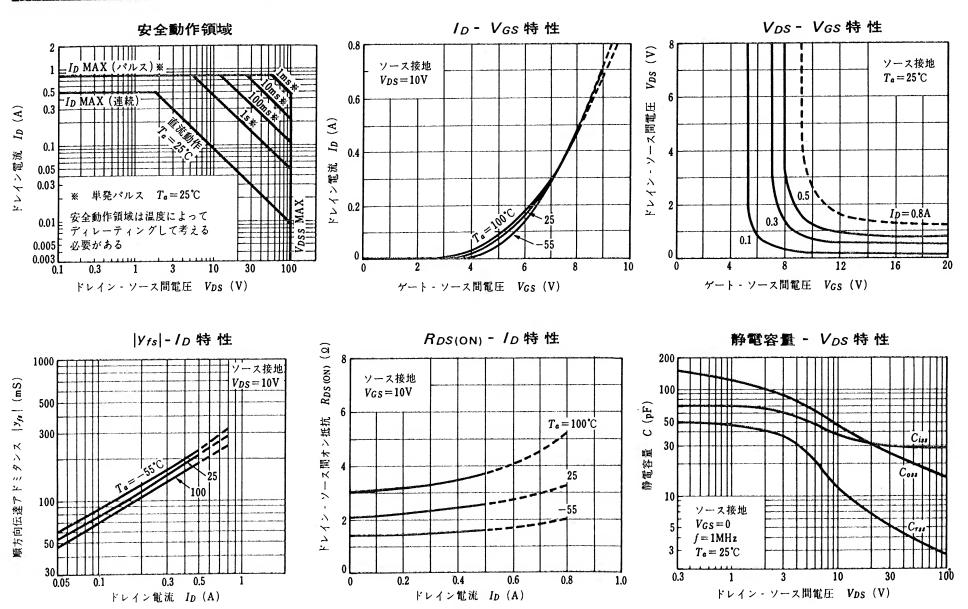




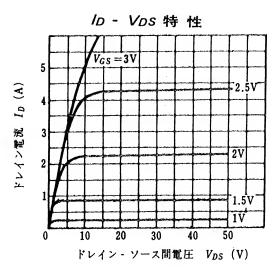


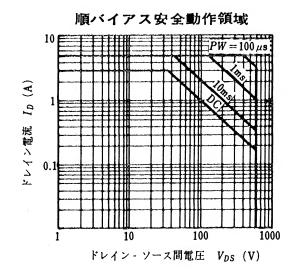


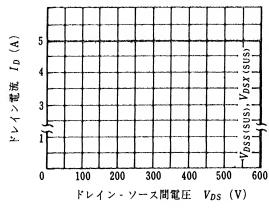
Si MOS型 Nチャンネル



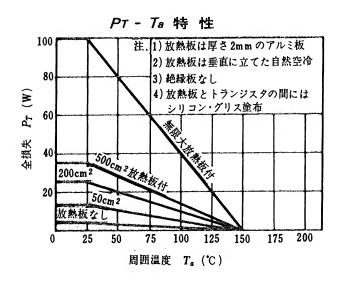
Si MOS型 Nチャンネル 日 電

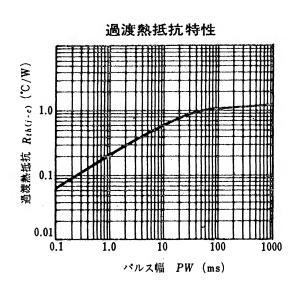


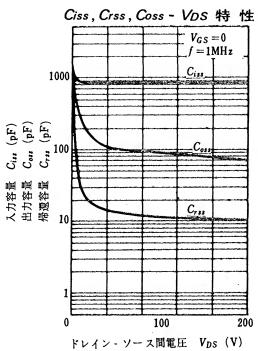




逆バイアス安全動作領域



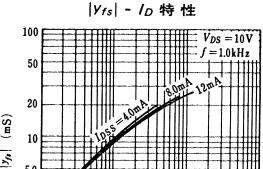


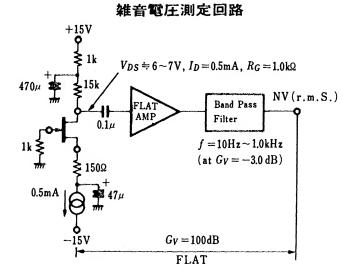


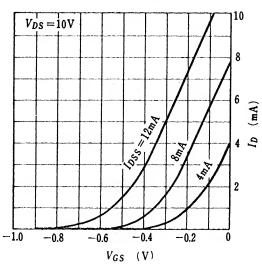
 $I_{DSS}$  (mA) 1~4 3~6 5~8 7~10 9~12 11~14 13~16 15~18 2SK425 X11 X12 X13 X14 X15 X16 X17 X18 2SK426

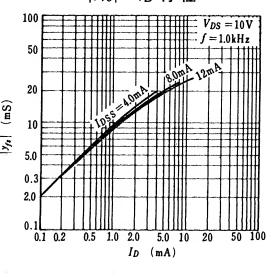
X21 X22 X23 X24 X25 X26 X28 X27

### /D - VGS 特性

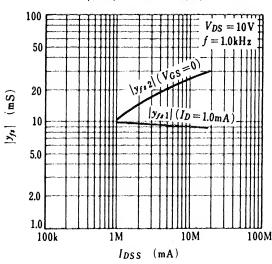


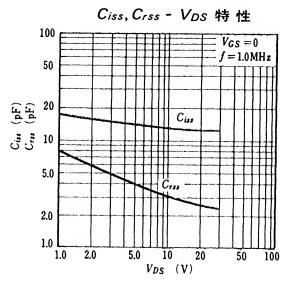


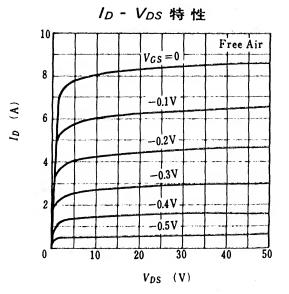










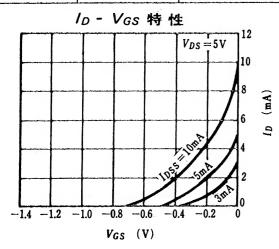


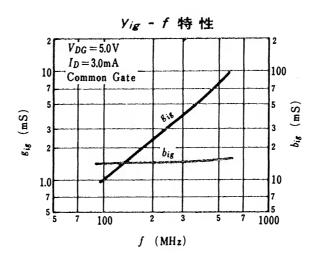
2SK427,436

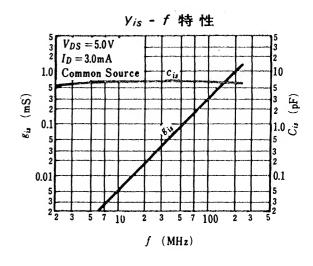
Si 接合型 Nチャンネル 三 洋

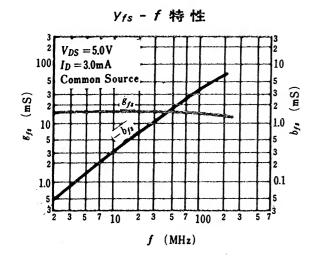
IDSS により次のように分類している(単位:mA)

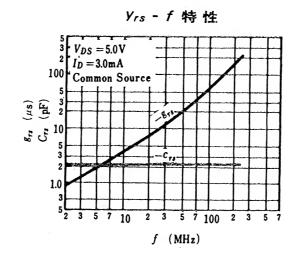
1.2	Ė	2.1	1.7	Q	3.0	2.5	R	4.2
3.5	S	6.0	5.0	Т	8.5	7.3	U	12.0

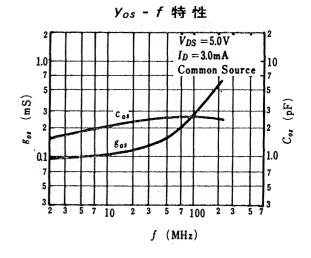




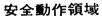


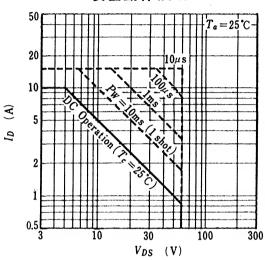




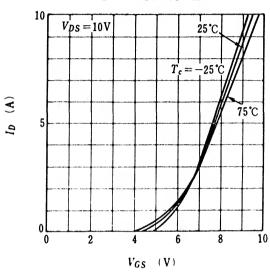


Si MOS型 Nチャンネル 日 立

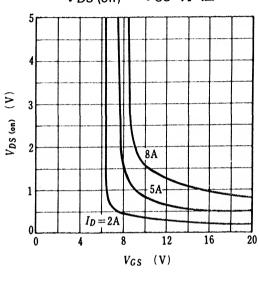




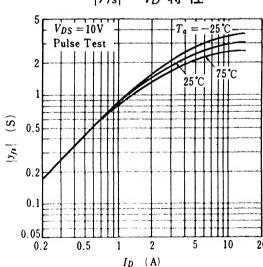
/D - VGS 特性



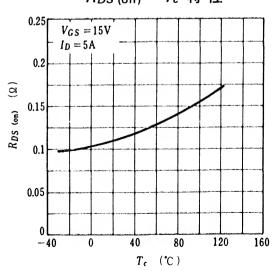
V<sub>DS (on)</sub> - V<sub>GS</sub> 特性



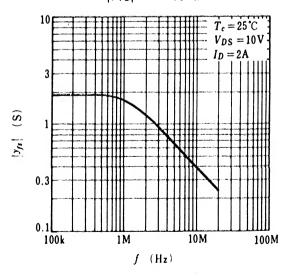
|Yfs| - ID 特性



RDS (on) - Tc 特性



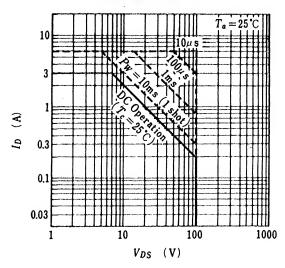
|Yfs| - f 特性



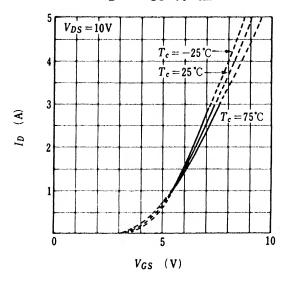
### Si MOS 型 Nチャンネル

日 立

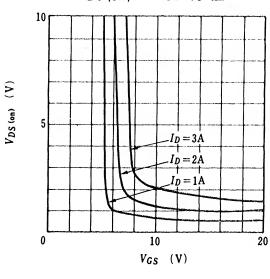
安全動作領域



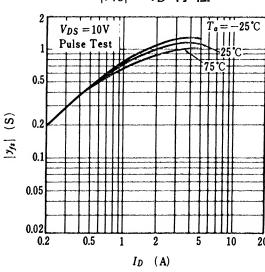
1D - VGS 特性



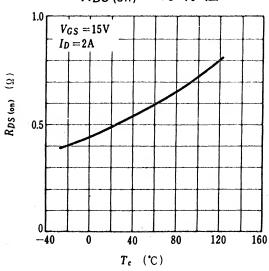
Vos (on) - Vgs 特性



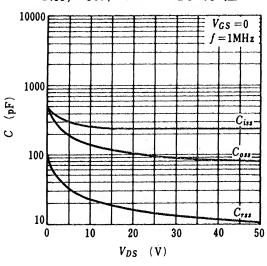
|Yfs| - ID 特性



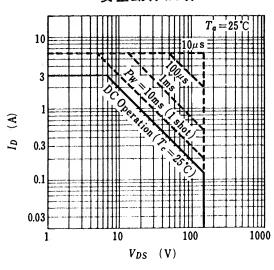
RDS (on) - Tc 特性



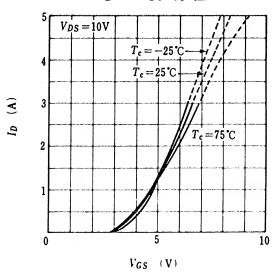
Ciss, Coss, Crss - Vos 特性



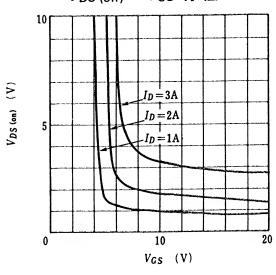
### 安全動作領域



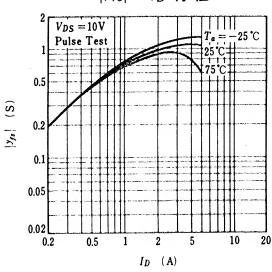
ID - VGS 特性



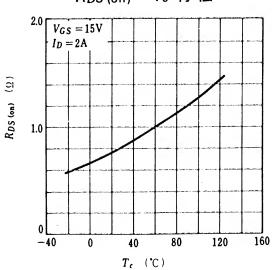
VDS (on) - VGS 特性



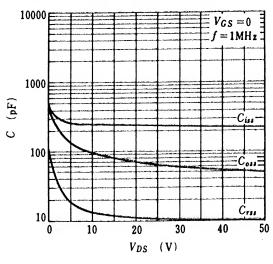
|Yfs| - 1D 特性



RDS (on) - Tc 特性



Ciss, Coss, Crss - VDS 特性



2SK435,494

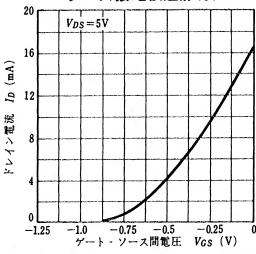
### Si 接合型 Nチャンネル

H 立

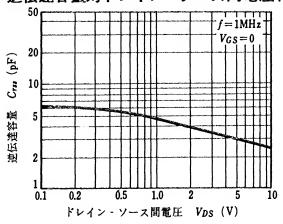
#### IDSS 区分

ВС		D	E	
6~14	12~22	18~30	26~40	

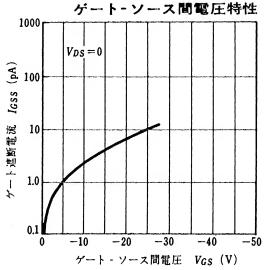
### ソース接地伝達静特性

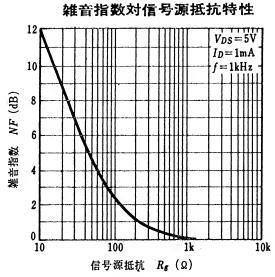


### 逆伝達容量対ドレイン - ソース間電圧特性

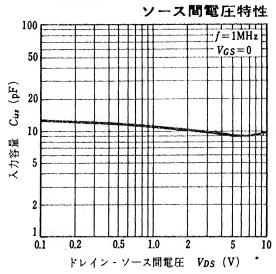


#### ゲート遮断電流対

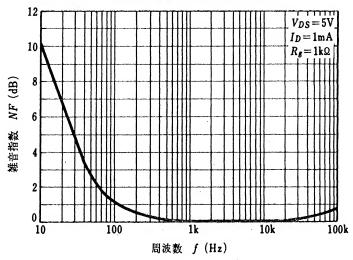


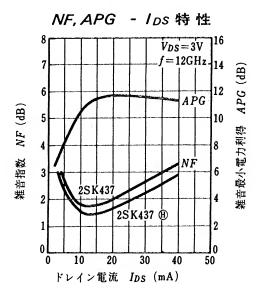


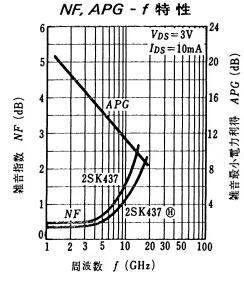
#### 入力容量対ドレイン -

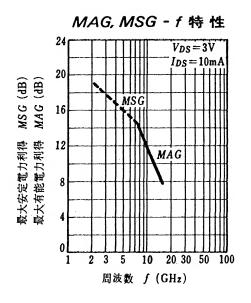


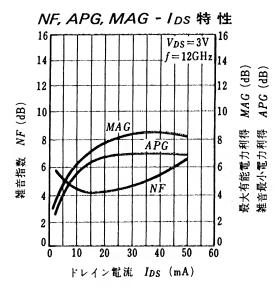
#### 雑音指数対周波数特性

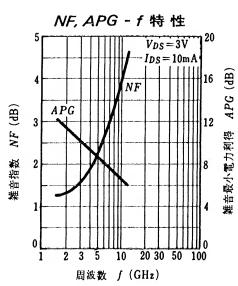


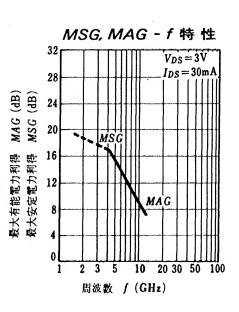






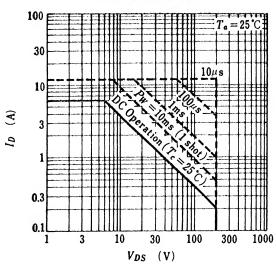




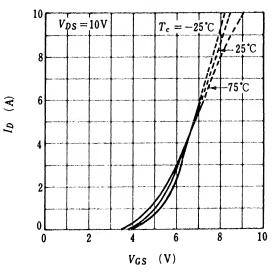


Si MOS型 Nチャンネル 日 立

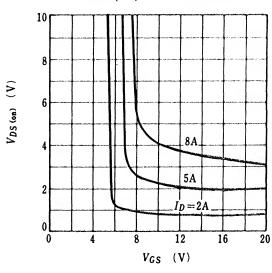
### 安全動作領域



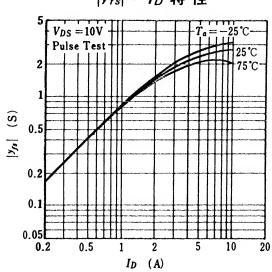
ID - VGS 特性



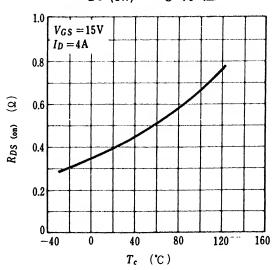
VDS (on) - VGS 特性



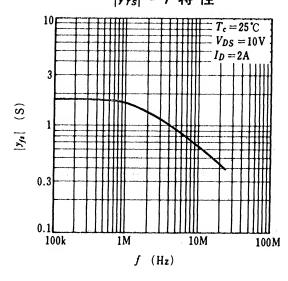
|Yfs| - 1D 特性



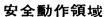
RDS (on) - Tc 特性

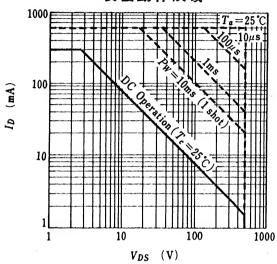


|Yfs| - f 特性

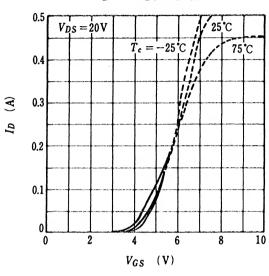


Si MOS型 Nチャンネル 日 立

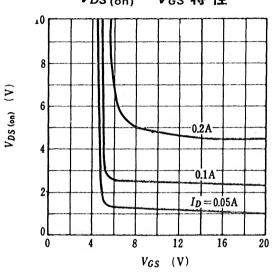




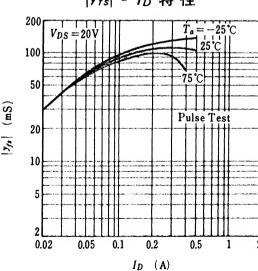
ID - VGS 特性



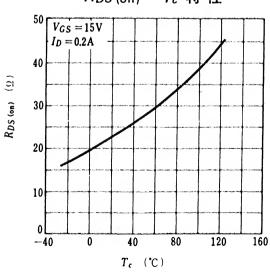
Vos (on) - VGS 特性



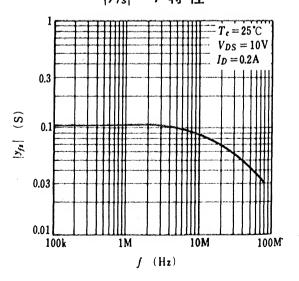
|Yfs| - ID 特性



RDS (on) - Tc 特性

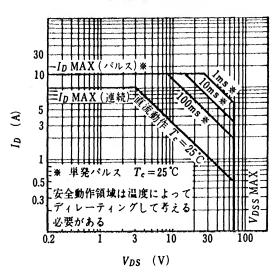


|Yfs| - f 特性

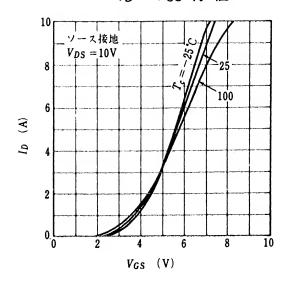


Si MOS型 \_ Nチャンネル 東芝

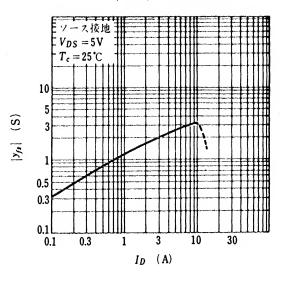
### 安全動作領域



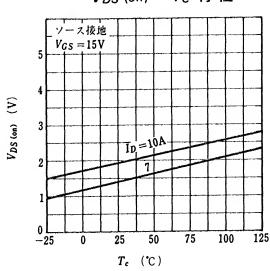
10 - VGS 特性



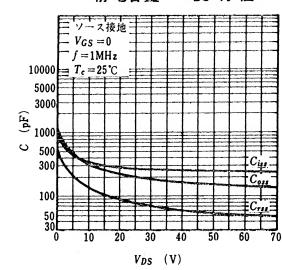
|Yfs| - ID 特性



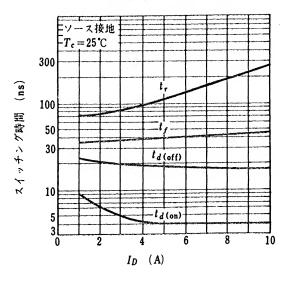
Vos (on) - Tc 特性



静電容量 - Vos 特性



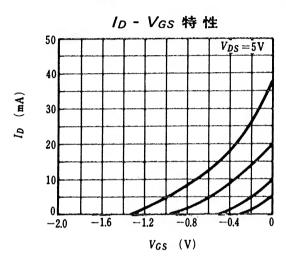
スイッチング特性

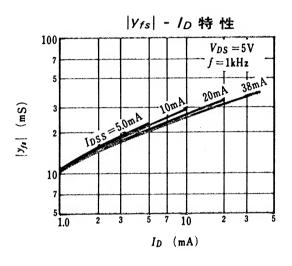


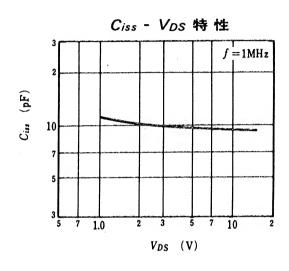
Si 接合型 N チャンネル 三 洋

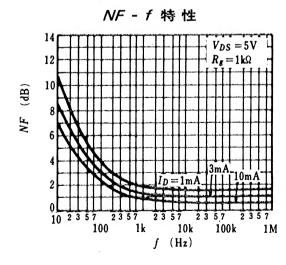
VDS=5V により次のように分類する.

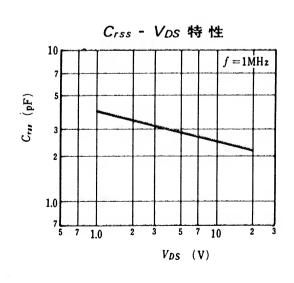
5.0 AJ5 12.0 10.0 AJ6 24.0 16.0 AJ7 38.0

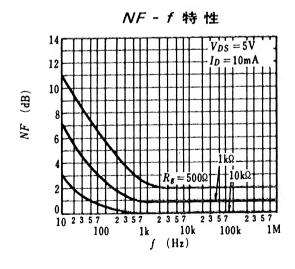






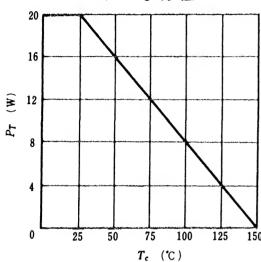




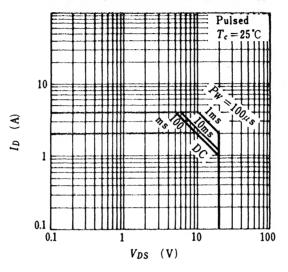


Si MOS型 Nチャンネル 日電

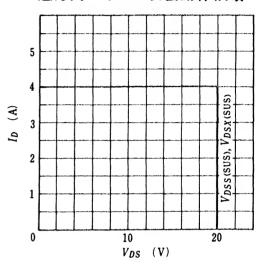
Pr - Tc 特性



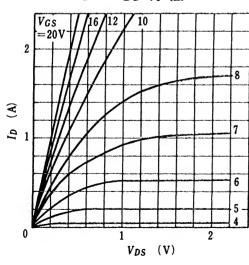
順方向バイアス安全動作領域



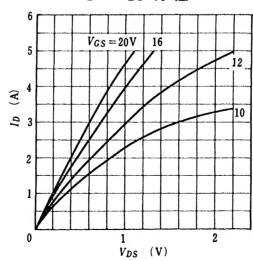
逆方向バイアス安全動作領域



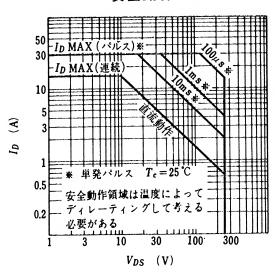
10 - Vos 特性



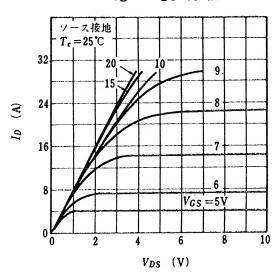
1o - Vos 特性



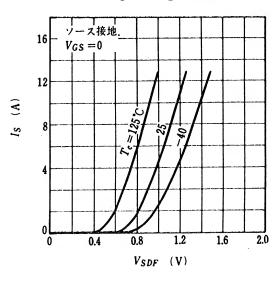
### 安全動作領域



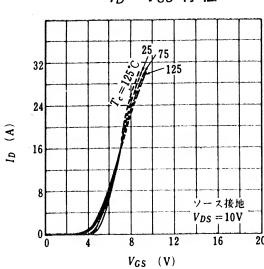
Ip - Vps 特性



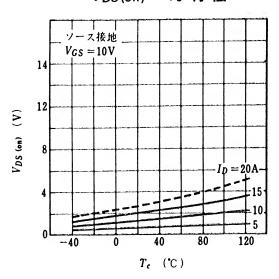
Is - VSDF 特性



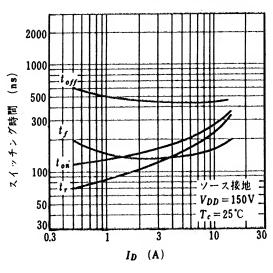
Ip - Vgs 特性



VDS(on) - Tc 特性

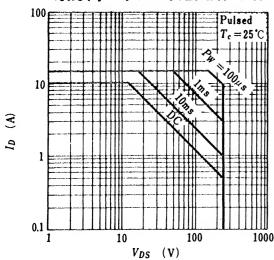


スイッチング特性

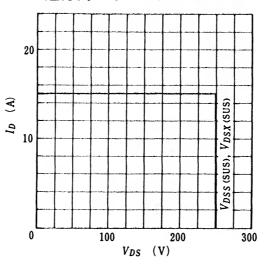


Si MOS型 B Nチャンネル

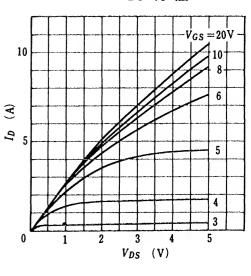




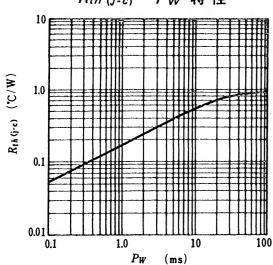
逆方向バイアス安全動作領域



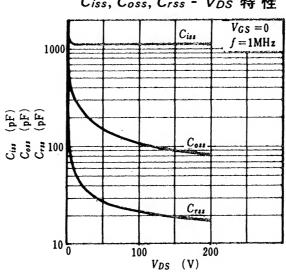
/D - VDS 特性



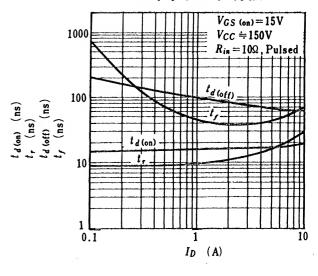
Rth (j-c) - PW 特性



Ciss, Coss, Crss - VDS 特性

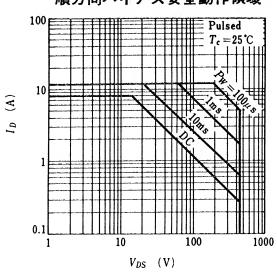


スイッチング特性

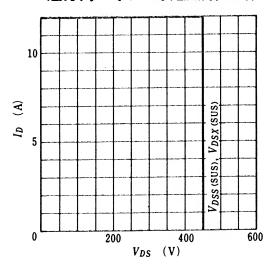


Si MOS型 Nチャンネル 日電

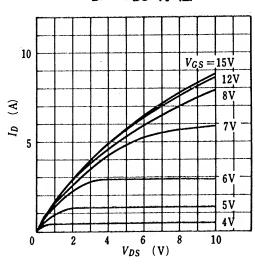
### 順方向バイアス安全動作領域



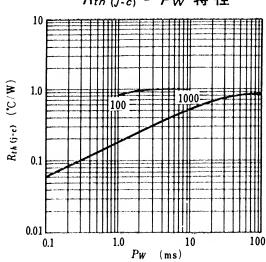
逆方向バイアス安全動作領域



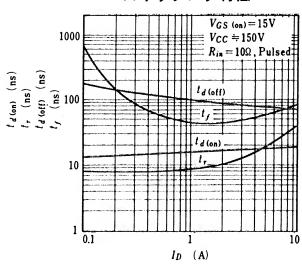
Ip - Vps 特性



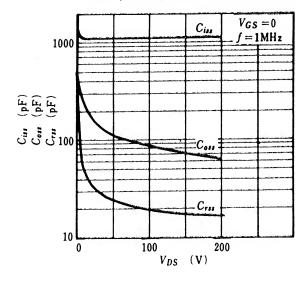
Rth (j-c) - Pw 特性



スイッチング特性



Ciss, Coss, Crss - VDS 特性



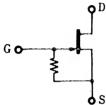
Si 接合型 Nチャンネル

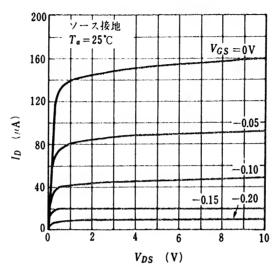
東 芝

IDDS 分類 R:60~120 O:100~200 Y:150~300 G:250~500μA

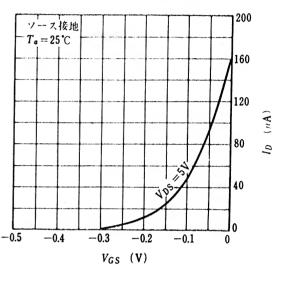
10 - Vos 特性

等価回路

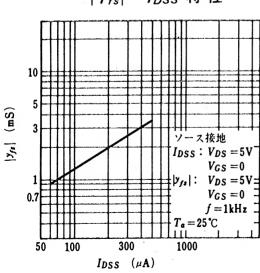




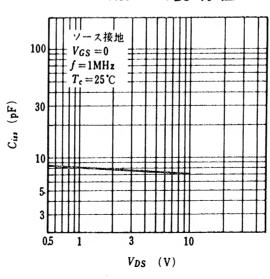
1<sub>D</sub> - V<sub>GS</sub> 特性



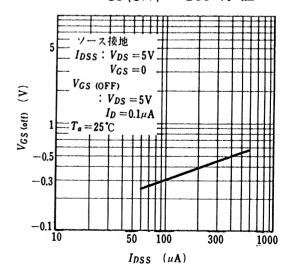
|Yfs| - IDSS 特性



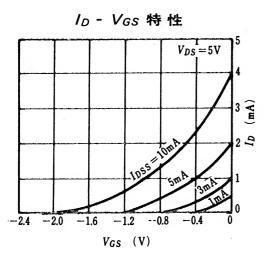
Ciss - Vos 特性

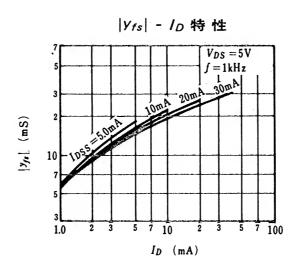


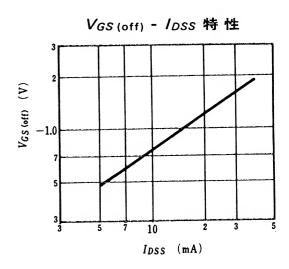
VGS (OFF) - IDSS 特性

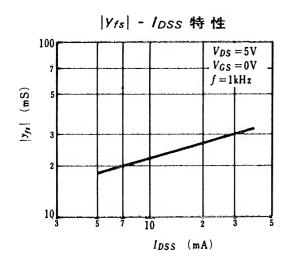


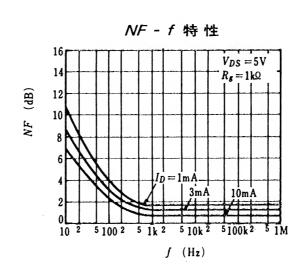
### Si 接合型 N チャンネル

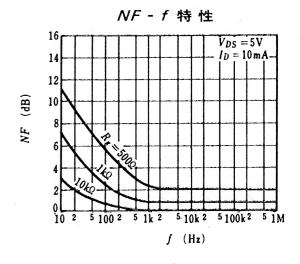












2SK505,507,508

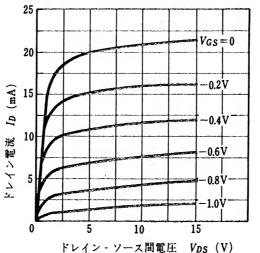
## Si 接合型 Nチャンネル

日電

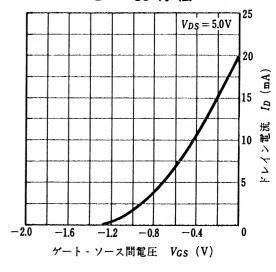
IDSS 区分

	10~20	15~30	25~50
2SK505, 507	Е	F H	
2SK 508	K51	K52	K53

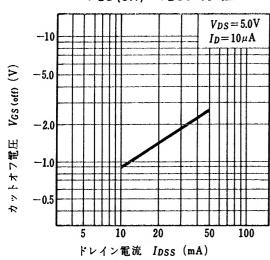
/o - Vos 特性



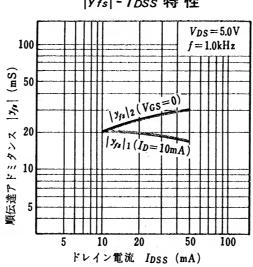
1p - Vgs 特性



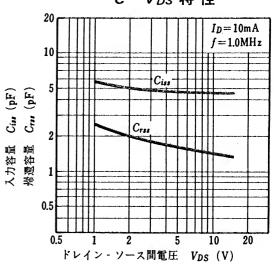
VGS (off) - IDSS 特性



|Yfs | - IDSS 特性



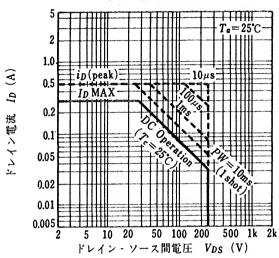
C - Vos 特性



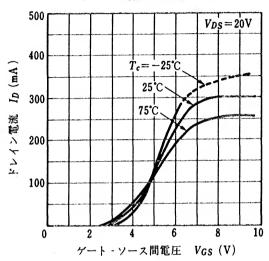
### Si MOS型 Nチャンネル

日 立

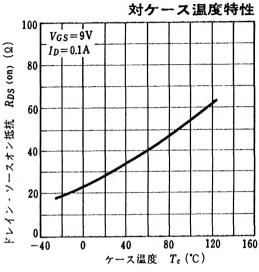
#### 安全動作領域



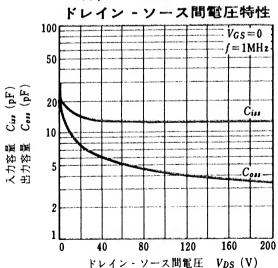
ソース接地伝達特性



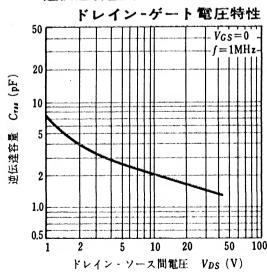
ドレイン・ソースオン抵抗



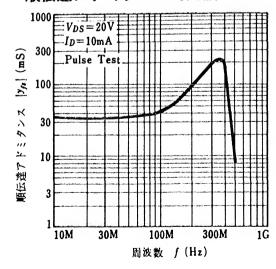
### 入力, 出力容量対



逆伝達容量対

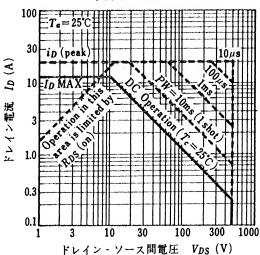


順伝達アドミタンス対周波数特性

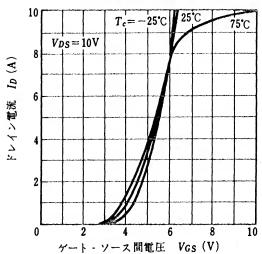


Si MOS型 \_ Nチャンネル 日 立

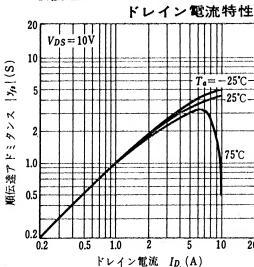
#### 安全動作領域



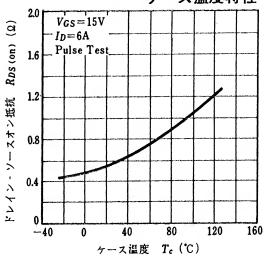
### ソース接地伝達静特性



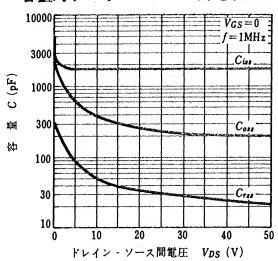
順伝達アドミタンス対



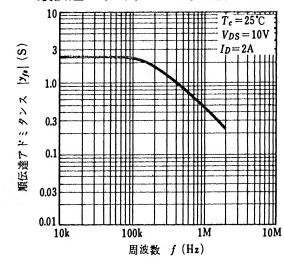
### ドレイン - ソースオン抵抗対 ケース温度特性



### 容量対ドレイン - ソース間電圧特性

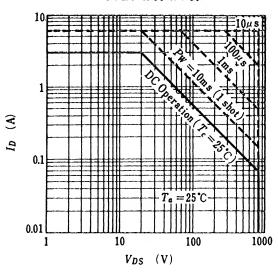


#### 順伝達アドミタンス対周波数特性

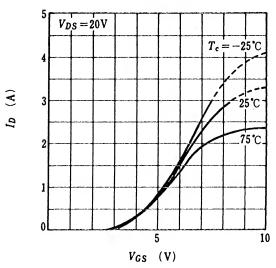


Si MOS型 日立 N チャンネル

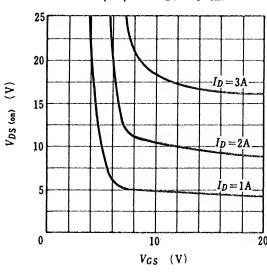
#### 安全動作領域

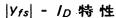


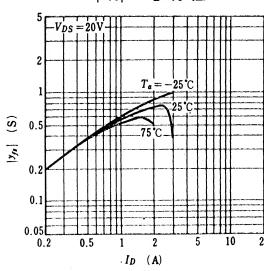
ID - VGS 特性



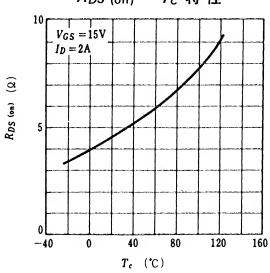
Vos (on) - Vos 特性



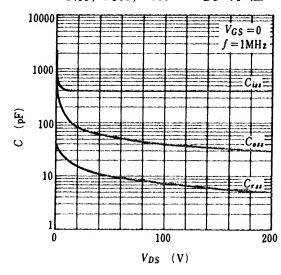




RDS (on) - TC 特性



Ciss, Coss, Crss - VDS 特性



2SK518,519,520

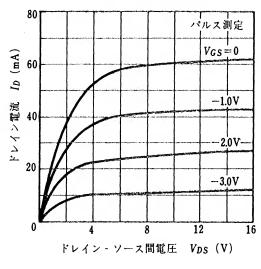
### Si 接合型 Nチャンネル

日電

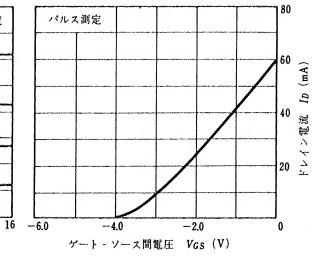
Ioss 区分

	30~50	45~65	60~80	75~95	90~110
2SK518, 519	E	F	Н	J	K
2SK520	K41	K42	K43	K44	K45

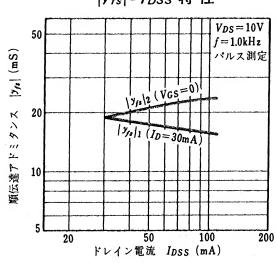
Io - Vos 特性



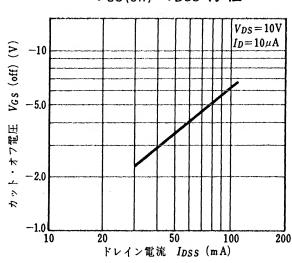
/p - V<sub>GS</sub> 特性



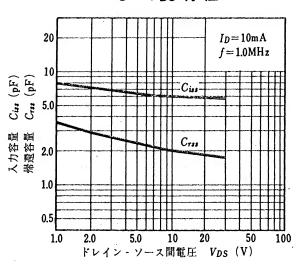
|Yfs| - IDSS 特性



VGS(off) - IDSS 特性

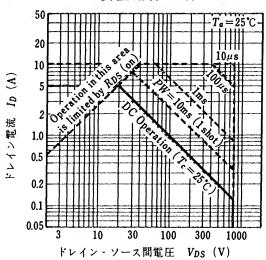


C - V<sub>DS</sub> 特性

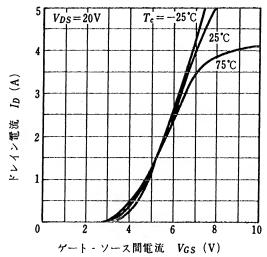


Si MOS型 Nチャンネル 日 立

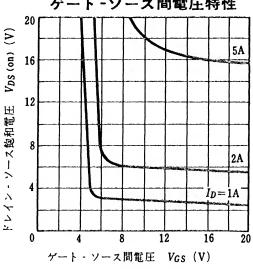
#### 安全動作領域



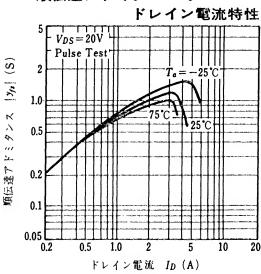
ソース接地伝達静特性



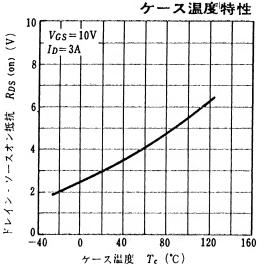
ドレイン-ソース飽和電圧対 ゲート-ソース間電圧特性



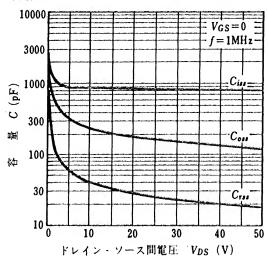
### 順伝達アドミタンス対



ドレイン・ソースオン抵抗対

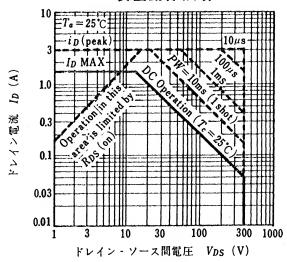


容量対ドレイン・ソース間電圧特性

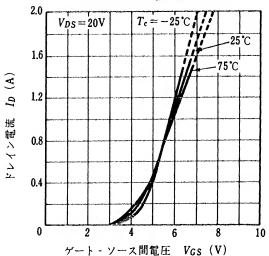


Si MOS型 Nチャンネル 日 立

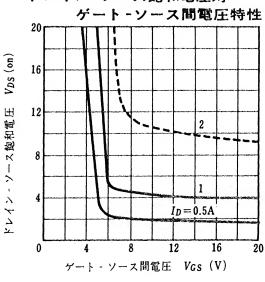
#### 安全動作領域



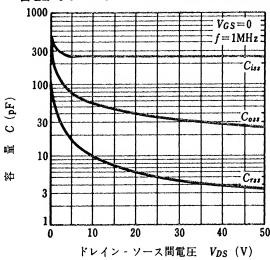
#### ソース接地伝遠静特性



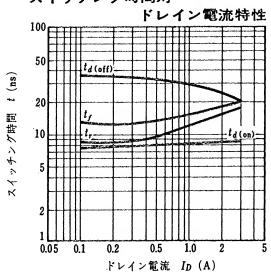
ドレイン-ソース飽和電圧対



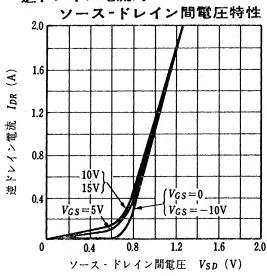
### 容量対ドレイン - ソース間電圧特性

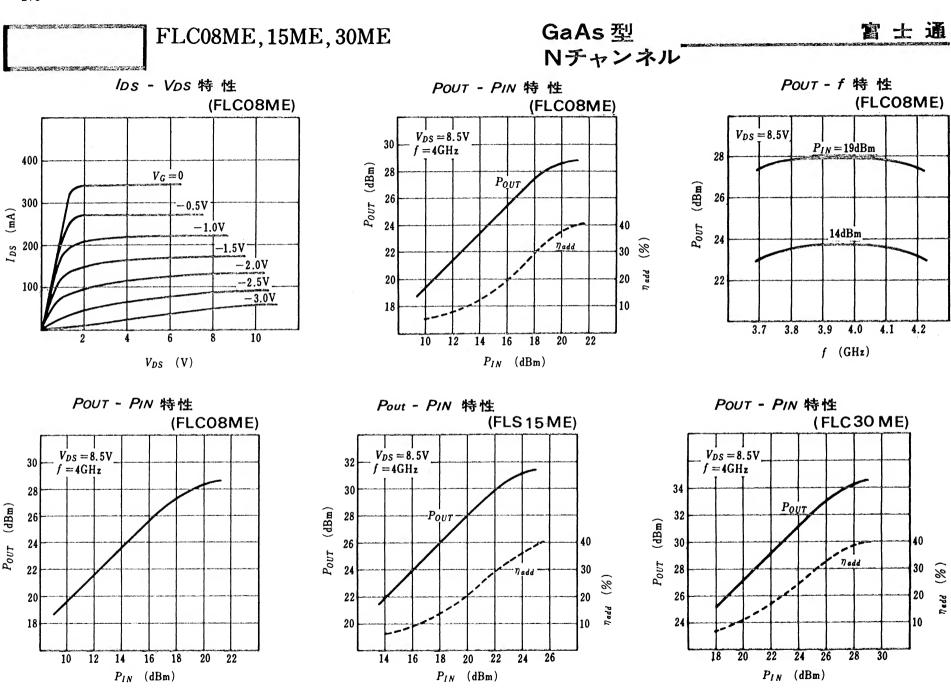


### スイッチング時間対



#### 逆ドレイン電流対

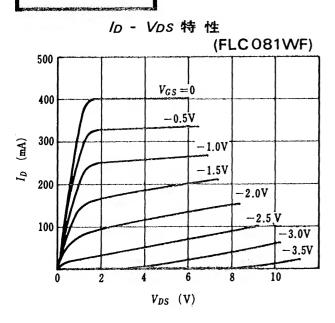


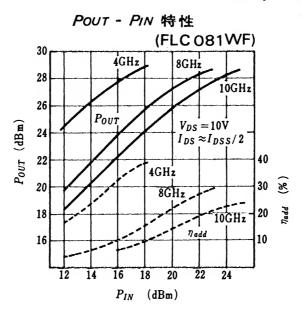


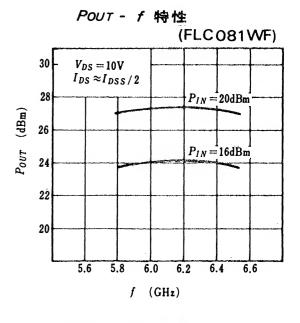
FLC081WF, 151WF, 301MG

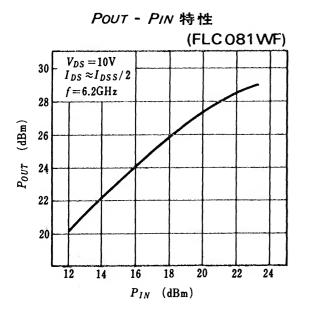
### GaAs型 Nチャンネル

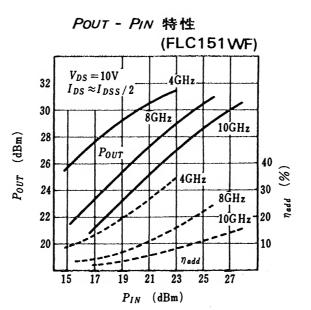
### 富士通

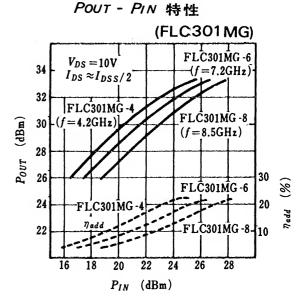






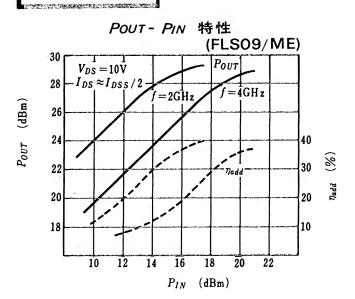


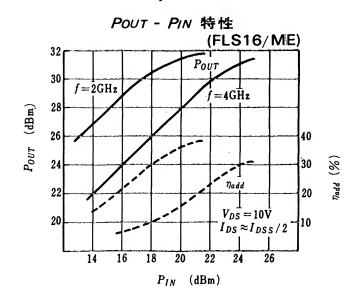


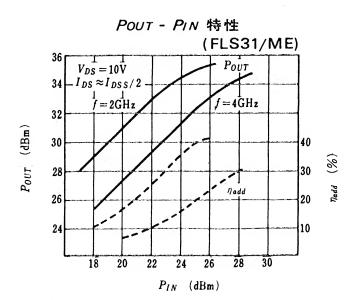


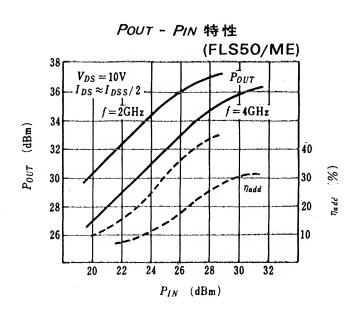
FLS09/ME, 16/ME, 31/ME, 50/ME

GaAs型 N チャンネル









松

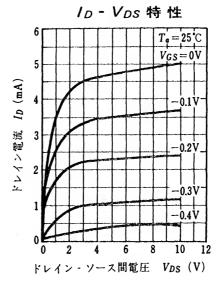
下

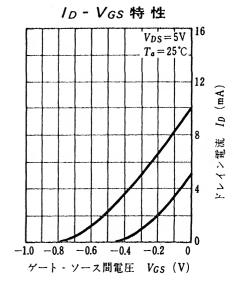
# M47F

IDSS ランク分類

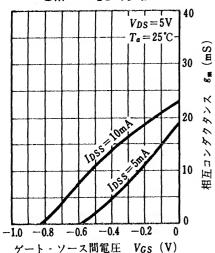
Class	A	В	С	D
IDSS (mA)	0.5~3	2~6	5~12	10~20

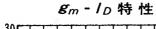
### Si 接合型 Nチャンネル

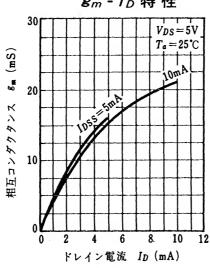




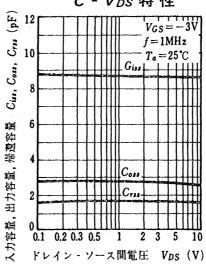




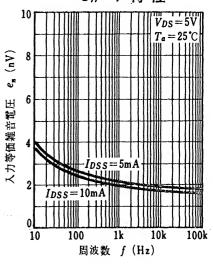




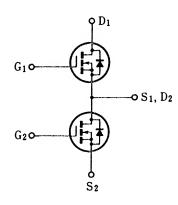
C - V<sub>DS</sub> 特性

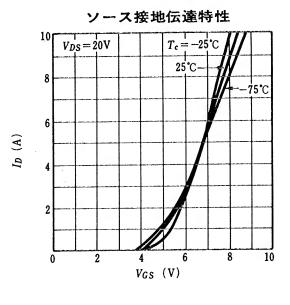


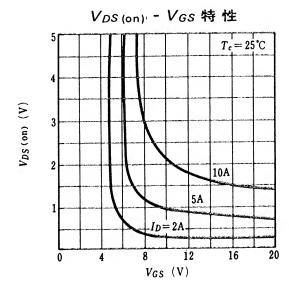
en-f特性

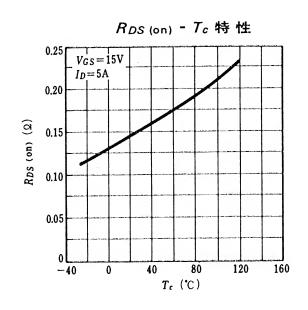


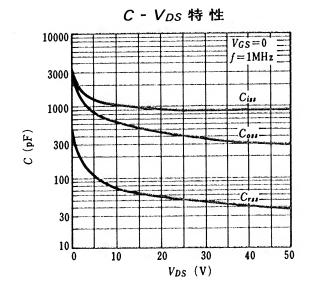








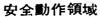


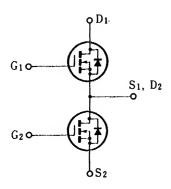


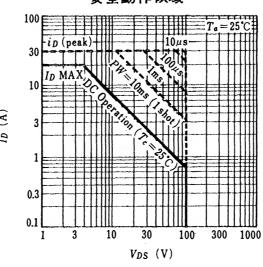
PM1220B

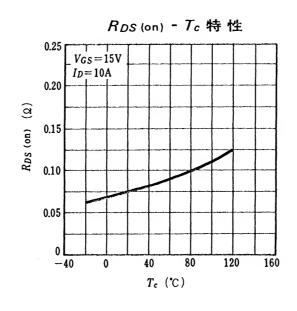
### Si MOS型 複合 Nチャンネル

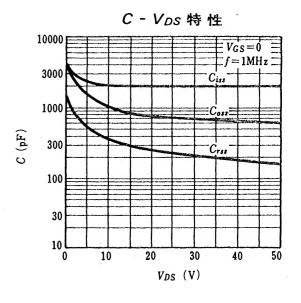
日立



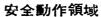


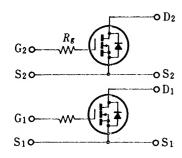


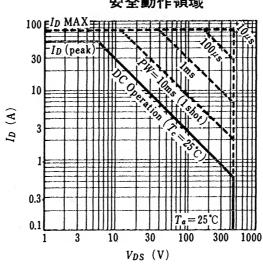




### Si MOS型 複合Nチャンネル

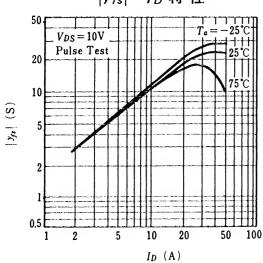




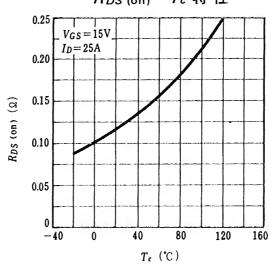


ソース接地伝達特性  $V_{DS} = 10V$ 40  $I_{D}(A)$ 10 8 10  $V_{GS}$  (V)

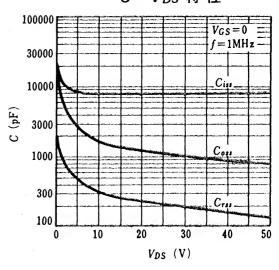
|Yfs| - 1D 特性



RDS (on) - Tc 特性

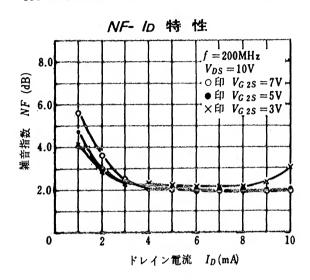


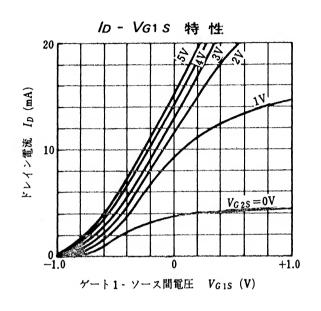
C - V<sub>DS</sub> 特性

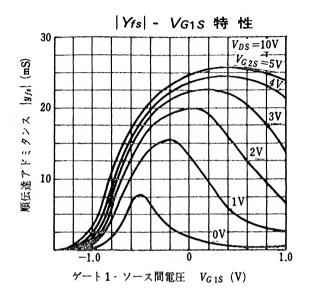


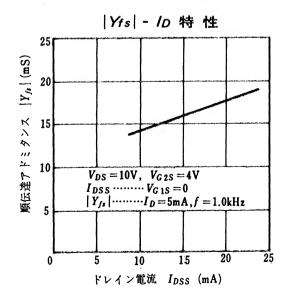
Si MOS型 Nチャンネル 日電

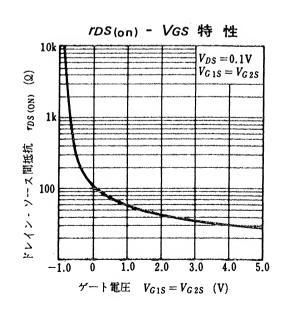
IDSS 区分/M:4~11mA L:9~19mA K:17~25mA



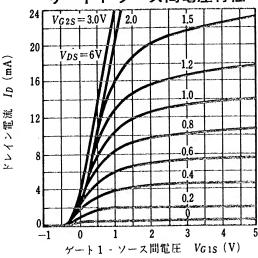




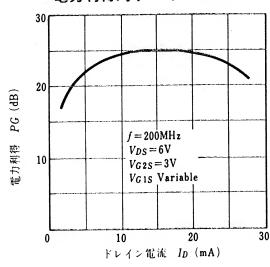




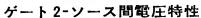
### ドレイン電流対 ゲート 1-ソース間電圧特性

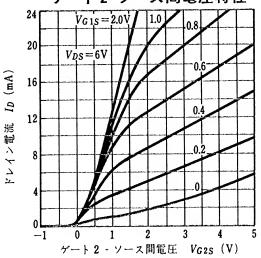


### 電力利得対ドレイン電流特性



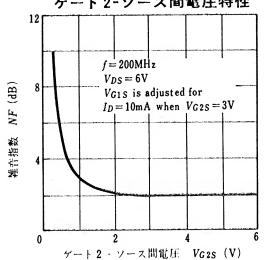
### ドレイン電流対



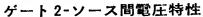


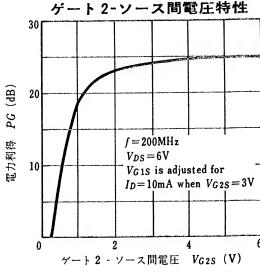
### 雑音指数対

#### ゲート2-ソース間電圧特性

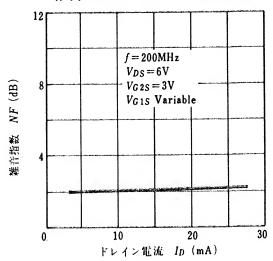


### 電力利得対

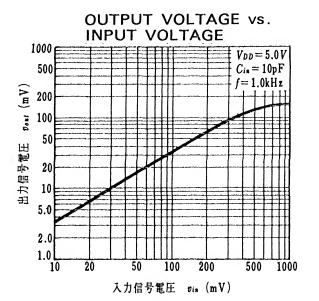




### 雑音指数対ドレイン電流特性

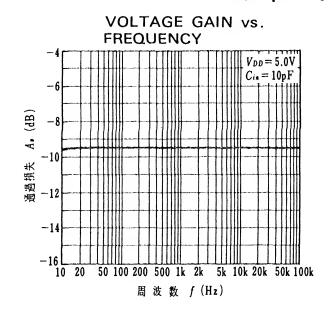


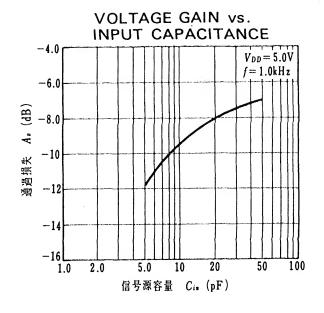
## 



### Si接合型 Nチャンネル

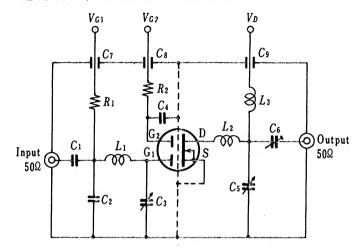






3SK81,136

## 電力利得, 雑音指数測定回路



 $R_1: 15k\Omega$  $R_2: 11k\Omega$  $C_1: 1000 pF$  $C_2$ : 47pF

C3, C5, C6: 10pF max 可変コンデンサ

C4: 1000pF 裸円板コンデンサ C1, C8, C9: 1000pF 貫通形コンデンサ

> L<sub>1</sub>,L<sub>2</sub>: φ0.8mm エナメル線 2.5T, 内径6mm L3: \$0.8mm エナメル線1.5T、内径6mm

# Si MOS型 Nチャンネル

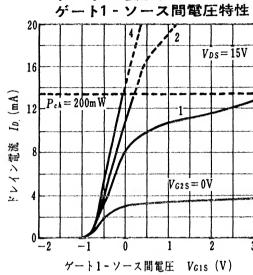
H

電力利得対

30

10

# ドレイン電流対



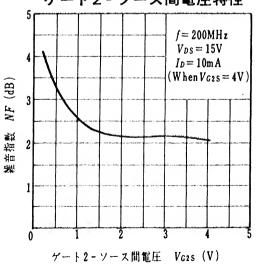
f = 200 MHz $V_{DS} = 15V$  $I_D = 10 \text{m A}$ 26  $(When V_{G2S} = 4V)$ (AB) 22 PG電力利得

ゲート2-ソース間電圧特性

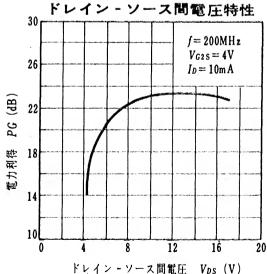
立

ゲート2-ソース間電圧 V<sub>G2S</sub> (V)

### 雑音指数対 ゲート2-ソース間電圧特性

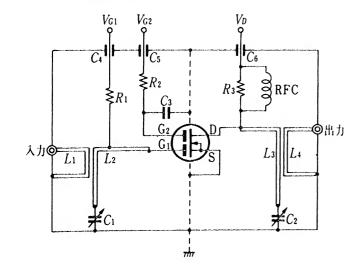


# 電力利得対

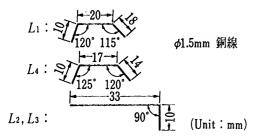


# J3SK82

#### 電力利得, 雑音指数測定回路



C<sub>1</sub>, C<sub>2</sub> : 10pF max可変コンデンサ C<sub>3</sub> : 1000pF裸円板コンデンサ C<sub>4</sub>~C<sub>6</sub>: 1000pF貫通形コンデンサ R<sub>1</sub>: 90kΩ R<sub>2</sub>: 47kΩ R<sub>3</sub>: 3.3kΩ

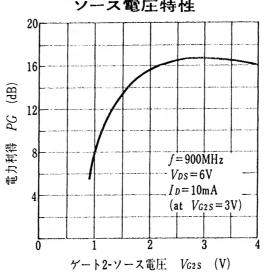


RFC: ø1.0mmエナメル線4T, 内径7mm

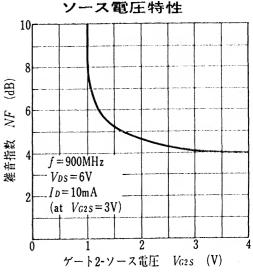
# Si MOS型 Nチャンネル

# 日 立

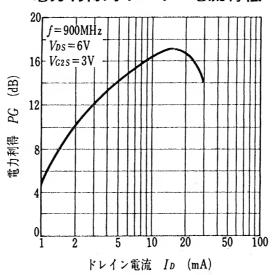
# 電力利得対ゲート2-ソース電圧特性



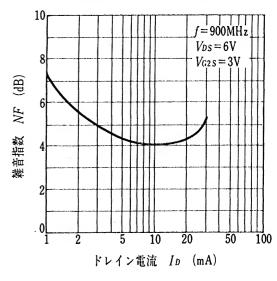
#### 雑音指数対ゲート2-ソース電圧特性



### 電力利得対ドレイン電流特性

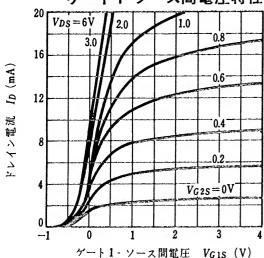


#### 雑音指数対ドレイン電流特性

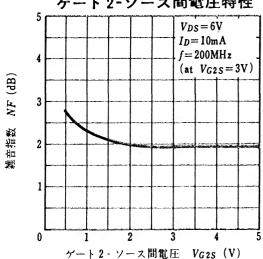


3SK96

## ドレイン電流対 ゲート1-ソース間電圧特性

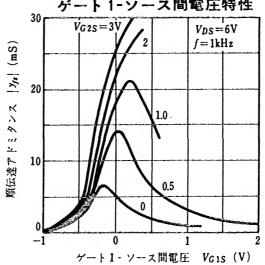


雑音指数対 ゲート 2-ソース間電圧特性

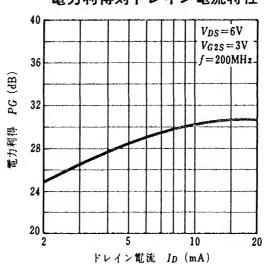


# Si MOS型 複合 N チャンネル

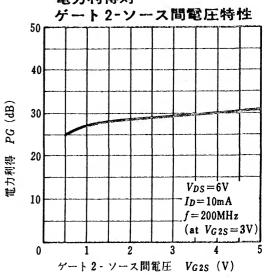
順伝達アドミタンス対 ゲート1-ソース間電圧特性



電力利得対ドレイン電流特性



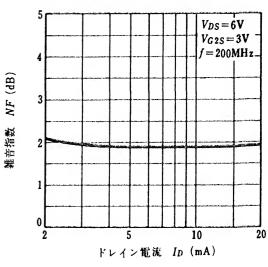
# 電力利得対



B

立

## 雑音指数対ドレイン電流特性

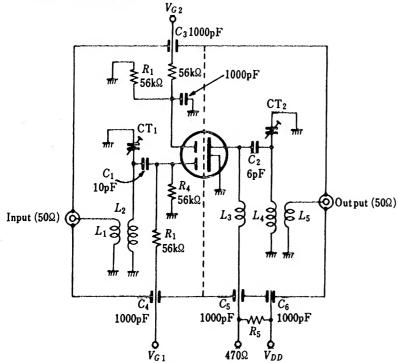


# 3SK100

#### IDSS ランク分類

	P	Q	R
$I_{DSS}$ (mA)	$0.5\!\sim\!2$	1.2~6	4~8

#### PG, NF 測定回路



 $L_1, L_5$  : 長さ  $1.5\phi$  のニッケル線

 $L_3$  : 0.15 $\phi$  7 9->

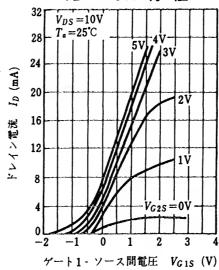
L<sub>2</sub>, L<sub>4</sub> : 6.0×28×0.8 銅板

CT, CT2:3~9pF シリンダ・トリマ

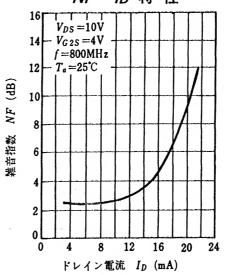
# Si MOS型 Nチャンネル

# 松下

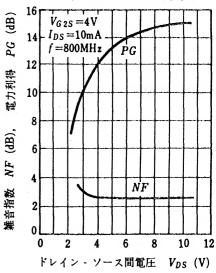
/D - VG1S 特性



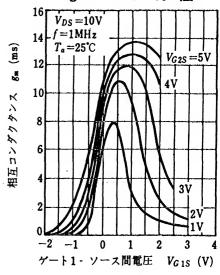
NF - ID 特性



NF, PG - Vos 特性

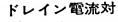


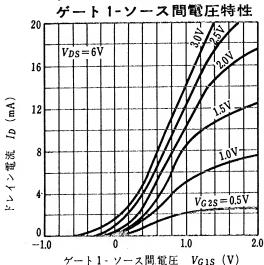
gm - VG1S 特 性



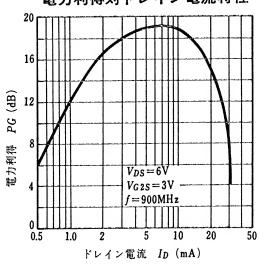
3SK103,138

# Si MOS型 複合Nチャンネル

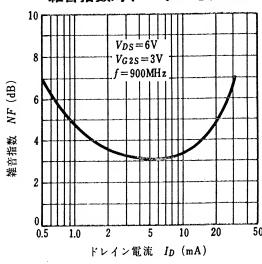




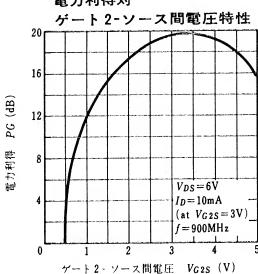
# 電力利得対ドレイン電流特性



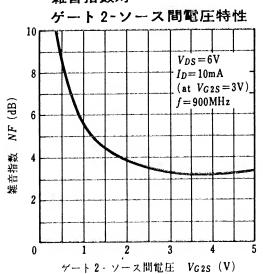
#### 雑音指数対ドレイン電流特性



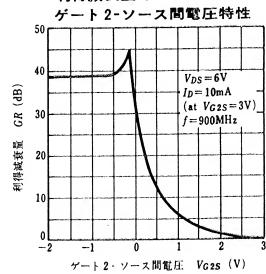
#### 電力利得対



## 雑音指数対



#### 利得減衰量対

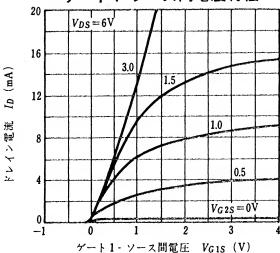


# 3SK104,104V,137 Si MOS型 複合 Nチャンネル

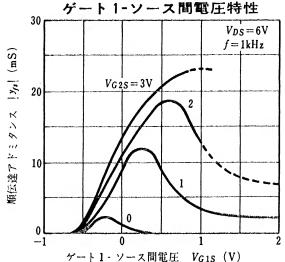
B 立



ゲート1-ソース間電圧特性

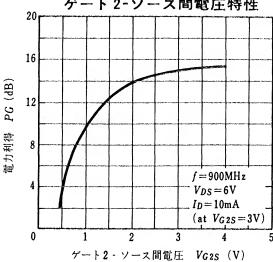


順伝達アドミタンス対



電力利得対

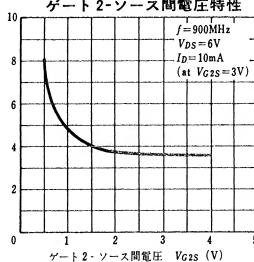
ゲート 2-ソース間電圧特性



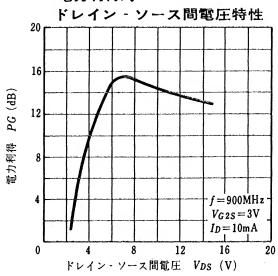
#### 雑音指数対

維育指数NF (dB)

ゲート 2-ソース間電圧特性

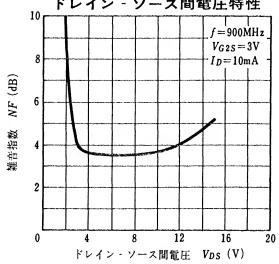


電力利得対



#### 維音指数対

ドレイン・ソース間電圧特性

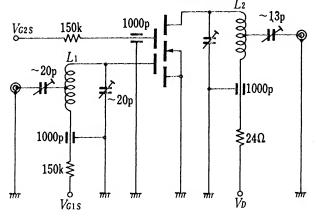


J3SK108

Si MOS型 複合Nチャンネル

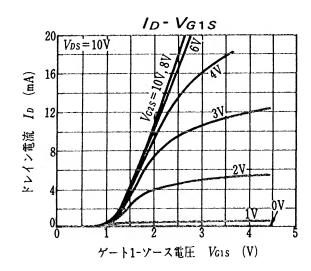
IDSX分類 3 Q 10 7 R 14 10 S 17 14 T 21

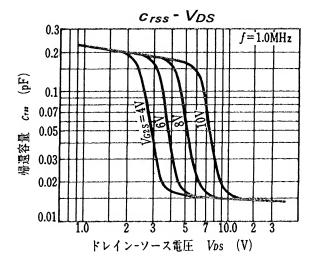
## PG, NF測定回路

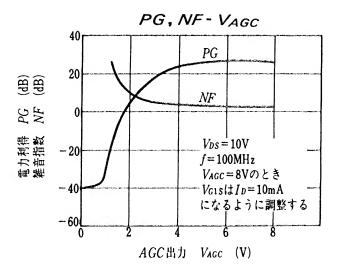


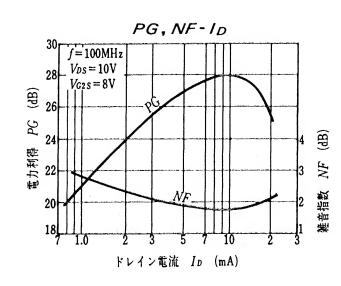
L1:1mmφメッキ線を10mmφ 4T, Gate側より1Tにタップ。

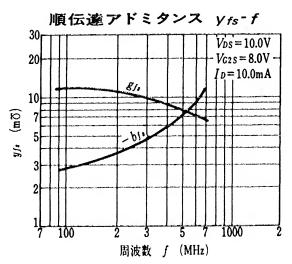
L2:1mmφメッキ線を10mmφ 6T, Drain側より1Tにタップ.









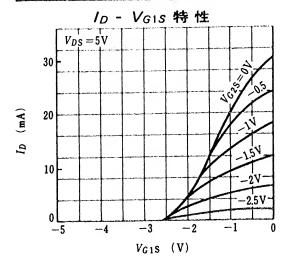


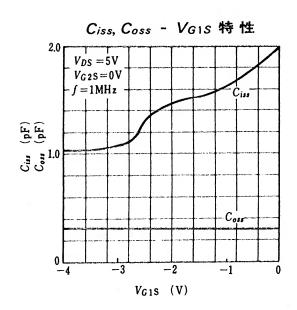
工工

E

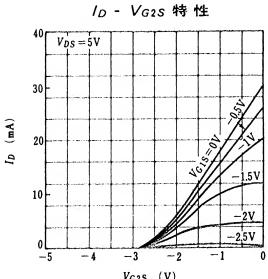
# ]3SK113

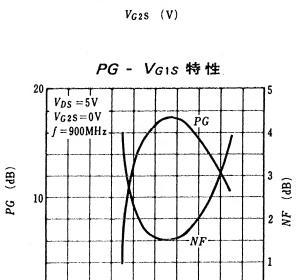
F	G	Н	J	
10~20	16~32	25~50	40~80	mA





# Ga A s 型 複合 Nチャンネル

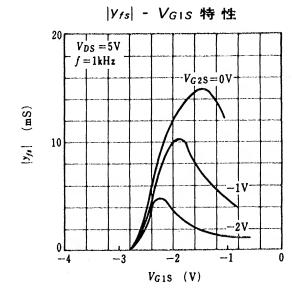


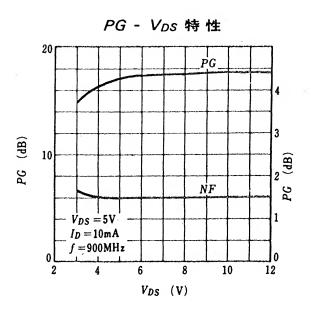


-2

 $V_{G1S}$  (V)

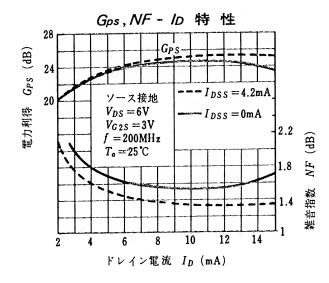
-3

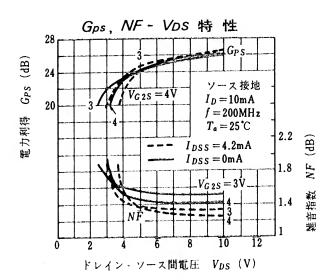


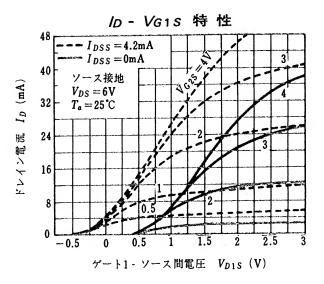


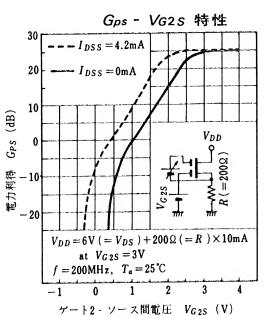
# 3SK114

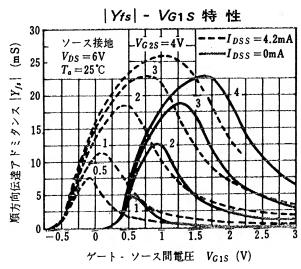
IDSS 区分 0:0~2, Y:1~6 (mA)

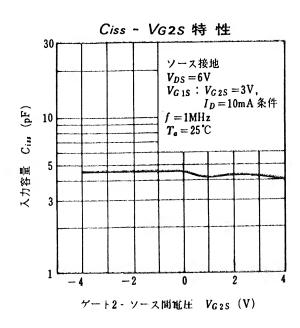










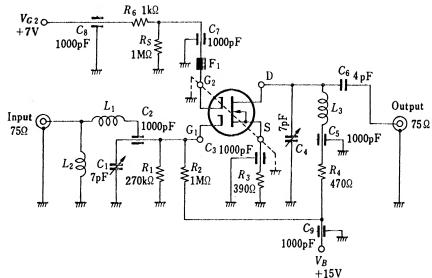


# 3SK116

#### IDSS ランク分類

1033 / /	/ / / / /		
	P	Q	R
IDSS (mA)	2.5~8	6~17	13~30

#### PG, NF 測定回路



 $L_1: 0.3\phi \text{ PUW} \quad 4.9\phi \ 3.5\text{T}$ 

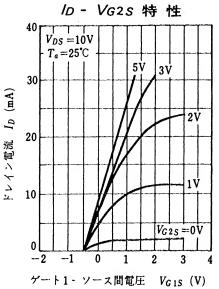
 $L_2: 0.3\phi \text{ PUW } 3.2\phi 1.5\text{T}$ 

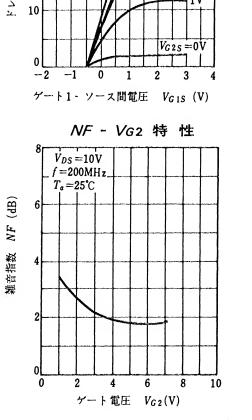
 $L_3: 0.3\phi \text{ PUW} \quad 3.2\phi \text{ 4.0T}$ 

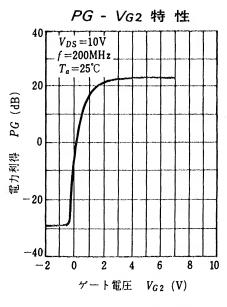
f = 200 MHz, BW : 8 MHz

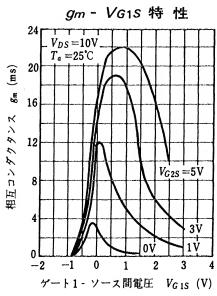
# Si MOS型. Nチャンネル







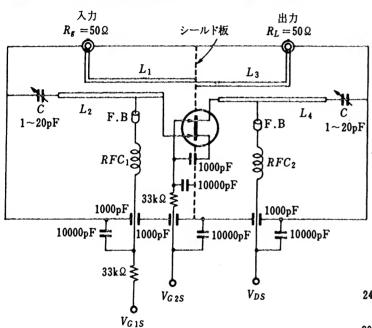




# GaAs 型 Nチャンネル

IDSS 区分 Y:20~35, GR:30~45 (mA)

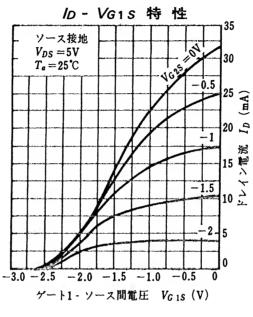
#### 電力利得, 雑音指数および GR 測定回路

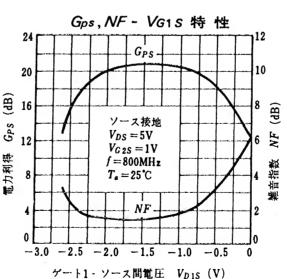


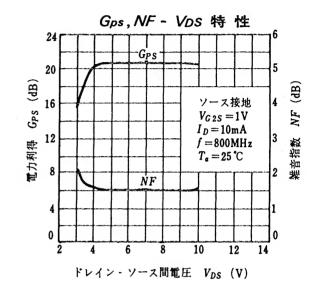
 $L_1 \sim L_4$ :  $\phi 0.8$ mm 銀メッキ線

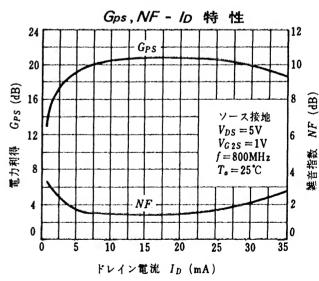
C : エアートリマ 村田 TTA 25A 200A

 $RFC_1$ :  $\phi 0.35$ mm UEW 3 ID 7T  $RFC_2$ :  $\phi 0.35$ mm UEW 3 ID 10T









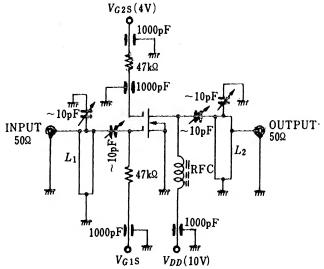
# 3SK123

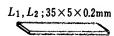
# Si MOS型 複合 N チャンネル

日電

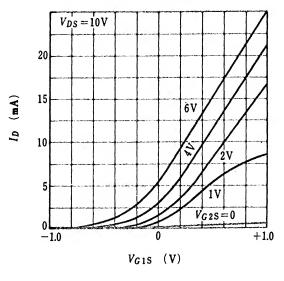
IDSS 区分 L:0.01~2mA K:1~6mA

#### 900MHz GPS, NF 測定回路

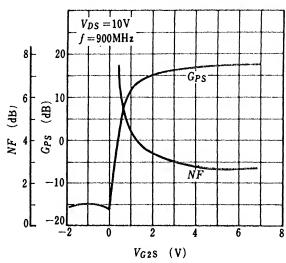




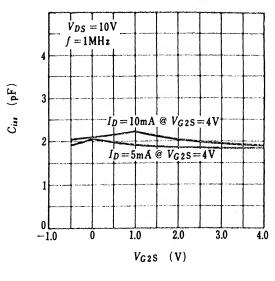
## ID - VGIS 特性



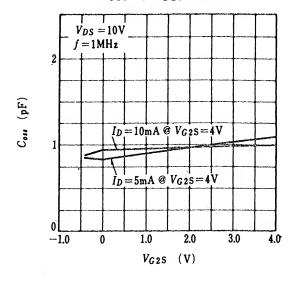
GPS, NF - VG2S 特性



Ciss - VG2S 特性

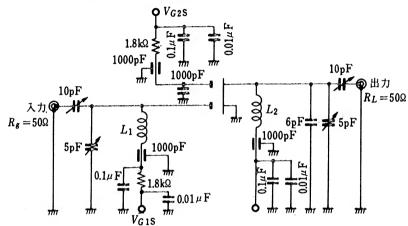


Coss - VG2S 特性



IDSS 区分 O:0~2mA, Y:1~6mA

## 200MHz 電力利得, 雑音指数 測定回路

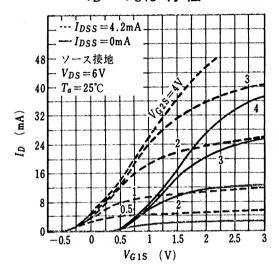


L1:1mmφ 銀メッキ銅線, 2T, 8mm 内径

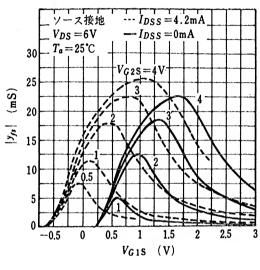
L2:1mm¢ 銀メッキ銅線, 2.5T, 8mm 内径

# Si MOS型 複合Nチャンネル

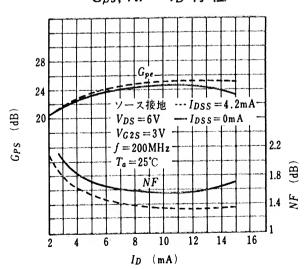
ID - VGIS 特性



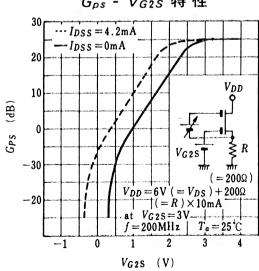
|Yfs| - VG1S 特性



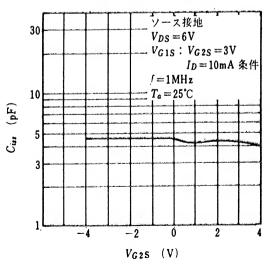
Gps, NF - ID 特性



Gps - VG2S 特性



Ciss - VG2S 特性



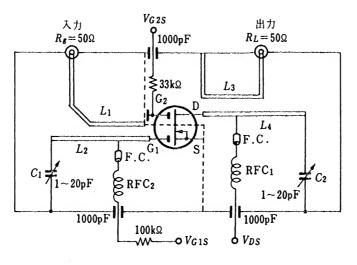
# Si MOS型 複合 Nチャンネル

#### 800MHz 電力利得, 雜音指数 測定回路

Ipss 区分

 $O:0\sim2mA$ 

Y:1~6mA



L1~L4: ø1.0mm 銀メッキ銅線

RFC<sub>1</sub> : Ø0.35mm 銅線, 7.0T, 内径 3mm RFC<sub>2</sub> : Ø0.35mm 銅線, 10.0T, 内径 3mm

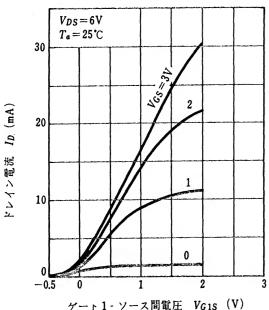
C1, C2: エアートリマ TTA 25A 200A

村田製作所あるいは相当品

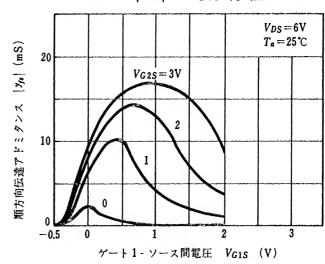
C3 : 1000pF (ディスクコンデンサ)

F.C. : フェライト・コア

In - Vais 特性



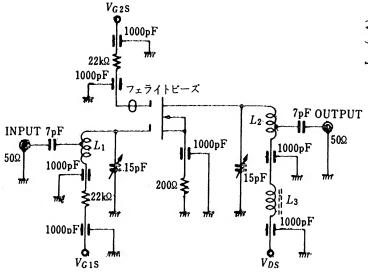
|Yfs| - VGIS 特性



Si MOS型 複合 N チャンネル 日電

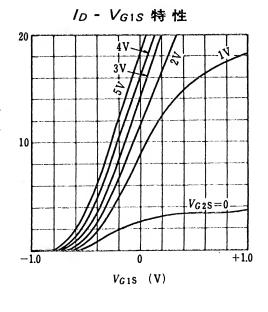
IDSS 区分 V10 7~13mA V11 11~19mA V12 17~25mA

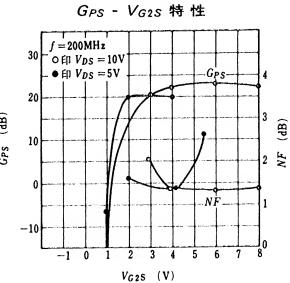
## 200MHz GPS, NF 測定回路

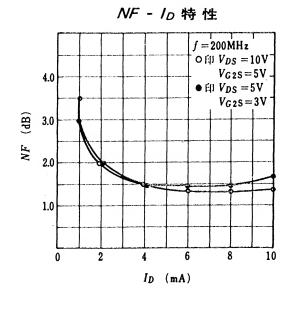


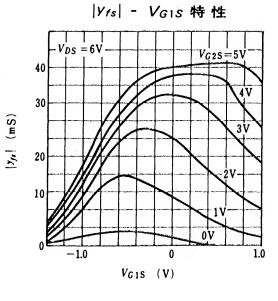
 $L_1: \phi 0.6 \text{mm} \text{ U.E.W. 7mm 3T}$  $L_2: \phi 0.6 \text{mm} \text{ U.E.W. 7mm 3T}$ 

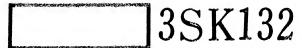
 $L_3$ : RFC 2.2 $\mu$ H







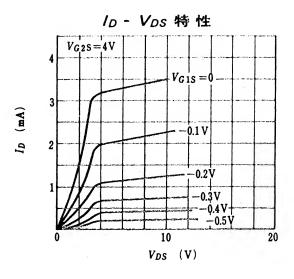


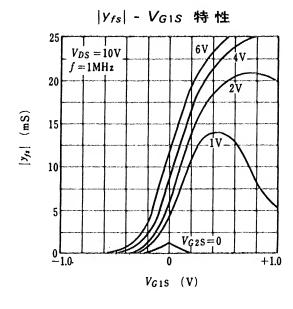


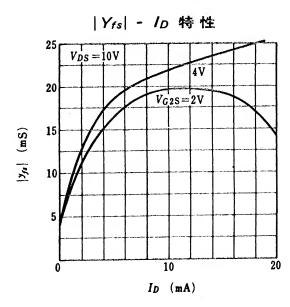
# Si MOS型 複合 N チャンネル

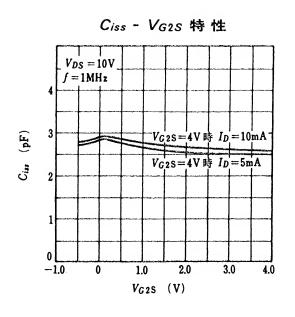
日電

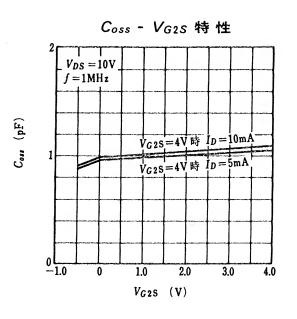
IDSS ランク U32 0.5~5mA U33 3~8mA



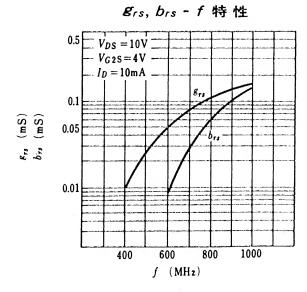




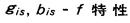


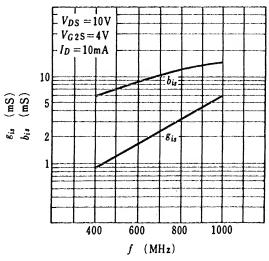


# GPS; $NF - V_{G2S}$ 特性 $\begin{pmatrix} gg \\ -10 \\ 2 \\ 2 \\ -20 \\ 0 \end{pmatrix}$ $\begin{pmatrix} gg \\ -10 \\ 2 \\ 2 \\ -20 \\ 0 \end{pmatrix}$ $\begin{pmatrix} gg \\ -10 \\ 2 \\ 4 \\ 6 \\ 8 \\ 10 \end{pmatrix}$



# Si MOS型 複合 N チャンネル

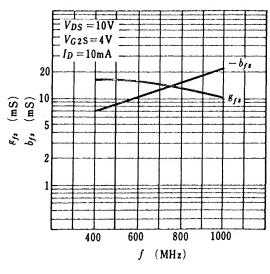




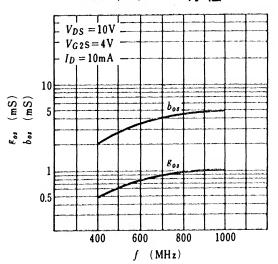
Bfs, bfs - f 特性

E

電



gos, bos - f 特性



3SK140

# Ga As MES型 複合 Nチャンネル

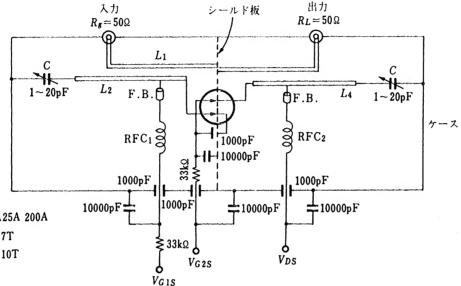
東 芝

#### 電力利得, 雑音指数および GR 測定回路

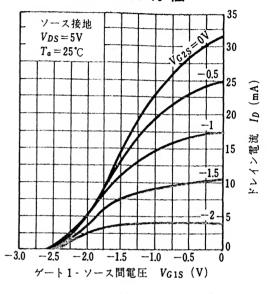
#### Ipss 区分

 $Y:20\sim35mA$ 

GR: 30~45mA



#### ID - VGIS 特性

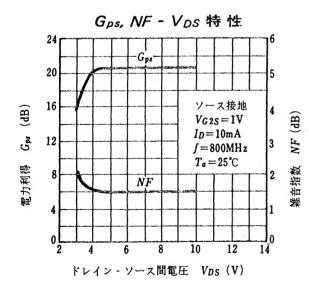


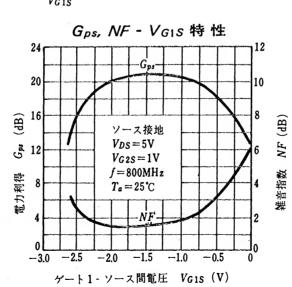
## L1~L4: 0.8mmø 銀メッキ線

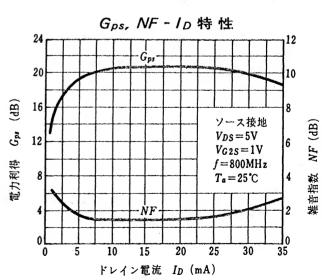
C : エアートリマ 村田 TTA25A 200A

RFC<sub>1</sub> : 0.35mm¢ UEW 3I. D. 7T

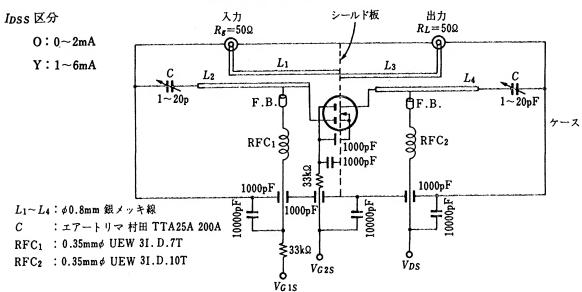
RFC<sub>2</sub>: 0.35mmø UEW 3I. D. 10T

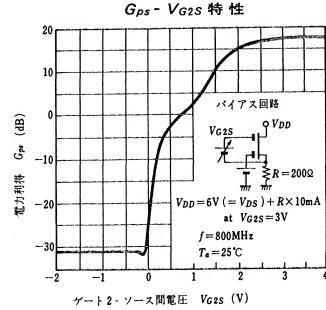


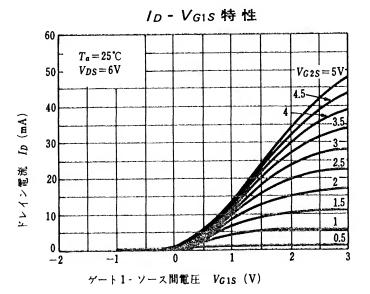


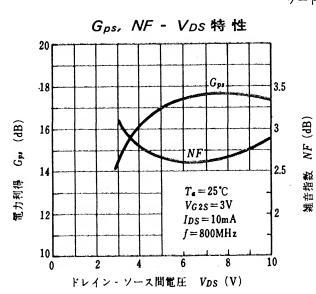


#### 電力利得および雑音指数測定回路









3SK150,151

# Si MOS型 複合Nチャンネル

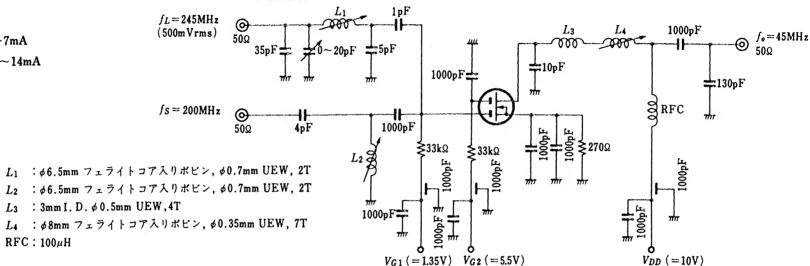
芝 東

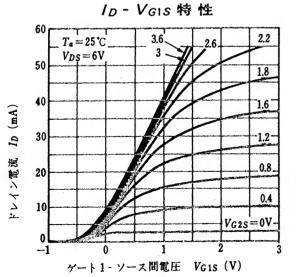


Ipss 区分

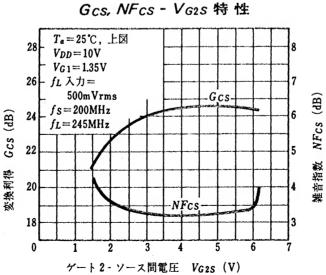
 $Y:3\sim7mA$ 

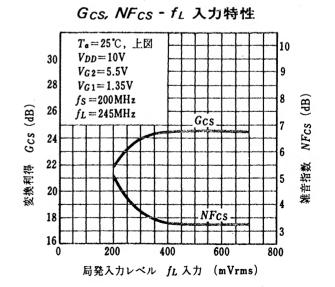
GR: 6~14mA





RFC: 100 µH





NFmin (dB)

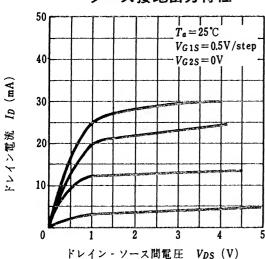
最小維音指数

(dB)

 $G_{\mathbf{S}}$ 

維音最小電力利得

#### ソース接地出力特性

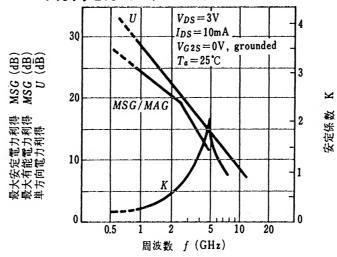


#### 最小雑音指数, 雑音最小電力利得

# 

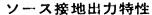
# Ga As型 複合 Nチャンネル

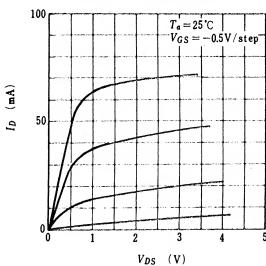
最大安定電力利得,最大有能電力利得, 単方向電力利得,安定係数 - 周波数特性



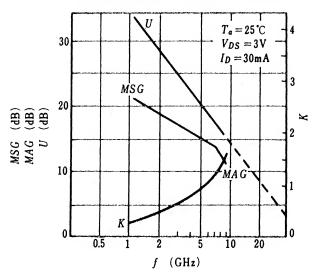
MGF1202

GaAs 型 Nチャンネル 三菱

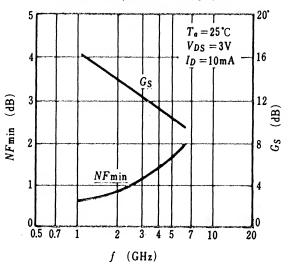


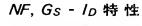


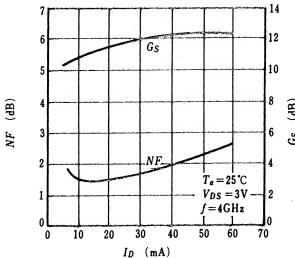
MSG, MAG, U, K-f特性

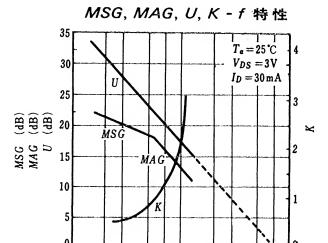


NFmin, Gs - f 特性







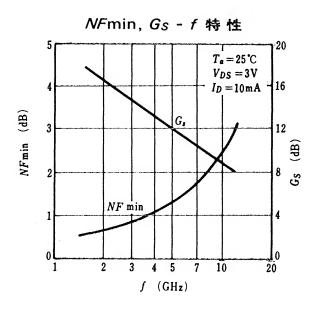


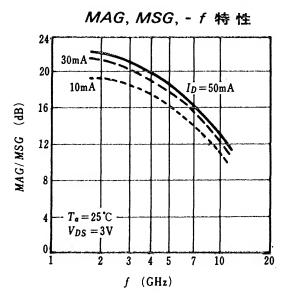
5 7 10

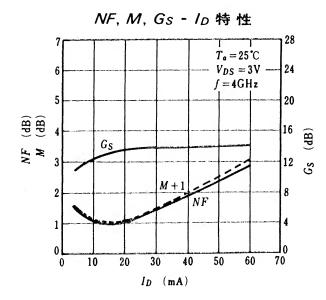
f (GHz)

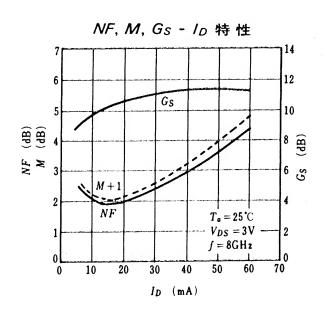
20 30

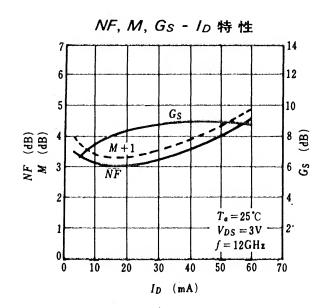
50 70 100

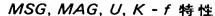


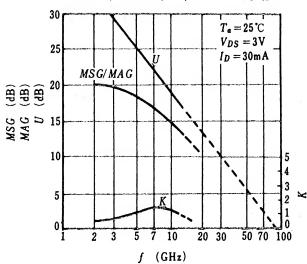




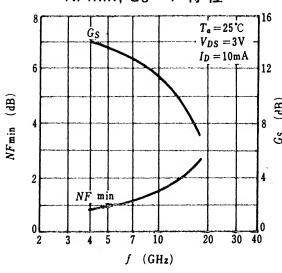




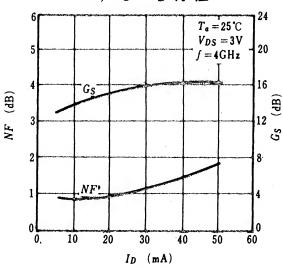




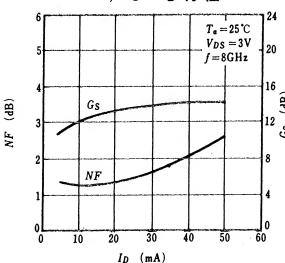
#### NFmin, Gs - f 特性



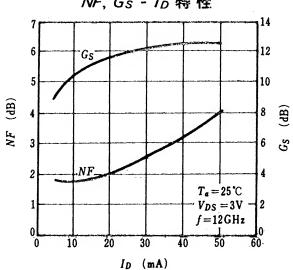
NF, Gs - ID 特性



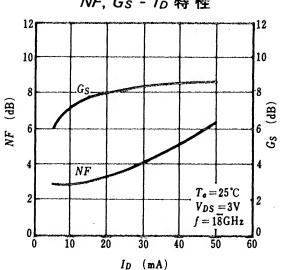
### NF, Gs - ID 特性



NF, Gs - 1D 特性



NF, Gs - ID 特性



(qB)

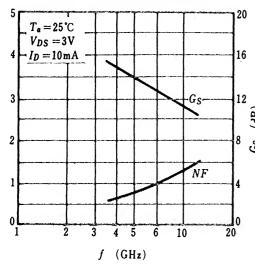
 $NF_{min}$ 

NF min

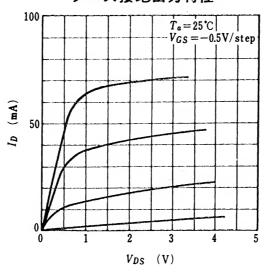
MGF1404, 1412

GaAs 型 Nチャンネル 三 菱

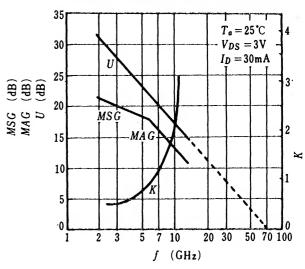
MGF1404 NFmin, Gs - f 特性



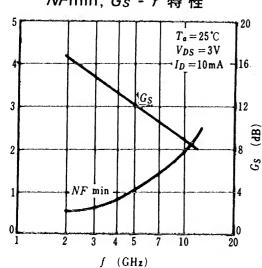
MGF1412 ソース接地出力特性



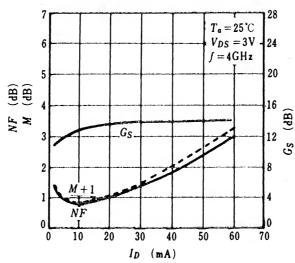
MGF1412 *MSG*, *MAG*, *U*, *K* - *f* 特性



MGF1412 NFmin, Gs - f 特性



MGF1412 *NF*, *M*, *Gs* - *I<sub>D</sub>* 特性

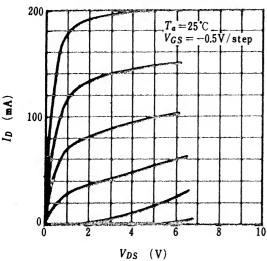


MGF1801, 1802

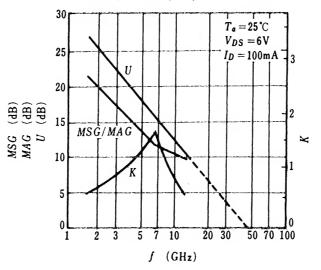
GaAs 型 Nチャンネル 三 菱



ソース接地出力特性

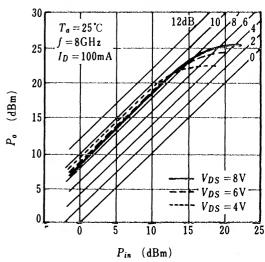


MGF1801 *MSG*, *MAG*, *U*, *K - f* 特性



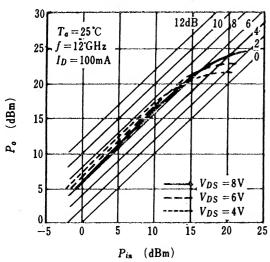
MGF1801

Po - Pin 特性



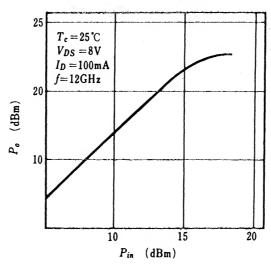
MGF1801

Po-Pin 特性



MGF1802

Po - Pin 特性

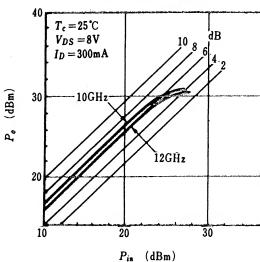


# MGF2124, F, G

GaAs 型 三 Nチャンネル

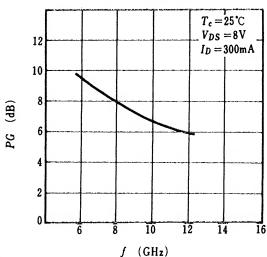


Po-Pin 特性



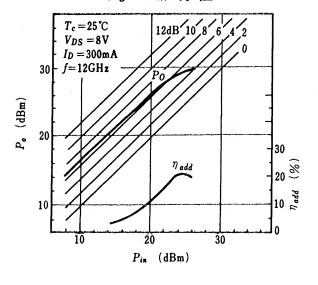
MGF2124

**GP-f特性** 



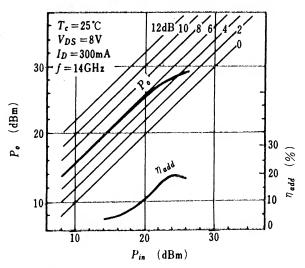
MGF2124F, G Po - Pin 特性

菱



MGF2124F, G

Po - Pin 特性

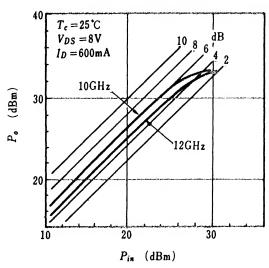


# JMGF2148, F, G

# Ga As 型 Nチャンネル

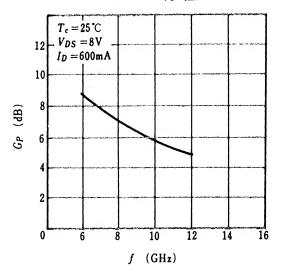
三 菱

MGF2148

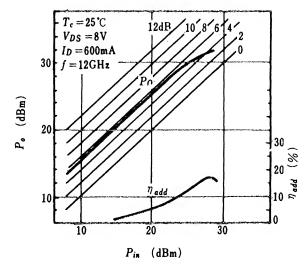


MGF2148

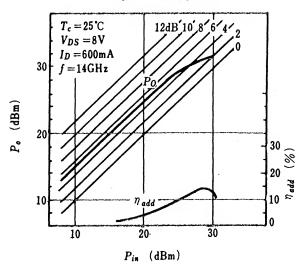
Gp - f 特性



MGF2148F, G



MGF2148F, G

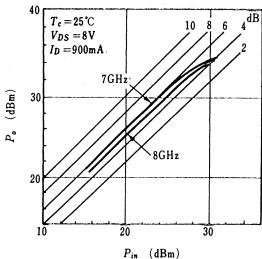


# MGF2172,2205,X34M GaAs型 Nチャンネル



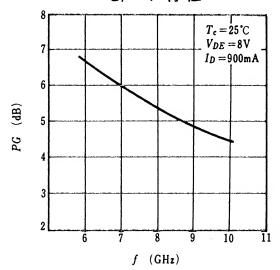




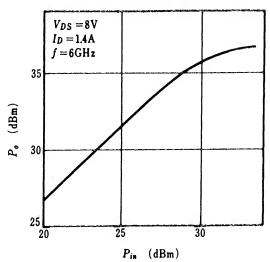


MGF2172

Gp - f 特性

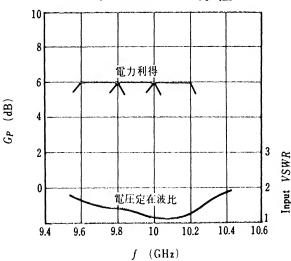


MGF2205

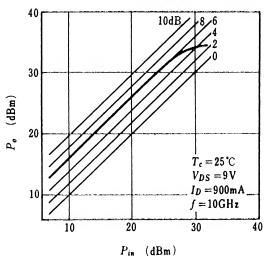


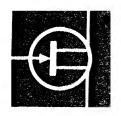
MGF - X34M

GP, VSWR - f 特性



MGF - X34M





パワーMOS FET 主要規格一覧表 (外国製)

## 規格表の見方

(1) 社名

ITS: Intersil Inc.

RCA: RCA Corp.

SL: Siliconix Inc.

SPT: Supertex Inc.

- (2) チャネルの欄の P/Nは、1 パッケージ内に P チャネルとNチャネルの両方のFETが入 っていることを示します。
- (3) 最大消費電力の欄の/Uは、1パッケージ内 に複数個入っているFETの、1個当りの最 大消費電力を示します。
- (4) 外囲器の欄のPDIP, CDIPは, それぞれプラスチックDIP, セラミックDIPのことです.
- (5) 備考の欄の"\*"は、1パッケージ内のFETの 個数を示します。

		最大消費		流ドレイン電流(A)			ドレイン・ソース間耐圧 (V) 最大値			+				
備考	外 囲 器	電力(W)	10.1	5.1	3.1	1.1	eng manikah diserda serimangkan (landrock - girdi)	501	301	101		ヤオ	社名	型名
		$Tc = 25^{\circ}C$	\$	10.0	5.0	3.0	1.0	1000	500	300	100	ル		
	TO-3	25				2					35	N	SL	2N6656
	TO-3	25				2					60	N	SL	2N6657
	TO-3	25				1.9					90	N	SL	2N6658
	TO-39	6.25				1.4					35	N	SL	2N6659
	TO-39	6.25				1.2					60	N	ITS	2N6660
	TO-39	6.25				1.1					60	N	SPT	2N6660
	TO-39	6.25				1.1					60	N	SL	2N6660
	TO-39	6.25				1.2		- 3			90	N	ITS	2N6661
	TO-39	6.25					0.9				90	N	SPT	2N6661
	TO-39	6.25	- Carlotte and Car				0.9				90	N	SL	2N6661
2SK*8	PDIP18P	1.5/U					0.03	participation of minimum in the configuration of th		200		N	SPT	ANO120NA
2SK*8	CDIP18P	2/U			and the Control of th		0.04			200	_	N	SPT	ANO120NB
CHIP										200	A CONTRACTOR OF STREET	N	SPT	ANO120ND
2SK*8	PDIP18P	1.5/U					0.03			300		N	SPT	ANO130NA
2SK*8	CDIP18P	2/U					0.04			300	Aug Service Ann and Commission of the Service	N	SPT	ANO130NB
CHIP			-							300		N	SPT	ANO130ND
2SK*8	PDIP18P	1.5/U	And the second second	The State of the S			0.03		400			N	SPT	ANO140NA
2SK*8	CDIP18P	2/U	And the second second second second second				0.04		400	<b></b>		N	SPT	NO140NB
CHIP			***************************************						400			N	SPT	NO140ND
2SJ*8	PDIP18P	1.5/U	, ,				015			-200	<b> </b>	P	SPT	AP0120NA
2SJ*8	CDIP18P	2/U					015			-200		P	SPT	AP0120NB
CHIP	and the first the second second second second second second second second second second second second second se									-200		P	SPT	AP0120ND
2SJ*8	PDIP18P	1.5/U					015			-300		P	SPT	AP0130NA
2SJ*8	CDIP18P	2/U					015			-300		P	SPT	P0130NB
CHIP	vienda viitation (1975) kai viinin kais viinin kaitelinen kappavaa piininka valta see ta Million (1975). T									-300		P	SPT	AP0130ND
2SJ*8	PDIP18P	1.5/U					015		-400		<del>                                     </del>	P	SPT	P0140NA
	CDIP18P						015		-400			P	SPT	P0140NB
CHIP		<u> </u>							-400		1	P	SPT	P0140ND
	TO-237	2					0.7				80	N	ITS	NV5000ANF
	TO-237	<u> </u>					0.7				100	N	ITS	NV5000ANH

		チ	ドレー	イン・ソー	ス間耐圧	(V)		最大直流	ドレイン	√電流(A	)	最大消費			**************************************
型名	社名	ヤネル	} 100	101 \$ 300	301 500	501 { 1000	ر 1.0	1.1	3.1 5.0	5.1	10.1	電力(W) Tc=25°C	外 囲 器	備	考
INV5001TND	ITS	N	40	300	500	1000	1.0	1.2		10.0		6.25	TO-39		
IRF120	SL	N	100					1.2		8			TO-33		
IRF121	SL	N	60	<b> </b>				<b>_</b>		8			TO-3		
IRF122	SL	N	100							7			TO-3		
IRF123	SL	N	60					-		7			TO-3		
IRF130	RCA	N	100								14	75	TO-204AE/AA		
IRF130	SL	N	100								14	75	TO-3		-
IRF131	RCA	N	60				ne gegagi sinagagan energe dia deningi di di dia sinda				14	75	TO-204AE/AA		
IRF131	SL	N	60				a balak Piranti Milatan Albandar Pira . Amerikaan A				14	75	TO-3		
IRF132	RCA	N	100				44,94,79, 450. BY BOX				12	75	TO-204AE/AA		
IRF132	SL	N	100								12	75	TO-3		
IRF133	RCA	N	60								12	75	TO-204AE/AA		
IRF133	SL	N	60								12	75	TO-3		
IRF140	SL	N	100								27	125	TO-3		
IRF141	SL	N	60				The second secon				27	125	TO-3		
IRF142	SL	N	100								24	125	TO-3		
IRF143	SL	N	60				The same the life CO September China & Colonbus				24	125	TO-3		
IRF150	SL	N	100					a company of the second second			40	150	TO-3		
IRF151	SL	N	60			Charles and Astronomy Street,	The second section of the second section of the sec				40	150	TO-3		
IRF152	SL	N	100								33	150	TO-3		
IRF153	SL	N	60				and have recent and the same an				33	150	TO-3		
IRF220	SL	N		200					5			40	TO-3		
IRF221	SL	N	-	150					5			40	TO-3		
IRF222	SL	N		200			and the second s		4			40	TO-3		
IRF223	SL	N		150					4			40	TO-3		
IRF230	SL	N		200						9		75	TO-3		
IRF231	SL	N		150			The second secon			9		75	TO-3		
IRF232	SL	N		200			AMERICAN PROPERTY.			8		75	TO-3		
IRF233	SL	N		150						8		75	TO-3		
IRF240	SL	N		200							18	125	TO-3		

	rita Africantin attingo o y utigo ot graffic Magazing		+	ドレ	イン・ソー	- ス間耐圧	(V)		最大直流	たドレイ:	ン電流(A	7)	最大消費			
型	名	社名	ヤネル	, 100	101 \$ 300	301 500	501 \$ 1000	, 1.0	1.1 \$ 3.0	3.1 5.0	5.1 , 10.0	10.1	電力(W) Tc=25°C	外 囲 器	備	考
IRF241		SL	N		150						tratafia (Latinorminorminofilità cabian, auto, australia	18	125	TO-3	Ÿ	
IRF242	antika da kalangan antan da kalangan da kalangan da kalangan da kalangan da kalangan da kalangan da kalangan d	SL	N	ter Saudinahilihingan SWENSAMA wakeruse Francis	200		- maneria anticon metalantente	e eth e house. Van vorreie en der der sommen skal	and the state of t			16	125	TO-3		
IRF243		SL	N		150			- Andrewson Andrewson W. B.				16	125	TO-3		
IRF250	Tatanama vid attantistica de Taya	SL	N	***************************************	200		Language Marine Marine Marine Control of the Contro	The second section of the second seco				30	150	TO-3		
IRF251	an and distributed by the order of the state	RCA	N		150			arrithminus and an environment of				30	150	TO-204AE/AA		
IRF251		SL	N		150		A	Andreadale Anna and Communication Communicat				30	150	TO-3		
IRF252		SL	N		200			THE RESERVE AND ADDRESS OF THE PARTY OF THE				25	150	TO-3		
IRF253		RCA	N		150			na kana ang kananana ang kananana ang kananana ang kananana ang kananana ang kananana ang kanananana ang kanan				25	150	TO-204AE/AA		
IRF253	-	SL	N		150			***************************************				25	150	TO-3		and a second
IRF320		SL	N			400	AND AND AND AND AND AND AND AND AND AND		3				40	TO-3		
IRF321		SL	N			350		received a service of the service of	3				40	TO-3		
IRF322		SL	N			400	AND THE PERSON NAMED AND ADDRESS OF	The second second second second second second second second second second second second second second second se	2.5				40	TO-3		
IRF323	***************************************	SL	N			350		***************************************	2.5				40	TO-3		
IRF330		SL	N		tera periorita de la completa del completa de la completa del completa de la completa del la completa del la completa de la completa de la completa del la completa de la completa de la completa del la completa del la completa del la completa del la completa del la completa del la completa del la completa del la completa	400	.,				5.5		75	TO-3		
IRF331		SL	N			350					5.5		75	TO-3		and the same and the same at
IRF332		SL	N	Table		400		-		4.5			75	TO-3		
IRF333		SL	N			350		And and the second between the second		4.5			75	TO-3		
IRF340		SL	N			400	***************************************			1		10	125	TO-3		
IRF341		SL	N			350				· · ·	10		125	TO-3		
IRF342		SL	N	and Managing to the control of the c		400		andrewen der Meisen auf Grant Photos de Aude Wildere			8		125	TO-3		
IRF343		SL	N			350		and the control of th			8		125	TO-3		
IRF350		SL	N	e de Primario de 18 de 19 - 18 de 19		400						15	150	TO-3		
IRF351		SL	N			350		alligation and pay to pay to the control of the same				15	150	TO-3		
IRF352		SL	N			400		00 - 40 - 40 - 40 - 40 - 40 - 40 - 40 -			-	13	150	TO-3		
IRF353		SL	N			350		The same of the sa				13	150	TO-3		
IRF420		RCA	N			500		marana nanara diana dia 1860 Marie Cadelle dia 187	2.5				40	TO-204AE/AA		
IRF420		SL	N			500			2.5				40	TO-3		
IRF421		RCA	N			450			2.5				40	TO-204AE/AA		
IRF421		SL	N			450			2.5				40	TO-3		
IRF422		RCA	N			500			2				40	TO-204AE/AA		

				<del></del> チ	ドレー	イン・ソー	・ス間耐圧	(V)		最大直流	ドレイン	·電流(A	)	最大消費			TOPON, POSTA DE POSTA DE LA PONTA DELA PONTA DEL PONTA DE LA PONTA DEL PONTA DE LA PONTA DEL PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DEL PONTA DEL PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DE LA PONTA DEL PONTA DEL PONTA DEL PONTA DEL PONTA DEL PONTA DEL PONTA DEL PONTA DEL PONTA DEL PONTA DEL PONTA DEL
型	名	社 4	名	ヤネル	, 100	101 \$ 300	301 5 500	501 \$ 1000	} 1.0	1.1 \$ 3.0	3.1 5.0	5.1 \$ 10.0	10.1	電力(W) Tc=25℃		備	考
IRF422		SL		N			500			2				40	TO-3		
IRF423		RCA		N			450			2				40	TO-204AE/AA	9	
IRF423		SL		N			450			2				40	TO-3		
IRF430		SL		N			500				4.5			75	TO-3		
IRF431		SL		N			450				4.5			75	TO-3		
IRF432		SL		N			500		The second secon		4			75	TO-3		
IRF433		SL		N			450				4			75	TO-3		
IRF440		SL		N			500	***************************************				8		125	TO-3		
IRF441		SL		N	Anne de Maria de Caracteria de		450					8		125	TO-3		
IRF442		SL	1	N			500		an andreway of an operation of the state of			7		125	TO-3		
IRF443		SL		N		A TABLE OF THE PARTY OF THE PAR	450		and the second s			7		125	TO-3		
IRF450		SL		N			500						13	150	TO-3		
IRF451		SL		N			450			and the state of t			13	150	TO-3	a mia ambi alkima mingi, na ilikudiri	
IRF452		SL		N	THE RESIDENCE OF THE PARTY OF T		500		Account of the State of the Sta	na of Amiliania i Managament to the Matter Control of the second of the			12	150	TO-3	and the second second second second	
IRF453		SL		N	PERSONAL PROPERTY AND AND AND AND AND AND AND AND AND AND		450		THE COLD STREET, AND STREET, A	and the same of th			12	150	TO-3		***************************************
IRF510		RCA		N	100						4		and the second second second second	20	TO-220AB		
IRF511		RCA		N	60					-	4			20	TO-220AB		ATTENDED TO A STATE OF THE STAT
IRF512		RCA		N	100				ar attenuit turilinnin illinoimin peter 6,2% – 1863.		3.5				TO-220AB	THE PLANE SHE STATE OF THE PARTY OF THE PART	And Michigan Walks with
IRF513		RCA		N	60						3.5		A SANTON A CONTRACT OF THE SANTON STATE OF THE		TO-220AB	and the second of the second of the second	
IRF520		RCA	_	N	100						a demonstration of the second second	8		40	TO-220AB		
IRF520		SL		N	100							8		40	TO-220AB		
IRF521		RCA	1	N	60				and the second second second second second second			8		40	TO-220AB		
IRF521		SL		N	60							8		40	TO-220AB		
IRF522		RCA		N	100							7		40	TO-220AB		
IRF522	****************	SL		N	100							7		40	TO-220AB		
IRF523		RCA		N	60							7		40	TO-220AB	***************************************	ANTONIO MARIO
IRF523		SL		N	60			A STATE OF S	The second distribution of the second	-	CONTRACTOR STATE OF THE PARTY O	7		40	TO-220AB		M-M-2000-0-7
IRF530		RCA	_	N	100				Address Schools and Advantage of Control of Control				14	75	TO-220AB		A Maria Control Control
IRF530		SL	-	N	100				****************				14		TO-220AB	***	
IRF531		RCA	-	N	60				Chiamber and Parking Chiad D	Color and Maria and Maria and a first and a service of			14	75	TO-220AB	COLUMN TO SERVICE SERVICE	

and the second s			Ŧ	ドレ	イン・ソー	- ス間耐圧	(V)	angila anima na katana na katana na katana na katana na katana na katana na katana na katana na katana na kata	最大直流	<b>売ドレイ</b> :	ン電流(A	7)	最大消費			
型	名	社名	ヤネル	, 100	101 5 300	301 500	501 \$ 1000	1.0	1.1 3.0	3.1 5.0	5.1 \ 10.0	10.1	電力(W) Tc=25℃	外 囲 器	備	考
IRF531	Typing out to go may receive the	SL	N	60			The state of the s	gan, de angligiff (1000 100) per die en normal die Adurbieren der der des		mark 2 de la Control de la Con		14	75	TO-220AB		
IRF532	THE IN COLUMN 2. TO	RCA	N	100	American de constitue o Aline Admi			manager and the second				12	75	TO-220AB		san and the san and the san and
IRF532		SL	N	100								12	75	TO-220AB		
IRF533	Control to the Party Control	RCA	N	60			,	and the second s				12	75	TO-220AB		anantina nagara na Albana
IRF533		SL	N	60								12	75	TO-220AB		~~~~~
IRF540		SL	N	100	Pro- Act on the Sharehouse become the day to and							27	125	TO-220AB		
IRF541	THE PERSON NAMED IN	SL	N	60	A UP SUMMER OF THE PERSONNELS			AND AND ASSESSMENT OF THE PARTY				27	125	TO-220AB		
IRF542		SL	N	100								24	125	TO-220AB		
IRF543		SL	N	60								24	125	TO-220AB		
IRF620	ericalistic langua esta sena	SL	N		200			The second secon		5			40	TO-220AB		
IRF621		SL	N		150					5			40	TO-220AB		
IRF622		SL	N		200					4			40	TO-220AB		
IRF623		SL	N		150					4			40	TO-220AB		
IRF630		SL	N		200						9		75	TO-220AB		
IRF631		SL	N		150						9		75	TO-220AB		
IRF632		SL	N		200						8		75	TO-220AB		
IRF633		SL	N		150						8		75	TO-220AB		
IRF640	# 4. T 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	SL	N		200							18	125	TO-220AB		
IRF641		SL	N		150							18	125	TO-220AB		
IRF642		SL	N		200							16	125	TO-220AB		
IRF643		SL	N		150							16	125	TO-220AB		
IRF720		SL	N			400			3				40	TO-220AB		
IRF721		SL	N			350			3				40	TO-220AB		
IRF722		SL	N			400			2.5				40	TO-220AB		
IRF723		SL	N			350			2.5				40	TO-220AB		
IRF730		SL	·N			400					5.5		75	TO-220AB		
IRF731		SL	N			350					5.5		75	TO-220AB		
IRF732		SL	N	-		400				4.5			75	TO-220AB		
IRF733		SL	N			350		The second secon		4.5			75	TO-220AB		
IRF740		SL	N			400					10		125	TO-220AB		

				チ	ドレ	イン・ソー	・ス間耐圧	(V)		最大直流	ドレイン	ノ電流(A	)	最大消費			
型	名	社	名	ャネル	\$ 100	101 \$ 300	301 500	501 \$ 1000	, 1.0	1.1	3.1	5.1 \$ 10.0	10.1	電力(W) Tc=25°C	外 囲 器	備	考
IRF741		SL		N	100	300	350	1000				10		125	TO-220AB		
IRF742		SL		N			400				-	8		125	TO-220AB	<u> </u>	-
IRF743		SL		N N			350				-	8		125	TO-220AB		
IRF820		SL		N			500			2.5	<del> </del>			40	TO-220AB	1	
IRF821		SL		N N			450			2.5	<del>                                     </del>			40	TO-220AB	1	
IRF822		SL		N			500			2				40	TO-220AB	<u> </u>	was and the second
IRF823		SL		N			450		AND AND AND AND AND AND AND AND AND AND	2				40	TO-220AB		
IRF830		SL		N			500			1	4.5	1		75	TO-220AB		
IRF831		SL		N			450			1	4.5	<b>-</b>		75	TO-220AB		
IRF832		SL		N			500			1	4			75	TO-220AB		
IRF833		SL		N			450			-	4			75	TO-220AB		
IRF840		SL	$\neg$	N			500					8		125	TO-220AB		
IRF841		SL		N			450					8		125	TO-220AB		
IRF842		SL		N			500					7		125	TO-220AB		
IRF843		SL		N			450		Marian Carana de Carana de Carana de Carana de Carana de Carana de Carana de Carana de Carana de Carana de Car			7		125	TO-220AB		
IRF9130	0	SL		P	-100				***************************************				-12	75	T0-3		
IRF913	1	SL		P	-60								-12	75	TO-3		
IRF9132	2	SL		P	-100				Time and the same second	e talanan saara self-1900 (1900 - hassadhin mallet - 1900)		-10		75	TO-3		
IRF913:	3	SL		P	-60				and the second second second second			-10		75	TO-3		
IRF9520	0	SL		P	-100	andro alphanet per sprace African a since appear			MANAGE FOR THE SPACE			-6		40	TO-220AB		and the second second second second
IRF952	1	SL		P	-60				The same of the same and the same of the			-6		40	TO-220AB		A STATE OF THE PARTY OF THE PAR
IRF9522	2	SL		P	-100						-5	and the first Control of the Control		40	TO-220AB		
IRF9523	3	SL		P	-60				**************************************		-5			40	TO-220AB		
IRF9530	0	SL		P	-100	***************************************			**************************************		and a secure ordered to part of the second o		-12	75	TO-220AB		Carried Torque Carried
IRF953	1	SL		P	-60				Processing and the second second second second second second second second second second second second second	And the state of t			-12	75	TO-220AB		Marie La La Company
IRF9532	2	SL		P	-100			THE WANTE OF THE PARTY OF THE P	# Principle State Committee Committee	THE TRANSPORT OF THE PARTY OF T		-10	and the contract of the contra	75	TO-220AB		MANAGEMENT AND ALL AND MANAGEMENT
IRF9533	3	SL		P	-60		Makes (Market ) 1995 (Makes Million) and	Angele participate and the second second second second second second second second second second second second	po una <sub>pro</sub> positiva de la compositiva della com		erministen att ett attacke daer subm	-10	automorphism realization shares de-	75	TO-220AB		
IRFF120	0	SL		N	100	***************************************		COME AND RESTRICTED AND ADDRESS.	entre entre de la constitución d	A THE PERSON NAMED AND ADDRESS OF THE PERSON NAMED AND ADDRESS	Section - Section - Property and American	6	entrelli et represente trima autólia. El cumpo	20	TO-39		Miles when many live in a
IRFF12	1	SL		N	60		nagyay albi da Shirilla Yakirila da albinda da albinda da albinda da albinda da albinda da albinda da albinda d	THE APPEL STATEMENT AT USE OF THE	AL TOLLE SE ALAPATRICA DE TOLLES	and the second s		6		20	TO-39		argania and a second
IRFF122	2	SL		N	100	The additional control of the special control	e majorganistico committe de servicio y specimento de la committa de la committa de la committa de la committa		Marker of Property and American Street		5	Name and Address of State of the State of th	y ji Transacan (Maja Memper 1999)	20	TO-39		and the second sections

		الله المتحددة المتحددة المتحددة المتحددة المتحددة المتحددة المتحددة المتحددة المتحددة المتحددة المتحددة المتحد	£	ドレイ	イン・ソー	ス間耐圧	(V)		最大直流	ミドレイン	・電流(A)	)	最大消費	galangan ang kananda ang kananda ang kananda ang ang ang ang kananda an ang ang ang an ang		a a musi munggapina a u
型 1	名	社名	ヤネル	, 100	101 5 300	301 5 500	501 \( \) 1000	, 1.0	1.1 3.0	3.1 5.0	5.1 \ 10.0	10.1	電力(W) Tc=25°C	外囲器	備	考
IRFF123		SL	N	60		MARCHAN CONTRACTOR	and the second second second	Augusta Service (Marie Constitution of the Con	*	5			20	TO-39		A STATE OF THE REST
IRFF130		SL	N	100				Delication (Book) and an arrange			8		Andrew Street, and the supplier of the last of the las	TO-39	<b>†</b>	
IRFF132		SL	N	100		and the second response to the second determinant					7		the state of the s	TO-39		Annual control of
IVN5000A	ND	ITS	N	40		A MANUFACTURE STREET, STREET, STREET, STREET, STREET, STREET, STREET, STREET, STREET, STREET, STREET, STREET,	And the second control of the second control of the	0.7					the same of the sa	TO-237		-eye major in translate
IVN5000A	Contract on 1 meters but	ITS	N	60		THE RESERVE THE PROPERTY OF THE PERSON NAMED IN		0.7			THE CONTRACT OF STREET, STREET			TO-237		
IVN5000S		ITS	N	40		make have a Make of the special and with the		0.9					the same of the sa	TO-52	1	PARAMETERS
IVN5000S	distance of the second	ITS	N	60			and the second s	0.9						TO-52		CONTRACTOR AND ADDRESS OF THE PARTY NAME OF
IVN5000S		ITS	N	80		ring of the state		0.9			Annual State of the State of th			TO-52		ALL WINDS TO THE TAX
IVN5000S		ITS	N	100		and the state of t		0.9					3.13	TO-52		
IVN5000T		ITS	N	40					1.2				6.25	TO-39		
IVN5000T		ITS	N	60					1.2					TO-39		
IVN5000T		ITS	N	80					1.2					TO-39		
IVN5000T		ITS	N	100					1.2					TO-39		
IVN5001A	ND	ITS	N	40				0.7						TO-237		
IVN5001A	NE	ITS	N	60				0.7						TO-237		
IVN5001A	NF	ITS	N	80				0.7					2	TO-237		
IVN5001A	NH	ITS	N	100				0.7	0.5					TO-237		
IVN5001S	ND	ITS	N	40				0.9						TO-52		
IVN5001S	NE	ITS	N	60				0.9						TO-52		
IVN5001S	NF	ITS	N	80				0.9						TO-52		
IVN5001S	NH	ITS	N	100				0.9						TO-52		
IVN5001T	'NE	ITS	N	60					1.2				and the same of th	TO-39		
IVN5001T	NF	ITS	N	80					1.2					TO-39		
IVN5001T	'NH	ITS	N	100					1.2				the same of the sa	TO-39		
IVN5200H	ND	ITS	N	40						5				TO-66		
IVN5200H		ITS	N	60			- manufacture discount relief -			5				TO-66		
IVN5200H	NF	ITS	N	80						5			the state of the s	TO-66		
IVN5200H	NH	ITS	N	100						5				TO-66		
IVN5200K	ND	ITS	N	40						5				TO-3		
IVN5200K	NE	ITS	N	60						5			50	TO-3		

Andrew Street St	<del>and a man as the start of the </del>		+	ドレ	イン・ソー	ス間耐圧	(V)		最大直流	ドレイン	電流(A)	)	最大消費			
型	名	社名	ヤネ		101	301	501		1.1	3.1	5.1	10.1	電力(W)	外 囲 器	備	考
			1 1	100	300	500	1000	1.0	3.0	5.0	10.0	. }	$Tc = 25^{\circ}C$	_		
IVN5200	OKNE	ITS	N	80						5		and the sale of the State of th	50	TO-3		
IVN5200		ITS	N	100						5			50	TO-3		
IVN5200		ITS	N	40				Control of the Contro		4			12.5	TO-39		
IVN5200		ITS	N	60				The second secon		4			12.5	TO-39		
IVN5200		ITS	N	80						4			12.5	TO-39		
IVN5200		ITS	N	100						4			12.5	TO-39		*
IVN5201		ITS	N	40						5			30	TO-220		
IVN5201		ITS	N	60						5			30	TO-220		
IVN5201		ITS	N	80				and the many of the same of the same		5			30	TO-220		
IVN5201		ITS	N	100						5			30	TO-220		
IVN5201	1HND	ITS	N	40						5			30	TO-66		
IVN5201	1 HNE	ITS	N	60						5			30	TO-66		
IVN5201	1HNF	ITS	N	80						5			30	TO-66		
IVN5201	1HNH	ITS	N	100	The second secon					5				TO-66		
IVN5201		ITS	N	40						5				TO-3		
IVN5201	IKNE	ITS	N	60		and the second s				5				TO-3		
IVN5201	1KNF	ITS	N	80						5			50	TO-3		
IVN5201	1KNH	ITS	N	100						5			50	TO-3		and the second second second
IVN5201	1TND	ITS	N	40						4			12.5	TO-39		
IVN5201	ITNE	ITS	N	60			a management of the second of the second			4			12.5	TO-39		
IVN5201	ITNF	ITS	N	80						4			12.5	TO-39		
IVN5201	ITNH	ITS	N	100						4				TO-39		\$65 078 0 5 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0
IVN6000	CNS	ITS	N			400		Andreas Commission of the Party	2 2					TO-220		
IVN6000		ITS	N			450			2					TO-220		
IVN6000	CNU	ITS	N		Complete the second sec	500		and the same the second	1.75					TO-220		
IVN6000	OKNR	ITS	N			350			2.5					TO-3		-
IVN6000	OKNS	ITS	N			400			2.5					TO-3		
IVN6000	OKNT	ITS	N			450			2.5					TO-3		
IVN6000	OKNU	ITS	N			500		AND THE PERSON NAMED IN COLUMN TWO IS NOT	2					TO-3		
IVN6000	TNS	ITS	N			400		1					12.5	TO-39		

<del>ga ga ang ang ang ang ang ang ang ang an</del>		チ	ドレ	イン・ソー	- ス間耐圧	E (V)		最大直流	ミドレイン	·電流(A)		最大消費			
型名	社名	ヤネル	, 100	101 \$ 300	301 500	501 \$ 1000	, 1.0	1.1 3.0	3.1 5.0	5.1 \$ 10.0	10.1	電力(W) Tc=25°C	外囲器	備	考
IVN6000TNT	ITS	N	and a second of the second of	************	450		1	a contraction of the state of t				12.5	TO-39		
IVN6000TNU	ITS	N	of the Control of the		500		0.9					12.5	TO-39		
IVN6100TNS	ITS	N			400	and the second s	0.3					6.25	TO-39		
IVN6100TNT	ITS	N			450		0.3					6.25	TO-39		mar Montale or James open green
IVN6100TNU	ITS	N			500		0.3					6.25	TO-39		****
IVN6200CNE	ITS	N	60					No. and Administration of the		10		100	TO-220		
IVN6200CNF	ITS	N	80							10		100	TO-220		
IVN6200CNH	ITS	N	100	with refresh, and care circles at the con-		*				10		100	TO-220		
IVN6200CNM	ITS	N		200						10		100	TO-220		
IVN6200CNP	ITS	N	Andrew State Control of	250	n en en en en en en en en en en en en en					10		100	TO-220		
IVN6200CNS	ITS	N		and the second second second second second	400				5			100	TO-220		
IVN6200CNT	ITS	N		The second secon	450				5			100	TO-220		
IVN6200CNU	ITS	N	1		500		a and the property of the same	a angle Apparite Marie Marie Marie (Marie )	5			100	TO-220		
IVN6200CNW	ITS	N				700		3				100	TO-220		
IVN6200CNX	ITS	N	A. S. Commercial Control of Contr			800	and which distributed the paper represents the same for the	2				100	TO-220		
IVN6200KNE	ITS	N	60							10		100	TO-3		
IVN6200KNF	ITS	N	80							10		100	TO-3		
IVN6200KNH	ITS	N	100					the state of the s		10		100	TO-3		
IVN6200KNM	ITS	N		200	ļ					10		100	TO-3		
IVN6200KNP	ITS	N		250						10		100	TO-3		
IVN6200KNS	ITS	N	<u> </u>		400				5			100	TO-3		
IVN6200KNT	ITS	N	and the second s	İ	450				5			100	TO-3		
IVN6200KNU	ITS	N	1		500				5			100	TO-3		
IVN6200KNW	ITS	N	1			700		3				100	TO-3		
IVN6200KNX	ITS	N				800		2.5	1			100	TO-3		
IVN6300ANE	ITS	N	60				0.25				***************************************	1.5	TO-237		
IVN6300ANF	ITS	N	80				0.25				and the second s	1.5	TO-237		
IVN6300ANH	ITS	N	100				0.25					1.5	TO-237		
IVN6300ANM	ITS	N		200			0.12	1	1			1.5	TO-237		page and the second sec
IVN6300ANP	ITS	N		250			0.12					1.5	TO-237		

		チ	ドレ	イン・ソー	- ス間耐圧	E (V)		最大直流	ミドレイン	 √電流( <i>A</i>	A)	最大消費		
型名	社 名	ヤネル	, 100	101 5 300	301 5 500	501 \$ 1000	, 1.0	1.1 \$ 3.0	3.1 5 5.0	5.1 5 10.0	10.1	電力(W) Tc=25°C		備考
IVN6300ANS	ITS	N			400		0.1					1.5	TO-237	
IVN6300ANT	ITS	N			450		0.1					1.5	TO-237	-
IVN6300ANU	ITS	N			500		0.1					1.5	TO-237	
IVN6300SNE	ITS	N	60				0.25					1.5	TO-52	
IVN6300SNF	ITS	N	80				0.25					1.5	TO-52	
IVN6300SNH	ITS	N	100				0.25					1.5	TO-52	
IVN6300SNM	ITS	N		200		AND THE RESIDENCE OF THE PARTY	0.12					1.5	TO-52	
IVN6300SNP	ITS	N		250			0.12					1.5	TO-52	
IVN6300SNS	ITS	N			400		0.1					1.5	TO-52	
IVN6300SNT	ITS	N			450		0.1				1	1.5	TO-52	
IVN6300SNU	ITS	N			500		0.1				<b></b>	1.5	TO-52	
IVN6660	ITS	N	60					1.2				6.25	TO-39	
IVN6661	ITS	N	90				***************************************	1.2				6.25	TO-39	
OCF25N18	RCA	N		180							25			CHIP
PCF10N12	RCA	N		120						10				CHIP
PCF10N45	RCA	N			450	and the production of the subdivine on the subdivine of t	a de la companya de l			10				CHIP
PCF12N08	RCA	N	80			ALIC ST. MAN (1) MAN (1) MAN (1) MAN (1)	10 - 2 - 10 - 10 - 2 - 2 - 2 - 2 - 2 - 2 - 2 - 2 - 2 -				12		and the second s	CHIP
PCF12N18	RCA	N		180							12			CHIP
PCF12P08	RCA	P	-80	AND THE RESIDENCE OF THE PARTY.		and the second of the second o		A CONTRACTOR OF THE STATE OF TH			-12			CHIP
PCF15N05	RCA	N	50				and the section of th			Andrea and the second of the second of	15			CHIP
PCF15N12	RCA	N	an an annual series and an annual series	120			an material control of a section of the section of	and the second s			15			CHIP
PCF18N08	RCA	N	80					and the control of th			18			CHIP
PCF2N05	RCA	N	50				The State of the S	2					-	CHIP
PCF2N08	RCA	N	80				and the same of th	2	ar the agent of the grant of th			A CONTRACTOR CONTRACTO		CHIP
PCF2N12	RCA	N		120		and the second s	and the second of the second second of the s	2	and providing and other springers, agency	en alle de la companya de la company				CHIP
PCF2N18	RCA	N	er territor - territor de la cercingua maschina per la	180	and the second	emercian magazinian a cara	attivitimi applittingajasting apotivistas vysivitinga vagativi	2	AND AND AND AND AND APPROXIMATION AND AND AND AND AND AND AND AND AND AN	and the second s		and the second s	antinostica antinostica, applicationa, professori, seguinator copes, emperanto a deconstruir de membra	CHIP
PCF30N12	RCA	N		120	The same of the sa		erikana darim duni in Managa da un untuk mendu	- Transfer of the second of the second	artina ar to produce and artists of the	WATER TO SEE ASSESSMENT TO SEE	30			CHIP
PCF35N08	RCA	N	80		ALLE AND TO A THE SECTION OF THE SECTION OF		CONTRACT TWO SAME ACTOR ASSESSMENT AND ASSESSMENT ASSES		ad harmaterial term to particulate of the	an industrial de la finition de la f	35		and the second s	CHIP
PCF3N45	RCA	N	Marie la list distribute la state consultant a		450		anne area area area area area area.	3		Tradical control of the second			na die in de promise des genérales en des la reconstruction de la reconstruction de la reconstruction de la rec	CHIP
PCF45N05	RCA	N	50	Commence of the second second							45			CHIP

		£	ドレー	イン・ソー	ス間耐圧	(V)		最大直流	ミドレイン	√電流(A	)	最大消費		
型名	社名	ヤネル	, 100	101 5 300	301 500	501 5 1000	, 1.0	1.1 5 3.0	3.1 5.0	5.1 5 10.0	10.1	電力(W) Tc=25°C	外 囲 器	備考
PCF5P12	RCA	P		-120		A CONTRACTOR OF THE PARTY OF TH			-5				gardenteranteranteranteranteranteranteranter	CHIP
PCF6P08	RCA	P	-80			Committee of the commit				-6				CHIP
PCF8N18	RCA	N	The state of the s	180	Provide Sport Published Addition of Provide Provide Sport					8				CHIP
PCF8P08	RCA	P	-80							-8				CHIP
RFH25P08	RCA	P	-80	Securitaria Managementa de Carlo Securitaria							-25		_	
RFH25P10	RCA	P	-100					- Secretaria di Hamiltonia 1984			-25			
RFH30N12	RCA	N		120		and the same of the same					30	_		
RFH30N15	RCA	N		150	-						30			
RFK10N45	RCA	N	A STATE OF THE PARTY OF THE PAR		450					10		150	TO-204AE	
RFK10N50	RCA	N			500		Annual of the second second second second	The state of the s		10		150	TO-204AE	
RFK25N18	RCA	N		180							25	150	TO-204AE	
RFK25N20	RCA	N	AND AND AND ASSESSMENT OF MALE AND ASSESSMENT AND ASSESSMENT AND ASSESSMENT A	200							25	150	TO-204AE	
RFK25P08	RCA	P	-80							and the same parameters are the pro-	-25	150	TO-204AE	
RFK25P10	RCA	P	-100				AND THE RESERVE THE PROPERTY OF THE PROPERTY O				-25	150	TO-204AE	
RFK30N12	RCA	N		120		and the second s					30	120	TO-204AE	
RFK30N15	RCA	N		150		an and the second secon					30	120	TO-204AE	
RFK35N08	RCA	N	80								35	150	TO-204AE	
RFK35N10	RCA	N	100	and the second s							35	150	TO-204AE	
RFK45N05	RCA	N	50								45	150	TO-204AE	
RFK45N06	RCA	N	60	and the second s							45	150	TO-204AE	
RFL1N08	RCA	N	80				1					8.33	TO-39	
RFL1N08L	RCA	N	80		a management of the second section of		1					8.33	TO-39	LL=5V
RFL1N10	RCA	N	100				1					8.33	TO-39	
RFL1N10L	RCA	N	100				1						TO-39	LL=5V
RFL1N12	RCA	N	and the second s	120			1					8.33	TO-39	
RFL1N12L	RCA	N		120			1					8.33	TO-39	LL=5V
RFL1N15	RCA	N		150			1					8.33	TO-39	
RFL1N15L	RCA	N	1	150			1					8.33	TO-39	LL=5V
RFL1N18	RCA	N		180			1					8.33	TO-39	
RFL1N18L	RCA	N		180								8.33	TO-39	LL=5V

		チ	ドレ	イン・ソー	ス間耐圧	(V)		最大直流	ドレイン	·電流(A	)	最大消費		
型名	社 名	ャネル	\$ 100	101 \$ 300	301 \$ 500	501 \$ 1000	\$ 1.0	1.1 \$ 3.0	3.1 5 5.0	5.1 \$ 10.0	10.1	電力(W) Tc=25℃	外 囲 器	備考
RFL1N20	RCA	N		200			1					8.33	TO-39	
RFL1N20L	RCA	N		200								8.33	TO-39	LL=5V
RFL1P08	RCA	P	-80				-1						TO-220	
RFL1P10	RCA	P	-100				-1						TO-220	
RFL2N05	RCA	N	50					2				8.33	TO-39	
RFL2N06	RCA	N	60				AND THE PERSON NAMED IN COLUMN TWO IS NOT THE OWNER.	2				8.33	TO-39	
RFL4N12	RCA	N		120					4			8.33	TO-39	
RFL4N15	RCA	N		150			AND THE RESERVE OF THE PARTY OF		4			8.33	TO-39	
RFM10N12	RCA	N	The State of State of the State	120						10		75	TO-204MA	
RFM10N15	RCA	N		150						10		75	TO-204MA	
RFM10P12	RCA	P		-120						-10				
RFM10P15	RCA	P		-150						-10				
RFM12N08	RCA	N	80								12	75	TO-204MA	
RFM12N08L	RCA	N	80								12	75	TO-204MA	LL=5V
RFM12N10	RCA	N	100								12	7.5	TO-204MA	
RFM12N10L	RCA	N	100								12	75	TO-204MA	LL=5V
RFM12N18	RCA	N		180							12	100	TO-204MA	
RFM12N20	RCA	N	A CONTRACTOR OF THE PARTY OF TH	200						-	12	100	TO-204MA	
RFM12P08	RCA	P	-80								-12	100	TO-204MA	
RFM12P10	RCA	P	-100								-12	100	TO-204MA	
RFM15N05	RCA	N	50	and the contract the contract of the contract			A. A. L. C. C. C. C. C. C. C. C. C. C. C. C. C.				15	75	TO-204MA	
RFM15N05L	RCA	N	50							,	15		TO-3	LL=5V
RFM15N06	RCA	N	60								15	75	TO-204MA	
RFM15N06L	RCA	N	60		and the second s	Andrew Control Control	AND DESCRIPTION OF THE PARTY OF				15		TO-3	LL=5V
RFM15N12	RCA	N		120					11-1		15	100	TO-204MA	
RFM15N15	RCA	N		150							15	100	TO-204MA	
RFM18N08	RCA	N	80								18	100	TO-204MA	and the state of t
RFM18N10	RCA	N	100								18	100	TO-204MA	
RFM25N05	RCA	N	50								25		то-3	LL=5V
RFM25N06	RCA	N	60		A STATE OF THE STA						25		TO-3	LL=5V

		チ	ドレ	イン・ソー	ス間耐圧	(V)		最大直流	ミドレイン	/電流(A	7)	最大消費			
型名	社 名	ヤネル	, 100	101 5 300	301 5 500	501 \$ 1000	, 1.0	1.1 3.0	3.1 5.0	5.1 10.0	10.1	電力(W) Tc=25°C	外 囲 器	備	考
RFM3N45	RCA	N		production the resident of the	450		ary passes a distantial	3	A Parameter of Par		A CONTRACTOR OF THE PARTY OF TH	75	TO-204MA		
RFM3N50	RCA	N	- ALAMAN AND AND AND AND AND AND AND AND AND A		500		And the state of t	3				75	TO-204MA		
RFM5P12	RCA	P	CONTRACTOR SERVICE SERVICE	-120			the state of the s		-5			75	TO-204MA		
RFM5P15	RCA	P		-150	has reasonable discoveraged to auditories	And the second second second		The special reported than t	-5			75	TO-204MA		
RFM6P08	RCA	P	-80		Carlot development of the Minister of the Control o					-6		75	TO-204MA		
RFM6P10	RCA	P	-100		and a second second second second second	- Marie and American Security Constitution (Security Constitution (S	Mad Standy - Married St. Co., 1970, 1994			-6		75	TO-204MA		
RFM8N18	RCA	N		180		And the later of t				8		75	TO-204MA		
RFM8N18L	RCA	N		180	and the second section of the section of the section		and any other part of the second distriction			8		75	TO-204MA	LL=5	V
RFM8N20	RCA	N		200			Property States and Coloring to Section 201			8		75	TO-204MA		
RFM8P08	RCA	P	-80				- Hayayan (1916-1916-1916-1916-1916)			-8	The second section of the section of the second	100	TO-204MA		.,
RFM8P10	RCA	P	-100		and the second s					-8		100	TO-204MA		
RFP10N12	RCA	N		120	Consideration of the State of the					10		60	TO-220AB		
RFP10N15	RCA	N		150	and the second s					10		60	TO-220AB		
RFP10P12	RCA	P		-120	and the second s					-10			TO-220		ACTION STANSAGE VALUE
RFP10P15	RCA	P		-150						-10					
RFP12N08	RCA	N	80							*****	12	60	TO-220AB		
RFP12N08L	RCA	N	80				***************************************			1	12	60	TO-220AB	LL=5	V
RFP12N10	RCA	N	100							-	12	60	TO-220AB		
RFP12N10L	RCA	N	100								12	60	TO-220AB	LL=5	V
RFP12N18	RCA	N		180							12	75	TO-220AB		-
RFP12N20	RCA	N		200							12	75	TO-220AB		
RFP12P08	RCA	P	-80					-			-12	75	TO-220AB		
RFP12P10	RCA	P	-100								-12	75	TO-220AB		
RFP15N05	RCA	N	50		- Language - Canada						15	60	TO-220AB		And the second second
RFP15N05L	RCA	N	50						<b></b>		15		TO-220	LL=5	V
RFP15N06	RCA	N	60		<u> </u>				<b></b>		15	60	TO-220AB		-
RFP15N06L	RCA	N	60				No. 200 April 1990 April 1990 April 1990 April 1990	1			15		TO-220	LL=5	V
RFP15N12	RCA	N		120				<u> </u>			15	75	TO-220AB		*****
RFP15N15	RCA	N	<del> </del>	150					1	1	15	75 .	TO-220AB		
RFP18N08	RCA	N	80						<del>                                     </del>	1	18	75	TO-220AB		alicinate de la constante de l

			<b>+</b>	ドレ	イン・ソー	・ス間耐圧	E (V)		最大直流	ミドレイン	√電流(A	)	最大消費		
型	名	社 名	ヤネル	\$ 100	101 \$ 300	301 500	501 \$ 1000	, 1.0	1.1 5 3.0	3.1 5.0	5.1 \$ 10.0	10.1	電力(W) Tc=25°C	外 囲 器	備考
RFP18N	110	RCA	N	100				and the second second second second second				18	75	TO-220AB	
RFP25N	105	RCA	N	50								25		TO-220	LL=5V
RFP25N	106	RCA	N	60								25		TO-220	
RFP2N0	)8	RCA	N	80					2				25	TO-220AB	
RFP2N0	)8L	RCA	N	80					2				25	TO-220AB	LL=5V
RFP2N1	0	RCA	N	100					2				25	TO-220AB	
RFP2N1	OL	RCA	N	100					2				25	TO-220AB	LL=5V
RFP2N1	2	RCA	N		120				2				25	TO-220AB	
RFP2N1	2L	RCA	N		120				2				25	TO-220AB	LL=5V
RFP2N1	5	RCA	N	<del> </del>	150				2				25	TO-220AB	
RFP2N1	5L	RCA	N		150		A TOTAL CONTRACTOR CON		2				25	TO-220AB	LL=5V
RFP2N1	8	RCA	N		180				2				25	TO-220AB	
RFP2N1		RCA	N		180								25	TO-220AB	LL=5V
RFP2N2		RCA	N		200			Production (CHI William) - April - Commission - Apr	2				25	TO-220AB	
RFP2N2	OL	RCA	N		200								25	TO-220AB	LL=5V
RFP2P0		RCA	P	-80				et and in terror to come the local time that and a first or a passar than the local training	-2						
RFP2P1		RCA	P	-100					-2						
RFP3N4		RCA	N			450			3	A CONTRACTOR OF THE PARTY OF			60	TO-220AB	
RFP3N5		RCA	N			500			3				60	TO-220AB	
RFP4N0	5	RCA	N	50	and the state of t					4			25	TO-220AB	
RFP4N0	6	RCA	N	60						4			25	TO-220AB	
RFP5P1	2	RCA	P		-120					-5			60	TO-220AB	
RFP5P1	5	RCA	P	and the second s	-150	and the second s		and in the late of		-5			60	TO-220AB	
RFP6P0	8	RCA	P	-80							-6		60	TO-220AB	
RFP6P1	0	RCA	P	-100	and the second s						-6		60	TO-220AB	
RFP8N1	8	RCA	N		180						8		60	TO-220AB	
RFP8N1	8L	RCA	N		180	and the second s	- Caracana Caracana As Wilder Wood				8		60	TO-220AB	LL=5V
RFP8N2	0	RCA	N		200	Linear Company of the Company					8		60	TO-220AB	and the same of th
RFP8N2	OL	RCA	N		200						8		60	TO-220AB	LL=5V
RFP8P0	8	RCA	P	-80							-8		75	TO-220AB	

		チ	ドレー	イン・ソー	- ス間耐圧	(V)		最大直流	ドレイン	電流 (A	)	最大消費		
型名	社名	ヤネル	, 100	101 5 300	301 500	501 5 1000	1.0	1.1	3.1 5.0	5.1	10.1	電力(W) Tc=25°C	外囲器	備考
RFP8P10	RCA	P	-100		rajena pienesta esperialista (esperiales e es e		A Maria Company of the Company of th			-8		75	TO-220AB	
TA9437A	RCA	N			350					10			TO-204MA	
TA9437B	RCA	N	The second secon		400	A CHARLES OF THE LOCAL PROPERTY OF THE PARTY				10			TO-204MA	
TA9438A	RCA	N		-	350	Andrew March and Andrew Co. Co. Co. Co. Co. Co. Co. Co. Co. Co.				10			TO-220AB	and analysis and the Walter Str. and the Street Street
TA9438B	RCA	N	And the second second second second second second		400				1	10			TO-220AB	
TFM8N20L	RCA	N		200		and the second s				8		75	TO-204MA	LL=5V
TN0106N2	SPT	N	60				0.8					3.5	TO-39	
TN0106N3	SPT	N	60				0.5					1	TO-92	
TN0106ND	SPT	N	60											CHIP
TN0110N2	SPT	N	100				0.8					3.5	TO-39	
TN0110N3	SPT	N	100	- No. Study and First produces about			0.5					1	TO-92	
TN0110ND	SPT	N	100	The second secon										CHIP
TN0520N2	SPT	N		200			0.7					3.5	TO-39	
TN0520N3	SPT	N		200			0.3					1	TO-92	
TN0520ND	SPT	N		200										CHIP
TN0524N2	SPT	N		240			0.7					3.5	TO-39	
TN0524N3	SPT	N		240			0.3	And the second s				1	TO-92	
TN0524ND	SPT	N	n, d. a. a. communicacy, ign applies half gave deposition. I then they higher the extra a	240										CHIP
VN0104N2	SPT	N	40				0.8					3.5	TO-39	
VN0104N3	SPT	N	40		ran and amount of the first of the		0.5					1	TO-92	
VN0104N5	SPT	N	40	and the second s				1.5				15	TO-220	
VN0104N6	SPT	N	40	Marcolon M. Miller Marcolon Ma			0.7					0.6/U	PDIP14P	2SK*4
VN0104N7	SPT	N	40			CONTRACTOR OF THE PROPERTY OF	0.7					0.6/U	CDIP14P	2SK*4
VN0104N9	SPT	N	40			ng afgangangan menanggan panggan 0.5					1	TO-52		
VN0104ND	SPT	N	40		and the second s									CHIP
VN0106N2	SPT	N	60				0.8					3.5	TO-39	
VN0106N3	SPT	N	60	THE RESERVE THE PARTY OF THE PA			0.5					1	TO-92	
VN0106N5	SPT	N	60					1.5				15	TO-220	
VN0106N6	SPT	N	60				0.7	ALC - ALC -				0.6/U	PDIP14P	2SK*4
VN0106N7	SPT	N	60				0.7					0.6/U	CDIP14P	2SK*4

	and agreement of the second of		チ	ドレ	イン・ソー	ス間耐圧	(V)		最大直流	ミドレイン	電流(A	)	最大消費		
型	名	社 名	ヤネル	, 100	101 5 300	301 \$ 500	501 \$ 1000	} 1.0	1.1 \$ 3.0	3.1 5.0	5.1	10.1	電力(W) Tc=25℃	外 囲 器	備
VN010	D6N9	SPT	N	60				0.5					1	TO-52	
VN010	-	SPT	N	60											CHIP
VN010		SPT	N	90				0.8					3.5	TO-39	
VN010	09N3	SPT	N	90				0.5					1	TO-92	
VN010		SPT	N	90					1.5				15	TO-220	
VN010		SPT	N	90				0.5					1	TO-52	
VN010		SPT	N	90				C. Marian (C. Maria), C. Maria (M. A., Asperta C. Maria							CHIP
VN01		SPT	N		160			0.35					3.5	TO-39	
VN01		SPT	N		160			0.25					1	TO-92	
VN01		SPT	N		160		THE PERSON NAMED OF THE PE	0.7					15	TO-220	
VN01		SPT	N		160										CHIP
VN012		SPT	N		200			0.35					3.5	TO-39	
VN012		SPT	N		200			0.25					1	TO-92	
VN012		SPT	N		200			0.7					15	TO-220	
VN012		SPT	N		200										CHIP
VN020		SPT	N	40					1.5				4	TO-39	
VN020		SPT	N	40			a a transfer de la constantina del constantina de la constantina de la constantina de la constantina de la constantina de la constantina de la constantina de la constantina del constantina de la constantina de la constantina de la constantina de la constantina de la constantina de la constantina de la constantina de la constantina de la constantina de la constantina de la constantina de	The same of the sa	3				28	TO-220	
VN020		SPT	N	40				1					1/U	PDIP14P	2SK*4
VN020	04N7	SPT	N	40				1					1/U	CDIP14P	2SK*4
VN020		SPT	N	40		and the same of th									CHIP
VN020		SPT	N	60				And the second s	1.5				4	TO-39	
VN020		SPT	N	60				0.8					1	TO-92	
VN020		SPT	N	60					3				28	TO-220	
VN020		SPT	N	60			. ,	1					1/U	PDIP14P	2SK*4
VN020	06N7	SPT	N	60				1					1/U	CDIP14P	2SK*4
VN020		SPT	N	60		and the second s									CHIP
VN02	10N2	SPT	N	100		ar angles o an in antibodier et la quantum per la constant	and the second s	and the second second second second	1.5				4	TO-39	
VN02	AND DESCRIPTION OF THE PARTY OF	SPT	N	100	- Was considered and the second and	Carlotte and Artistantian Control of the Control of		0.8					1	TO-92	
VN02		SPT	N	100		And the second s	and the second second		3				28	TO-220	
VN02		SPT	N	100		A CONTRACTOR OF THE PARTY OF TH									CHIP

		チ	ドレ	イン・ソー	- ス間耐圧	(V)		最大直流	ミドレイン	電流 (A)		最大消費		
型名	社名	ヤネル	, 100	101 \$ 300	301 500	501 5 1000	, 1.0	1.1 3.0	3.1 5.0	5.1 5 10.0	10.1	電力(W) Tc=25°C	外 囲 器	備考
VN0216N2	SPT	N	-24.000	160				1.5				4	TO-39	
VN0216N3	SPT	N		160			0.8					1	TO-92	
VN0216N5	SPT	N		160				3				28	TO-220	
VN0216ND	SPT	N		160										CHIP
VN0220N2	SPT	N	A PART AND ADDRESS AND A PORTUGUES OF THE PARTY OF THE PA	200			0.7					4	TO-39	
VN0220N3	SPT	N		200			0.4					1	TO-92	
VN0220N5	SPT	N		200				1.5				28	TO-220	
VN0220ND	SPT	N		200										CHIP
VN0300D	SL	N	30					2.5				20	TO-220AB	
VN0300L	SL	N	30				0.44					0.4	TO-92	
VN0300M	SL	N	30				0.7					1	TO-237	
VN0335N1	SPT	N		350					3.5			100	TO-3	
VN0335N2	SPT	N		350			1					6	TO-39	
VN0335N5	SPT	N		350				2.1				50	TO-220	
VN0335ND	SPT	N		350										CHIP
VN0340N1	SPT	N		400					3.5			100	TO-3	
VN0340N2	SPT	N		400			1					6	TO-39	
VN0340N5	SPT	N		400				2.1				50	TO-220	
VN0340ND	SPT	N		400										CHIP
VN0345N1	SPT	N		450				2.5				100	TO-3	
VN0345N2	SPT	N		450			0.35					6	TO-39	
VN0345N5	SPT	N		450				1.5				50	TO-220	
VN0345ND	SPT	N		450										CHIP
VN0350N1	SPT	N		500				2.5				100	TO-3	
VN0350N2	SPT	N		500			0.35					6	TO-39	
VN0350N5	SPT	N	*	500			***************************************	1.5				50	TO-220	
VN0350ND	SPT	N		500										CHIP
VN03551N1	SPT	• <b>N</b>			550			2.5				100	TO-3	
VN0355N5	SPT	N			550			1.5				50	TO-220	
VN0355ND	SPT	N			550		-							CHIP

		チ	ドレ	イン・ソー	- ス間耐圧	E (V)		最大直流	ミドレイン	電流(A	)	最大消費		
型名	社名	ヤネル	, 100	10 \$ 300	301 \$ 500	501 \$ 1000	\$ 1.0	1.1 \$ 3.0	3.1 5 5.0	5.1 \$ 10.0	10.1	電力(W) Tc=25°C		備考
VN0360N1	SPT	N			600			2.5				100	TO-3	
VN0360N5	SPT	N			600			1.5				50	TO-220	
VN0360ND	SPT	N			600									CHIP
VNO400A	SL	N	40								18	100	TO-3	
VN0400D	SL	N	40								18	75	TO-220AB	
VN0401A	SL	N	40								16	100	TO-3	
VN0401D	SL	N	40							***************************************	16	75	TO-220AB	
VN0535N2	SPT	N		350			0.25					6	TO-39	
VN0535N3	SPT	N		350			0.1					1	TO-92	
VN0535ND	SPT	N		350										CHIP
VN0540N2	SPT	N			400		0.25					6	TO-39	
VN0540N3	SPT	N			400		0.1					1	TO-92	
VN0540ND	SPT	N			400									CHIP
VN0545N2	SPT	N			450		0.1					6	TO-39	
VN0545N3	SPT	N			450		0.05				CONTRACTOR CONTRACTOR CONTRACTOR	1	TO-92	
VN0545ND	SPT	N			450									CHIP
VN0550N2	SPT	N		***************************************	500		0.1			The same Anthony and the Control of the Same of the Sa	the condition had not adding any only of the state of the	6	TO-39	
VN0550N3	SPT	N			500		0.05					1	TO-92	
VN0550ND	SPT	N		The second secon	500			-						CHIP
VN0600A	SL	N	60								18	100	TO-3	
VN0600D	SL	N	60			APER APPROXIMATE AND APPROXIMA					18	75	TO-220AB	-
VN0601A	SL	N	60				The state of the s				16	100	TO-3	
VN0601D	SL	N	60				and a section of the				16	75	TO-220AB	
VN0606M	SL	N	60				0.4					1	TO-237	
VN0610L	SL	N	60				0.2					0.4	TO-92	
VN0800A	SL	N	80							- Marie Marie Marie / Marie de La millocation (Marie de Ma	14	100	TO-3	
VN0800D	SL	N	80	THE SECTION AND THE SECTION ASSESSMENT			er der er sam <sub>ere</sub> er ber in engeliche gezeichte. An die er der		and the second s		14	75	TO-220AB	
VN0801A	SL	N	80				Proceedings of the Control of the Co			alan i 170 alan 1886, analan an an agree	12	100	TO-3	water retended the description of the contract
VN0801D	SL	N	80			rende etti danitri lää ettima etema	After the residence of the latest the second second			gardina again lagura di are de album are	12	75	TO-220AB	The second secon
VN0808M	SL	N	80				0.35	CAT STATE OF THE PARTY OF THE P	And the second s		grand Warren Carrier Street Control	1	TO-237	

		チ	ドレ	イン・ソー	ス間耐圧	(V)		最大直流	ドレイン	·電流(A	.)	最大消費		
型名	社 名	ヤネル	, 100	101 5 300	301 5 500	501 \$ 1000	; 1.0	1.1 \$ 3.0	3.1 5.0	5.1 10.0	10.1	電力(W) Tc=25°C	外 囲 器	備考
VN1000A	SL	N	100		and the second s	and the second second second second					14	100	TO-3	
VN1000D	SL	N	100								14	75	TO-220AB	
VN1001A	SL	N	100								12	100	TO-3	
VN1001D	SL	N	100								12	75	TO-220AB	
VN10KE	SL	N	60				0.2					0.315	TO-52	
VN10KM	ITS	N	60	and an individual and an indiv			0.5					1	TO-237	
VN10KM	SL	N	60			and the second s	0.3	A CONTRACTOR OF THE PARTY OF TH				1	TO-237	
VN10KN3	SPT	N	60			AND COMMENTS OF THE PROPERTY OF THE PARTY OF	0.3					1	TO-92	
VN10LE	SL	N	60		-magazinina, amazinina wilamozinina di madi fiv	paragina McMathallian - MPA - Baggion - Maharit Para	0.2					0.315	TO-52	
VN10LM	SL	N	60				0.3					1	TO-237	
VN1106N1	SPT	N	60							9		75	TO-3	
VN1106N2	SPT	N	60			and the sphericity and according to the section of		2.5				6	TO-39	
VN1106N5	SPT	N	60					-		7		45	TO-220	
VN1106ND	SPT	N	60			A CONTRACTOR OF THE PARTY OF TH								CHIP
VN1110N1	SPT	N	100				Parameter Company Community Co.	A CONTRACTOR OF STREET		9		75	TO-3	
VN1110N2	SPT	N	100					2.5				6	TO-39	
VN1110N5	SPT	N	100			JU 142, MILE MANAGE AND MANAGE AN				7		45	TO-220	
VN1110ND	SPT	N	100				ente una se diducto e das regionos Partir						and the second section of the second	CHIP
VN1116N1	SPT	N	an and a second representation of the second second	160			******	3				100	TO-3	
VN1116N2	SPT	N		160			1					4	TO-39	
VN1116N5	SPT	N		160				2				45	TO-220	
VN1116ND	SPT	N		160										CHIP
VN1120N1	SPT	N	and the second transfer of the second transfe	200		and the second s	and the state of t	3			1	100	TO-3	
VN1120N2	SPT	N	<del> </del>	200				1			And to Photography and the Pro-	4	TO-39	and the second s
VN1120N5	SPT	N		200				2				45	TO-220	
VN1120ND	SPT	N		200										CHIP
VN1200A	SL	N		120				1			14	75	TO-3	
VN1200D	SL	N	<del> </del>	120			and the second of the second o				14	75	TO-220AB	
VN1201A	SL	N		120		The second secon					12	100	TO-3	
VN1201D	SL	N		120			and the second of the second o	1			12	75	TO-220AB	

		+	ドレ	イン・ソー	- ス間耐圧	E (V)		最大直流	ミドレイン	·電流(A	)	最大消費		
型名	社 名	ヤネル	, 100	101 \$ 300	301 5 500	501 \$ 1000	, 1.0	1.1 5 3.0	3.1 5.0	5.1 \$ 10.0	10.1	電力(W) Tc=25°C	外囲器	備考
VN1204N1	SPT	N	40								12	100	TO-3	
VN1204N2	SPT	N	40						3.5			6.5	TO-39	*
VN1204N5	SPT	N	40							9		45	TO-220	
VN1204ND	SPT	N	40											CHIP
VN1206B	SL	N		120			0.8					6.25	TO-39	
VN1206D	SL	N		120				1.4				20	TO-220AB	
VN1206L	SL	N		120			0.21					0.4	TO-92	
VN1206M	SL	N		120			0.3				<u> </u>	1	TO-237	
VN1206N1	SPT	N	60								12	100	TO-3	
VN1206N2	SPT	N	60	-				1	3.5			6.5	TO-39	
VN1206N5	SPT	N	60		*					9		45	TO-220	
VN1206ND	SPT	N	60											CHIP
VN1210L	SL	N	1	120			0.16	<del> </del>	1			0.4	TO-92	
VN1210M	SL	N	<u> </u>	120			0.25					1	TO-237	
VN1210N1	SPT	N	100							1	12	100	TO-3	
VN1210N2	SPT	N	100						3.5	1		6.5	TO-39	
VN1210N5	SPT	N	100							9		45	TO-220	
VN1210ND	SPT	N	100											CHIP
VN1216N1	SPT	N		160					-	6		100	TO-3	
VN1216N2	SPT	N		160			A. Sec	3.0		-		6.5	TO-39	
VN1216N5	SPT	N		160		AND THE PROPERTY OF THE PARTY O		<u> </u>	4.5			45	TO-220	
VN1216ND	SPT	N		160			at the state of th	<del> </del>	<b>-</b>	1			The second section of the second section of the second section of the second section of the second section of the second section secti	CHIP
VN1220N1	SPT	N		200						6		100	TO-3	
VN1220N2	SPT	N		200				3		1			TO-39	
VN1220N5	SPT	N	İ	200					4.5				TO-220	
VN1220ND	SPT	N	1	200				-						CHIP
VN1304N2	SPT	N	40				0.4		<b> </b>	1	<u> </u>	3	TO-39	and the state of t
VN1304N3	SPT	N	40		ALLE STATES AND STREET	A. LORGICO PLANTON AND PLANTON	0.25		·				TO-92	
VN1304N6	SPT	N	40		en a anti-re-cisi anti-regular de entrigia de		0.4	n de la constitue de la consti	de americalist de l'est manier seus				PDIP14P	2SK*4
VN1304N7	SPT	N	40			and the street of the street o	0.4			-			CDIP14P	2SK*4

	and American Section (Control of the Section Section Section Section Section Section Section Section Section Sec	チ	FV.	イン・ソー	・ス間耐圧	(V)		最大直流	ドレイン	電流 (A)	, alle parties (the first of the second seco	最大消費		
型名	社名	ヤネル	, 100	101 5 300	301 500	501 \$ 1000	, 1.0	1.1	3.1 5.0	5.1 5 10.0	10.1	電力(W) Tc=25°C	外 囲 器	備考
VN1304ND	SPT	N	40	, a continue de la contraction	And the second second		The state of the s	The same of the sa						CHIP
VN1306N2	SPT	N	60				0.4	The second secon	and the second s		and the second second second second second	3	TO-39	
VN1306N3	SPT	N	60		and a second second second second		0.25					1	TO-92	
VN1306N6	SPT	N	60	Description of the second		And and an Addition for the second	0.4					0.5/U	PDIP14P	2SK*4
VN1306N7	SPT	N	60	and the second section of			0.4					0.6/U	CDIP14P	2SK*4
VN1306ND	SPT	N	60	- Commission of the Commission							- La Marie Marie Space Communication of the Communi			CHIP
VN1310N2	SPT	N	100				0.4					3	TO-39	
VN1310N3	SPT	N	100				0.25				Annual Property and the State of the State o	1	TO-92	
VN1310ND	SPT	N	100				grader manuals et al. or of the subject of the thirty of t							CHIP
VN1316N2	SPT	N		160			0.15					3	TO-39	
VN1316N3	SPT	N		160			0.1					0.8	TO-92	
VN1316ND	SPT	N		160									The Bandhan Laurelle Will (Blackle Br. 1884) and the property of the American Property of the Control of the Co	CHIP
VN1320N2	SPT	N		200			0.15					3	TO-39	
VN1320N3	SPT	N		200			0.1					0.8	TO-92	and an experience of the control of
VN1320ND	SPT	N		200									The state of the s	CHIP
VN1706B	SL	N		170		and in accept and for publish depotents.	0.8	, and the second			and the second second second second	6.25	TO-39	
VN1706D	SL	N	+	170				1.4		****		20	TO-220AB	
VN1706L	SL	N		170			0.21					0.4	TO-92	
VN1706M	SL	N		170			0.3					1	TO-237	*
VN1700M VN1710L	SL	N		170			0.16					0.4	TO-92	
VN1710H	SL	N		170			0.25					1	TO-237	
VN2222KM	SL	N	60				0.25					1	TO-237	
VN2222L	SL	N	60	-			0.15	<u> </u>				0.4	TO-92	
VN2222LM	SL	N	60				0.25					1	TO-237	
VN2306N1	SPT	N	60			-					30	125	TO-3	
VN2306N5	SPT	N	60								20	50	TO-220	
VN2306ND	SPT	N	60					1	<del> </del>					CHIP
VN2300ND VN2310N1	SPT	N	100	<del> </del>							30	125	TO-3	
VN2310N1 VN2310N5	SPT	N	100						<del> </del>		20	50	TO-3	
VN2310ND VN2310ND	SPT	N	100						<b> </b>					CHIP

		+	ドレ	イン・ソー	- ス間耐圧	(V)		最大直流	たドレイ:	ン電流(A	)	最大消費		
型名	社名	ヤネル	, 100	101 \$ 300	301 \$ 500	501 \$ 1000	, 1.0	1.1 \$ 3.0	3.1 5 5.0	5.1 \$ 10.0	10.1	電力(W) Tc=25°C		備考
VN2316N1	SPT	N		160							18	125	TO-3	
VN2316N5	SPT	N		160							12	50	TO-220	
VN2316ND	SPT	N		160										CHIP
VN2320N1	SPT	N		200							18	125	TO-3	
VN2320N5	SPT	N		200							12	50	TO-220	
VN2320ND	SPT	N		200										CHIP
VN2335N1	SPT	N			350					8		125	то-3	
VN2335N5	SPT	N			350					6		50	TO-220	
VN2335ND	SPT	N			350									CHIP
VN2340N1	SPT	N			400					8		125	TO-3	
VN2340N5	SPT	N			400					6		50	TO-220	
VN2340ND	SPT	N			400									CHIP
VN2345N1	SPT	N			450					6		125	TO-3	
VN2345N5	SPT	N			450				4			50	TO-220	
VN2345ND	SPT	N			450									CHIP
VN2350N1	SPT	N			500					6		125	TO-3	
VN2350N5	SPT	N			500				4			50	TO-220	
VN2350ND	SPT	N			500									CHIP
VN2406B	SL	N		240			0.8					6.25	TO-39	
VN2406D	SL	N		240				1.4			a service administrative	20	TO-220AB	
VN2406L	SL	N		240			0.21					0.4	TO-92	
VN2406M	SL	N		240			0.3					1	TO-237	
VN2410L	SL	N		240			0.16					0.4	TO-92	and the second contract of the second second second
VN2410M	SL	N		240			0.25					1	TO-237	
VN30AB	ITS	N	35			1+1		1.2				6.25	TO-39	
VN3500A	SL	N			350					6		125	TO-3	
VN3500D	SL	N			350					6		75	TO-220AB	
VN3501A	SL	N			350				5		annata ang manaka sakhilakan sakhil	125	TO-3	
VN3501D	SL	N			350				5			75	TO-220AB	
VN35AA	SL	N	35					2				25	TO-3	

Market and Grant Art Stradford Tree and Art Strade and Art Strade and Art Strade Art Str		£	ドレ	イン・ソー	ス間耐圧	(V)		最大直流	ミドレイン	√電流(A	)	最大消費			
型名	社名	ヤネル	, 100	101 5 300	301 500	501 \( \) 1000	, 1.0	1.1 5 3.0	3.1 5.0	5.1 , 10.0	10.1	電力(W) Tc=25°C	外 囲 器	備	考
VN35AB	ITS	N	35	Proposition of the State of the	A COLUMN TO THE PARTY OF THE PA	and the second s	Auric Annaile (married	1.2		The second second second second second second		6.25	TO-39		
VN35AB	SL	N	35	A THE CONTRACT OF THE PARTY OF		and the second of the second of the second	and the second second second second	1.2	to the Table of the State of th	***************************************		6.25	TO-39		
VN35AK	ITS	N	35					1.2				6.25	TO-39		
VN4000A	SL	N			400					6		125	TO-3		
VN4000D	SL	N			400	territoria de la caracteria de la caract	The second second second			6		75	TO-220AB		
VN4001A	SL	N			400		Andrews are an incident of the same		5			125	TO-3		
VN4001D	SL	N			400				5			75	TO-220AB		
VN40AD	SL	N	40		The state of the s			1.5				40	TO-220AB		
VN40AF	ITS	N	40			a transference of the second s	e and and publishing from the complete of	1.2				12	TO-202		
VN40AF	SL	N	40	Annaharina and the sof a ferromanum daugh		a management with a constant of the		1.3				15	TO-202AA		
VN4501A	SL	N		Co. The series we have a series of the	450	and the second s			4.5			100	TO-3		
VN4501D	SL	N			450		A STATE OF THE PARTY OF THE PAR	- may comment the state of the	4.5	****		75	TO-220AB		
VN4502A	SL	N			450				4			100	TO-3		
VN4502D	SL	N			450				4			75	TO-220AB		
VN46AD	SL	N	40					1.9				40	TO-220AB		
VN46AF	ITS	N	40			and the second s	· ····································	1.2				12	TO-202		
VN46AF	SL	N	40					1.6				15	TO-202AA		
VN5001A	SL	N			500				4.5			100	TO-3		
VN5001D	SL	N			500				4.5			75	TO-220AB		
VN5002A	SL	N			500		Marie Commission of Section 18.000		4			100	TO-3		
VN5002D	SL	N			500				4			75	TO-220AB		
VN64GA	SL	N	60		*****************		parameter anning at the Color of the Color o			10		80	TO-3		
VN66AD	SL	N	60					1.9				20	TO-220AB		
VN66AF	ITS	N	60					1.2				12	TO-202		
VN66AF	SL	N	60					1.7				15	TO-202AA		
VN66AK	ITS	N	60					1.2				6.25	TO-39		
VN67AA	SL	N	60					2				25	TO-3		
VN67AB	ITS	N	60					1.2				6.25	TO-39		
VN67AB	SL	N	60				1					6.25	TO-39		
VN67AD	SL	N	60					1.8				20	TO-220AB		

			チ	ドレ	イン・ソー	-ス間耐圧	(V)		最大直流	ミドレイン	√電流(A	)	最大消費			
型	名	社 名	ヤネ		101	301	501		1.1	3.1	5.1	10.1	電力(W)	外囲器	備	考
			ル	100	300	500	1000	1.0	3.0	5.0	10.0		$Tc = 25^{\circ}C$			
VN67AF		ITS	N	60					1.2				12	TO-202		
VN67AF	er med and street have been been as	SL	N	60					1.6				15	TO-202AA		
VN67AK		ITS	N	60					1.2				6.25	TO-39		
VN80AF		SL	N	80					1.3				15	TO-202AA		
VN88AD		SL	N	80					1.7				20	TO-220AB		
VN88AF		ITS	N	80					1.2				12	TO-202		
VN88AF		SL	N	80					1.5				15	TO-202AA		
VN89AB		ITS	N	80					1.2				6.25	TO-39		
VN89AD		SL	N	80					1.6				20	TO-220AB		
VN89AF		ITS	N	80					1.2				12	TO-202		
VN89AF		SL	N	80					1.4				15	TO-202AA		
VN90AA		SL	N.	90				and the second s	1.7				25	TO-3		
VN90AB		ITS	N	90					1.2				6.25	TO-39		
VN90AB		SL	N	90				0.8					6.25	TO-39		
VN98AK		ITS	N	90					1.2				6.25	TO-39		
VN99AA		SL	N	90				the state of the s	1.8				25	TO-3		
VN99AB		SL	N	90				0.9					6.25	TO-39		
VN99AK		ITS	N	90				and the second second second second	1.2				6.25	TO-39		
VNC003A	A	SL	N	60			The second secon					60	250	TO-3		
VNC010E	3	SL	N	60						4			15	TO-39		
VNC011E	3	SL	N	60						4			15	TO-39		-
VND010E	3	SL	N	80	The state of the s					4			15	TO-39		
VND011E	3	SL	N	80						4			15	TO-39		
VNE003A	4	SL	N	100								60	250	TO-3		
VNE010E	3	SL	N	100						4			15	TO-39		
VNE011E	3	SL	N	100						4			15	TO-39		
VNG004A	1	SL	N	***************************************	150							45	250	TO-3		
VNJ004A	1	SL	N		200	and the second s		And the second s				45	250	TO-3		
VNL001A	1	SL	N			350	A Paris Communication of the Paris Communication				8		175	TO-3		
VNL005A	1	SL	N	y-		350						25	250	TO-3		And a supple of the supple of

American Parameter Parameter Stage and Stage a		J.	ドレ	イン・ソー	・ス間耐圧	(V)		最大直流	ミドレイン	√電流(A	۲)	最大消費		
型名	社名	ヤネル	) 100	101 5 300	301 500	501 5 1000	, 1.0	5.1 5 10.0	1.1 3.0	3.1 5.0	10.1	電力(W) Tc=25°C	外囲器	備考
VNM001A	SL	N	a page de la manufactura de la constitución de la c		400	· Granding majoranija mje na godin	to the specific state of the specific section of the s	والمراجعة والمستونة والمداعة والمداعة والمداعة والمستونة والمداعة والمداعة والمداعة والمداعة والمداعة والمداعة	A CONTRACTOR OF THE STATE OF	8		175	TO-3	
VNM005A	SL	N			400	A resignative annual des addresses de la particular					25	250	TO-3	
VNN002A	SL	N		- Character - Char	450	temperature of a disconnection of helps, with a	a Lade Million conductor have a William to Major have to			6.5		175	TO-3	The second secon
VNN006A	SL	N			450		and the second s				20	250	TO-3	
VNP002A	SL	N	ander to a seculo respect to the state of the Parameter of the		500		The state of the s			6.5		175	TO-3	
VNP006A	SL	N			500					and the same of th	20	250	TO-3	
VNS008A	SL	N		***************************************		600		COMMENTS CONTROL OF THE PARTY O	A STATE OF THE STA	6		125	TO-3	
VNS008D	SL	N	1			600				6		125	TO-220AB	
VNS009A	SL	N				600			5			125	TO-3	
VNS009D	SL	N	-	-		600			5			125	TO-220AB	
VNT008A	SL	N	-	1		650			1	6		125	TO-3	
VNT008D	SL	N				650				6		125	TO-220AB	
VNT009A	SL	N				650			5			125	TO-3	
VNT009D	SL	N	·	The Contract Manager Contract Assets (Bally Contract)		650			5	-		125	TO-220AB	
V00104ND	SPT	P	-40										The second secon	CHIP
V00106N2	SPT	P	-60				-0.5		<b></b>			3.5	TO-39	
V00116N3	SPT	P		-160			-0.1					1	TO-92	
V00204N2	SPT	P	-40				-0.8					6	TO-39	
VP0104N2	SPT	P	-40	<del> </del>			-0.5					3.5	TO-39	
VP0104N3	SPT	P	-40				-0.4			-		1	TO-92	
VP0104N5	SPT	P	-40				-1.0					15	TO-220	
VP0104N6	SPT	P	-40				-0.4					0.6/U	PDIP14P	2SJ*4
VP0104N7	SPT	P	-40				-0.4					0.6/U	CDIP14P	2SJ*4
VP0104N9	SPT	P	-40				-0.4					1	TO-52	
VP0106N3	SPT	P	-60			Towns and Alberta Strong control to the Section St	-0.4					1	TO-92	
VP0106N5	SPT	P	-60				-1					15	TO-220	
VP0106N6	SPT	P	-60				-0.4					0.6/U	PDIP14P	2SJ*4
VP0106N7	SPT	P	-60				-0.4						CDIP14P	2SJ*4
VP0106N9	SPT	 P	-60				-0.4					1	TO-52	
VP0106ND	SPT	P	-60						and any in the course of the c				The state of the s	CHIP

			チ	ドレイ	イン・ソー	ス間耐圧	(V)	-	最大直流	ミドレイン	電流(A)		最大消費		
型名	社	名	ヤネル	, 100	101 \$ 300	301 5 500	501 \$ 1000	, 1.0	1.1 \$ 3.0	3.1 \$ 5.0	5.1	10.1	電力(W) Tc=25℃	外囲器	備考
VP0109N2	SPT	r	P	-90				-0.5					3.5	TO-39	
VP0109N3	SPI		P	-90		***************************************		-0.4					1	TO-92	
VP0109N5	SPT	r	P	-90				-1					15	TO-220	
VP0109N9	SPT	r	P	-90				-0.4					1	TO-52	
VP0109ND	SPT	Г	P	-90											CHIP
VP0116N2	SPT	r	P		-160			-0.2					3.5	TO-39	
VP0116N5	SP		P		-160		**************************************	425					15	TO-220	
VP0116ND	SPT		P		-160										CHIP
VP0120N2	SP		P		-200			-0.2					3.5	TO-39	
VP0120N3	SPI		P		-200		and the second s	-0.1					1	TO-92	
VP0120N5	SP		P		-200			425					15	TO-220	
VP0120ND	SPT		P		-200				Management and American State of the Control of the						CHIP
VP0204N5	SPT		P	-40					-2				27	TO-220	
VP0204N6	SPT		P	-40				-0.4					1/U	PDIP14P	2SJ*4
VP0204N7	SPT		P	-40				-0.4	and the second second second				1/U	CDIP14P	2SJ*4
VP0204ND	SPI		P	-40											CHIP
VP0206N2	SPI		P	-60			earmand the continue of the second of the second	-0.8					6	TO-39	
VP0206N3	SPI		P	-60				-0.4					1	TO-92	
VP0206N5	SPI	r	P	-60					-2				27	TO-220	
VP0206N6	SPI		P	-60				-0.4	and the same of th			- ALLES AND AND AND AND AND AND AND AND AND AND	1/U	PDIP14P	2SJ*4
VP0206N7	SPI	r	P	-60			and the second s	-0.4	A STATE OF THE PARTY OF THE PAR				1/U	CDIP14P	2SJ*4
VP0206ND	SPT	r	P	-60											CHIP
VP0210N2	SPI	r	P	-100				-0.8					6	TO-39	
VP0210N3	SPI	r	P	-100			umbanic kalandarin Vibrationadore	-0.4					1	TO-92	
VP0210N5	SPI	r	P	-100				and a state of the	-2				27	TO-220	
VP0210ND	SPI	r	P	-100				and the second s	CALLEST AND CARLOTTERS THE POPULATION OF THE POP						CHIP
VP0216N2	SPI		P		-160			-0.35					4	TO-39	
VP0216N3	SPI		P		-160		anders heritaredisale at 910	-0.2	rati Alli amini din radi lare riffi njemen politica dimedi	an validation to the Principles		1	1	TO-92	
VP0216N5	SPI	r	P		-160	AND AND ADDRESS OF THE PARTY OF	ACTION OF A CONTROL WITH STREET AND THE ST	-0.8	gydy of the Management of The Co				27	TO-220	
VP0216ND	SPI	r	P		-160		and the property of the contract of the contra	n de Maria de la Calenda de la Calenda de la Calenda de la Calenda de la Calenda de la Calenda de la Calenda d							CHIP

		チ	ドレ	イン・ソー	・ス間耐圧	(V)		最大直流	ドレイン	電流(A)	)	最大消費		
型名	社名	ヤネル	\$ 100	101 \$ 300	301 500	501 { 1000	, 1.0	1.1 , 3.0	3.1 5.0	5.1 5 10.0	10.1	電力(W) Tc=25°C		備考
VP0220N2	SPT	P		-200			-0.35					4	TO-39	
VP0220N3	SPT	P	And the second second second second second	-200			-0.2	em, successingual to effect to these presents				1	TO-92	
VP0220N5	SPT	P		-200			-0.8				And the second comments of the second comment	27	TO-220	
VP0220ND	SPT	P		-200										CHIP
VP0300B	SL	P	-30		The second section of the second	namen o Considerate Mathematica Pro-Mile		-1.3				6.25	TO-39	
VP0300L	SL	P	-30				-0.48					1	TO-92	
VP0300M	SL	P	-30			Andrew States and Constitution of the Constitu	-0.48			and the Court of t		1	TO-237	-
VP0335N1	SPT	P			-350			-2.7		A Company of the Comp		100	TO-3	
VP0335N2	SPT	P			-350		-0.7					6	TO-39	
VP0335N5	SPT	P		an angle of Participant Contraction of the Contract	-350	THE PERSON AND THE RESIDENCE OF THE PERSON AND THE		-1.6				50	TO-220	
VP0335ND	SPT	P		an merikahilan ceramanan merikanan adara	-350		in the straight the same devices and require commences at the street	and the second of the second s						CHIP
VP0340N1	SPT	P			-400			-2.7				100	TO-3	
VP0340N2	SPT	P	- COUNTY AND THE PARENTS AND ADDRESS.		-400		-0.7					6	TO-39	
VP0340N5	SPT	P			-400			-1.6				50	TO-220	
VP0340ND	SPT	P			-400									CHIP
VP0345N1	SPT	P			-450		and the state of t	-1.5					TO-3	
VP0345N2	SPT	P			-450		-0.4				A STATE OF THE STA	6	TO-39	
VP0345N5	SPT	P			-450		-1.0					50	TO-220	
VP0345ND	SPT	P			-450									CHIP
VP0350N1	SPT	P			-500			-1.5				100	TO-3	
VP0350N2	SPT	P			-500		-0.4					6	TO-39	
VP0350N5	SPT	P			-500		-1.0					50	TO-220	
VP0350ND	SPT	P			-500									CHIP
VP0535N2	SPT	P			-350		-0.2	alasat y yell in the state by the second				3.5	TO-39	
VP0535N3	SPT	P			-350		-0.1					1	TO-92	
VP0535ND	SPT	P			-350									CHIP
VP0540N2	SPT	P			-400		-0.2					3.5	TO-39	
VP0540N3	SPT	P			-400		-0.1						TO-92	
VP0540ND	SPT	P			-400									CHIP
VP0545N2	SPT	P			-450		125			l		3.5	TO-39	

			チ	ドレ・	イン・ソー	・ス間耐圧	(V)		最大直流	ミドレイン	✓電流 (A)		最大消費		
型名	社	名	ャネル	\$ 100	101 \$ 300	301 \$ 500	501 \$ 1000	, 1.0	1.1 \$ 3.0	3.1 5.0	5.1 \$ 10.0	10.1	電力(W) Tc=25°C	外 囲 器	備考
VP0545N3	SP	T	P			-450	- Colored Colo	-0.07					1	TO-92	
VP0545ND	SP	T	P			-450									CHIP
VP0550N2	SP	T	P			-500		125					3.5	TO-39	
VP0550N3	SP	T	P			-500		07					1	TO-92	
VP0550ND	SP	T	P			-500									CHIP
VP0808L	SL		P	-80			and it was taken a taken a taken a	-0.37					0.4	TO-92	
VP0808M	SL		P	-80				-0.37					1	TO-237	
VP1008B	SL		P	-100				-0.9					6.25	TO-39	
VP1008L	SL		P	-100				-0.37					0.4	TO-92	
VP1008M	SL		P	-100				-0.37					1	TO-237	
VP1106N1	SP	T	P	-60	and the section of th						-6		75	TO-3	
VP1106N2	SP	T	P	-60					-1.5				6	TO-39	
VP1106N5	SP	T	P	-60					-	-4			45	TO-220	
VP1106ND	SP	T	P	-60											CHIP
VP1110N1	SP	T	P	-100				an paris de la Presidente de la Carta de l			-6		75	TO-3	
VP1110N2	SP'	T	P	-100					-1.5			ara dikana Kanasar Pekkinde Berlika di Hena	6	TO-39	
VP1110N5	SP'	T	P	-100						-4			45	TO-220	
VP1110ND	SP'	T	P	-100									-		CHIP
VP1116N1	SP'	T	P		-160			and the second of the second section of	-2.5				75	TO-3	
VP1116N2	SP'	r	P		-160			-0.8	and an order or to the or Topologica				6	TO-39	
VP1116N5	SP'	r	P		-160				-1.8				45	TO-220	
VP1116ND	SP'	r	P		-160										CHIP
VP1120N1	SP'	r	P		-200				-2.5				75	TO-3	
VP1120N2	SP		P	NAMES OF THE PERSON OF THE PER	-200			-0.8		<u> </u>			6	TO-39	
VP1120N5	SP'	r	P		-200		Antonia de Carlos de Carlos de Maria de Carlos de Maria de Carlos	vilantinalisti, metti uti tikata tikanan vilan	-1.8				45	TO-220	
VP1120ND	SP		P		-200			elleredr schiller Fielder sanden eine von Witer	AND DESCRIPTION OF THE PERSON		-				CHIP
VP1204N1	SP'		P	-40				anipeli, eksejatilan, Anapelana Mennibel	-	-	-7	ARAMAN AND AND AND AND AND AND AND AND AND A	100	TO-3	
VP1204N2	SP'	r	P	-40				The abidical Color of the abidical Color of the Color of	-2.5				6.5	TO-39	
VP1204N5	SP	-	P	-40				and the construction of the spinor to the description of		-5	in benevin with granter (wheel		45	TO-220	
VP1204ND	SP		P	-40	and the state of t					1					CHIP

Marie Person (P. 1944). Ar delan nggaringa awa Asaman ya Makalina		チ	ドレ	イン・ソー	ス間耐圧	(V)		最大直流	ミドレイン	·電流(A	)	最大消費		
型名	社 名	ヤネル	100	101 \$ 300	301 5 500	501 \$ 1000	, 1.0	1.1 5 3.0	3.1 5 5.0	5.1	10.1	電力(W) Tc=25°C	外川器	備考
VP1206N1	SPT	P	-60		to the company of the second the contract of t	AND DESCRIPTION OF THE PARTY OF	THE RESERVE OF THE PARTY OF THE			-7	Special and the second second	100	TO-3	-
VP1206N2	SPT	P	-60	erangan at distinguish in Balancian Au	termediate transport states to de-	and the second s		-2.5				6.5	TO-39	
VP1206N5	SPT	P	-60		THE RESERVE THE PARTY OF THE PA		gamen globyle d'Ordere y nel en nyglobyle de alle d'Ordere de		-5			4.5	TO-220	
VP1206ND	SPT	P	-60											CHIP
VP1210N1	SPT	P	-100							-7		100	TO-3	D. 172
VP1210N2	SPT	Р	-100					-2.5				6.5	TO-39	
VP1210N5	SPT	P	-100						-5	and and the constant of the same of the		45	TO-220	M. In the Proceedings of the Process
VP1210ND	SPT	P	-100											CHIP
VP1216N1	SPT	P		-160					-4.5			100	TO-3	
VP1216N2	SPT	P		-160			and the second s	-2				6.5	TO-39	
VP1216N5	SPT	P		-160					-3.5			45	TO-220	
VP1216ND	SPT	P		-160										CHIP
VP1220N1	SPT	P	:	-200					-4.5			100	TO-3	
VP1220N2	SPT	Р		-200			er aller kommunet franklikerk millede	-2				6.5	TO-39	dental and confidence
VP1220N5	SPT	P		-200					-3.5			45	TO-220	
VP1220ND	SPT	P		-200					The same of the sa					CHIP
VP1304N2	SPT	P	-40				-0.25	and the second s			-	3	TO-39	The second of th
VP1304N3	SPT	P	-40	Alle an all above come (MA). To see the			-0.15			The second of th		0.8	TO-92	
VP1304N6	SPT	P	-40	e salanda merili sanda menerili salah salah salah salah salah salah salah salah salah salah salah salah salah			-0.2			-		0.5/U	PDIP14P	2SJ*4
VP1304N7	SPT	P	-40				-0.2				***	0.5/U	CDIP14P	2SJ*4
VP1304ND	SPT	P	-40	uniformation publical fractional transport and										CHIP
VP1306N2	SPT	P	-60	des an constitute manual			-0.25					3	TO-39	
VP1306N3	SPT	P	-60	A-10 1000 B-100 - 10-100	and the second of the second		-0.15					0.8	TO-92	
VP1306N6	SPT	P	-60	, pangandadi 1940 sada. Sangai Kapada mistalingan	atala atalah di Palah di Angara da Palah da Pal		-0.2		1	ī		0.5/U	PDIP14P	2SJ*4
VP1306N7	SPT	P	-60		in any in Plan Addressed from	Contract of the Contract of th	-0.2					0.5/U	CDIP14P	2SJ*4
VP1306ND	SPT	P	-60		olimpiani a o tr E Passili a	2. The small late the manifestor devillator and	ad terminal terminal adaptivas de la Maria del Maria de la Maria de la Maria del Maria de la Maria dela Maria de la Maria de la Maria dela Maria							CHIP
VP1310N2	SPT	P	-100		na, sine tri remitet Candinover, dece i	والمستحدث فالمستوال في الأستوال الميتوانية	-0.25					3	TO-39	
VP1310N3	SPT	P	-100	- Market Make the Care	ediction in the little on the state of	والمعالمية والمعالمين المستولية المستولية	-0.15					0.8	TO-92	
VP1310ND	SPT	P	-100		man and the state of the state	Children (18 c.) Britis seemble Describ								CHIP
VP1316N2	SPT	 P		-160	A SECURIO SE SECURIO DE LA CASA A C	and the second of the second o	-0.1					3	TO-39	

		チ	ドレイン・ソース間耐圧(V)				最大直流ドレイン電流(A)					最大消費		
型名	社 名	ャネル	5	101	301	501 s	s	5.1 s	1.1	3.1	10.1	電力(W)	外 囲 器	備考
		,	100	300	500	1000	1.0	10.0	3.0	5.0		$Tc = 25^{\circ}C$		
VP1316N3	SPT	P		-160			-0.06					0.8	TO-92	
VP1316ND	SPT	P		-160										CHIP
VP1320N2	SPT	P		-200			-0.1					3	TO-39	
VP1320N3	SPT	P		-200			-0.06					0.8	TO-92	
VP1320ND	SPT	P		-200										CHIP
VQ0808B	SL	P	-80				-0.9					6.25	TO-39	
VQ1000CJ	ITS	N	60				0.3						DIP14P	2SK*4
VQ1000J	SL	N	60				0.225					0.5/U	PDIP14P	2SK*4
VQ1000N6	SPT	N	60									1.2/U	PDIP14P	2SK*4
VQ1000N7	SPT	N	60									2/U	CDIP14P	2SK*4
VQ1000P	SL	N	60				0.225					0.5/U	CDIP14P	2SK*4
VQ1001J	SL	N	30				0.85					1.3/U	PDIP14P	2SK*4
VQ1001P	SL	N	30				0.85				***************************************	1.3/U	CDIP14P	2SK*4
VQ1004J	SL	N	60				0.46					1.3/U	PDIP14P	2SK*4
VQ1004P	SL	N	60				0.46					1.3/U	CDIP14P	2SK*4
VQ1006J	SL	N	90				0.4					1.3/U	PDIP14P	2SK*4
VQ1006P	SL	N	90				0.4					1.3/U	CDIP14P	2SK*4
VQ2001J	SL	Р	-30				-0.6					1.3/U	PDIP14P	2SJ*4
VQ2001P	SL	P	-30				-0.6					1.3/U	CDIP14P	2SJ*4
VQ2004J	SL	P	-60				-0.6					1.3/U	PDIP14P	2SJ*4
VQ2004P	SL	P	-60		***************************************		-0.6				Processing and the second	1.3/U	CDIP14P	2SJ*4
VQ2006J	SL	P	-90	i ya engere tira anagoni ji pasini ni napeni haya ina aya ana			-0.6					1.3/U	PDIP14P	2SJ*4
VQ2006P	SL	P	-90				-0.6					1.3/U	CDIP14P	2SJ*4
VQ3001J	SL	P/N										1.3/U	PDIP14P	J*2,K*2
VQ3001P	SL	P/N			and the second s							1.3/U	CDIP14P	J*2,K*2
VQ7254J	SL	P/N										1.3/U	PDIP14P	J*2,K*2
VQ7254N6	SPT	P/N				and the second s						1.5/U	PDIP14P	
VQ7254N7	SPT	P/N										2/U	CDIP14P	
VQ7254P	SL	P/N										1.3/U	CDIP14P	J*2,K*2

このページは空白です.

1985年版

## 最新FET [香幣縣] 規格表

昭和43年4月1日 初 版 発 行 昭和60年6月20日 発 行

S60. 6. 20 第1刷

©1968 編 著 者 漆 原 健 彦

編集発行人 飛坐 博

発 行 所 СQ出版株式会社

₩ 170 東京都豊島区巣鴨1-14-2

電話(03)947-6311(代表)

振 替 東京0-10665

定価 900円

印刷·製本 株式会社 丹誠社

ISBN4-7898-4018-2 C3055 ¥900E